



NAND Flash with Mobile LPDDR2 162-Ball MCP

MT29AZ5A3CHHTB-18AIT.109, MT29AZ5A3CHHTB-18AAT.109

Features

- Micron NAND Flash and LPDDR2 components
- RoHS-compliant, “green” package
- Separate NAND Flash and LPDDR2 interfaces
- Space-saving multichip package (MCP)
- Low-voltage operation
- Industrial temperature range (IT): –40°C to +85°C
- Automotive temperature range (AT): –40°C to +105°C
- AEC-Q100

NAND Flash-Specific Features

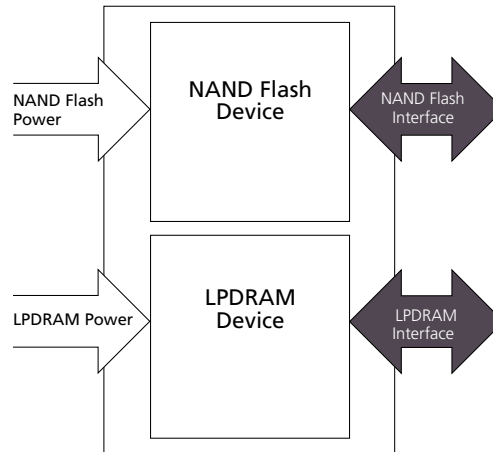
Organization

- Page size
 - x8: 4352 bytes (4096 + 256bytes)
 - Block size: 64 pages
 - Number of planes: 1
- V_{CC} = 1.70–1.95V; 1.80V nominal

LPDDR2-Specific Features

- Ultra-low-voltage 1.2V core power supply
- 1.2V HSUL-compatible inputs
- Programmable READ and WRITE latencies
- Programmable burst lengths: 4, 8, or 16
- Partial-array self refresh (PASR)
- Deep power-down (DPD) mode
- Selectable output drive strength
- Adjustable clock frequency and clock stop capabilities

Figure 1: MCP Block Diagram



Note: 1. For physical part markings, see Part Numbering Information.

Table 1: Key Timing Parameters

Speed Grade	Clock Rate (MHz)	Data Rate (Mb/s/pin)	READ Latency	WRITE Latency
-18	533	1066	8	4

Table 2: S4 Configuration Addressing

Architecture	64 Meg x 32
Die configuration	2 x 8 Meg x 16 x 8 banks
Row addressing	8K (A[12:0])
Column addressing	1K (A[9:0])
Number of die	2
Die per rank	2
Ranks per channel ¹	1

Note: 1. A channel is a complete LPDRAM interface, including command/address and data pins.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Table 3: Part Number References

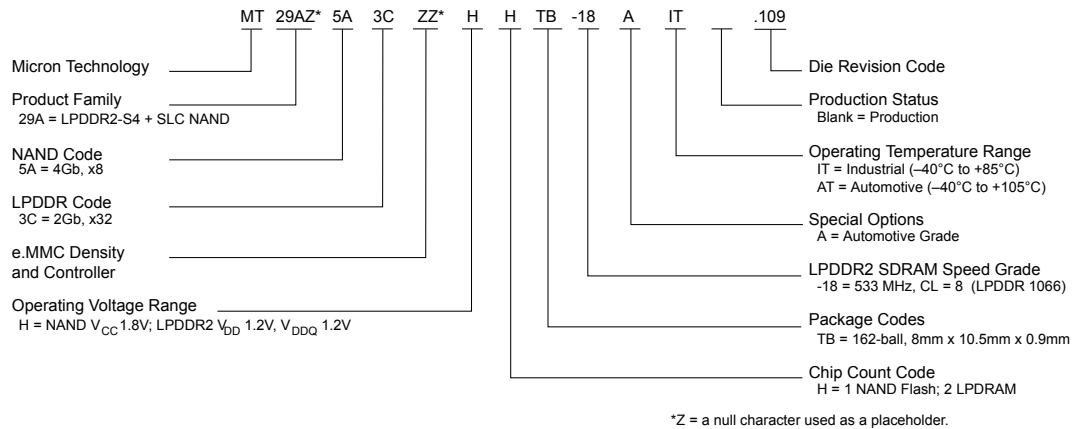
MCP	NAND Discrete	NAND READ ID Parameter
MT29AZ5A3CHHTB-18AIT.109, MT29AZ5A3CHHTB-18AAT.109	MT29F4G08	MT29F4G08ABBFA 4Gb, x8, 1.8V

Note: 1. While this is the NAND 1.8V device, the lock pin is not supported, and the LOCK feature does not apply.

Part Numbering Information

Micron NAND Flash and LPDRAM devices are available in different configurations and densities. The MCP/PoP part numbering guide is available at www.micron.com/numbering.

Figure 2: Part Number Chart



Device Marking

Due to the size of the package, the Micron-standard part number is not printed on the top of the device. Instead, an abbreviated device mark consisting of a 5-digit alphanumeric code is used. The abbreviated device marks are cross-referenced to the Micron part numbers at the FBGA Part Marking Decoder site: www.micron.com/decoder. To view the location of the abbreviated mark on the device, refer to customer service note CSN-11, "Product Mark/Label," at www.micron.com/csn.



Contents

Important Notes and Warnings	14
MCP General Description	14
Ball Assignments and Descriptions	16
Electrical Specifications	19
Device Diagrams	20
Package Dimensions	21
4Gb: x8, x16 NAND Flash Memory	22
Features	22
General Description	23
Architecture	24
Device and Array Organization	25
Asynchronous Interface Bus Operation	28
Asynchronous Enable/Standby	28
Asynchronous Commands	28
Asynchronous Addresses	29
Asynchronous Data Input	30
Asynchronous Data Output	32
Write Protect#	33
Ready/Busy#	34
Device Initialization	37
Power Cycle Requirements	38
Command Definitions	39
Reset Operations	41
RESET (FFh)	41
Identification Operations	42
READ ID (90h)	42
READ ID Parameter Tables	43
READ PARAMETER PAGE (ECh)	45
Parameter Page Data Structure Table	46
READ UNIQUE ID (EDh)	48
Feature Operations	49
SET FEATURES (EFh)	50
GET FEATURES (EEh)	50
Status Operations	53
READ STATUS (70h)	54
READ STATUS ENHANCED (78h)	54
Column Address Operations	56
RANDOM DATA READ (05h-E0h)	56
RANDOM DATA INPUT (85h)	58
PROGRAM FOR INTERNAL DATA INPUT (85h)	59
Read Operations	60
READ MODE (00h)	61
READ PAGE (00h-30h)	61
READ PAGE CACHE SEQUENTIAL (31h)	62
READ PAGE CACHE RANDOM (00h-31h)	63
READ PAGE CACHE LAST (3Fh)	64
Program Operations	65
PROGRAM PAGE (80h-10h)	65
PROGRAM PAGE CACHE (80h-15h)	66
Erase Operations	68



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

ERASE BLOCK (60h-D0h)	68
Internal Data Move Operations	69
READ FOR INTERNAL DATA MOVE (00h-35h)	69
PROGRAM FOR INTERNAL DATA MOVE (85h-10h)	70
Block Lock Feature	72
WP# and Block Lock	72
UNLOCK (23h-24h)	72
LOCK (2Ah)	74
LOCK TIGHT (2Ch)	75
BLOCK LOCK READ STATUS (7Ah)	76
PROTECT Command	78
Protection Command Details	79
Permanent Block Lock Disable Mode	80
One-Time Programmable (OTP) Operations	81
Legacy OTP Commands	81
OTP DATA PROGRAM (80h-10h)	81
RANDOM DATA INPUT (85h)	82
OTP DATA PROTECT (80h-10)	83
OTP DATA READ (00h-30h)	84
ECC Protection	85
Error Management	89
Electrical Specifications	90
Electrical Specifications – DC Characteristics and Operating Conditions	92
Electrical Specifications – AC Characteristics and Operating Conditions	94
Electrical Specifications – Program/Erase Characteristics	97
Asynchronous Interface Timing Diagrams	98
1Gb: x16, x32 Mobile LPDDR2 SDRAM	108
Features	108
General Description	108
General Notes	109
General Description	110
General Notes	110
I _{DD} Specifications	111
Functional Description	116
Power-Up	117
Initialization After RESET (Without Voltage Ramp)	119
Power-Off	119
Uncontrolled Power-Off	120
Mode Register Definition	120
Mode Register Assignments and Definitions	120
ACTIVATE Command	131
8-Bank Device Operation	131
Read and Write Access Modes	132
Burst READ Command	132
READs Interrupted by a READ	139
Burst WRITE Command	139
WRITEs Interrupted by a WRITE	142
BURST TERMINATE Command	142
Write Data Mask	144
PRECHARGE Command	145
READ Burst Followed by PRECHARGE	146
WRITE Burst Followed by PRECHARGE	147



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Auto Precharge	148
READ Burst with Auto Precharge	148
WRITE Burst with Auto Precharge	149
REFRESH Command	151
REFRESH Requirements	157
SELF REFRESH Operation	159
Partial-Array Self Refresh – Bank Masking	160
Partial-Array Self Refresh – Segment Masking	161
MODE REGISTER READ	162
Temperature Sensor	164
DQ Calibration	166
MODE REGISTER WRITE Command	168
MRW RESET Command	168
MRW ZQ Calibration Commands	169
ZQ External Resistor Value, Tolerance, and Capacitive Loading	171
Power-Down	171
Deep Power-Down	178
Input Clock Frequency Changes and Stop Events	179
Input Clock Frequency Changes and Clock Stop with CKE LOW	179
Input Clock Frequency Changes and Clock Stop with CKE HIGH	180
NO OPERATION Command	180
Simplified Bus Interface State Diagram	180
Truth Tables	182
Electrical Specifications	189
Absolute Maximum Ratings	189
Input/Output Capacitance	189
Electrical Specifications – I _{DD} Specifications and Conditions	190
AC and DC Operating Conditions	194
AC and DC Logic Input Measurement Levels for Single-Ended Signals	195
V _{REF} Tolerances	196
Input Signal	197
AC and DC Logic Input Measurement Levels for Differential Signals	199
Single-Ended Requirements for Differential Signals	200
Differential Input Crosspoint Voltage	202
Input Slew Rate	202
Output Characteristics and Operating Conditions	203
Single-Ended Output Slew Rate	204
Differential Output Slew Rate	205
HSUL ₁₂ Driver Output Timing Reference Load	207
Output Driver Impedance	207
Output Driver Impedance Characteristics with ZQ Calibration	208
Output Driver Temperature and Voltage Sensitivity	209
Output Impedance Characteristics Without ZQ Calibration	209
Clock Specification	213
t _{CK(abs)} , t _{CH(abs)} , and t _{CL(abs)}	214
Clock Period Jitter	214
Clock Period Jitter Effects on Core Timing Parameters	214
Cycle Time Derating for Core Timing Parameters	215
Clock Cycle Derating for Core Timing Parameters	215
Clock Jitter Effects on Command/Address Timing Parameters	215
Clock Jitter Effects on READ Timing Parameters	215
Clock Jitter Effects on WRITE Timing Parameters	216



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Refresh Requirements	217
AC Timing	218
CA and CS# Setup, Hold, and Derating	224
Data Setup, Hold, and Slew Rate Derating	231
Revision History	238
Rev. C – 07/2020	238
Rev. B – 03/2020	238
Rev. A – 03/2020	238



List of Figures

Figure 1: MCP Block Diagram	1
Figure 2: Part Number Chart	2
Figure 3: 162-Ball FBGA (x8, x16 NAND; x32 LPDDR2) Ball Assignments	16
Figure 4: Functional Block Diagram	20
Figure 5: 162-Ball VFBGA (Package Code: TB)	21
Figure 6: NAND Flash Die (LUN) Functional Block Diagram	24
Figure 7: Array Organization - MT29F4G08	25
Figure 8: Array Organization - MT29F8G08	26
Figure 9: Array Organization - MT29F4G16	27
Figure 10: Asynchronous Command Latch Cycle	29
Figure 11: Asynchronous Address Latch Cycle	30
Figure 12: Asynchronous Data Input Cycles	31
Figure 13: Asynchronous Data Output Cycles	33
Figure 14: Asynchronous Data Output Cycles (EDO Mode)	33
Figure 15: READ/BUSY# Open Drain	35
Figure 16: t_{Fall} and t_{Rise} (3.3V V_{CC})	35
Figure 17: I_{OL} vs. R_p ($V_{\text{CC}} = 3.3V_{\text{CC}}$)	36
Figure 18: T_C vs. R_p	36
Figure 19: R/B# Power-On Behavior	37
Figure 20: RESET (FFh) Operation	41
Figure 21: READ ID (90h) with 00h Address Operation	42
Figure 22: READ ID (90h) with 20h Address Operation	42
Figure 23: READ PARAMETER (ECh) Operation	45
Figure 24: READ UNIQUE ID (EDh) Operation	48
Figure 25: SET FEATURES (EFh) Operation	50
Figure 26: GET FEATURES (EEh) Operation	51
Figure 27: READ STATUS (70h) Operation	54
Figure 28: READ STATUS ENHANCED (78h) Operation	55
Figure 29: RANDOM DATA READ (05h-E0h) Operation	57
Figure 30: RANDOM DATA INPUT (85h) Operation	58
Figure 31: PROGRAM FOR INTERNAL DATA INPUT (85h) Operation	59
Figure 32: READ PAGE (00h-30h) Operation	61
Figure 33: READ PAGE (00h-30h) Operation with Internal ECC Enabled	62
Figure 34: READ PAGE CACHE SEQUENTIAL (31h) Operation	62
Figure 35: READ PAGE CACHE RANDOM (00h-31h) Operation	63
Figure 36: READ PAGE CACHE LAST (3Fh) Operation	64
Figure 37: PROGRAM PAGE (80h-10h) Operation	66
Figure 38: PROGRAM PAGE CACHE (80h-15h) Operation (Start)	67
Figure 39: PROGRAM PAGE CACHE (80h-15h) Operation (End)	67
Figure 40: ERASE BLOCK (60h-D0h) Operation	68
Figure 41: READ FOR INTERNAL DATA MOVE (00h-35h) Operation	69
Figure 42: READ FOR INTERNAL DATA MOVE (00h-35h) with RANDOM DATA READ (05h-E0h)	70
Figure 43: INTERNAL DATA MOVE (85h-10h) with Internal ECC Enabled	70
Figure 44: INTERNAL DATA MOVE (85h-10h) with RANDOM DATA INPUT with Internal ECC Enabled	70
Figure 45: PROGRAM FOR INTERNAL DATA MOVE (85h-10h) Operation	71
Figure 46: PROGRAM FOR INTERNAL DATA MOVE (85h-10h) with RANDOM DATA INPUT (85h)	71
Figure 47: Flash Array Protected: Invert Area Bit = 0	73
Figure 48: Flash Array Protected: Invert Area Bit = 1	73
Figure 49: UNLOCK Operation	74
Figure 50: LOCK Operation	75



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Figure 51: LOCK TIGHT Operation	76
Figure 52: PROGRAM/ERASE Issued to Locked Block	76
Figure 53: BLOCK LOCK READ STATUS	77
Figure 54: BLOCK LOCK Flowchart	78
Figure 55: Address and Command Cycles	79
Figure 56: OTP DATA PROGRAM (After Entering OTP Operation Mode)	82
Figure 57: OTP DATA PROGRAM Operation with RANDOM DATA INPUT (After Entering OTP Operation Mode)	83
Figure 58: OTP DATA PROTECT Operation (After Entering OTP Protect Mode)	84
Figure 59: OTP DATA READ	85
Figure 60: OTP DATA READ with RANDOM DATA READ Operation	85
Figure 61: RESET Operation	98
Figure 62: READ STATUS Cycle	98
Figure 63: READ STATUS ENHANCED Cycle	99
Figure 64: READ PARAMETER PAGE	99
Figure 65: READ PAGE	100
Figure 66: READ PAGE Operation with CE# "Don't Care"	101
Figure 67: RANDOM DATA READ	101
Figure 68: READ PAGE CACHE SEQUENTIAL	102
Figure 69: READ PAGE CACHE RANDOM	103
Figure 70: READ ID Operation	104
Figure 71: PROGRAM PAGE Operation	104
Figure 72: PROGRAM PAGE Operation with CE# "Don't Care"	105
Figure 73: PROGRAM PAGE Operation with RANDOM DATA INPUT	105
Figure 74: PROGRAM PAGE CACHE	106
Figure 75: PROGRAM PAGE CACHE Ending on 15h	106
Figure 76: INTERNAL DATA MOVE	107
Figure 77: ERASE BLOCK Operation	107
Figure 78: V_{DD1} Typical Self-Refresh Current vs. Temperature (Per Die)	115
Figure 79: V_{DD2} Typical Self-Refresh Current vs. Temperature (Per Die)	115
Figure 80: Functional Block Diagram	116
Figure 81: Voltage Ramp and Initialization Sequence	119
Figure 82: ACTIVATE Command	131
Figure 83: t_{FAW} Timing (8-Bank Devices)	132
Figure 84: READ Output Timing – t_{DQCK} (MAX)	133
Figure 85: READ Output Timing – t_{DQCK} (MIN)	133
Figure 86: Burst READ – $RL = 5$, $BL = 4$, $t_{DQCK} > t_{CK}$	134
Figure 87: Burst READ – $RL = 3$, $BL = 8$, $t_{DQCK} < t_{CK}$	134
Figure 88: t_{DQCKDL} Timing	135
Figure 89: t_{DQCKDM} Timing	136
Figure 90: t_{DQCKDS} Timing	137
Figure 91: Burst READ Followed by Burst WRITE – $RL = 3$, $WL = 1$, $BL = 4$	138
Figure 92: Seamless Burst READ – $RL = 3$, $BL = 4$, $t_{CCD} = 2$	138
Figure 93: READ Burst Interrupt Example – $RL = 3$, $BL = 8$, $t_{CCD} = 2$	139
Figure 94: Data Input (WRITE) Timing	140
Figure 95: Burst WRITE – $WL = 1$, $BL = 4$	140
Figure 96: Burst WRITE Followed by Burst READ – $RL = 3$, $WL = 1$, $BL = 4$	141
Figure 97: Seamless Burst WRITE – $WL = 1$, $BL = 4$, $t_{CCD} = 2$	141
Figure 98: WRITE Burst Interrupt Timing – $WL = 1$, $BL = 8$, $t_{CCD} = 2$	142
Figure 99: Burst WRITE Truncated by BST – $WL = 1$, $BL = 16$	143
Figure 100: Burst READ Truncated by BST – $RL = 3$, $BL = 16$	144
Figure 101: Data Mask Timing	144
Figure 102: Write Data Mask – Second Data Bit Masked	145



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Figure 103: READ Burst Followed by PRECHARGE – RL = 3, BL = 8, $RU(t_{RTP(MIN)})/t_{CK} = 2$	146
Figure 104: READ Burst Followed by PRECHARGE – RL = 3, BL = 4, $RU(t_{RTP(MIN)})/t_{CK} = 3$	147
Figure 105: WRITE Burst Followed by PRECHARGE – WL = 1, BL = 4	148
Figure 106: READ Burst with Auto Precharge – RL = 3, BL = 4, $RU(t_{RTP(MIN)})/t_{CK} = 2$	149
Figure 107: WRITE Burst with Auto Precharge – WL = 1, BL = 4	150
Figure 108: Regular Distributed Refresh Pattern	154
Figure 109: Supported Transition from Repetitive REFRESH Burst	155
Figure 110: Nonsupported Transition from Repetitive REFRESH Burst	156
Figure 111: Recommended Self Refresh Entry and Exit	157
Figure 112: t_{SRF} Definition	158
Figure 113: All-Bank REFRESH Operation	158
Figure 114: Per-Bank REFRESH Operation	159
Figure 115: SELF REFRESH Operation	160
Figure 116: MRR Timing – RL = 3, $t_{MRR} = 2$	162
Figure 117: READ to MRR Timing – RL = 3, $t_{MRR} = 2$	163
Figure 118: Burst WRITE Followed by MRR – RL = 3, WL = 1, BL = 4	164
Figure 119: Temperature Sensor Timing	166
Figure 120: MR32 and MR40 DQ Calibration Timing – RL = 3, $t_{MRR} = 2$	167
Figure 121: MODE REGISTER WRITE Timing – RL = 3, $t_{MRW} = 5$	168
Figure 122: ZQ Timings	170
Figure 123: Power-Down Entry and Exit Timing	172
Figure 124: CKE Intensive Environment	172
Figure 125: REFRESH-to-REFRESH Timing in CKE Intensive Environments	172
Figure 126: READ to Power-Down Entry	173
Figure 127: READ with Auto Precharge to Power-Down Entry	174
Figure 128: WRITE to Power-Down Entry	175
Figure 129: WRITE with Auto Precharge to Power-Down Entry	176
Figure 130: REFRESH Command to Power-Down Entry	177
Figure 131: ACTIVATE Command to Power-Down Entry	177
Figure 132: PRECHARGE Command to Power-Down Entry	177
Figure 133: MRR Command to Power-Down Entry	178
Figure 134: MRW Command to Power-Down Entry	178
Figure 135: Deep Power-Down Entry and Exit Timing	179
Figure 136: Simplified Bus Interface State Diagram	181
Figure 137: V_{REF} DC Tolerance and V_{REF} AC Noise Limits	196
Figure 138: LPDDR2-466 to LPDDR2-1066 Input Signal	197
Figure 139: LPDDR2-200 to LPDDR2-400 Input Signal	198
Figure 140: Differential AC Swing Time and t_{DVAC}	199
Figure 141: Single-Ended Requirements for Differential Signals	201
Figure 142: V_{IX} Definition	202
Figure 143: Differential Input Slew Rate Definition for CK, CK#, DQS, and DQS#	203
Figure 144: Single-Ended Output Slew Rate Definition	204
Figure 145: Differential Output Slew Rate Definition	206
Figure 146: Overshoot and Undershoot Definition	207
Figure 147: HSUL_12 Driver Output Reference Load for Timing and Slew Rate	207
Figure 148: Output Driver	208
Figure 149: Output Impedance = 240 Ohms, I-V Curves After ZQRESET	211
Figure 150: Output Impedance = 240 Ohms, I-V Curves After Calibration	212
Figure 151: Command Input Setup and Hold Timing	224
Figure 152: Typical Slew Rate and $t_{VAC} - t_{IS}$ for CA and CS# Relative to Clock	227
Figure 153: Typical Slew Rate – t_{IH} for CA and CS# Relative to Clock	228
Figure 154: Tangent Line – t_{IS} for CA and CS# Relative to Clock	229



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Figure 155: Tangent Line – t_{IH} for CA and CS# Relative to Clock	230
Figure 156: Typical Slew Rate and t_{VAC} – t_{DS} for DQ Relative to Strobe	234
Figure 157: Typical Slew Rate – t_{DH} for DQ Relative to Strobe	235
Figure 158: Tangent Line – t_{DS} for DQ with Respect to Strobe	236
Figure 159: Tangent Line – t_{DH} for DQ with Respect to Strobe	237



List of Tables

Table 1: Key Timing Parameters	1
Table 2: S4 Configuration Addressing	1
Table 3: Part Number References	2
Table 4: NAND Ball Descriptions	17
Table 5: LPDDR2 Ball/Pad Descriptions	17
Table 6: Non-Device-Specific Descriptions	18
Table 7: Absolute Maximum Ratings	19
Table 8: Recommended Operating Conditions	19
Table 9: Array Addressing (x8)	25
Table 10: Array Addressing (x8)	26
Table 11: Array Addressing (x16)	27
Table 12: Asynchronous Interface Mode Selection	28
Table 13: Power Cycle Requirements	38
Table 14: Command Set	39
Table 15: READ ID Parameters for Address 00h	43
Table 16: READ ID Parameters for Address 20h	44
Table 17: Parameter Page Data Structure	46
Table 18: Feature Address Definitions	49
Table 19: Feature Addresses 90h: Timing Mode	49
Table 20: Feature Addresses 01h: Timing Mode	51
Table 21: Feature Addresses 80h: Programmable I/O Drive Strength	51
Table 22: Feature Addresses 81h: Programmable R/B# Pull-Down Strength	52
Table 23: Status Register Definition	53
Table 24: Block Lock Address Cycle Assignments	73
Table 25: Block Lock Status Register Bit Definitions	76
Table 26: Spare Area Mapping (x8)	86
Table 27: Spare Area Mapping (x16)	87
Table 28: ECC Status	88
Table 29: Error Management Details	89
Table 30: Absolute Maximum Ratings	90
Table 31: Recommended Operating Conditions	90
Table 32: Capacitance	90
Table 33: Test Conditions	90
Table 34: DC Characteristics and Operating Conditions (3.3V)	92
Table 35: DC Characteristics and Operating Conditions (1.8V)	93
Table 36: AC Characteristics: Command, Data, and Address Input (3.3V)	94
Table 37: AC Characteristics: Command, Data, and Address Input (1.8V)	94
Table 38: AC Characteristics: Normal Operation (3.3V)	95
Table 39: AC Characteristics: Normal Operation (1.8V)	96
Table 40: Program/Erase Characteristics	97
Table 41: S4 Configuration Addressing	108
Table 42: I _{DD} Specifications (32 Meg x 16)	111
Table 43: I _{DD6} Partial-Array Self Refresh Current (32 Meg x 16)	112
Table 44: I _{DD} Specifications (64 Meg x 32)	113
Table 45: I _{DD6} Partial-Array Self Refresh Current (64 Meg x 32)	114
Table 46: Initialization Timing Parameters	119
Table 47: Power-Off Timing	120
Table 48: Mode Register Assignments	121
Table 49: MR0 Device Information (MA[7:0] = 00h)	122
Table 50: MR0 Op-Code Bit Definitions	122



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Table 51: MR1 Device Feature 1 (MA[7:0] = 01h)	122
Table 52: MR1 Op-Code Bit Definitions	123
Table 53: Burst Sequence by Burst Length (BL), Burst Type (BT), and Wrap Control (WC)	123
Table 54: No-Wrap Restrictions	124
Table 55: MR2 Device Feature 2 (MA[7:0] = 02h)	124
Table 56: MR2 Op-Code Bit Definitions	125
Table 57: MR3 I/O Configuration 1 (MA[7:0] = 03h)	125
Table 58: MR3 Op-Code Bit Definitions	125
Table 59: MR4 Device Temperature (MA[7:0] = 04h)	125
Table 60: MR4 Op-Code Bit Definitions	126
Table 61: MR5 Basic Configuration 1 (MA[7:0] = 05h)	126
Table 62: MR5 Op-Code Bit Definitions	126
Table 63: MR6 Basic Configuration 2 (MA[7:0] = 06h)	127
Table 64: MR6 Op-Code Bit Definitions	127
Table 65: MR7 Basic Configuration 3 (MA[7:0] = 07h)	127
Table 66: MR7 Op-Code Bit Definitions	127
Table 67: MR8 Basic Configuration 4 (MA[7:0] = 08h)	127
Table 68: MR8 Op-Code Bit Definitions	127
Table 69: MR9 Test Mode (MA[7:0] = 09h)	128
Table 70: MR10 Calibration (MA[7:0] = 0Ah)	128
Table 71: MR10 Op-Code Bit Definitions	128
Table 72: MR[11:15] Reserved (MA[7:0] = 0Bh–0Fh)	129
Table 73: MR16 PASR Bank Mask (MA[7:0] = 010h)	129
Table 74: MR16 Op-Code Bit Definitions	129
Table 75: MR17 PASR Segment Mask (MA[7:0] = 011h)	129
Table 76: MR17 PASR Segment Mask Definitions	129
Table 77: MR17 PASR Row Address Ranges in Masked Segments	129
Table 78: Reserved Mode Registers	130
Table 79: MR63 RESET (MA[7:0] = 3Fh) – MRW Only	130
Table 80: Bank Selection for PRECHARGE by Address Bits	146
Table 81: PRECHARGE and Auto Precharge Clarification	150
Table 82: REFRESH Command Scheduling Separation Requirements	152
Table 83: Bank and Segment Masking Example	161
Table 84: Temperature Sensor Definitions and Operating Conditions	165
Table 85: Data Calibration Pattern Description	167
Table 86: Truth Table for MRR and MRW	168
Table 87: Command Truth Table	182
Table 88: CKE Truth Table	183
Table 89: Current State Bank <i>n</i> to Command to Bank <i>n</i> Truth Table	184
Table 90: Current State Bank <i>n</i> to Command to Bank <i>m</i> Truth Table	186
Table 91: DM Truth Table	189
Table 92: Absolute Maximum DC Ratings	189
Table 93: Input/Output Capacitance	189
Table 94: Switching for CA Input Signals	190
Table 95: Switching for I _{DD4R}	191
Table 96: Switching for I _{DD4W}	191
Table 97: I _{DD} Specification Parameters and Operating Conditions	192
Table 98: Recommended DC Operating Conditions	194
Table 99: Input Leakage Current	194
Table 100: Operating Temperature Range	194
Table 101: Single-Ended AC and DC Input Levels for CA and CS# Inputs	195
Table 102: Single-Ended AC and DC Input Levels for CKE	195



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Features

Table 103: Single-Ended AC and DC Input Levels for DQ and DM	195
Table 104: Differential AC and DC Input Levels	199
Table 105: CK/CK# and DQS/DQS# Time Requirements Before Ringback (t_{DVAC})	200
Table 106: Single-Ended Levels for CK, CK#, DQS, DQS#	201
Table 107: Crosspoint Voltage for Differential Input Signals (CK, CK#, DQS, DQS#)	202
Table 108: Differential Input Slew Rate Definition	203
Table 109: Single-Ended AC and DC Output Levels	203
Table 110: Differential AC and DC Output Levels	204
Table 111: Single-Ended Output Slew Rate Definition	204
Table 112: Single-Ended Output Slew Rate	204
Table 113: Differential Output Slew Rate Definition	205
Table 114: Differential Output Slew Rate	206
Table 115: AC Overshoot/Undershoot Specification	206
Table 116: Output Driver DC Electrical Characteristics with ZQ Calibration	208
Table 117: Output Driver Sensitivity Definition	209
Table 118: Output Driver Temperature and Voltage Sensitivity	209
Table 119: Output Driver DC Electrical Characteristics Without ZQ Calibration	209
Table 120: I-V Curves	210
Table 121: Definitions and Calculations	213
Table 122: $t_{CK(ABS)}$, $t_{CH(ABS)}$, and $t_{CL(ABS)}$ Definitions	214
Table 123: Refresh Requirement Parameters (Per Density)	217
Table 124: AC Timing	218
Table 125: CA and CS# Setup and Hold Base Values (>400 MHz, 1 V/ns Slew Rate)	225
Table 126: CA and CS# Setup and Hold Base Values (<400 MHz, 1 V/ns Slew Rate)	225
Table 127: Derating Values for AC/DC-Based t_{IS}/t_{IH} (AC220)	226
Table 128: Derating Values for AC/DC-Based t_{IS}/t_{IH} (AC300)	226
Table 129: Required Time for Valid Transition – $t_{VAC} > V_{IH(AC)}$ and $< V_{IL(AC)}$	226
Table 130: Data Setup and Hold Base Values (>400 MHz, 1 V/ns Slew Rate)	231
Table 131: Data Setup and Hold Base Values (<400 MHz, 1 V/ns Slew Rate)	232
Table 132: Derating Values for AC/DC-Based t_{DS}/t_{DH} (AC220)	232
Table 133: Derating Values for AC/DC-Based t_{DS}/t_{DH} (AC300)	233
Table 134: Required Time for Valid Transition – $t_{VAC} > V_{IH(AC)}$ or $< V_{IL(AC)}$	233



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Important Notes and Warnings

Important Notes and Warnings

Micron Technology, Inc. ("Micron") reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions. This document supersedes and replaces all information supplied prior to the publication hereof. You may not rely on any information set forth in this document if you obtain the product described herein from any unauthorized distributor or other source not authorized by Micron.

Automotive Applications. Products are not designed or intended for use in automotive applications unless specifically designated by Micron as automotive-grade by their respective data sheets. Distributor and customer/distributor shall assume the sole risk and liability for and shall indemnify and hold Micron harmless against all claims, costs, damages, and expenses and reasonable attorneys' fees arising out of, directly or indirectly, any claim of product liability, personal injury, death, or property damage resulting directly or indirectly from any use of non-automotive-grade products in automotive applications. Customer/distributor shall ensure that the terms and conditions of sale between customer/distributor and any customer of distributor/customer (1) state that Micron products are not designed or intended for use in automotive applications unless specifically designated by Micron as automotive-grade by their respective data sheets and (2) require such customer of distributor/customer to indemnify and hold Micron harmless against all claims, costs, damages, and expenses and reasonable attorneys' fees arising out of, directly or indirectly, any claim of product liability, personal injury, death, or property damage resulting from any use of non-automotive-grade products in automotive applications.

Critical Applications. Products are not authorized for use in applications in which failure of the Micron component could result, directly or indirectly in death, personal injury, or severe property or environmental damage ("Critical Applications"). Customer must protect against death, personal injury, and severe property and environmental damage by incorporating safety design measures into customer's applications to ensure that failure of the Micron component will not result in such harms. Should customer or distributor purchase, use, or sell any Micron component for any critical application, customer and distributor shall indemnify and hold harmless Micron and its subsidiaries, subcontractors, and affiliates and the directors, officers, and employees of each against all claims, costs, damages, and expenses and reasonable attorneys' fees arising out of, directly or indirectly, any claim of product liability, personal injury, or death arising in any way out of such critical application, whether or not Micron or its subsidiaries, subcontractors, or affiliates were negligent in the design, manufacture, or warning of the Micron product.

Customer Responsibility. Customers are responsible for the design, manufacture, and operation of their systems, applications, and products using Micron products. ALL SEMICONDUCTOR PRODUCTS HAVE INHERENT FAILURE RATES AND LIMITED USEFUL LIVES. IT IS THE CUSTOMER'S SOLE RESPONSIBILITY TO DETERMINE WHETHER THE MICRON PRODUCT IS SUITABLE AND FIT FOR THE CUSTOMER'S SYSTEM, APPLICATION, OR PRODUCT. Customers must ensure that adequate design, manufacturing, and operating safeguards are included in customer's applications and products to eliminate the risk that personal injury, death, or severe property or environmental damages will result from failure of any semiconductor component.

Limited Warranty. In no event shall Micron be liable for any indirect, incidental, punitive, special or consequential damages (including without limitation lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort, warranty, breach of contract or other legal theory, unless explicitly stated in a written agreement executed by Micron's duly authorized representative.

MCP General Description

Micron MCP products combine NAND Flash and Mobile LPDRAM devices in a single MCP. These products target mobile applications with low-power, high-performance, and minimal package-footprint design requirements. The NAND Flash and Mobile LPDRAM devices are also members of the Micron memory products portfolio.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP MCP General Description

The NAND Flash and Mobile LPDRAM devices are packaged with separate interfaces (no shared address, control, data, or power balls). This bus architecture supports an optimized interface to processors with separate NAND Flash and Mobile LPDRAM buses. The NAND Flash and Mobile LPDRAM devices have separate core power connections and share a common ground (that is, V_{SS} is tied together on the two devices).

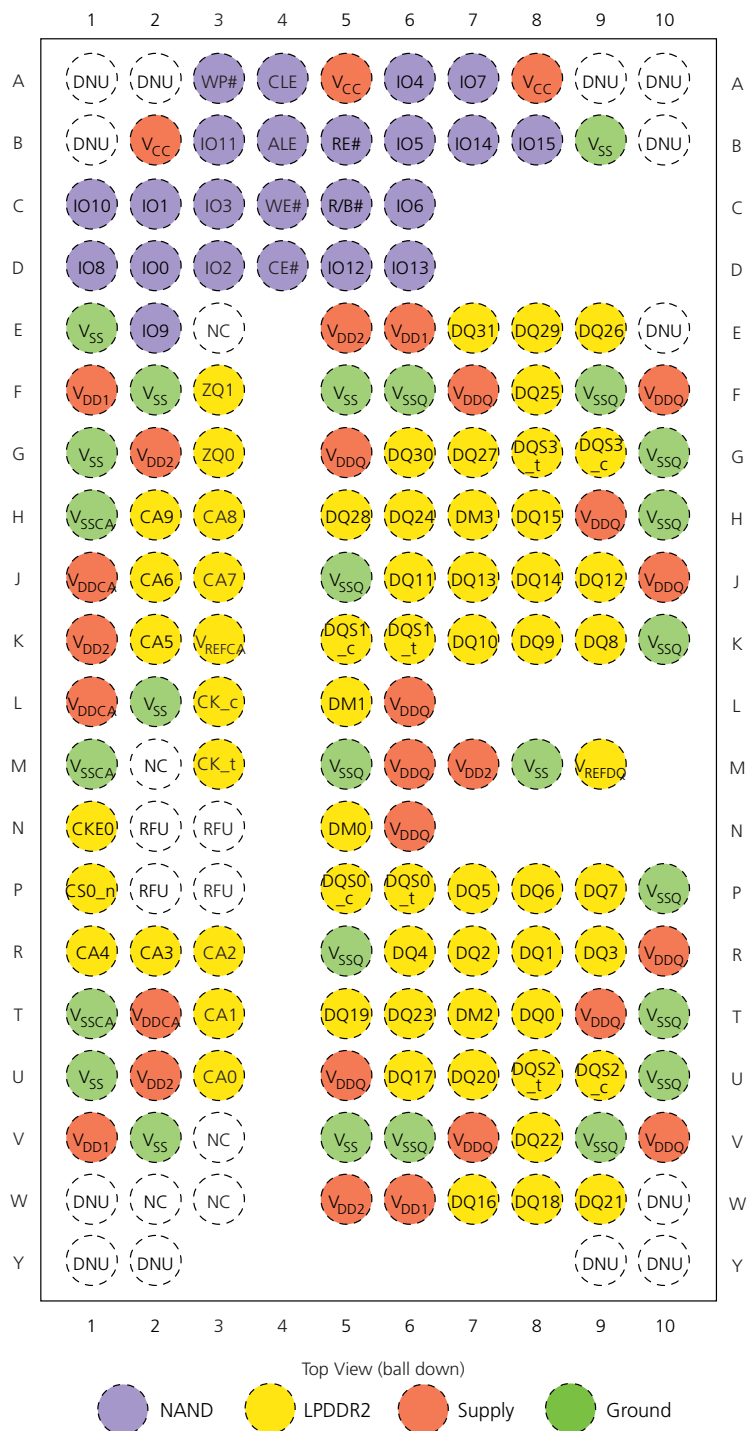
The bus architecture of this device also supports separate NAND Flash and Mobile LPDRAM functionality without concern for device interaction.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Ball Assignments and Descriptions

Ball Assignments and Descriptions

Figure 3: 162-Ball FBGA (x8, x16 NAND; x32 LPDDR2) Ball Assignments





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Ball Assignments and Descriptions

Table 4: NAND Ball Descriptions

Symbol	Type	Description
ALE	Input	Address latch enable: When ALE is HIGH, addresses can be transferred to the on-chip address register.
CE#	Input	Chip enable: Gates transfers between the host system and the NAND device.
CLE	Input	Command latch enable: When CLE is HIGH, commands can be transferred to the on-chip command register.
RE#	Input	Read enable: Gates information from the NAND device to the host system.
WE#	Input	Write enable: Gates information from the host system to the NAND device.
WP#	Input	Write protect: Driving WP# LOW blocks ERASE and PROGRAM operations.
I/O[7:0] (x8) I/O[15:0] (x16)	Input/ output	Data inputs/outputs: The bidirectional I/Os transfer address, data, and instruction information. Data is output only during READ operations; at other times the I/Os are inputs. I/O[15:8] are RFU ¹ for NAND x8 devices.
R/B#	Output	Ready/busy: Open-drain, active-LOW output that indicates when an internal operation is in progress.
V _{CC}	Supply	V _{CC} : NAND power supply

Note: 1. Balls marked RFU may or may not be connected internally. These balls should not be used. Contact factory for details.

Table 5: LPDDR2 Ball/Pad Descriptions

Symbol	Type	Description
CA[9:0]	Input	Command/address inputs: Provide the command and address inputs according to the command truth table.
CK _t , CK _c	Input	Clock: Differential clock inputs. All CA inputs are sampled on both rising and falling edges of CK. CS and CKE inputs are sampled at the rising edge of CK. AC timings are referenced to clock.
CKE0	Input	Clock enable: CKE HIGH activates and CKE LOW deactivates the internal clock signals, input buffers, and output drivers. Power-saving modes are entered and exited via CKE transitions. CKE is considered part of the command code. CKE is sampled on the rising edge of CK.
CS _n	Input	Chip select: Considered part of the command code and is sampled on the rising edge of CK.
DM[3:0]	Input	Input data mask: Input mask signal for write data. Although DM balls are input-only, the DM loading is designed to match that of DQ and DQS balls. DM[3:0] is DM for each of the four data bytes, respectively.
DQ[31:0]	I/O	Data input/output: Bidirectional data bus
DQS[3:0] _t , DQS[3:0] _c	I/O	Data strobe: Bidirectional (used for read and write data) and complementary (DQS _t and DQS _c). It is edge-aligned output with read data and centered input with write data. DQS[3:0] _t /DQS[3:0] _c is DQS for each of the four data bytes, respectively.
V _{DDQ}	Supply	DQ power supply: Isolated on the die for improved noise immunity
V _{SSQ}	Supply	DQ ground: Isolated on the die for improved noise immunity



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Ball Assignments and Descriptions

Table 5: LPDDR2 Ball/Pad Descriptions (Continued)

Symbol	Type	Description
V_{DD1}	Supply	Core power: Supply 1
V_{DD2}	Supply	Core power: Supply 2
V_{SS}	Supply	Common ground.
V_{REFCA}, V_{REFDQ}	Supply	Reference voltage: V_{REFCA} is reference for command/address input buffers, V_{REFDQ} is reference for DQ input buffers.
ZQ0, ZQ1	Reference	External reference ball for output drive calibration: This ball is tied to an external 240Ω resistor (RZQ), which is tied to V_{SSQ} .

Table 6: Non-Device-Specific Descriptions

Symbol	Type	Description
V_{SS}	Supply	V_{SS} : Shared ground
Symbol	Type	Description
DNU	–	Do not use: Must be grounded or left floating
NC	–	No connect: Not internally connected
RFU ¹	–	Reserved for future use

Note: 1. Balls marked RFU may or may not be connected internally. These balls should not be used. Contact factory for details.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications

Electrical Specifications

Table 7: Absolute Maximum Ratings

Parameters/Conditions	Symbol	Min	Max	Unit
V_{CC} supply voltage relative to V_{SS}	V_{CC}	-0.6	2.4	V
V_{DD1} supply voltage relative to V_{SS}	V_{DD1}	-0.4	2.3	V
V_{DD2} supply voltage relative to V_{SS}	V_{DD2}	-0.4	1.8	V
V_{DDCA} and V_{DDQ} supply voltage relative to V_{SS}	V_{DDCA} , V_{DDQ}	-0.4	1.6	V
Voltage on any pin relative to V_{SS}	V_{IN}	-0.4	1.6 or ($V_{DDQ} + 0.3$), whichever is less	V
Storage temperature range	—	-55	+125	°C

Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Table 8: Recommended Operating Conditions

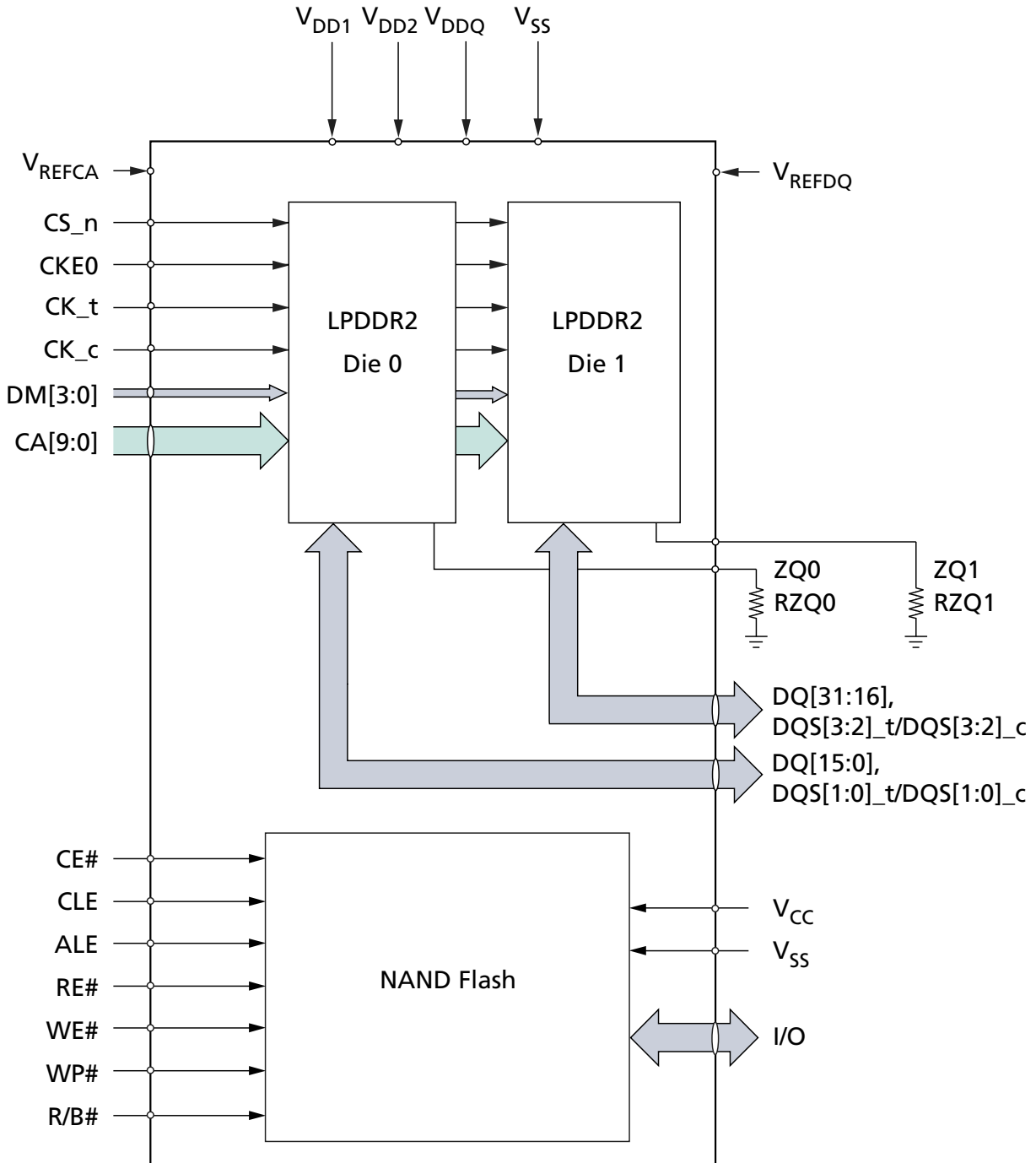
Parameters		Symbol	Min	Typ	Max	Unit
Supply voltage		V_{CC}	1.70	1.80	1.95	V
Supply voltage		V_{DD1}	1.70	1.80	1.95	V
Supply voltage		V_{DD2}	1.14	1.20	1.30	V
I/O supply voltage		V_{DDCA}/V_{DDQ}	1.14	1.20	1.30	V
Operating temperature range	Industrial temperature	—	-40	—	+85	°C
	Automotive temperature	—	-40	—	+105	°C

Note: 1. This operating temperature range pertains to this MCP device. Other temperature ranges mentioned in data sheet apply to discrete components, respectively.



Device Diagrams

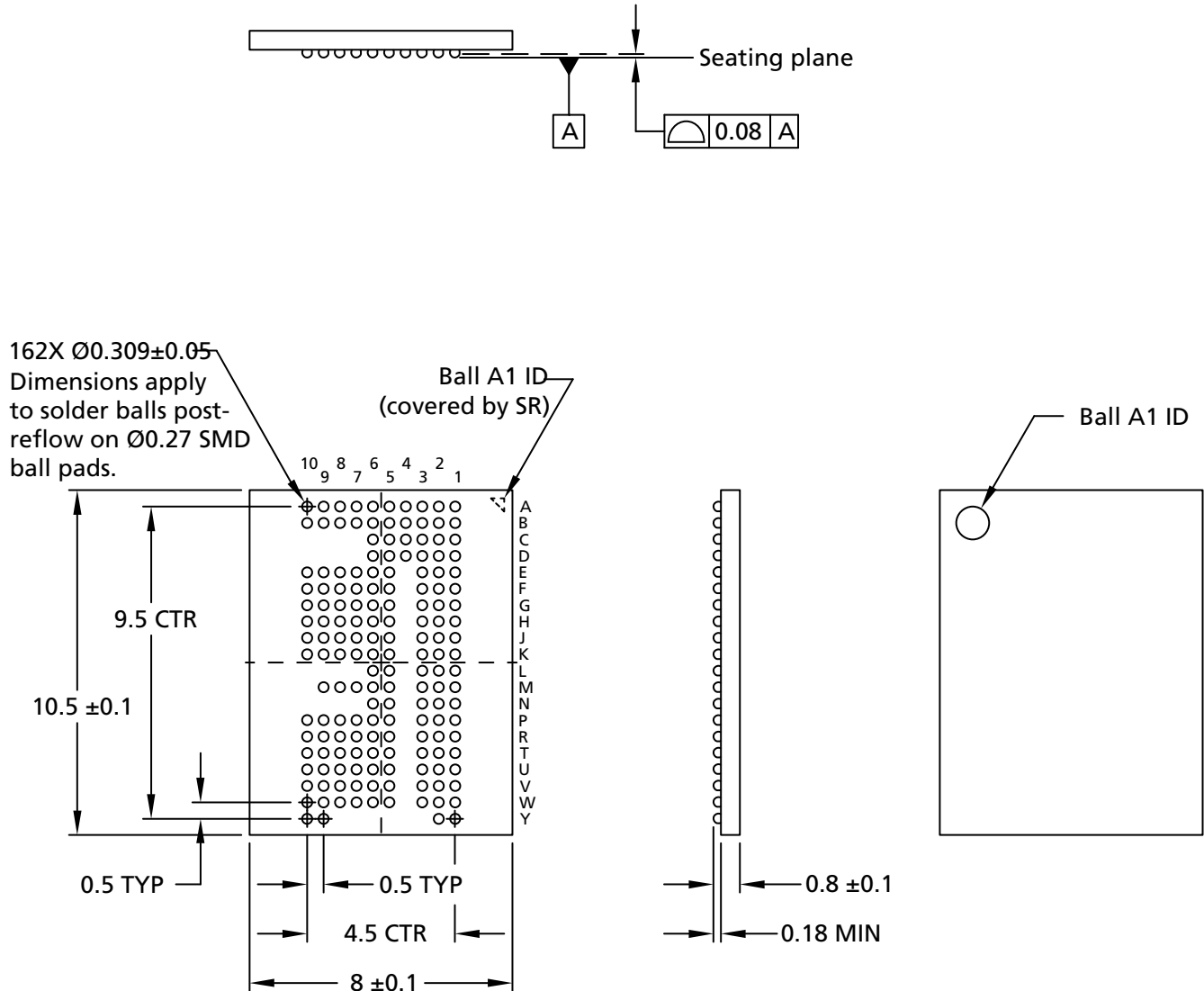
Figure 4: Functional Block Diagram





Package Dimensions

Figure 5: 162-Ball VFBGA (Package Code: TB)



- Notes:
1. Solder ball composition: SACQ with Cu OSP ball pads (92.45% Sn, 4% Ag, 0.5% Cu, 3% Bi, 0.05% Ni).
 2. All dimensions are in millimeters.



4Gb: x8, x16 NAND Flash Memory

Features

- Open NAND Flash Interface (ONFI) 1.0-compliant¹
- Single-level cell (SLC) technology
- Organization
 - Page size x8: 4352 bytes (4096 + 256 bytes)
 - Page size x16: 2176 words (2048 + 128 words)
 - Block size: 64 pages
 - Plane size: 1
 - Device size: 4Gb: 2048 blocks
- Asynchronous I/O performance
 - ^tRC/^tWC: 20ns (3.3V), 30ns (1.8V)
- Array performance
 - Read page: 25μs
 - Program page: 200μs (TYP)
 - Erase block: 2ms (TYP)
- Command set: ONFI NAND Flash Protocol
- Advanced command set
 - Program page cache mode
 - Read page cache mode
 - Permanent block locking (blocks 47:0)
 - One-time programmable (OTP) mode
 - Block lock
 - Programmable drive strength
 - Read unique ID
 - Internal data move
- Operation status byte provides software method for detecting
 - Operation completion
 - Pass/fail condition
 - Write-protect status
- Ready/Busy# (R/B#) provides a hardware method of detecting operation completion
- WP#: Write protect entire device
- Blocks 7–0 are valid when shipped from factory with ECC. For minimum required ECC, see Error Management.
- RESET (FFh) required as first command after power-on
- Alternate method of device initialization after power-up (contact factory)
- Internal data move operations supported within the plane from which data is read
- Quality and reliability
 - Endurance: 100,000 PROGRAM/ERASE cycles IT temperature range
 - Endurance: 100,000 PROGRAM/ERASE cycles AT temperature range
 - Data retention: JESD47G-compliant; see qualification report
- Additional: Uncycled data retention: 10 years 24/7 @ 85°C

Note: 1. The ONFI 1.0 specification is available at www.onfi.org.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP General Description

General Description

Micron NAND Flash devices include an asynchronous data interface for high-performance I/O operations. These devices use a highly multiplexed 8-bit bus (I/Ox) to transfer commands, address, and data. There are five control signals used to implement the asynchronous data interface: CE#, CLE, ALE, WE#, and RE#. Additional signals control hardware write protection and monitor device status (R/B#).

This hardware interface creates a low pin-count device with a standard pinout that remains the same from one density to another, enabling future upgrades to higher densities with no board redesign.

A target is the unit of memory accessed by a chip enable signal. A target contains one or more NAND Flash die. A NAND Flash die is the minimum unit that can independently execute commands and report status. A NAND Flash die, in the ONFI specification, is referred to as a logical unit (LUN). There is at least one NAND Flash die per chip enable signal. For further details, see Device and Array Organization.



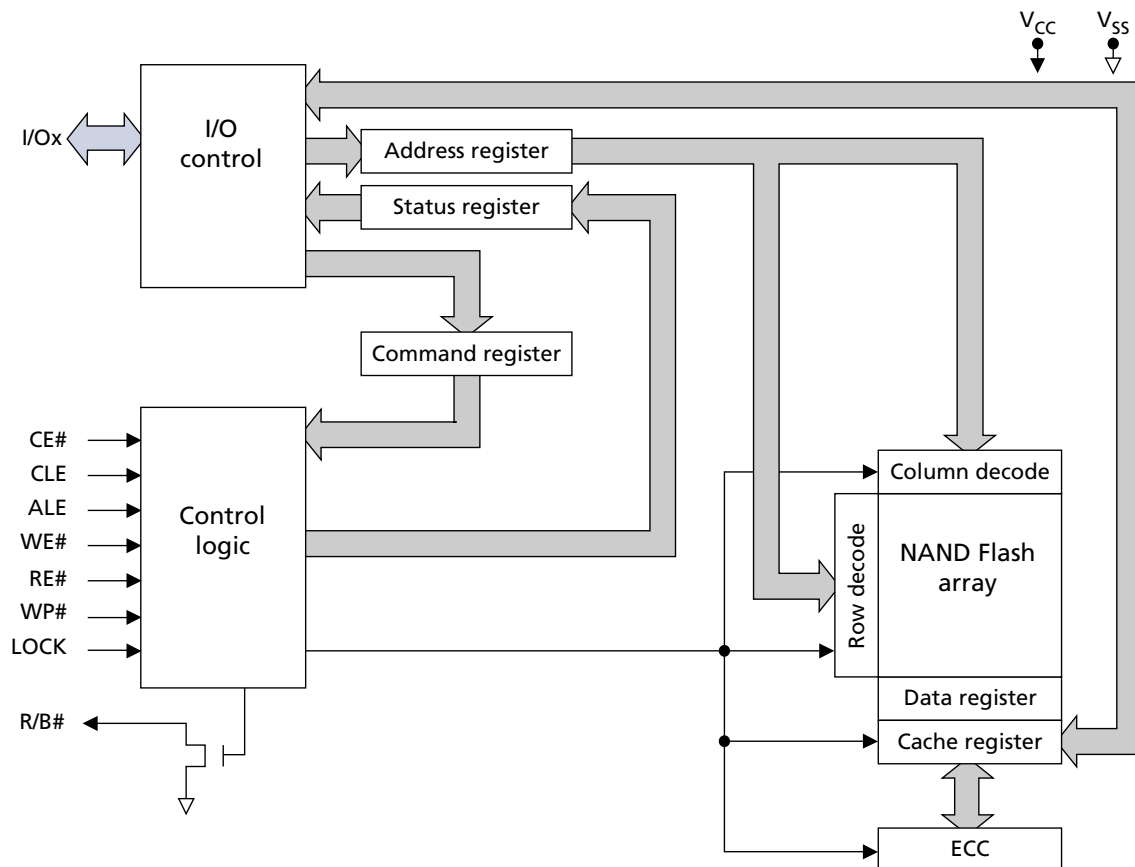
Architecture

These devices use NAND Flash electrical and command interfaces. Data, commands, and addresses are multiplexed onto the same pins and received by I/O control circuits. The commands received at the I/O control circuits are latched by a command register and are transferred to control logic circuits for generating internal signals to control device operations. The addresses are latched by an address register and sent to a row decoder to select a row address, or to a column decoder to select a column address.

Data is transferred to or from the NAND Flash memory array, byte by byte (x8) or word by word (x16), through a data register and a cache register.

The NAND Flash memory array is programmed and read using page-based operations and is erased using block-based operations. During normal page operations, the data and cache registers act as a single register. During cache operations, the data and cache registers operate independently to increase data throughput. The status register reports the status of die operations.

Figure 6: NAND Flash Die (LUN) Functional Block Diagram





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Device and Array Organization

Device and Array Organization

Figure 7: Array Organization - MT29F4G08

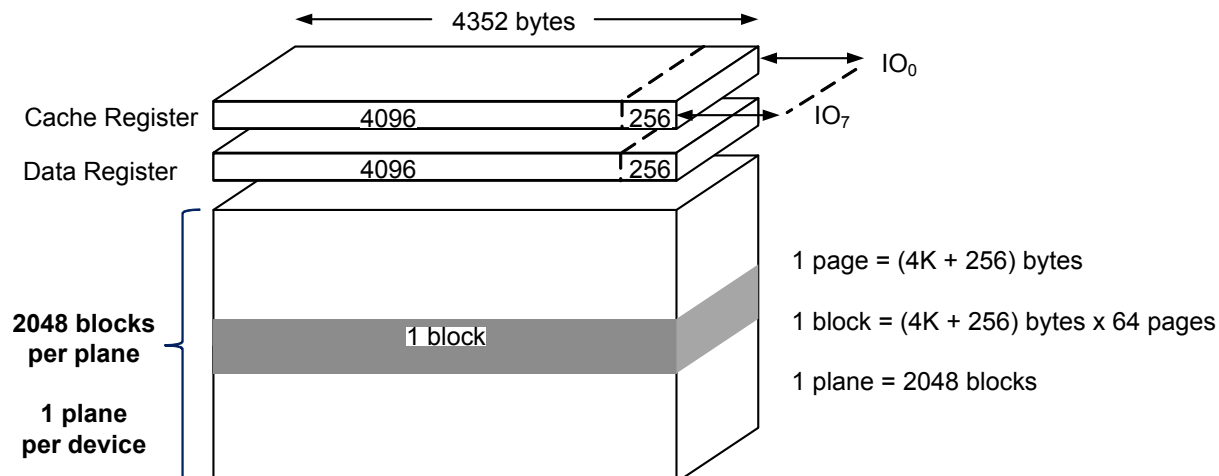


Table 9: Array Addressing (x8)

Cycle	I/07	I/06	I/05	I/04	I/03	I/02	I/01	I/00
First	CA7	CA6	CA5	CA4	CA3	CA2	CA1	CA0
Second	LOW	LOW	LOW	CA12 ²	CA11	CA10	CA9	CA8
Third	BA7	BA6	PA5	PA4	PA3	PA2	PA1	PA0
Fourth	BA15	BA14	BA13	BA12	BA11	BA10	BA9	BA8
Fifth	LOW	LOW	LOW	LOW	LOW	LOW	LOW	BA16

- Notes:
1. Block address concatenated with page address = actual page address. CA_x = column address; PA_x = page address; BA_x = block address.
 2. If CA12 is 1, then CA[11:8] must be 0.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Device and Array Organization

Figure 8: Array Organization - MT29F8G08

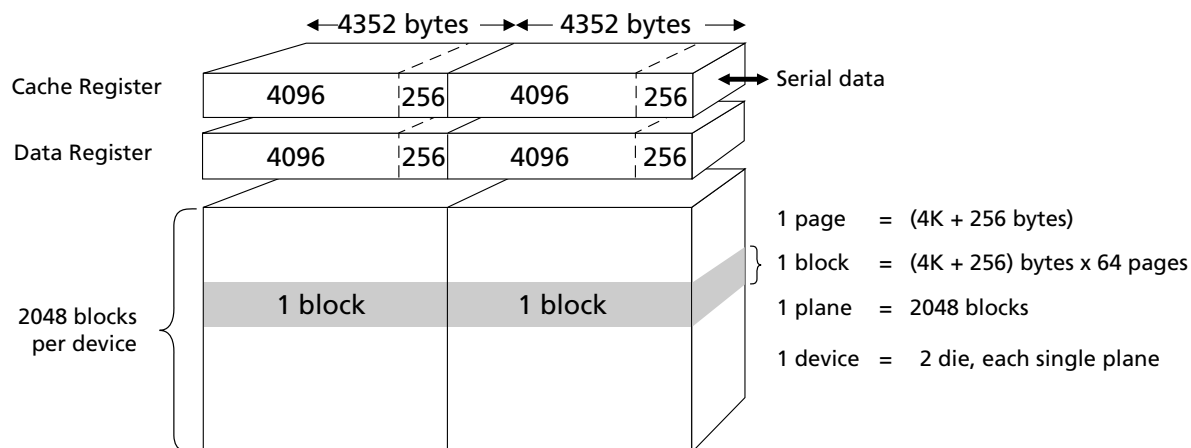


Table 10: Array Addressing (x8)

Cycle	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0
First	CA7	CA6	CA5	CA4	CA3	CA2	CA1	CA0
Second	LOW	LOW	LOW	CA12 ²	CA11	CA10	CA9	CA8
Third	BA7	BA6	PA5	PA4	PA3	PA2	PA1	PA0
Fourth	BA15	BA14	BA13	BA12	BA11	BA10	BA9	BA8
Fifth	LOW	LOW	LOW	LOW	LOW	LOW	LUA0 ³	BA16

- Notes:
1. Block address concatenated with page address = actual page address. CAx = column address; PAx = page address; BAx = block address.
 2. If CA12 is 1, then CA[11:8] must be 0.
 3. LUA0 is used to select die in multi-LUN configuration.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Device and Array Organization

Figure 9: Array Organization - MT29F4G16

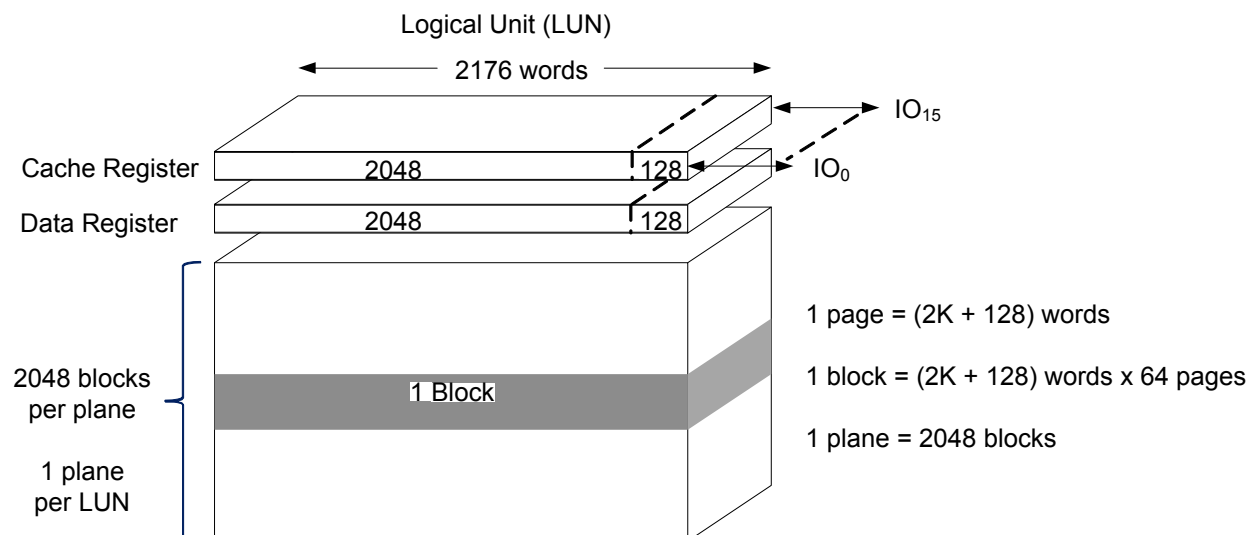


Table 11: Array Addressing (×16)

Cycle	I/O[15:8]	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0
First	LOW	CA7	CA6	CA5	CA4	CA3	CA2	CA1	CA0
Second	LOW	LOW	LOW	LOW	LOW	CA11 ²	CA10	CA9	CA8
Third	LOW	BA7	BA6	PA5	PA4	PA3	PA2	PA1	PA0
Fourth	LOW	BA15	BA14	BA13	BA12	BA11	BA10	BA9	BA8
Fifth	LOW	LOW	LOW	LOW	LOW	LOW	LOW	LOW	BA16

- Notes:
1. Block address concatenated with page address = actual page address. CAx = column address; PAx = page address; BAx = block address.
 2. If CA11 is 1, then CA[10:7] must be 0.







4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Asynchronous Interface Bus Operation

The bus on the device is multiplexed. Data I/O, addresses, and commands all share the same pins. I/O[15:8] are used only for data in the $\times 16$ configuration. Addresses and commands are always supplied on I/O[7:0].

The command sequence typically consists of a COMMAND LATCH cycle, ADDRESS INPUT cycles, and one or more DATA cycles, either READ or WRITE.

Table 12: Asynchronous Interface Mode Selection

Mode ¹	CE#	CLE	ALE	WE#	RE#	I/Ox	WP#
Standby ²	H	X	X	X	X	X	0V/V _{CC}
Command input	L	H	L		H	X	H
Address input	L	L	H		H	X	H
Data input	L	L	L		H	X	H
Data output	L	L	L	H		X	X
Write protect	X	X	X	X	X	X	L

- Notes:
1. Mode selection settings for this table: H = Logic level HIGH; L = Logic level LOW; X = V_{IH} or V_{IL}.
 2. WP# should be biased to CMOS LOW or HIGH for standby.

Asynchronous Enable/Standby

When the device is not performing an operation, the CE# pin is typically driven HIGH and the device enters standby mode. The memory will enter standby if CE# goes HIGH while data is being transferred and the device is not busy. This helps to reduce power consumption.

The CE# “Don’t Care” operation enables the NAND Flash to reside on the same asynchronous memory bus as other Flash or SRAM devices. Other devices on the memory bus can then be accessed while the NAND Flash is busy with internal operations. This capability is important for designs that require multiple NAND Flash devices on the same bus.

A HIGH CLE signal indicates that a command cycle is taking place. A HIGH ALE signal signifies that an ADDRESS INPUT cycle is occurring.

Asynchronous Commands

An asynchronous command is written from I/O[7:0] to the command register on the rising edge of WE# when CE# is LOW, ALE is LOW, CLE is HIGH, and RE# is HIGH.

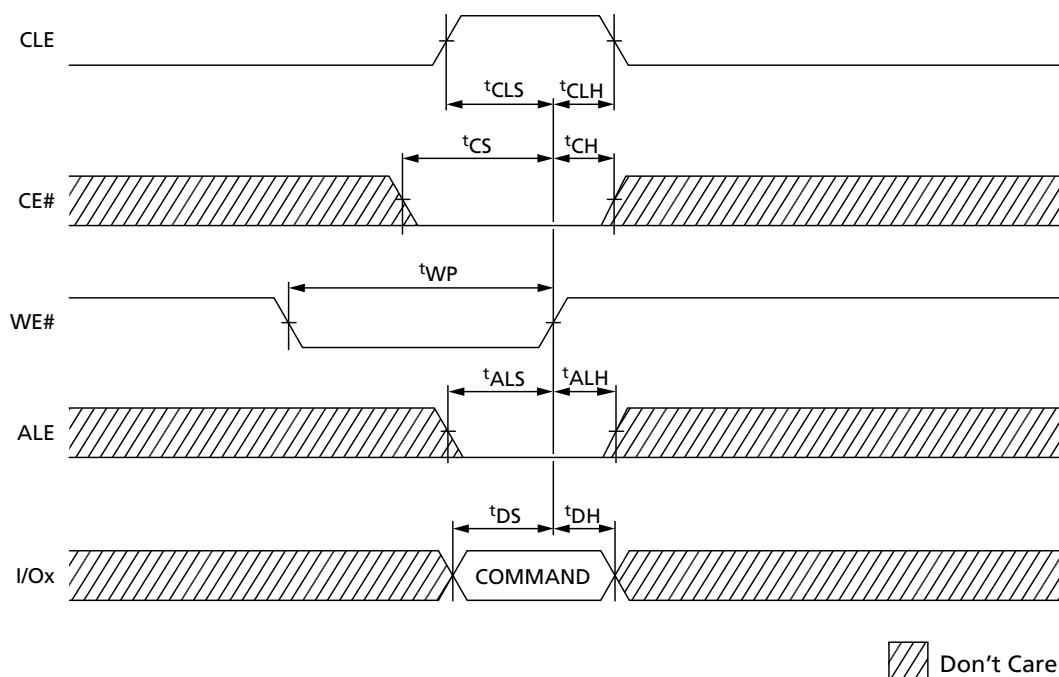
Commands are typically ignored by die (LUNs) that are busy (RDY = 0); however, some commands, including READ STATUS (70h) and READ STATUS ENHANCED (78h), are accepted by die (LUNs) even when they are busy.

For devices with a $\times 16$ interface, I/O[15:8] must be written with zeros when a command is issued.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Figure 10: Asynchronous Command Latch Cycle



Asynchronous Addresses

An asynchronous address is written from I/O[7:0] to the address register on the rising edge of WE# when CE# is LOW, ALE is HIGH, CLE is LOW, and RE# is HIGH.

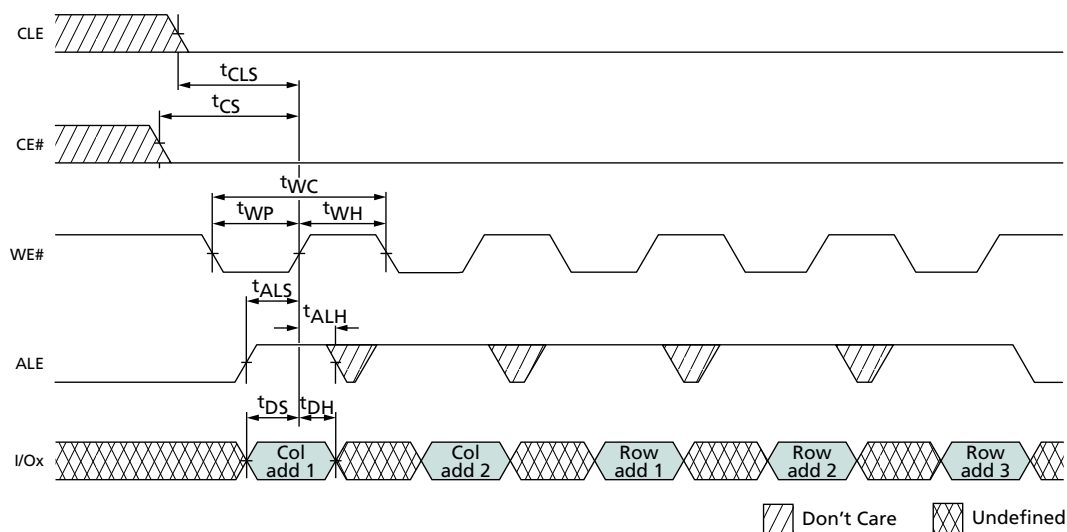
Bits that are not part of the address space must be LOW (see Device and Array Organization). The number of cycles required for each command varies. Refer to the command descriptions to determine addressing requirements.

Addresses are typically ignored by die (LUNs) that are busy (RDY = 0); however, some addresses are accepted by die (LUNs) even when they are busy; for example, like address cycles that follow the READ STATUS ENHANCED (78h) command.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Figure 11: Asynchronous Address Latch Cycle



Asynchronous Data Input

Data is written from I/O[7:0] to the cache register of the selected die (LUN) on the rising edge of WE# when CE# is LOW, ALE is LOW, CLE is LOW, and RE# is HIGH.

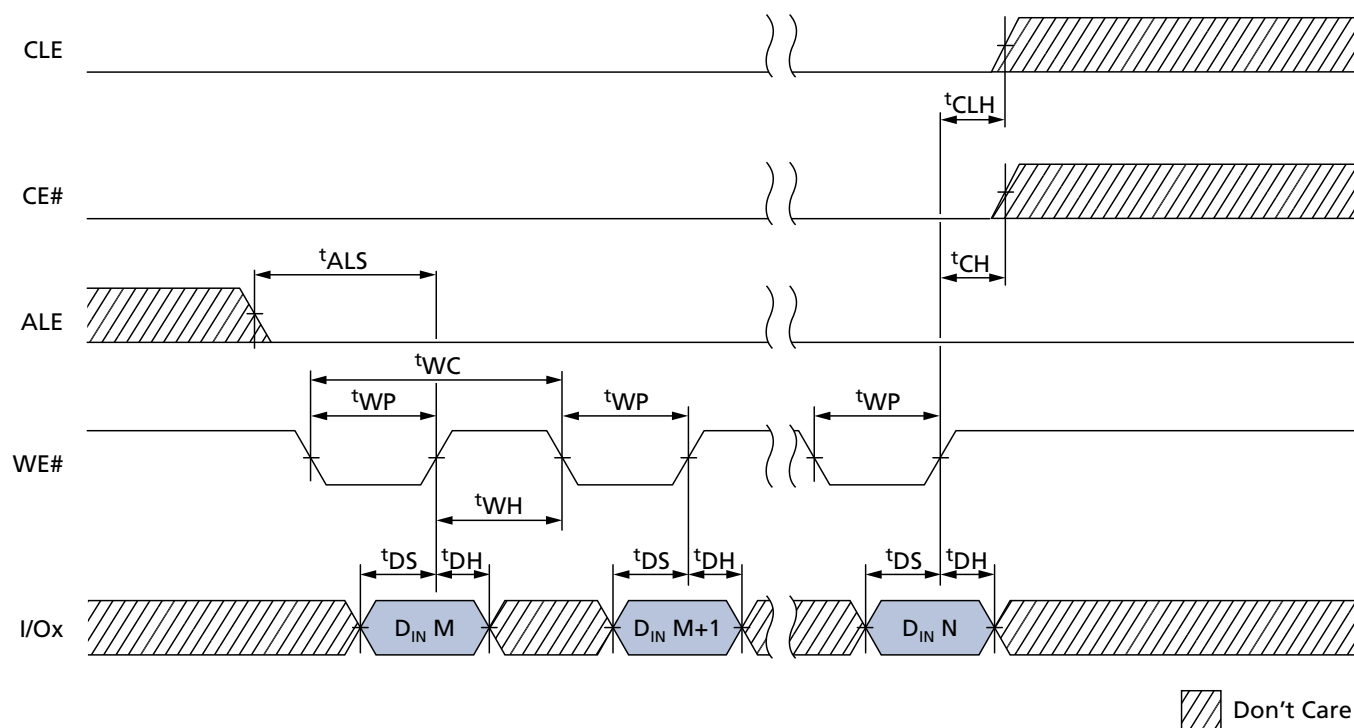
Data input is ignored by die (LUNs) that are not selected or are busy (RDY = 0). Data is written to the data register on the rising edge of WE# when CE#, CLE, and ALE are LOW, and the device is not busy.

Data input utilizes I/O[7:0] on x8 devices and I/O[15:0] on x16 devices.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Figure 12: Asynchronous Data Input Cycles





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Asynchronous Data Output

Data can be output from a die (LUN) if it is in a ready state. Data output is supported following a READ operation from the NAND Flash array. Data is output from the cache register of the selected die (LUN) to IO bus on the falling edge of RE# when CE# is LOW, ALE is LOW, CLE is LOW, and WE# is HIGH.

If the host controller is using a t_{RC} of 30ns or greater, the host can latch the data on the rising edge of RE# (see the figure below for proper timing). If the host controller is using a t_{RC} of less than 30ns, the host can latch the data on the next falling edge of RE#.

Using the READ STATUS ENHANCED (78h) command prevents data contention following an interleaved die (multi-LUN) operation. After issuing the READ STATUS ENHANCED (78h) command, to enable data output, issue the READ MODE (00h) command.

Data output requests are typically ignored by a die (LUN) that is busy (RDY = 0); however, it is possible to output data from the status register even when a die (LUN) is busy by first issuing the READ STATUS or READ STATUS ENHANCED (78h) command.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Figure 13: Asynchronous Data Output Cycles

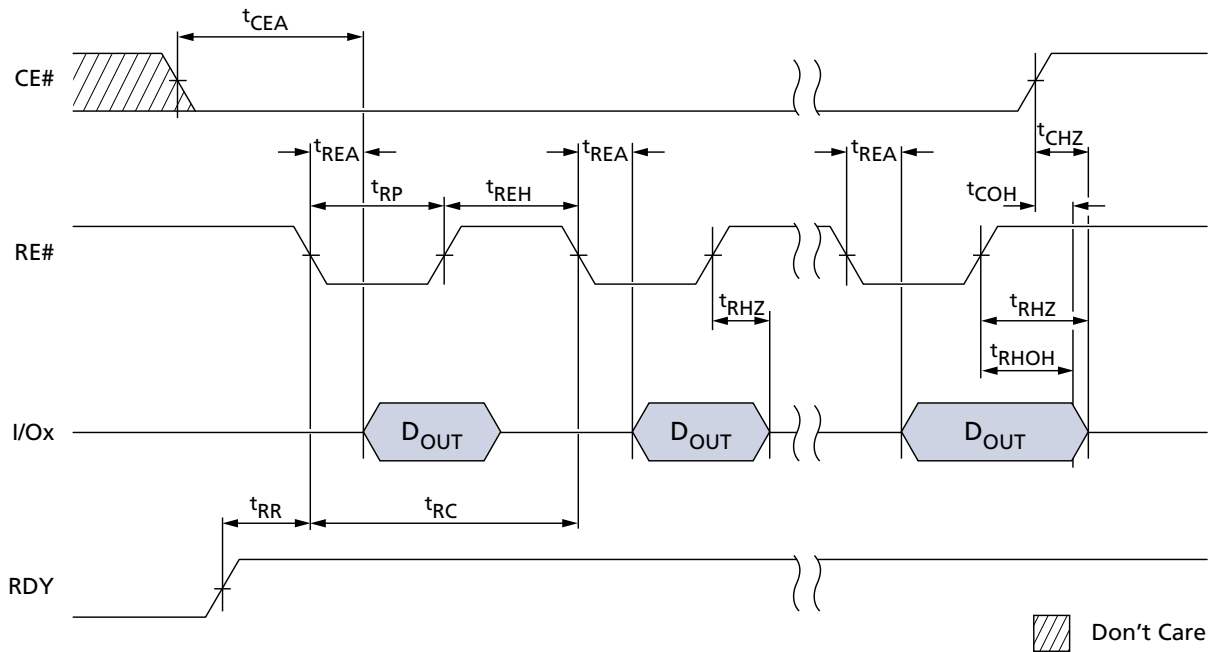
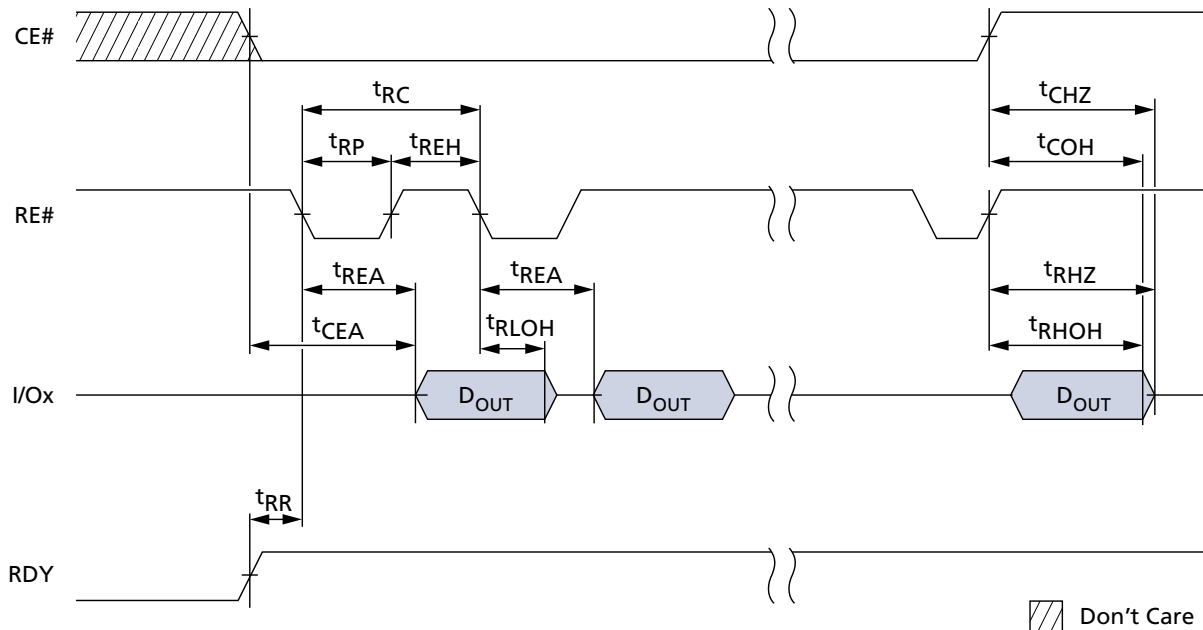


Figure 14: Asynchronous Data Output Cycles (EDO Mode)



Write Protect#

The write protect# (WP#) signal enables or disables PROGRAM and ERASE operations to a target. When WP# is LOW, PROGRAM and ERASE operations are disabled. When WP# is HIGH, PROGRAM and ERASE operations are enabled.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

It is recommended that the host drive WP# LOW during power-on until V_{CC} is stable to prevent inadvertent PROGRAM and ERASE operations (see Device Initialization for additional details).

WP# must be transitioned only when the target is not busy and prior to beginning a command sequence. After a command sequence is complete and the target is ready, WP# can be transitioned. After WP# is transitioned, the host must wait t_{WW} before issuing a new command.

The WP# signal is always an active input, even when CE# is HIGH. This signal should not be multiplexed with other signals.

Ready/Busy#

The ready/busy# (R/B#) signal provides a hardware method of indicating whether a target is ready or busy. A target is busy when one or more of its die (LUNs) are busy (RDY = 0). A target is ready when all of its die (LUNs) are ready (RDY = 1). Because each die (LUN) contains a status register, it is possible to determine the independent status of each die (LUN) by polling its status register instead of using the R/B# signal (see Status Operations for details regarding die (LUN) status).

This signal requires a pull-up resistor, R_p , for proper operation. R/B# is HIGH when the target is ready, and transitions LOW when the target is busy. The signal's open-drain driver enables multiple R/B# outputs to be OR-tied. Typically, R/B# is connected to an interrupt pin on the system controller.

The combination of R_p and capacitive loading of the R/B# circuit determines the rise time of the R/B# signal. The actual value used for R_p depends on the system timing requirements. Large values of R_p cause R/B# to be delayed significantly. Between the 10% and 90% points on the R/B# waveform, the rise time is approximately two time constants (T_C).

$$T_C = R \times C$$

Where $R = R_p$ (resistance of pull-up resistor), and $C =$ total capacitive load.

The fall time of the R/B# signal is determined mainly by the output impedance of the R/B# signal and the total load capacitance. Approximate R_p values using a circuit load of 100pF are provided in Figure 18 (page 36).

The minimum value for R_p is determined by the output drive capability of the R/B# signal, the output voltage swing, and V_{CC} .

$$R_p = \frac{V_{CC} (MAX) - V_{OL} (MAX)}{I_{OL} + \Sigma I_L}$$

Where ΣI_L is the sum of the input currents of all devices tied to the R/B# pin.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Figure 15: READ/BUSY# Open Drain

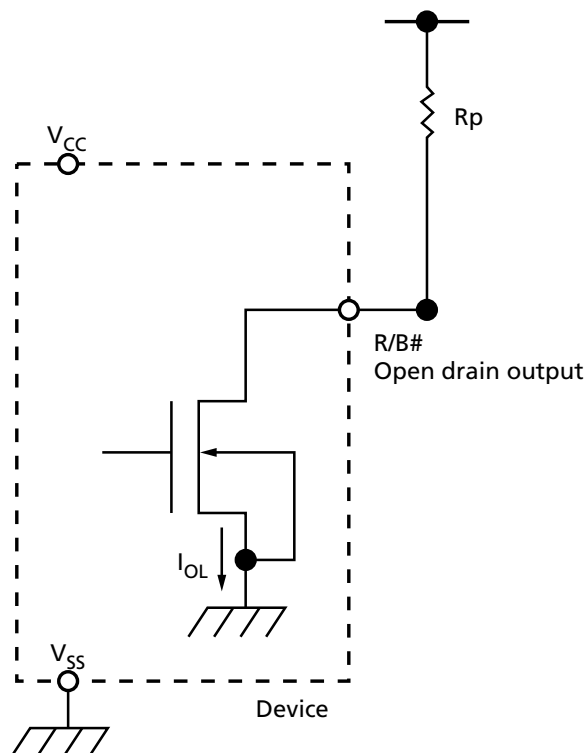
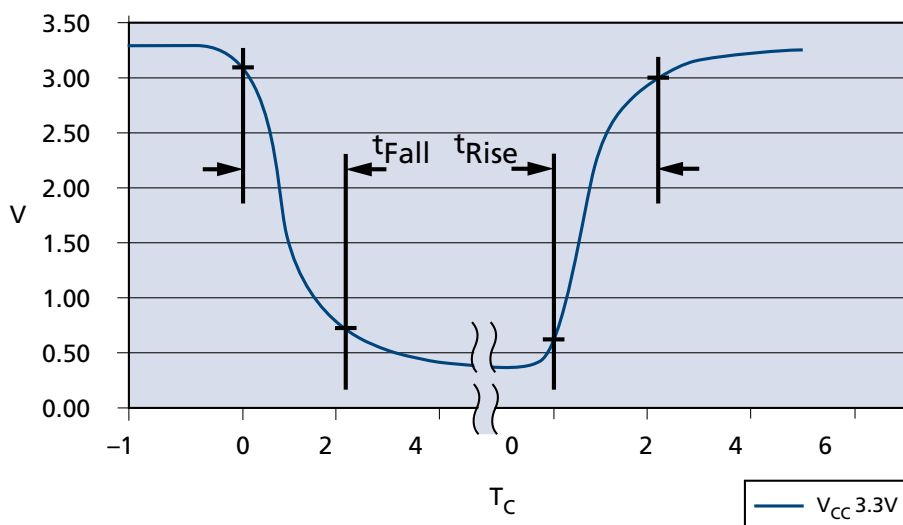


Figure 16: t_{Fall} and t_{Rise} (3.3V V_{CC})



- Notes:
1. t_{Fall} and t_{Rise} calculated at 10% and 90% points.
 2. t_{Rise} dependent on external capacitance and resistive loading and output transistor impedance.
 3. t_{Rise} primarily dependent on external pull-up resistor and external capacitive loading.
 4. $t_{\text{Fall}} = 10\text{ns}$ at 3.3V.
 5. See T_C values in Figure 18 (page 36) for approximate R_p value and T_C .



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Bus Operation

Figure 17: I_{OL} vs. R_p ($V_{CC} = 3.3V$ V_{CC})

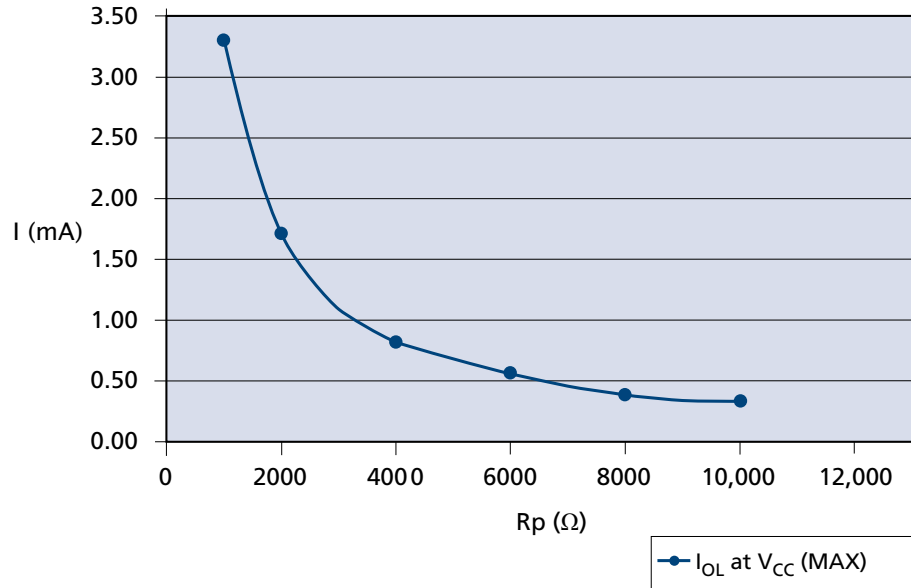
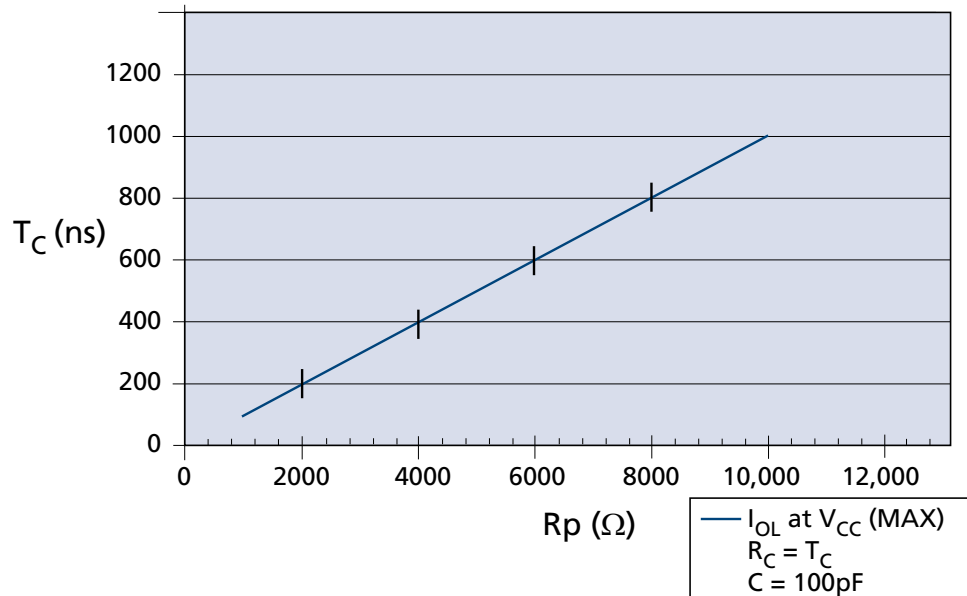


Figure 18: T_C vs. R_p



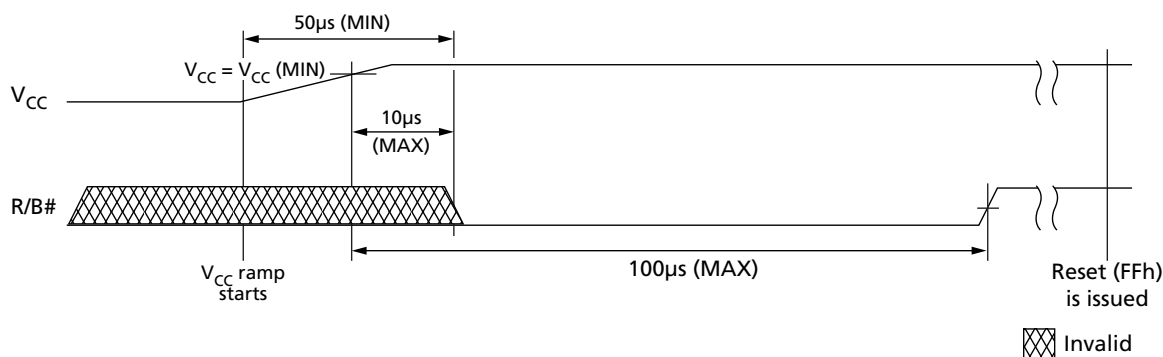


Device Initialization

Micron NAND Flash devices are designed to prevent data corruption during power transitions. V_{CC} is internally monitored. (The $WP\#$ signal supports additional hardware protection during power transitions.) When ramping V_{CC} , use the following procedure to initialize the device:

1. Ramp V_{CC} .
2. The host must wait for $R/B\#$ to be valid and HIGH before issuing RESET (FFh) to any target. The $R/B\#$ signal becomes valid when $50\mu s$ has elapsed since the beginning the V_{CC} ramp, and $10\mu s$ has elapsed since V_{CC} reaches $V_{CC,min}$.
3. If not monitoring $R/B\#$, the host must wait at least $100\mu s$ after V_{CC} reaches $V_{CC,min}$. If monitoring $R/B\#$, the host must wait until $R/B\#$ is HIGH.
4. The asynchronous interface is active by default for each target. Each LUN draws less than an average of $10mA$ (I_{ST}) measured over intervals of $1ms$ until the RESET (FFh) command is issued.
5. The RESET (FFh) command must be the first command issued to all targets (CE#s) after the NAND Flash device is powered on. Each target will be busy for $1ms$ after a RESET command is issued. The RESET busy time can be monitored by polling $R/B\#$ or issuing the READ STATUS (70h) command to poll the status register.
6. The device is now initialized and ready for normal operation.

Figure 19: R/B# Power-On Behavior



**4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP
Power Cycle Requirements****Power Cycle Requirements**

Upon power-down the NAND device requires a maximum voltage and minimum time that the host must hold V_{CC} and V_{CCQ} below the voltage prior to power-on.

Table 13: Power Cycle Requirements

Device can not operate correctly when V_{CC} is lower than 2.5V@3.3V or 1.5V@1.8V.

Parameter	Value	Unit
Maximum V_{CC}/V_{CCQ}	100	mV
Minimum time below maximum voltage	100	nS



Command Definitions

Table 14: Command Set

Command	Command Cycle #1	Number of Valid Address Cycles	Data Input Cycles	Command Cycle #2	Valid While Selected LUN is Busy ¹	Valid While Other LUNs are Busy ¹	Notes
Reset Operations							
RESET	FFh	0	–	–	Yes	Yes	–
Identification Operation							
READ ID	90h	1	–	–	No	No	–
READ PARAMETER PAGE	ECh	1	–	–	No	No	–
READ UNIQUE ID	EDh	1	–	–	No	No	–
Feature Operations							
GET FEATURES	EEh	1	–	–	No	No	–
SET FEATURES	EFh	1	4	–	No	No	–
Status Operations							
READ STATUS	70h	0	–	–	Yes	N/A	–
READ STATUS ENHANCED	78h	3	–	–	Yes	Yes	2
Column Address Operations							
RANDOM DATA READ	05h	2	–	E0h	No	Yes	–
RANDOM DATA INPUT	85h	2	Optional	–	No	Yes	–
PROGRAM FOR INTERNAL DATA MOVE	85h	5	Optional	–	No	Yes	3
READ Operations							
READ MODE	00h	0	–	–	No	Yes	–
READ PAGE	00h	5	–	30h	No	Yes	–
READ PAGE CACHE SEQUENTIAL	31h	0	–	–	No	Yes	4
READ PAGE CACHE RANDOM	00h	5	–	31h	No	Yes	4
READ PAGE CACHE LAST	3Fh	0	–	–	No	Yes	4
Program Operations							
PROGRAM PAGE	80h	5	Yes	10h	No	Yes	2
PROGRAM PAGE CACHE	80h	5	Yes	15h	No	Yes	2, 5
Erase Operations							
ERASE BLOCK	60h	3	–	D0h	No	Yes	–
Internal Data Move Operations							
READ FOR INTERNAL DATA MOVE	00h	5	–	35h	No	Yes	3



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Command Definitions

Table 14: Command Set (Continued)

Command	Command Cycle #1	Number of Valid Address Cycles	Data Input Cycles	Command Cycle #2	Valid While Selected LUN is Busy ¹	Valid While Other LUNs are Busy ¹	Notes
PROGRAM FOR INTERNAL DATA MOVE	85h	5	Optional	10h	No	Yes	–
Block Lock Operations							
BLOCK UNLOCK LOW	23h	3	–	–	No	Yes	–
BLOCK UNLOCK HIGH	24h	3	–	–	No	Yes	–
BLOCK LOCK	2Ah	–	–	–	No	Yes	–
BLOCK LOCK-TIGHT	2Ch	–	–	–	No	Yes	–
BLOCK LOCK READ STATUS	7Ah	3	–	–	No	Yes	–
PERMANENT BOOT BLOCK PROTECT	–	–	–	–	No	Yes	–
PERMANENT BOOT BLOCK PROTECT	83h	5	–	10h	No	Yes	–
PERMANENT BOOT BLOCK PROTECT Disable	80h	5	Yes	10h	No	No	–
One-Time Programmable (OTP) Operations							
OTP DATA LOCK BY BLOCK (ONFI)	80h	5	No	10h	No	No	6
OTP DATA PROGRAM (ONFI)	80h	5	Yes	10h	No	No	6
OTP DATA READ (ONFI)	00h	5	No	30h	No	No	6

- Notes:
1. Busy means RDY = 0.
 2. These commands can be used for interleaved die (multi-LUN) operations (applicable to Multi-LUN Operations).
 3. Do not cross plane address boundaries when using READ for INTERNAL DATA MOVE and PROGRAM for INTERNAL DATA MOVE.
 4. Issuing a READ PAGE CACHE series (31h, 00h-31h, 00h-32h, 3Fh) command when the array is busy (RDY = 1, ARDY = 0) is supported if the previous command was a READ PAGE (00h-30h) or READ PAGE CACHE series command; otherwise, it is prohibited.
 5. Issuing a PROGRAM PAGE CACHE (80h-15h) command when the array is busy (RDY = 1, ARDY = 0) is supported if the previous command was a PROGRAM PAGE CACHE (80h-15h) command; otherwise, it is prohibited.
 6. OTP commands can be entered only after issuing the SET FEATURES command with the feature address.



Reset Operations

RESET (FFh)

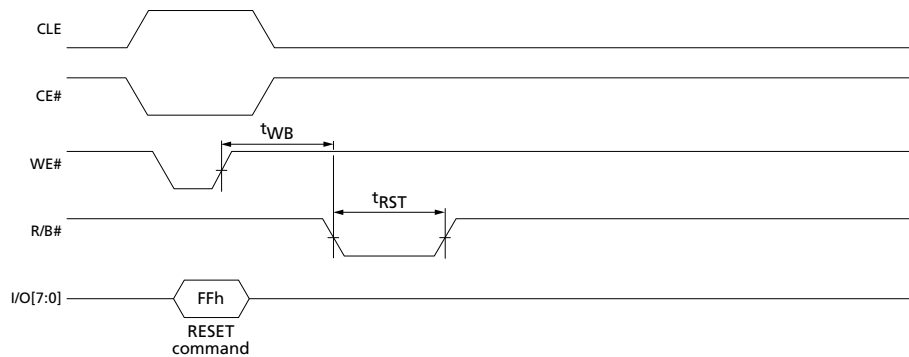
The RESET command is used to put the memory device into a known condition and to abort the command sequence in progress.

READ, PROGRAM, and ERASE commands can be aborted while the device is in the busy state. The contents of the memory location being programmed or the block being erased are no longer valid. The data may be partially erased or programmed, and is invalid. The command register is cleared and is ready for the next command. The data register and cache register contents are marked invalid.

The status register contains the value E0h when WP# is HIGH; otherwise it is written with a 60h value. R/B# goes LOW for t_{RST} after the RESET command is written to the command register.

The RESET command must be issued to all CE#s as the first command after power-on. The device will be busy for a maximum of 1ms.

Figure 20: RESET (FFh) Operation





Identification Operations

READ ID (90h)

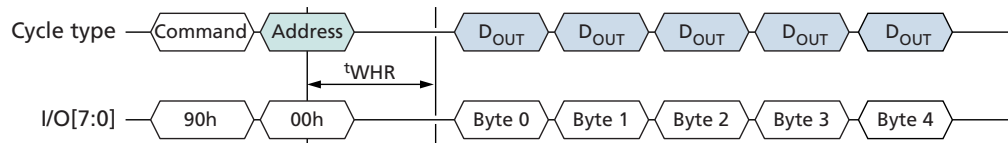
The READ ID (90h) command is used to read identifier codes programmed into the target. This command is accepted by the target only when all die (LUNs) on the target are idle.

Writing 90h to the command register puts the target in read ID mode. The target stays in this mode until another valid command is issued.

When the 90h command is followed by an 00h address cycle, the target returns a 5-byte identifier code that includes the manufacturer ID, device configuration, and part-specific information.

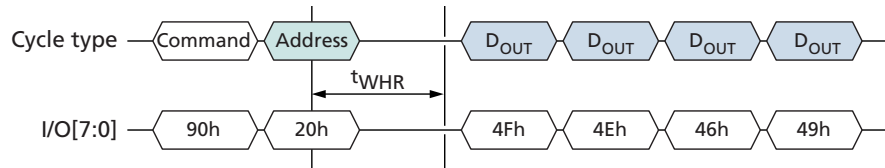
When the 90h command is followed by a 20h address cycle, the target returns the 4-byte ONFI identifier code.

Figure 21: READ ID (90h) with 00h Address Operation



Note: 1. See READ ID Parameter tables for byte definitions.

Figure 22: READ ID (90h) with 20h Address Operation



Note: 1. See READ ID Parameter tables for byte definitions.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP READ ID Parameter Tables

READ ID Parameter Tables

Table 15: READ ID Parameters for Address 00h

Byte	Options	I/07	I/06	I/05	I/04	I/03	I/02	I/01	I/00	Value
Byte 0 – Manufacturer ID										
Manufacturer	Micron	0	0	1	0	1	1	0	0	2Ch
Byte 1 – Device ID										
MT29F4G08ABBFA	4Gb, x8, 1.8V	1	0	1	0	1	1	0	0	ACh
MT29F4G16ABBFA	4Gb, x16, 1.8V	1	0	1	1	1	1	0	0	BCh
MT29F4G08ABAFA	4Gb, x8, 3.3V	1	1	0	1	1	1	0	0	DCh
MT29F4G16ABAFA	4Gb, x16, 3.3V	1	1	0	0	1	1	0	0	CCh
MT29F8G08ADAFA	8Gb, x8, 3.3V	1	1	0	1	0	0	1	1	D3h
MT29F8G08ADBFA	8Gb, x8, 1.8V	1	0	1	0	0	0	1	1	A3h
Byte 2										
Number of die per CE	1							0	0	00b
Cell type	SLC					0	0			00b
Number of simultaneously programmed pages	1 (4Gb)			0	0					00b
	2 (8Gb)			0	1					01b
Interleaved operations between multiple die	Not supported (4Gb)		0							0b
	Supported (8Gb)		1							1b
Cache programming	Supported	1								1b
Byte value	4Gb	1	0	0	0	0	0	0	0	80h
	8Gb	1	1	0	1	0	0	0	0	D0h
Byte 3										
Page size	4KB							1	0	10b
Spare area size (bytes)	256B						1			1b
Block size (without spare)	256KB			1	0					10b
Organization	x8		0							0b
Organization	x16		1							1b
Serial access (MIN)	1.8V	0				0				0b
	3.3V	1				0				10b
Byte value	x8, 1.8V	0	0	1	0	0	1	1	0	26h
	x8, 3.3V	1	0	1	0	0	1	1	0	A6h
	x16, 1.8V	0	1	1	0	0	1	1	0	66h
	x16, 3.3V	1	1	1	0	0	1	1	0	E6h
Byte 4										
Internal ECC level	8-bit ECC/512B (main) + 16B (Spare)+16B (parity) bytes							1	0	10b
Planes per CE#	1					0	0			00b
	2					0	1			01b



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP READ ID Parameter Tables

Table 15: READ ID Parameters for Address 00h (Continued)

Byte	Options	I/07	I/06	I/05	I/04	I/03	I/02	I/01	I/00	Value
Plane size	4Gb		1	1	0					110b
Internal ECC	ECC Disabled	0								0b
	ECC Enabled	1								1b
Byte value	4Gb	x	1	1	0	0	0	1	0	62h
	8Gb	x	1	1	0	0	1	1	0	66h

Note: 1. b = binary; h = hexadecimal.

Table 16: READ ID Parameters for Address 20h

Byte	Options	I/07	I/06	I/05	I/04	I/03	I/02	I/01	I/00	Value
0	"O"	0	1	0	0	1	1	1	1	4Fh
1	"N"	0	1	0	0	1	1	1	0	4Eh
2	"F"	0	1	0	0	0	1	1	0	46h
3	"I"	0	1	0	0	1	0	0	1	49h
4	Undefined	X	X	X	X	X	X	X	X	XXh

Note: 1. h = hexadecimal; X = V_{IH} or V_{IL} .



READ PARAMETER PAGE (ECh)

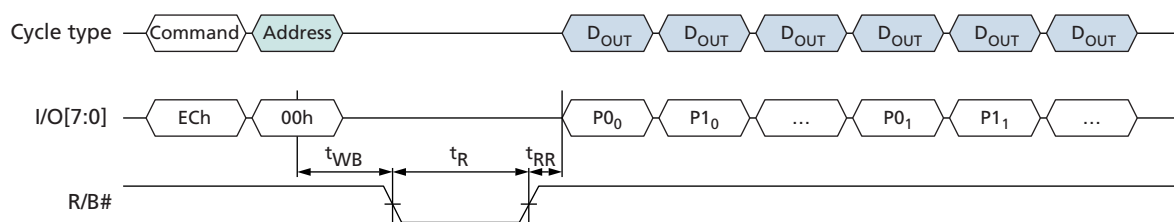
The READ PARAMETER PAGE (ECh) command is used to read the ONFI parameter page programmed into the target. This command is accepted by the target only when all die (LUNs) on the target are idle.

Writing ECh to the command register puts the target in read parameter page mode. The target stays in this mode until another valid command is issued.

When the ECh command is followed by an 00h address cycle, the target goes busy for t_R . If the READ STATUS (70h) command is used to monitor for command completion, the READ MODE (00h) command must be used to re-enable data output mode. Use of the READ STATUS ENHANCED (78h) command is prohibited while the target is busy and during data output.

A minimum of three copies of the parameter page are stored in the device. Each parameter page is 256 bytes. If desired, the RANDOM DATA READ (05h-E0h) command can be used to change the location of data output.

Figure 23: READ PARAMETER (ECh) Operation





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Parameter Page Data Structure Table

Parameter Page Data Structure Table

Table 17: Parameter Page Data Structure

Byte	Description	Value (hex)
0–3	Parameter page signature	4Fh, 4Eh, 46h, 49h
4–5	Revision number	02h, 00h
6–7	Features Supported	4Gb (x8 I/O)
		4Gb (x16 I/O)
		8Gb (x8 I/O)
8–9	Optional commands support	3Fh, 00h
10–31	Reserved	00h
32–43	Device manufacturer	4Dh, 49h, 43h, 52h, 4Fh, 4Eh, 20h, 20h, 20h, 20h, 20h, 20h
44–63	Device model	MT29F4G08ABAF4H4
		4Dh, 54h, 32h, 39h, 46h, 34h, 47h, 30h, 38h, 41h, 42h, 41h, 46h, 41h, 48h, 34h, 20h, 20h, 20h, 20h
		MT29F4G16ABAF4H4
		4Dh, 54h, 32h, 39h, 46h, 34h, 47h, 31h, 36h, 41h, 42h, 41h, 46h, 41h, 48h, 34h, 20h, 20h, 20h, 20h
		MT29F4G08ABAF4WP
		4Dh, 54h, 32h, 39h, 46h, 34h, 47h, 30h, 38h, 41h, 42h, 41h, 46h, 41h, 57h, 50h, 20h, 20h, 20h, 20h
		MT29F8G08ADAF4H4
		4Dh, 54h, 32h, 39h, 46h, 38h, 47h, 30h, 38h, 41h, 44h, 41h, 46h, 41h, 48h, 34h, 20h, 20h, 20h, 20h
		MT29F8G08ADAF4WP
		4Dh, 54h, 32h, 39h, 46h, 38h, 47h, 30h, 38h, 41h, 44h, 41h, 46h, 41h, 57h, 50h, 20h, 20h, 20h, 20h
		MT29F8G08ADBFAH4
		4Dh, 54h, 32h, 39h, 46h, 38h, 47h, 30h, 38h, 41h, 44h, 42h, 46h, 41h, 48h, 34h, 20h, 20h, 20h, 20h
		MT29F4G08ABBFAH4
		4Dh, 54h, 32h, 39h, 46h, 34h, 47h, 30h, 38h, 41h, 42h, 42h, 46h, 41h, 48h, 34h, 20h, 20h, 20h, 20h
		MT29F4G16ABBFAH4
		4Dh, 54h, 32h, 39h, 46h, 34h, 47h, 31h, 36h, 41h, 42h, 42h, 46h, 41h, 48h, 34h, 20h, 20h, 20h, 20h
64	Manufacturer ID	2Ch
65–66	Date code	00h
67–79	Reserved	00h
80–83	Number of data bytes per page	00h, 10h, 00h, 00h
84–85	Number of spare bytes per page	00h, 01h
86–89	Number of data bytes per partial page	00h, 04h, 00h, 00h
90–91	Number of spare bytes per partial page	40h, 00h
92–95	Number of pages per block	40h, 00h, 00h, 00h
96–99	Number of blocks per unit	00h, 08h, 00h, 00h
100	Number of logical units (4Gb)	01h
	Number of logical units (8Gb)	02h
101	Number of address cycles	23h



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Parameter Page Data Structure Table

Table 17: Parameter Page Data Structure (Continued)

Byte	Description	Value (hex)
102	Number of bits per cell	01h
103–104	Bad blocks maximum per unit	28h, 00h
105–106	Block endurance	01h, 05h
107	Guaranteed valid blocks at beginning of target	08h
108–109	Block endurance for guaranteed valid blocks	00h
110	Number of programs per page	04h
111	Partial programming attributes	00h
112	Number of ECC bits	08h
113	Number of interleaved address bits	01h
114	Interleaved operation attributes	0Eh
115–127	Reserved	00h
128	I/O pin capacitance	08h
129–130	Timing mode support	V _{CC} = 3.3V
		V _{CC} = 1.8V
131–132	Program cache timing mode support	V _{CC} = 3.3V
		V _{CC} = 1.8V
133–134	t _{PROG} (MAX) page program time	58h, 02h
135–136	t _{ERS} (MAX) block erase time	10h, 27h
137–138	t _R (MAX) page read time	19h, 00h
139–140	t _{CCS} (MIN)	64h, 00h
141–163	Reserved	00h
164–165	Vendor-specific revision number	01h, 00h
166–179	Vendor-specific	00h, 00h, 00h, 02h, 04h, 80h, 01h, 81h, 04h, 03h, 02h, 01h, 30h, 90h
180–247	Reserved	00h
248	ECC maximum correct ability	00h
249	Die select feature	00h
250–253	Reserved	00h
254–255	Integrity CRC	Calculated
256–512	2nd copy of the parameter table	
513–768	3rd copy of the parameter table	
769–2048	Additional redundant parameter pages	



READ UNIQUE ID (EDh)

The READ UNIQUE ID (EDh) command is used to read a unique identifier programmed into the target. This command is accepted by the target only when all die (LUNs) on the target are idle.

Writing EDh to the command register puts the target in read unique ID mode. The target stays in this mode until another valid command is issued.

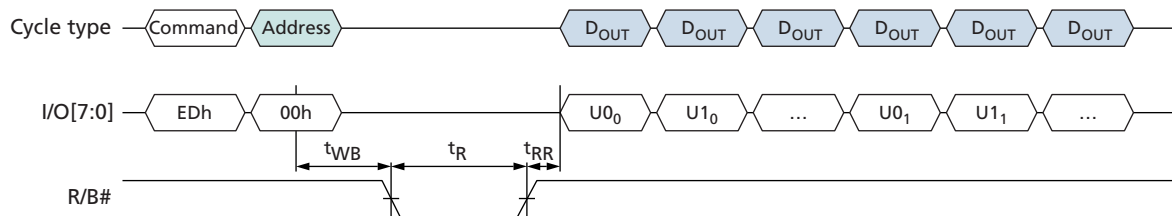
When the EDh command is followed by an 00h address cycle, the target goes busy for t_R . If the READ STATUS (70h) command is used to monitor for command completion, the READ MODE (00h) command must be used to re-enable data output mode.

After t_R completes, the host enables data output mode to read the unique ID. When the asynchronous interface is active, one data byte is output per RE# toggle.

Sixteen copies of the unique ID data are stored in the device. Each copy is 32 bytes. The first 16 bytes of a 32-byte copy are unique data, and the second 16 bytes are the complement of the first 16 bytes. The host should XOR the first 16 bytes with the second 16 bytes. If the result is 16 bytes of FFh, then that copy of the unique ID data is correct. In the event that a non-FFh result is returned, the host can repeat the XOR operation on a subsequent copy of the unique ID data. If desired, the RANDOM DATA READ (05h-E0h) command can be used to change the data output location.

The upper eight I/Os on a x16 device are not used and are a “Don’t Care” for x16 devices.

Figure 24: READ UNIQUE ID (EDh) Operation





Feature Operations

The SET FEATURES (EFh) and GET FEATURES (EEh) commands are used to modify the target's default power-on behavior. These commands use a one-byte feature address to determine which sub-feature parameters will be read or modified. Each feature address (in the 00h to FFh range) is defined in below. The SET FEATURES (EFh) command writes sub-feature parameters (P1–P4) to the specified feature address. The GET FEATURES command reads the sub-feature parameters (P1–P4) at the specified feature address.

Table 18: Feature Address Definitions

Feature Address	Definition
00h	Reserved
01h	Timing mode
02h–7Fh	Reserved
80h	Programmable output drive strength
81h	Programmable RB# pull-down strength
82h–FFh	Reserved
90h	Array operation mode

Table 19: Feature Addresses 90h: Timing Mode

Sub-feature Parameter	Options	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0	Value	Notes
P1											
Timing mode	Normal	Reserved (0)							0	00h	1
	OTP operation	Reserved (0)							1	01h	
	OTP protection	Reserved (0)						1	1	03h	
	Disable ECC	Reserved (0)				0	0	0	0	00h	3
	Enable ECC	Reserved (0)				1	0	0	0	08h	1, 2
	Permanent block lock disable	Reserved (0)			1	0	0	0	0	10h	4
P2											
		Reserved (0)								00h	
P3											
		Reserved (0)								00h	
P4											
		Reserved (0)								00h	

- Notes:
1. These bits are reset to 00h after power cycle.
 2. Bit3 is used to enable/disable ECC. For ECC always on or ECC always off configuration, bit3 is reserved (0) and should be set to 0.
 3. For MPNs with "-ITE" ECC enabled by default, this bit is Reserved.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Feature Operations

- If Permanent block lock disable sequence is issued again to a part that has already been disabled, the part will be busy for t_{OBSY} and exit with SR=60h. The part will be busy for t_{OBSY_ECC} when ECC is enabled.

SET FEATURES (EFh)

The SET FEATURES (EFh) command writes the subfeature parameters (P1–P4) to the specified feature address to enable or disable target-specific features.

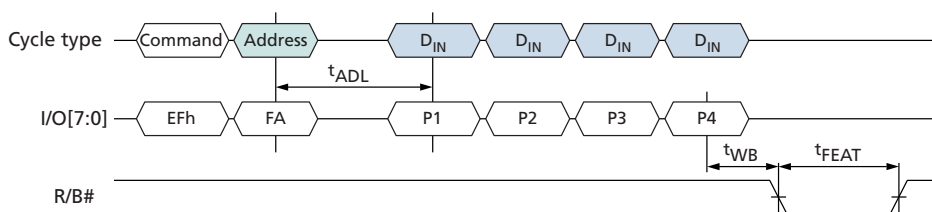
Writing EFh to the command register puts the target in the set features mode. The target stays in this mode until another command is issued.

The EFh command is followed by a valid feature address. The host waits for t_{ADL} before the subfeature parameters are input. When the asynchronous interface is active, one subfeature parameter is latched per rising edge of WE#.

After all four subfeature parameters are input, the target goes busy for t_{FEAT} . The READ STATUS (70h) command can be used to monitor for command completion.

Feature address 01h (timing mode) operation is unique. If SET FEATURES is used to modify the interface type, the target will be busy for t_{ITC} .

Figure 25: SET FEATURES (EFh) Operation



GET FEATURES (EEh)

The GET FEATURES (EEh) command reads the subfeature parameters (P1–P4) from the specified feature address. This command is accepted by the target only when all die (LUNs) on the target are idle.

Writing EEh to the command register puts the target in get features mode. The target stays in this mode until another valid command is issued.

When the EEh command is followed by a feature address, the target goes busy for t_{FEAT} . If the READ STATUS (70h) command is used to monitor for command completion, the READ MODE (00h) command must be used to re-enable data output mode. During and prior to data output, use of the READ STATUS ENHANCED (78h) command is prohibited.

After t_{FEAT} completes, the host enables data output mode to read the subfeature parameters.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Feature Operations

Figure 26: GET FEATURES (EEh) Operation

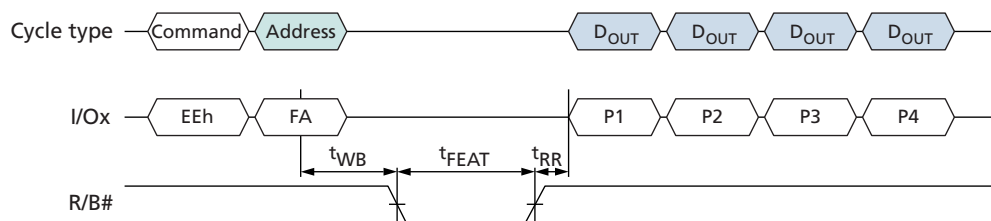


Table 20: Feature Addresses 01h: Timing Mode

Subfeature Parameter	Options	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0	Value	Notes
P1											
Timing mode	Mode 0 (default)	Reserved (0)					0	0	0	00h	1
	Mode 1	Reserved (0)					0	0	1	01h	
	Mode 2	Reserved (0)					0	1	0	02h	
	Mode 3	Reserved (0)					0	1	1	03h	
	Mode 4	Reserved (0)					1	0	0	04h	
	Mode 5	Reserved (0)					1	0	1	05h	
P2											
		Reserved (0)								00h	
P3											
		Reserved (0)								00h	
P4											
		Reserved (0)								00h	

Note: 1. The timing mode feature address is used to change the default timing mode. The timing mode should be selected to indicate the maximum speed at which the device will receive commands, addresses, and data cycles. The five supported settings for the timing mode are shown. The default timing mode is mode 0. The device returns to mode 0 when the device is power cycled. Supported timing modes are reported in the parameter page.

Table 21: Feature Addresses 80h: Programmable I/O Drive Strength

Subfeature Parameter	Options	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0	Value	Notes
P1											
I/O drive strength	Full (default)	Reserved (0)						0	0	00h	1
	Three-quarters	Reserved (0)						0	1	01h	
	One-half	Reserved (0)						1	0	02h	
	One-quarter	Reserved (0)						1	1	03h	
P2											



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Feature Operations

Table 21: Feature Addresses 80h: Programmable I/O Drive Strength (Continued)

Subfeature Parameter	Options	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0	Value	Notes	
		Reserved (0)									00h	
P3												
		Reserved (0)									00h	
P4												
		Reserved (0)									00h	

Note: 1. The programmable drive strength feature address is used to change the default I/O drive strength. Drive strength should be selected based on expected loading of the memory bus. This table shows the four supported output drive strength settings. The default drive strength is full strength. The device returns to the default drive strength mode when the device is power cycled. AC timing parameters may need to be relaxed if I/O drive strength is not set to full.

Table 22: Feature Addresses 81h: Programmable R/B# Pull-Down Strength

Subfeature Parameter	Options	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0	Value	Notes
P1											
R/B# pull-down strength	Full (default)							0	0	00h	1
	Three-quarters							0	1	01h	
	One-half							1	0	02h	
	One-quarter							1	1	03h	
P2											
		Reserved (0)								00h	
P3											
		Reserved (0)								00h	
P4											
		Reserved (0)								00h	

Note: 1. This feature address is used to change the default R/B# pull-down strength. Its strength should be selected based on the expected loading of R/B#. Full strength is the default, power-on value.



Status Operations

Each die (LUN) provides its status independently of other die (LUNs) on the same target through its 8-bit status register.

When a READ STATUS (70h) or READ STATUS ENHANCED (78h) command is issued, status register output is enabled. Status register contents are returned on I/O[7:0] for each data output request.

When the asynchronous interface is active and status register output is enabled, changes in the status register are seen on I/O[7:0] when CE# and RE# are LOW; it is not necessary to toggle RE# to see the status register update.

While monitoring the status register for completion of a data transfer from the Flash array to the data register (R), the host must issue the READ MODE (00h) command to disable the status register and enable data output (see Read Operations).

The READ STATUS (70h) command returns the status of the most recently selected die (LUN). To prevent data contention during or following an interleaved die (multi-LUN) operation, the host must enable only one die (LUN) for status output by using the READ STATUS ENHANCED (78h) command (see Interleaved Die (Multi-LUN) Operations).

Table 23: Status Register Definition

SR Bit	Program Page	Program Page Cache Mode	Page Read	Page Read Cache Mode	Block Erase	Description
7	Write protect	Write protect	Write protect	Write protect	Write protect	0 = Protected 1 = Not protected
6	RDY	RDY cache	RDY	RDY cache	RDY	0 = Busy (PROGRAM operation in progress) 1 = Ready (Cache can accept data; R/B# follows)
5	ARDY	ARDY	ARDY	ARDY	ARDY	0 = Busy (PROGRAM operation in progress) 1 = Ready (Internal operations completed, if cache mode is used)
4	0	0	ECC status ¹	ECC status (N-1) ¹	0	00 = Normal or uncorrectable 01 = 4~6 10 = 1~3 11 = 7~8 (Rewrite recommended)
3	0	0			0	
2	–	–	–	–	–	Don't Care
1	FAILC (N-1)	FAILC (N-1)	Reserved	–	–	0 = Pass 1 = Fail This bit is valid only when RDY (SR bit 6) is 1. This bit retains the status of the previous valid program operation when the most recent program operation is complete.


Table 23: Status Register Definition (Continued)

SR Bit	Program Page	Program Page Cache Mode	Page Read	Page Read Cache Mode	Block Erase	Description
0	FAIL	FAIL (N)	FAIL ²	FAIL (N-1)	FAIL	0 = Pass 1 = Fail This bit is set if the most recent finished operation on the selected die (LUN) failed. This bit is valid only when ARDY (SR bit 5) is 1.

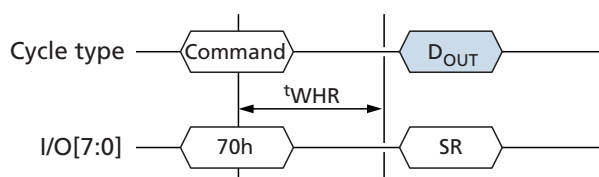
- Notes:
1. Bit = 11 when a rewrite is recommended because the page includes READ errors per sector (512-Byte [main] + 16-Byte [spare] + 16-Byte [parity]). When ECC is enabled, up to 7~8-bit error is corrected automatically.
 2. A status register bit defined as FAIL signifies that an uncorrectable READ error has occurred.

READ STATUS (70h)

The READ STATUS (70h) command returns the status of the last-selected die (LUN) on a target. This command is accepted by the last-selected die (LUN) even when it is busy (RDY = 0).

If there is only one die (LUN) per target, the READ STATUS (70h) command can be used to return status following any NAND command.

In devices that have more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations, the READ STATUS ENHANCED (78h) command must be used to select the die (LUN) that should report status. In this situation, using the READ STATUS (70h) command will result in bus contention, as two or more die (LUNs) could respond until the next operation is issued. The READ STATUS (70h) command can be used following all single die (LUN) operations.

Figure 27: READ STATUS (70h) Operation


READ STATUS ENHANCED (78h)

The READ STATUS ENHANCED (78h) command returns the status of the addressed die (LUN) on a target even when it is busy (RDY = 0). This command is accepted by all die (LUNs), even when they are BUSY (RDY = 0).

Writing 78h to the command register, followed by row address cycles containing the page, block, and LUN addresses, puts the selected die (LUN) into read status mode. The selected die (LUN) stays in this mode until another valid command is issued. Die (LUNs) that are not addressed are deselected to avoid bus contention.



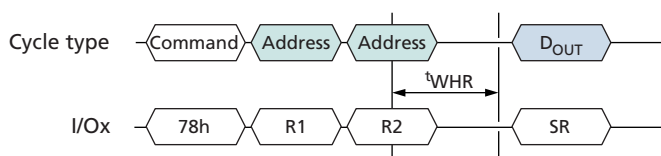
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Status Operations

The selected LUN's status is returned when the host requests data output. The RDY and ARDY bits of the status register are shared for all planes on the selected die (LUN). The FAILC and FAIL bits are specific to the plane specified in the row address.

The READ STATUS ENHANCED (78h) command also enables the selected die (LUN) for data output. To begin data output following a READ-series operation after the selected die (LUN) is ready (RDY = 1), issue the READ MODE (00h) command, then begin data output.

Use of the READ STATUS ENHANCED (78h) command is prohibited during the power-on RESET (FFh) command and when OTP mode is enabled. It is also prohibited following some of the other reset, identification, and configuration operations. See individual operations for specific details.

Figure 28: READ STATUS ENHANCED (78h) Operation





Column Address Operations

The column address operations affect how data is input to and output from the cache registers within the selected die (LUNs). These features provide host flexibility for managing data, especially when the host internal buffer is smaller than the number of data bytes or words in the cache register.

When the asynchronous interface is active, column address operations can address any byte in the selected cache register.

RANDOM DATA READ (05h-E0h)

The RANDOM DATA READ (05h-E0h) command changes the column address of the selected cache register and enables data output from the last selected die (LUN). This command is accepted by the selected die (LUN) when it is ready (RDY = 1; ARDY = 1). It is also accepted by the selected die (LUN) during CACHE READ operations (RDY = 1; ARDY = 0).

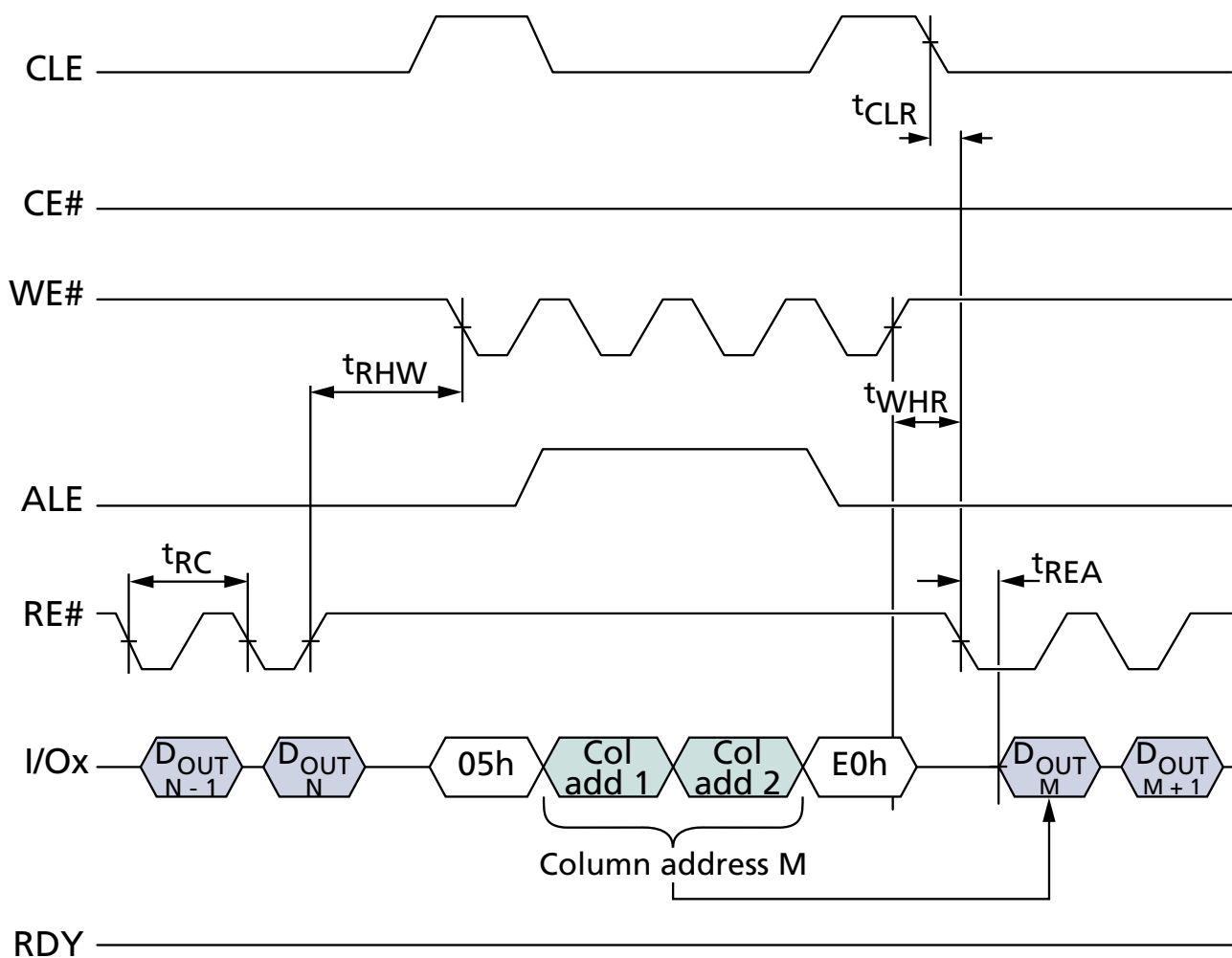
Writing 05h to the command register, followed by two column address cycles containing the column address, followed by the E0h command, puts the selected die (LUN) into data output mode. After the E0h command cycle is issued, the host must wait at least t_{WHR} before requesting data output. The selected die (LUN) stays in data output mode until another valid command is issued.

In devices with more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations, the READ STATUS ENHANCED (78h) command must be issued prior to issuing the RANDOM DATA READ (05h-E0h). In this situation, using the RANDOM DATA READ (05h-E0h) command without the READ STATUS ENHANCED (78h) command will result in bus contention because two or more die (LUNs) could output data.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Column Address Operations

Figure 29: RANDOM DATA READ (05h-E0h) Operation





RANDOM DATA INPUT (85h)

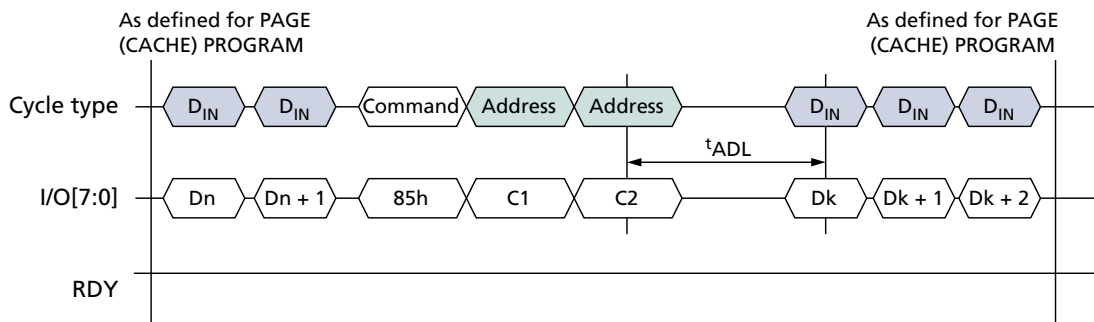
The RANDOM DATA INPUT (85h) command changes the column address of the selected cache register and enables data input on the last-selected die (LUN). This command is accepted by the selected die (LUN) when it is ready (RDY = 1; ARDY = 1). It is also accepted by the selected die (LUN) during cache program operations (RDY = 1; ARDY = 0).

Writing 85h to the command register, followed by two column address cycles containing the column address, puts the selected die (LUN) into data input mode. After the second address cycle is issued, the host must wait at least t_{ADL} before inputting data. The selected die (LUN) stays in data input mode until another valid command is issued. Though data input mode is enabled, data input from the host is optional. Data input begins at the column address specified.

The RANDOM DATA INPUT (85h) command is allowed after the required address cycles are specified, but prior to the final command cycle (10h, 11h, 15h) of the following commands while data input is permitted: PROGRAM PAGE (80h-10h), PROGRAM PAGE CACHE (80h-15h) and PROGRAM FOR INTERNAL DATA MOVE (85h-10h).

In devices that have more than one die (LUN) per target, the RANDOM DATA INPUT (85h) command can be used with other commands that support interleaved die (multi-LUN) operations.

Figure 30: RANDOM DATA INPUT (85h) Operation





PROGRAM FOR INTERNAL DATA INPUT (85h)

The PROGRAM FOR INTERNAL DATA INPUT (85h) command changes the row address (block and page) where the cache register contents will be programmed in the NAND Flash array. It also changes the column address of the selected cache register and enables data input on the specified die (LUN). This command is accepted by the selected die (LUN) when it is ready (RDY = 1; ARDY = 1). It is also accepted by the selected die (LUN) during cache programming operations (RDY = 1; ARDY = 0).

Write 85h to the command register. Then write two column address cycles and row address cycles. This updates the page and block destination of the selected device for the addressed LUN and puts the cache register into data input mode. After the fifth address cycle is issued the host must wait at least t_{ADL} before inputting data. The selected LUN stays in data input mode until another valid command is issued. Though data input mode is enabled, data input from the host is optional. Data input begins at the column address specified.

The PROGRAM FOR INTERNAL DATA INPUT (85h) command is allowed after the required address cycles are specified, but prior to the final command cycle (10h, 11h, 15h) of the following commands while data input is permitted: PROGRAM PAGE (80h-10h), PROGRAM PAGE CACHE (80h-15h) and PROGRAM FOR INTERNAL DATA MOVE (85h-10h). When used with these commands, the LUN address and plane select bits are required to be identical to the LUN address and plane select bits originally specified.

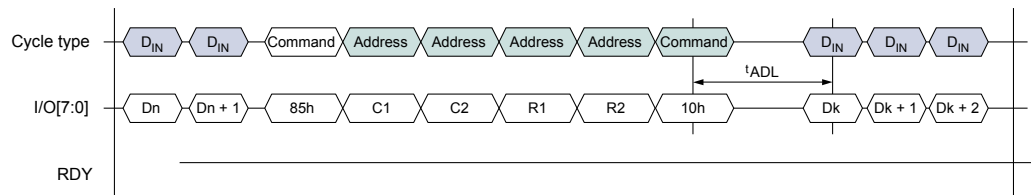
The PROGRAM FOR INTERNAL DATA INPUT (85h) command enables the host to modify the original page and block address for the data in the cache register to a new page and block address.

In devices that have more than one die (LUN) per target, the PROGRAM FOR INTERNAL DATA INPUT (85h) command can be used with other commands that support interleaved die (multi-LUN) operations.

The PROGRAM FOR INTERNAL DATA INPUT (85h) command can be used with the RANDOM DATA READ (05h-E0h) commands to read and modify cache register contents in small sections prior to programming cache register contents to the NAND Flash array. This capability can reduce the amount of buffer memory used in the host controller.

The RANDOM DATA INPUT (85h) command can be used during the PROGRAM FOR INTERNAL DATA MOVE command sequence to modify one or more bytes of the original data. First, data is copied into the cache register using the 00h-35h command sequence, then the RANDOM DATA INPUT (85h) command is written along with the address of the data to be modified next. New data is input on the external data pins. This copies the new data into the cache register.

Figure 31: PROGRAM FOR INTERNAL DATA INPUT (85h) Operation





Read Operations

The READ PAGE (00h-30h) command, when issued by itself, reads one page from the NAND Flash array to its cache register and enables data output for that cache register.

During data output the following commands can be used to read and modify the data in the cache registers: RANDOM DATA READ (05h-E0h) and RANDOM DATA INPUT (85h).

Read Cache Operations

To increase data throughput, the READ PAGE CACHE series (31h, 00h-31h) commands can be used to output data from the cache register while concurrently copying a page from the NAND Flash array to the data register.

To begin a read page cache sequence, begin by reading a page from the NAND Flash array to its corresponding cache register using the READ PAGE (00h-30h) command. R/B# goes LOW during ^tR and the selected die (LUN) is busy (RDY = 0, ARDY = 0). After ^tR (R/B# is HIGH and RDY = 1, ARDY = 1), issue either of these commands:

- READ PAGE CACHE SEQUENTIAL (31h) – copies the next sequential page from the NAND Flash array to the data register
- READ PAGE CACHE RANDOM (00h-31h) – copies the page specified in this command from the NAND Flash array to its corresponding data register

After the READ PAGE CACHE series (31h, 00h-31h) command has been issued, R/B# goes LOW on the target, and RDY = 0 and ARDY = 0 on the die (LUN) for ^tRCBSY while the next page begins copying data from the array to the data register. After ^tRCBSY, R/B# goes HIGH and the die's (LUN's) status register bits indicate the device is busy with a cache operation (RDY = 1, ARDY = 0). The cache register becomes available and the page requested in the READ PAGE CACHE operation is transferred to the data register. At this point, data can be output from the cache register, beginning at column address 0. The RANDOM DATA READ (05h-E0h) command can be used to change the column address of the data output by the die (LUN).

After outputting the desired number of bytes from the cache register, either an additional READ PAGE CACHE series (31h, 00h-31h) operation can be started or the READ PAGE CACHE LAST (3Fh) command can be issued.

If the READ PAGE CACHE LAST (3Fh) command is issued, R/B# goes LOW on the target, and RDY = 0 and ARDY = 0 on the die (LUN) for ^tRCBSY while the data register is copied into the cache register. After ^tRCBSY, R/B# goes HIGH and RDY = 1 and ARDY = 1, indicating that the cache register is available and that the die (LUN) is ready. Data can then be output from the cache register, beginning at column address 0. The RANDOM DATA READ (05h-E0h) command can be used to change the column address of the data being output.

For READ PAGE CACHE series (31h, 00h-31h, 3Fh), during the die (LUN) busy time, ^tRCBSY, when RDY = 0 and ARDY = 0, the only valid commands are status operations (70h, 78h) and RESET (FFh). When RDY = 1 and ARDY = 0, the only valid commands during READ PAGE CACHE series (31h, 00h-31h) operations are status operations (70h, 78h), READ MODE (00h), READ PAGE CACHE series (31h, 00h-31h), RANDOM DATA READ (05h-E0h), and RESET (FFh).



READ MODE (00h)

The READ MODE (00h) command disables status output and enables data output for the last-selected die (LUN) and cache register after a READ operation (00h-30h, 00h-3Ah, 00h-35h) has been monitored with a status operation (70h, 78h). This command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1). It is also accepted by the die (LUN) during READ PAGE CACHE (31h, 00h-31h) operations (RDY = 1 and ARDY = 0).

In devices that have more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations, the READ STATUS ENHANCED (78h) command must be used to select only one die (LUN) prior to issuing the READ MODE (00h) command. This prevents bus contention.

READ PAGE (00h-30h)

The READ PAGE (00h-30h) command copies a page from the NAND Flash array to its respective cache register and enables data output. This command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1).

To read a page from the NAND Flash array, write the 00h command to the command register, then write n address cycles to the address registers, and conclude with the 30h command. The selected die (LUN) will go busy (RDY = 0, ARDY = 0) for t_R as data is transferred.

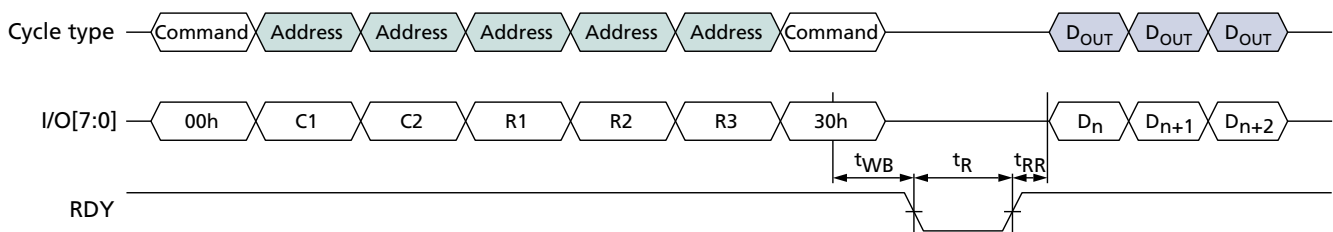
To determine the progress of the data transfer, the host can monitor the target's R/B# signal or, alternatively, the status operations (70h, 78h) can be used. If the status operations are used to monitor the LUN's status, when the die (LUN) is ready (RDY = 1, ARDY = 1), the host disables status output and enables data output by issuing the READ MODE (00h) command. When the host requests data output, output begins at the column address specified.

During data output the RANDOM DATA READ (05h-E0h) command can be issued.

When internal ECC is enabled, the READ STATUS (70h) command is required after the completion of the data transfer (t_{R_ECC}) to determine whether an uncorrectable read error occurred. (t_{R_ECC} is the data transferred with internal ECC enabled.)

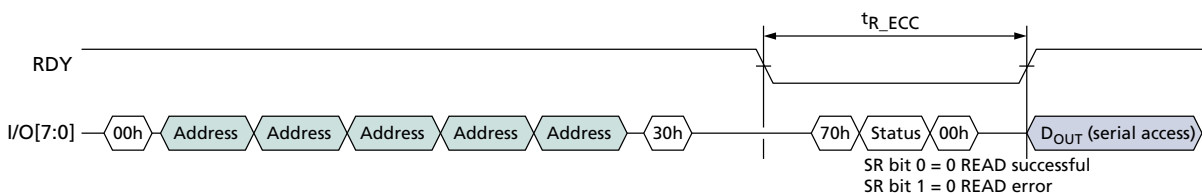
In devices that have more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations the READ STATUS ENHANCED (78h) command must be used to select only one die (LUN) prior to the issue of the READ MODE (00h) command. This prevents bus contention.

Figure 32: READ PAGE (00h-30h) Operation



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Read Operations

Figure 33: READ PAGE (00h-30h) Operation with Internal ECC Enabled



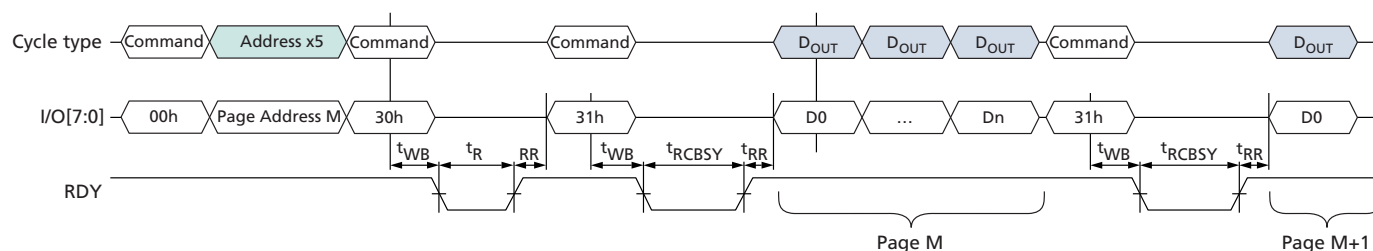
READ PAGE CACHE SEQUENTIAL (31h)

The READ PAGE CACHE SEQUENTIAL (31h) command reads the next sequential page within a block into the data register while the previous page is output from the cache register. This command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1). It is also accepted by the die (LUN) during READ PAGE CACHE (31h, 00h-31h) operations (RDY = 1 and ARDY = 0).

To issue this command, write 31h to the command register. After this command is issued, R/B# goes LOW and the die (LUN) is busy (RDY = 0, ARDY = 0) for ^tRCBSY. After ^tRCBSY, R/B# goes HIGH and the die (LUN) is busy with a cache operation (RDY = 1, ARDY = 0), indicating that the cache register is available and that the specified page is copying from the NAND Flash array to the data register. At this point, data can be output from the cache register beginning at column address 0. The RANDOM DATA READ (05h-E0h) command can be used to change the column address of the data being output from the cache register.

The READ PAGE CACHE SEQUENTIAL (31h) command can be used to cross block boundaries. If the READ PAGE CACHE SEQUENTIAL (31h) command is issued after the last page of a block is read into the data register, the next page read will be the next logical block in which the 31h command was issued. Do not issue the READ PAGE CACHE SEQUENTIAL (31h) to cross die (LUN) boundaries. Instead, issue the READ PAGE CACHE LAST (3Fh) command.

Figure 34: READ PAGE CACHE SEQUENTIAL (31h) Operation



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Read Operations

READ PAGE CACHE RANDOM (00h-31h)

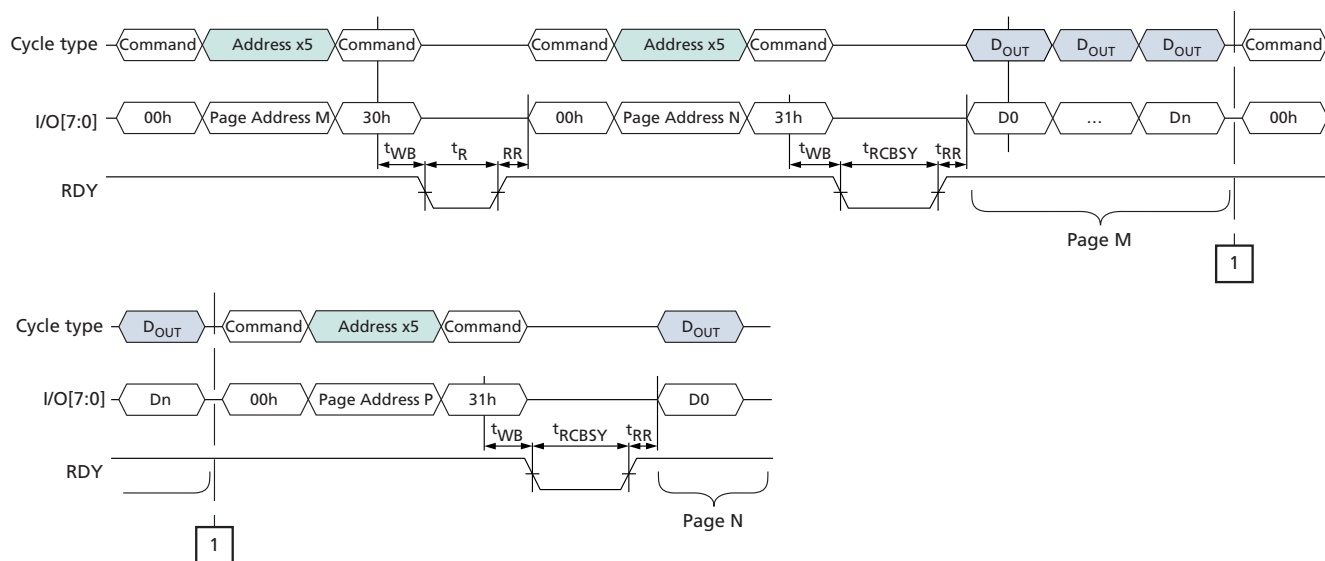
The READ PAGE CACHE RANDOM (00h-31h) command reads the specified block and page into the data register while the previous page is output from the cache register. This command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1). It is also accepted by the die (LUN) during READ PAGE CACHE (31h, 00h-31h) operations (RDY = 1 and ARDY = 0).

To issue this command, write 00h to the command register, then write n address cycles to the address register, and conclude by writing 31h to the command register. The column address in the address specified is ignored. The die (LUN) address must match the same die (LUN) address as the previous READ PAGE (00h-30h) command or, if applicable, the previous READ PAGE CACHE RANDOM (00h-31h) command.

After this command is issued, R/B# goes LOW and the die (LUN) is busy (RDY = 0, ARDY = 0) for ^tRCBSY. After ^tRCBSY, R/B# goes HIGH and the die (LUN) is busy with a cache operation (RDY = 1, ARDY = 0), indicating that the cache register is available and that the specified page is copying from the NAND Flash array to the data register. At this point, data can be output from the cache register beginning at column address 0. The RANDOM DATA READ (05h-E0h) command can be used to change the column address of the data being output from the cache register.

In devices that have more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations the READ STATUS ENHANCED (78h) command followed by the READ MODE (00h) command must be used to select only one die (LUN) and prevent bus contention.

Figure 35: READ PAGE CACHE RANDOM (00h-31h) Operation





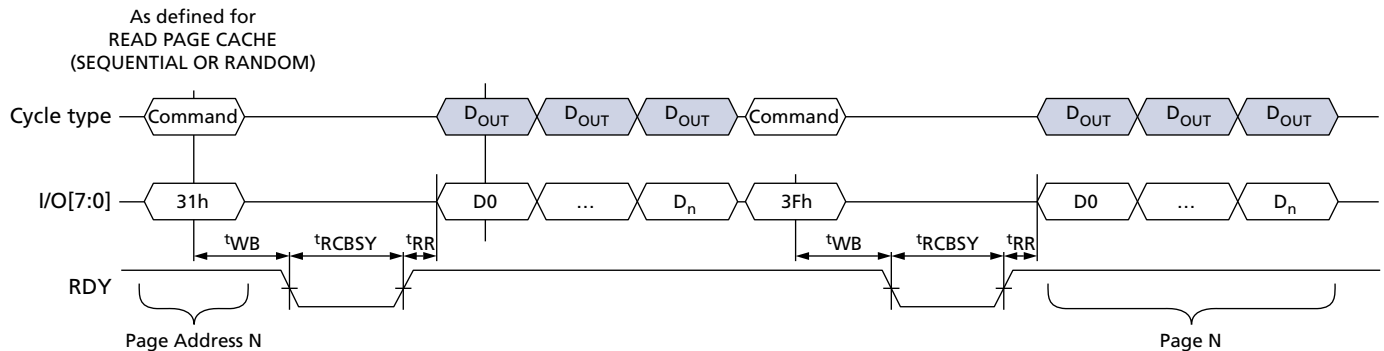
READ PAGE CACHE LAST (3Fh)

The READ PAGE CACHE LAST (3Fh) command ends the read page cache sequence and copies a page from the data register to the cache register. This command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1). It is also accepted by the die (LUN) during READ PAGE CACHE (31h, 00h-31h) operations (RDY = 1 and ARDY = 0).

To issue the READ PAGE CACHE LAST (3Fh) command, write 3Fh to the command register. After this command is issued, R/B# goes LOW and the die (LUN) is busy (RDY = 0, ARDY = 0) for t_{RCBSY} . After t_{RCBSY} , R/B# goes HIGH and the die (LUN) is ready (RDY = 1, ARDY = 1). At this point, data can be output from the cache register, beginning at column address 0. The RANDOM DATA READ (05h-E0h) command can be used to change the column address of the data being output from the cache register.

In devices that have more than one LUN per target, during and following interleaved die (multi-LUN) operations the READ STATUS ENHANCED (78h) command followed by the READ MODE (00h) command must be used to select only one die (LUN) and prevent bus contention.

Figure 36: READ PAGE CACHE LAST (3Fh) Operation





Program Operations

Program operations are used to move data from the cache or data registers to the NAND array. During a program operation the contents of the cache and/or data registers are modified by the internal control logic.

Within a block, pages must be programmed sequentially from the least significant page address to the most significant page address (0, 1, 2,, 63). During a program operation, the contents of the cache and/or data registers are modified by the internal control logic.

Program Operations

The PROGRAM PAGE (80h-10h) command programs one page from the cache register to the NAND Flash array. When the die (LUN) is ready (RDY = 1, ARDY = 1), the host should check the FAIL bit to verify that the operation has completed successfully.

Program Cache Operations

The PROGRAM PAGE CACHE (80h-15h) command can be used to improve program operation system performance. When this command is issued, the die (LUN) goes busy (RDY = 0, ARDY = 0) while the cache register contents are copied to the data register, and the die (LUN) is busy with a PROGRAM CACHE operation (RDY = 1, ARDY = 0). While the contents of the data register are moved to the NAND Flash array, the cache register is available for an additional PROGRAM PAGE CACHE (80h-15h) or PROGRAM PAGE (80h-10h) command.

For PROGRAM PAGE CACHE series (80h-15h) operations, during the die (LUN) busy times, ^tCBSY and ^tLPROG, when RDY = 0 and ARDY = 0, the only valid commands are status operations (70h, 78h) and reset (FFh). When RDY = 1 and ARDY = 0, the only valid commands during PROGRAM PAGE CACHE series (80h-15h) operations are status operations (70h, 78h), PROGRAM PAGE CACHE (80h-15h), PROGRAM PAGE (80h-10h), RANDOM DATA INPUT (85h), PROGRAM FOR INTERNAL DATA INPUT (85h), and RESET (FFh).

PROGRAM PAGE (80h-10h)

The PROGRAM PAGE (80h-10h) command enables the host to input data to a cache register, and moves the data from the cache register to the specified block and page address in the array of the selected die (LUN). This command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1). It is also accepted by the die (LUN) when it is busy with a PROGRAM PAGE CACHE (80h-15h) operation (RDY = 1, ARDY = 0).

To input a page to the cache register and move it to the NAND array at the block and page address specified, write 80h to the command register. Issuing the 80h to the command register clears all of the cache registers' contents on the selected target. Then write *n* address cycles containing the column address and row address. Data input cycles follow. Serial data is input beginning at the column address specified. At any time during the data input cycle the RANDOM DATA INPUT (85h) and PROGRAM FOR INTERNAL DATA INPUT (85h) commands may be issued. When data input is complete, write 10h to the command register. The selected LUN will go busy (RDY = 0, ARDY = 0) for ^tPROG as data is transferred.

To determine the progress of the data transfer, the host can monitor the target's R/B# signal or, alternatively, the status operations (70h, 78h) may be used. When the die (LUN) is ready (RDY = 1, ARDY = 1), the host should check the status of the FAIL bit.

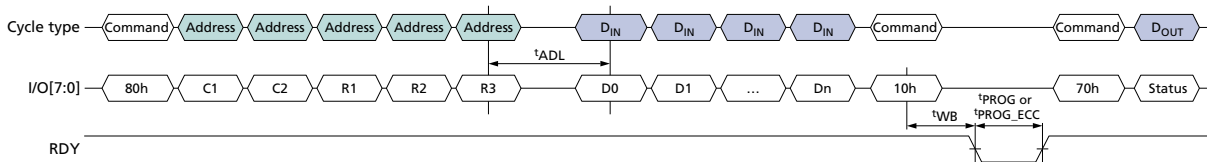


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Program Operations

In devices that have more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations, the READ STATUS ENHANCED (78h) command must be used to select only one die (LUN) for status output. Use of the READ STATUS (70h) command could cause more than one die (LUN) to respond, resulting in bus contention.

When internal ECC is enabled, the duration of array programming time is $t_{\text{PROG_ECC}}$. During $t_{\text{PROG_ECC}}$, the internal ECC generates parity bits when error detection is complete.

Figure 37: PROGRAM PAGE (80h-10h) Operation



PROGRAM PAGE CACHE (80h-15h)

The PROGRAM PAGE CACHE (80h-15h) command enables the host to input data to a cache register; copies the data from the cache register to the data register; then moves the data register contents to the specified block and page address in the array of the selected die (LUN). After the data is copied to the data register, the cache register is available for additional PROGRAM PAGE CACHE (80h-15h) or PROGRAM PAGE (80h-10h) commands. The PROGRAM PAGE CACHE (80h-15h) command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1). It is also accepted by the die (LUN) when busy with a PROGRAM PAGE CACHE (80h-15h) operation (RDY = 1, ARDY = 0).

To input a page to the cache register to move it to the NAND array at the block and page address specified, write 80h to the command register. Issuing the 80h to the command register clears all of the cache registers' contents on the selected target. Then write n address cycles containing the column address and row address. Data input cycles follow. Serial data is input beginning at the column address specified. At any time during the data input cycle the RANDOM DATA INPUT (85h) and PROGRAM FOR INTERNAL DATA INPUT (85h) commands may be issued. When data input is complete, write 15h to the command register. The selected LUN will go busy (RDY = 0, ARDY = 0) for t_{CBSY} to allow the data register to become available from a previous program cache operation, to copy data from the cache register to the data register, and then to begin moving the data register contents to the specified page and block address.

To determine the progress of t_{CBSY} , the host can monitor the target's R/B# signal or, alternatively, the status operations (70h, 78h) can be used. When the LUN's status shows that it is busy with a PROGRAM CACHE operation (RDY = 1, ARDY = 0), the host should check the status of the FAILC bit to see if a previous cache operation was successful.

If, after t_{CBSY} , the host wants to wait for the PROGRAM CACHE operation to complete, without issuing the PROGRAM PAGE (80h-10h) command, the host should monitor ARDY until it is 1. The host should then check the status of the FAIL and FAILC bits.

In devices with more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations, the READ STATUS ENHANCED (78h) command must be



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Program Operations

used to select only one die (LUN) for status output. Use of the READ STATUS (70h) command could cause more than one die (LUN) to respond, resulting in bus contention.

Figure 38: PROGRAM PAGE CACHE (80h–15h) Operation (Start)

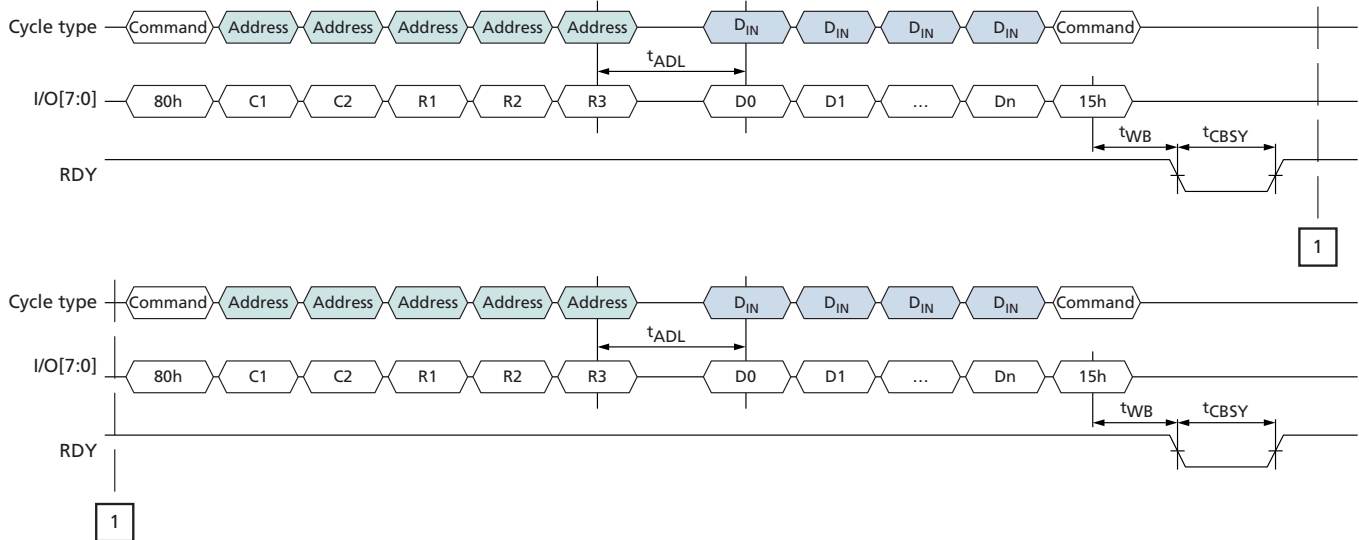
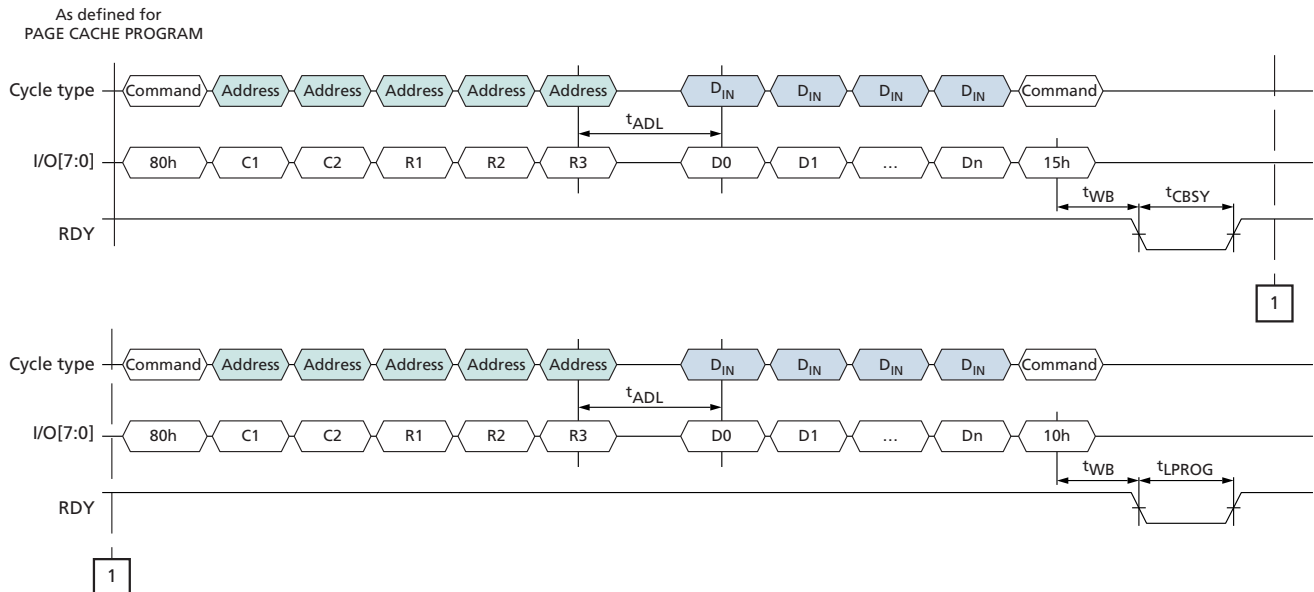


Figure 39: PROGRAM PAGE CACHE (80h–15h) Operation (End)





Erase Operations

Erase operations are used to clear the contents of a block in the NAND Flash array to prepare its pages for program operations.

Erase Operations

The ERASE BLOCK (60h-D0h) command, erases one block in the NAND Flash array. When the die (LUN) is ready (RDY = 1, ARDY = 1), the host should check the FAIL bit to verify that this operation completed successfully.

ERASE BLOCK (60h-D0h)

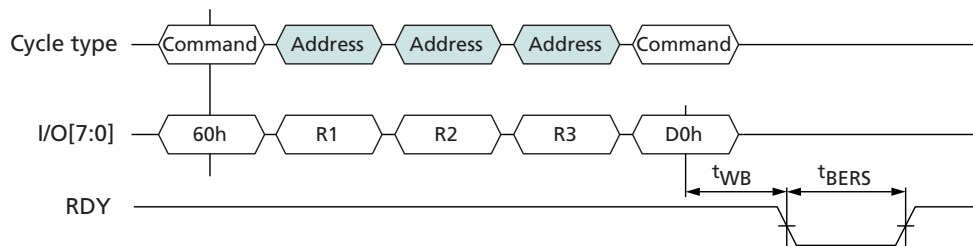
The ERASE BLOCK (60h-D0h) command erases the specified block in the NAND Flash array. This command is accepted by the die (LUN) when it is ready (RDY = 1, ARDY = 1).

To erase a block, write 60h to the command register. Then write three address cycles containing the row address; the page address is ignored. Conclude by writing D0h to the command register. The selected die (LUN) will go busy (RDY = 0, ARDY = 0) for t_{BERS} while the block is erased.

To determine the progress of an ERASE operation, the host can monitor the target's R/B# signal, or alternatively, the status operations (70h, 78h) can be used. When the die (LUN) is ready (RDY = 1, ARDY = 1) the host should check the status of the FAIL bit.

In devices that have more than one die (LUN) per target, during and following interleaved die (multi-LUN) operations, the READ STATUS ENHANCED (78h) command must be used to select only one die (LUN) for status output. Use of the READ STATUS (70h) command could cause more than one die (LUN) to respond, resulting in bus contention.

Figure 40: ERASE BLOCK (60h-D0h) Operation





Internal Data Move Operations

Internal data move operations make it possible to transfer data within a device from one page to another, on the same plane, using the cache register. This is particularly useful for block management and wear leveling.

It is not possible to use the READ FOR INTERNAL DATA MOVE operation to move data from one die (LUN) to another. Instead, use a READ PAGE (00h-30h) or READ FOR INTERNAL DATA MOVE (00h-35h) command to read the data out of the NAND, and then use a PROGRAM PAGE (80h-10h) command with data input to program the data to a new die (LUN).

Between the READ FOR INTERNAL DATA MOVE (00h-35h) and PROGRAM FOR INTERNAL DATA MOVE (85h-10h) commands, the following commands are supported: status operations (70h, 78h) and column address operations (05h-E0h, 06h-E0h, 85h). The RESET operation (FFh) can be issued after READ FOR INTERNAL DATA MOVE (00h-35h), but the contents of the cache registers on the target are not valid.

In devices that have more than one die (LUN) per target, once the READ FOR INTERNAL DATA MOVE (00h-35h) is issued, interleaved die (multi-LUN) operations are prohibited until after the PROGRAM FOR INTERNAL DATA MOVE (85h-10h) command is issued.

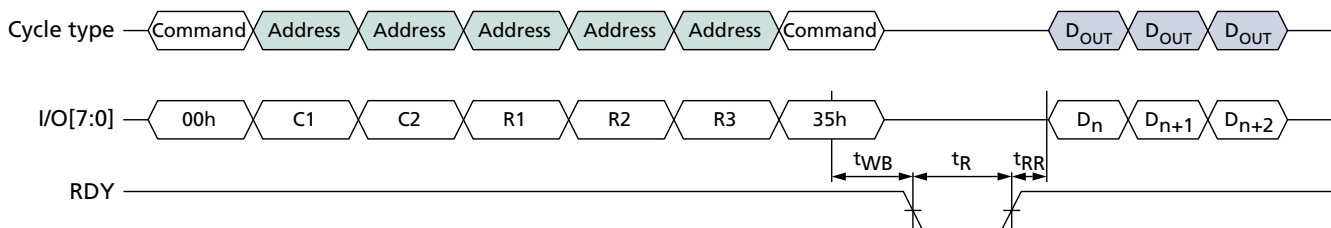
READ FOR INTERNAL DATA MOVE (00h-35h)

The READ FOR INTERNAL DATA MOVE (00h-35h) command is functionally identical to the READ PAGE (00h-30h) command, except that 35h is written to the command register instead of 30h.

Though it is not required, it is recommended that the host read the data out of the device to verify the data prior to issuing the PROGRAM FOR INTERNAL DATA MOVE (85h-10h) command to prevent the propagation of data errors.

If internal ECC is enabled, the data does not need to be toggled out by the host to be corrected and moving data can then be written to a new page without data reloading, which improves system performance.

Figure 41: READ FOR INTERNAL DATA MOVE (00h-35h) Operation





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Internal Data Move Operations

Figure 42: READ FOR INTERNAL DATA MOVE (00h–35h) with RANDOM DATA READ (05h–E0h)

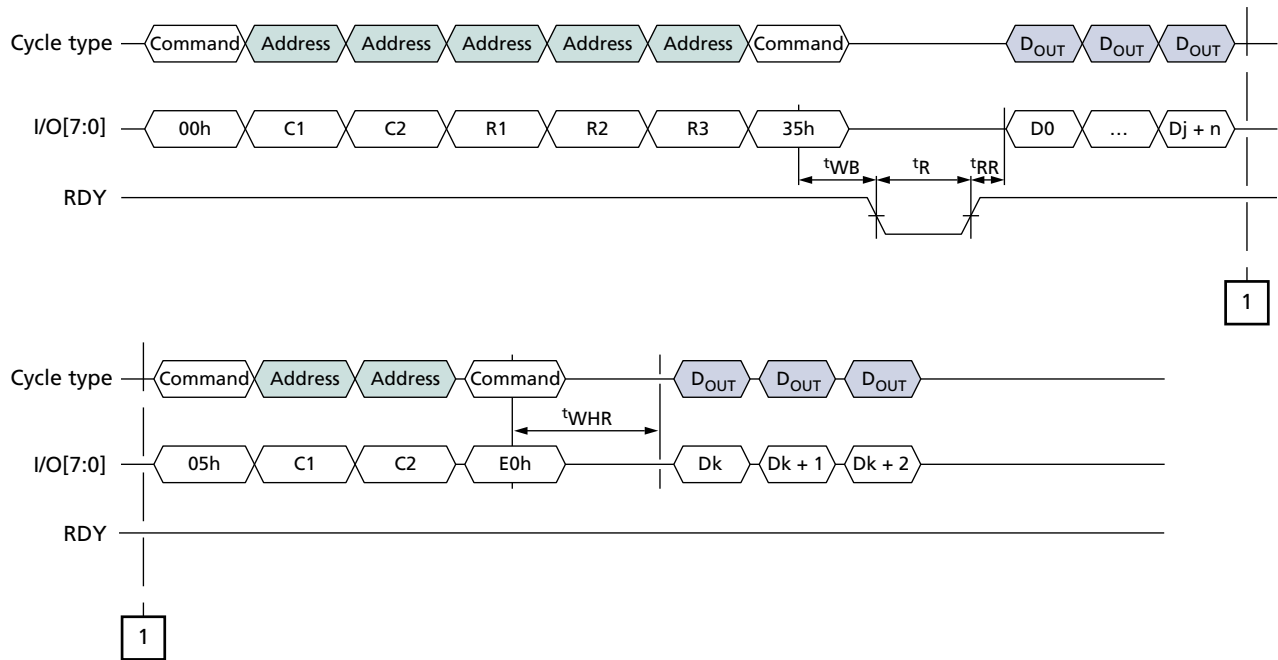


Figure 43: INTERNAL DATA MOVE (85h–10h) with Internal ECC Enabled

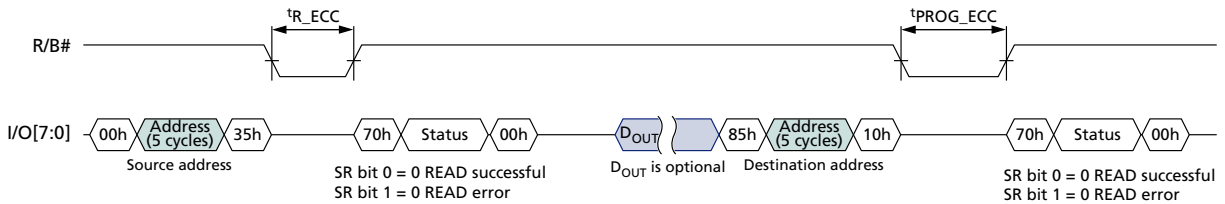
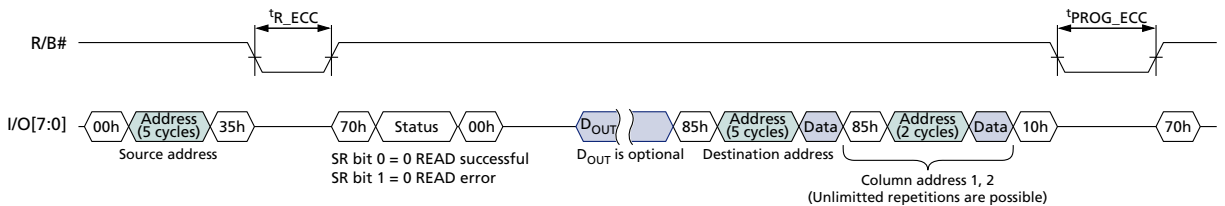


Figure 44: INTERNAL DATA MOVE (85h–10h) with RANDOM DATA INPUT with Internal ECC Enabled



PROGRAM FOR INTERNAL DATA MOVE (85h–10h)

The PROGRAM FOR INTERNAL DATA MOVE (85h–10h) command is functionally identical to the PROGRAM PAGE (80h–10h) command, except that when 85h is written to the command register, cache register contents are not cleared.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Internal Data Move Operations

Figure 45: PROGRAM FOR INTERNAL DATA MOVE (85h–10h) Operation

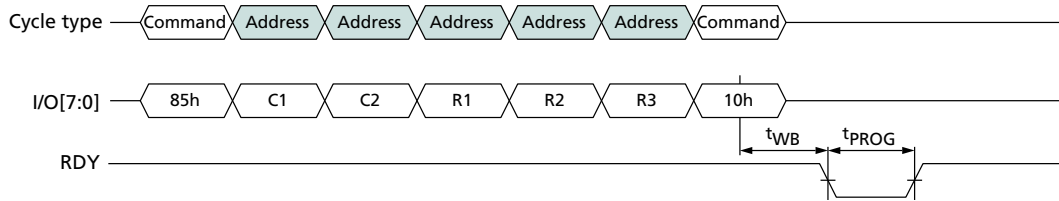
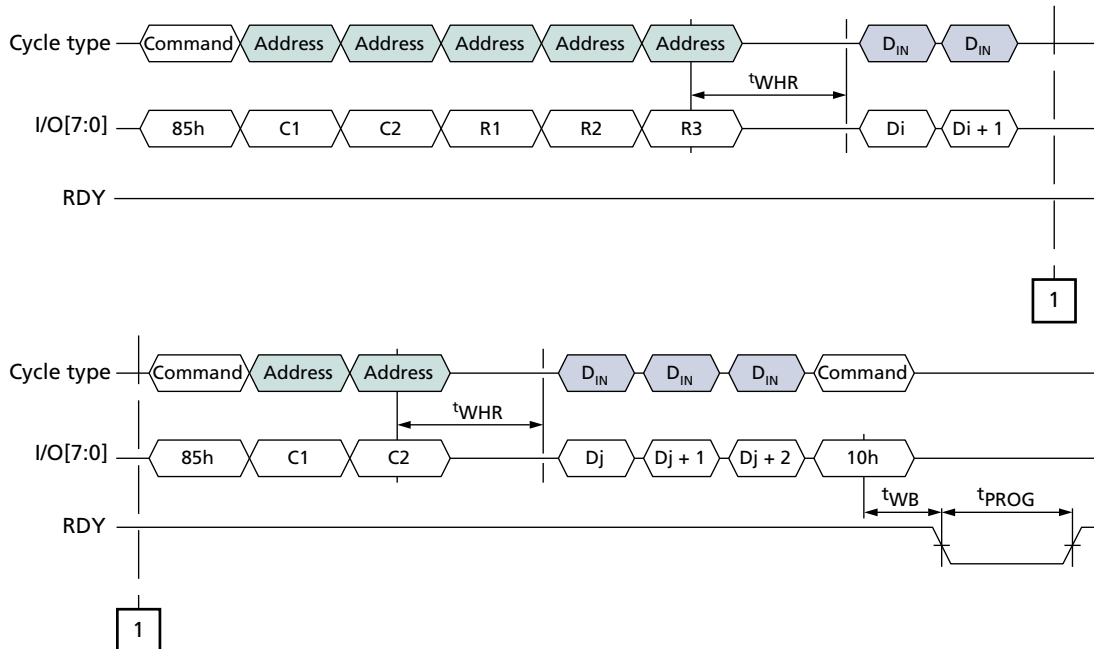


Figure 46: PROGRAM FOR INTERNAL DATA MOVE (85h–10h) with RANDOM DATA INPUT (85h)





Block Lock Feature

The block lock feature protects either the entire device or ranges of blocks from being programmed and erased. Using the block lock feature is preferable to using WP# to prevent PROGRAM and ERASE operations.

Block lock is enabled and disabled at power-on through the LOCK pin. At power-on, if LOCK is LOW, all BLOCK LOCK commands are disabled. However if LOCK is HIGH at power-on, the BLOCK LOCK commands are enabled and, by default, all the blocks on the device are protected, or locked, from PROGRAM and ERASE operations, even if WP# is HIGH.

Before the contents of the device can be modified, the device must first be unlocked. Either a range of blocks or the entire device may be unlocked. PROGRAM and ERASE operations complete successfully only in the block ranges that have been unlocked. Blocks, once unlocked, can be locked again to protect them from further PROGRAM and ERASE operations.

Blocks that are locked can be protected further, or locked tight. When locked tight, the device's blocks can no longer be locked or unlocked.

WP# and Block Lock

The following is true when the block lock feature is enabled:

- Holding WP# LOW locks all blocks, provided the blocks are not locked tight.
- If WP# is held LOW to lock blocks, then returned to HIGH, a new UNLOCK command must be issued to unlock blocks.

UNLOCK (23h-24h)

By default at power-on, if LOCK is HIGH, all the blocks are locked and protected from PROGRAM and ERASE operations. The UNLOCK (23h) command is used to unlock a range of blocks. Unlocked blocks have no protection and can be programmed or erased.

The UNLOCK command uses two registers, a lower boundary block address register and an upper boundary block address register, and the invert area bit to determine what range of blocks are unlocked. When the invert area bit = 0, the range of blocks within the lower and upper boundary address registers are unlocked. When the invert area bit = 1, the range of blocks outside the boundaries of the lower and upper boundary address registers are unlocked. The lower boundary block address must be less than the upper boundary block address. The figures below show examples of how the lower and upper boundary address registers work with the invert area bit.

To unlock a range of blocks, issue the UNLOCK (23h) command followed by the appropriate address cycles that indicate the lower boundary block address. Then issue the 24h command followed by the appropriate address cycles that indicate the upper boundary block address. The least significant page address bit, PA0, should be set to 1 if setting the invert area bit; otherwise, it should be 0. The other page address bits should be 0.

Only one range of blocks can be specified in the lower and upper boundary block address registers. If after unlocking a range of blocks the UNLOCK command is again issued, the new block address range determines which blocks are unlocked. The previous unlocked block address range is not retained.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Block Lock Feature

Figure 47: Flash Array Protected: Invert Area Bit = 0

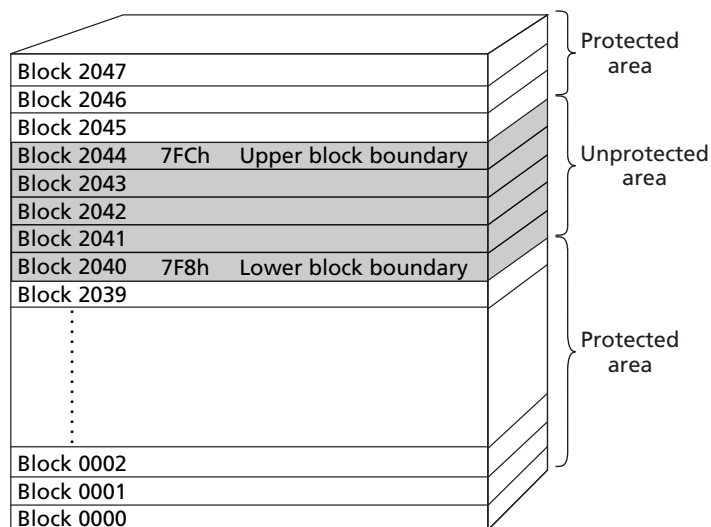


Figure 48: Flash Array Protected: Invert Area Bit = 1

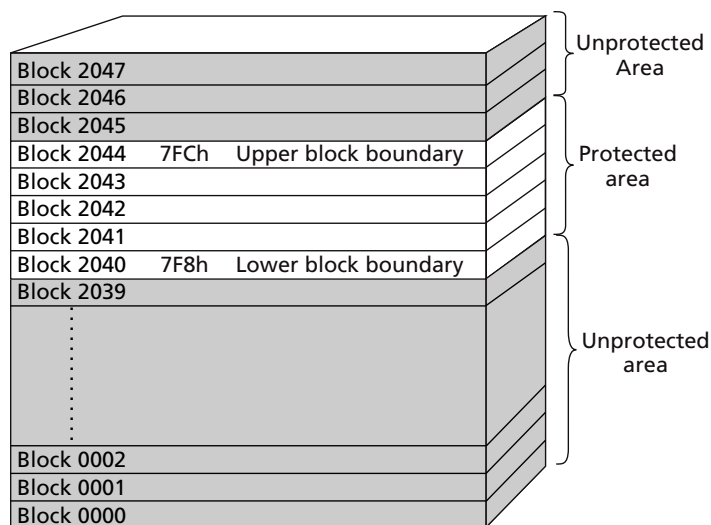
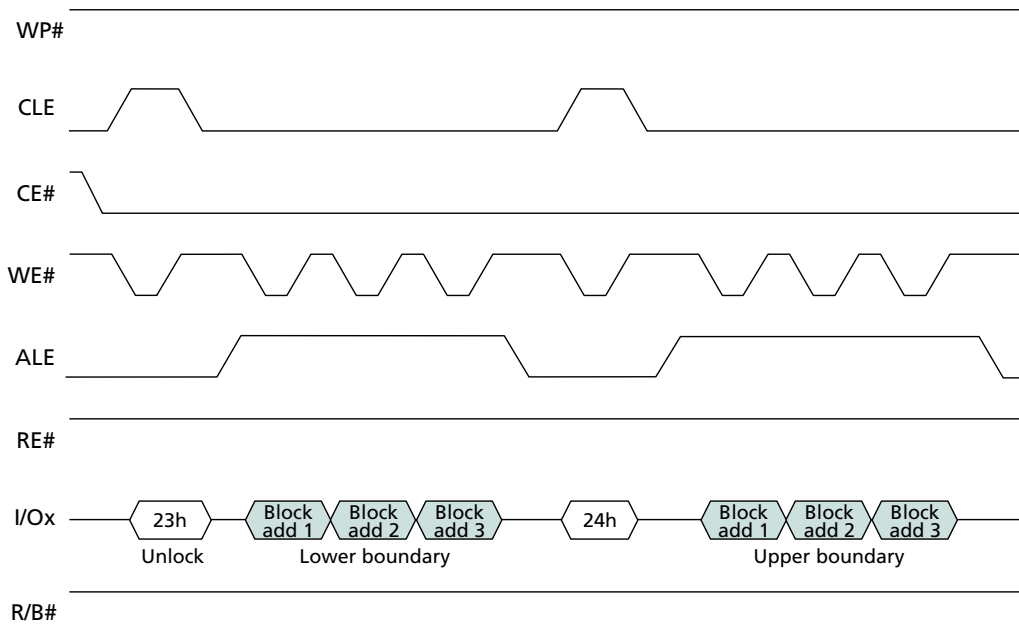


Table 24: Block Lock Address Cycle Assignments

ALE Cycle	I/O[15:8] ¹	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	I/O0
First	LOW	BA7	BA6	LOW	LOW	LOW	LOW	LOW	Invert area bit ²
Second	LOW	BA15	BA14	BA13	BA12	BA11	BA10	BA9	BA8
Third	LOW	LOW	LOW	LOW	LOW	LOW	LOW	BA17	BA16

- Notes:
1. I/O[15:8] is applicable only for x16 devices.
 2. Invert area bit is applicable for 24h command; it may be LOW or HIGH for 23h command.


Figure 49: UNLOCK Operation


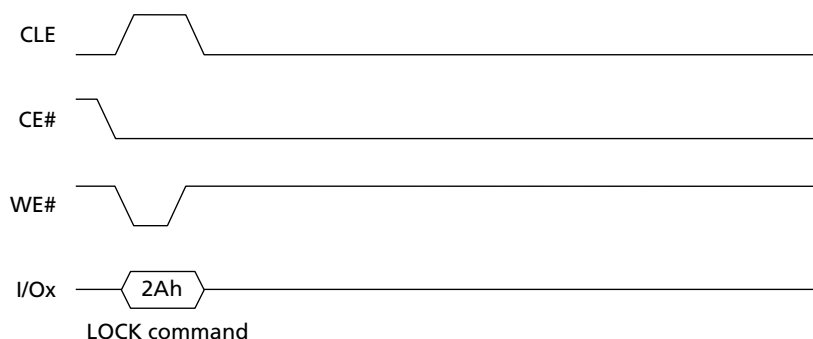
LOCK (2Ah)

By default at power-on, if LOCK is HIGH, all the blocks are locked and protected from PROGRAM and ERASE operations. If portions of the device are unlocked using the UNLOCK (23h) command, they can be locked again using the LOCK (2Ah) command. The LOCK command locks all of the blocks in the device. Locked blocks are write-protected from PROGRAM and ERASE operations.

To lock all of the blocks in the device, issue the LOCK (2Ah) command.

When a PROGRAM or ERASE operation is issued to a locked block, R/B# goes LOW for 'LBSY. The PROGRAM or ERASE operation does not complete. Any READ STATUS command reports bit 7 as 0, indicating that the block is protected.

The LOCK (2Ah) command is disabled if LOCK is LOW at power-on or if the device is locked tight.


Figure 50: LOCK Operation


LOCK TIGHT (2Ch)

The LOCK TIGHT (2Ch) command prevents locked blocks from being unlocked and also prevents unlocked blocks from being locked. When this command is issued, the UNLOCK (23h) and LOCK (2Ah) commands are disabled. This provides an additional level of protection against inadvertent PROGRAM and ERASE operations to locked blocks.

To implement LOCK TIGHT in all of the locked blocks in the device, verify that WP# is HIGH and then issue the LOCK TIGHT (2Ch) command.

When a PROGRAM or ERASE operation is issued to a locked block that has also been locked tight, R/B# goes LOW for t_{LBSY} . The PROGRAM or ERASE operation does not complete. The READ STATUS (70h) command reports bit 7 as 0, indicating that the block is protected. PROGRAM and ERASE operations complete successfully to blocks that were not locked at the time the LOCK TIGHT command was issued.

After the LOCK TIGHT command is issued, the command cannot be disabled via a software command. Lock tight status can be disabled only by power cycling the device or toggling WP#. When the lock tight status is disabled, all of the blocks become locked, the same as if the LOCK (2Ah) command had been issued.

The LOCK TIGHT (2Ch) command is disabled if LOCK is LOW at power-on.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Block Lock Feature

Figure 51: LOCK TIGHT Operation

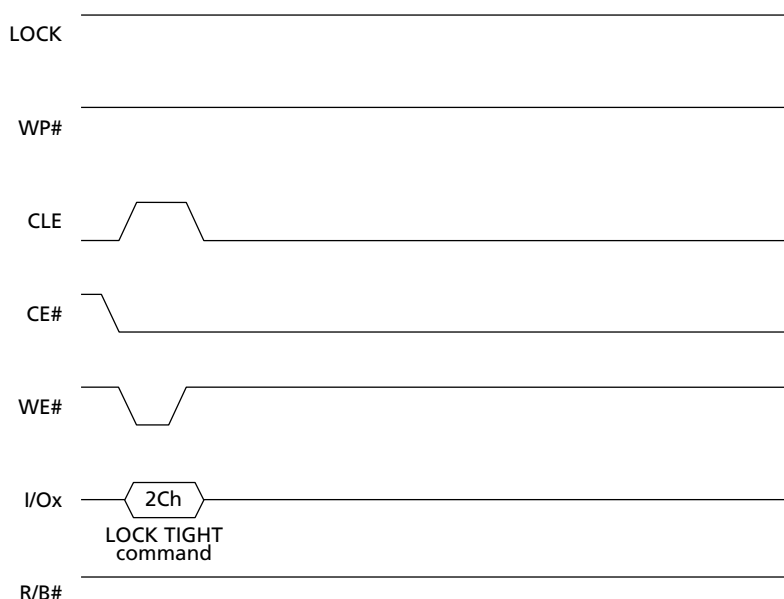
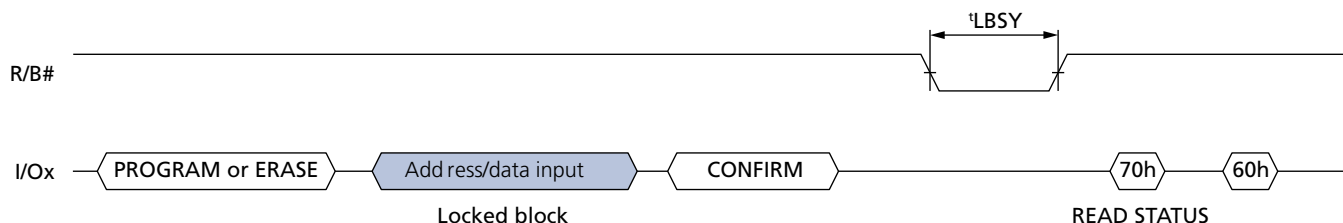


Figure 52: PROGRAM/ERASE Issued to Locked Block



BLOCK LOCK READ STATUS (7Ah)

The BLOCK LOCK READ STATUS (7Ah) command is used to determine the protection status of individual blocks. The address cycles have the same format, as shown below, and the invert area bit should be set LOW. On the falling edge of RE# the I/O pins output the block lock status register, which contains the information on the protection status of the block.

Table 25: Block Lock Status Register Bit Definitions

Block Lock Status Register Definitions	I/O[7:4]	I/O3 (Protect#)	I/O2 (Lock#)	I/O1 (LT#)	I/O0 (LT)
Block is locked tight	X	1	0	0	1
Block is locked	X	1	0	1	0
Block is unlocked, and device is locked tight	X	1	1	0	1
Block is unlocked, and device is not locked tight	X	1	1	1	0
Block is permanently protected	X	0	x	x	x



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Block Lock Feature

Figure 53: BLOCK LOCK READ STATUS

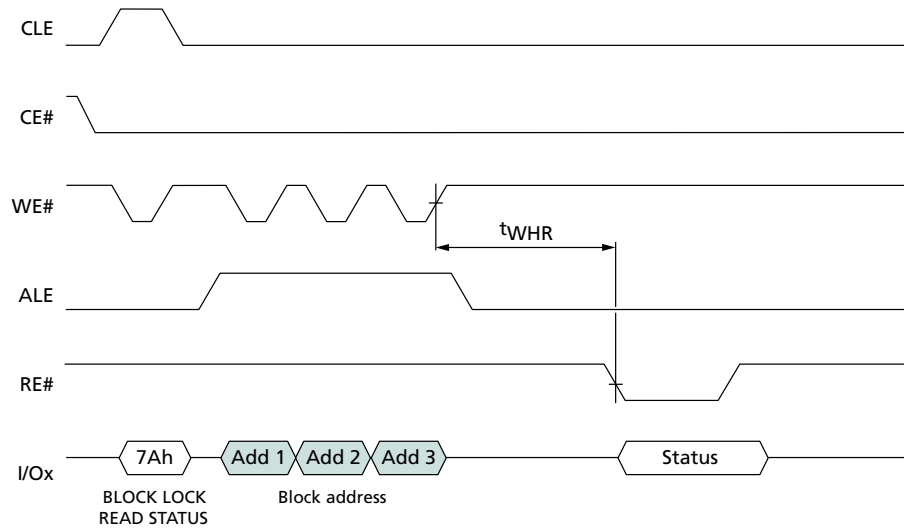
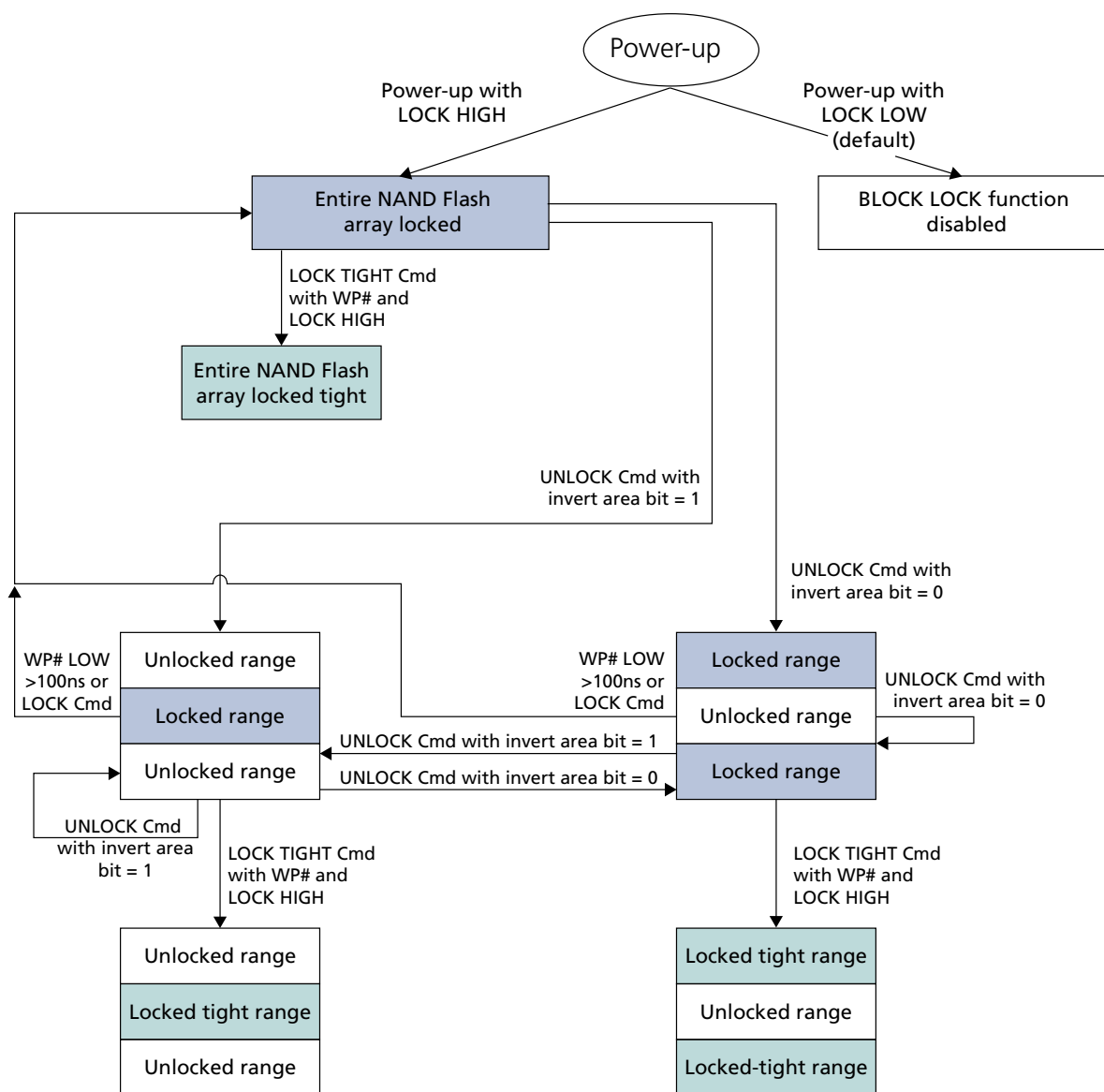



Figure 54: BLOCK LOCK Flowchart


PROTECT Command

Blocks 00h–07h are guaranteed valid with ECC when shipped from the factory. The PROTECT command provides nonvolatile, irreversible protection of up to twelve groups (48 blocks total). Implementation of the protection is group-based, which means that a minimum of one group (4 blocks) is protected when the PROTECT command is issued.

Because block protection is nonvolatile, a power-on or power-off sequence does not affect the block status after the PROTECT command is issued. The device ships from the factory with no blocks protected so that users can program or erase the blocks before issuing the PROTECT command. Block protection is also irreversible in that when pro-

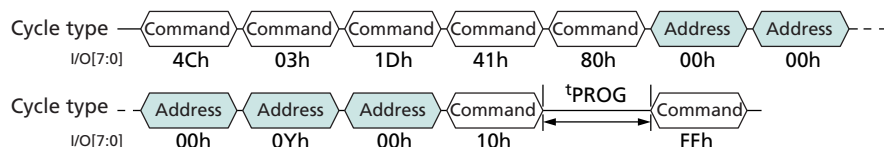


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Block Lock Feature

tection is enabled by the issuing PROTECT command, the protected blocks can no longer be programmed or erased.

The PROTECT command includes the steps detailed below.

Figure 55: Address and Command Cycles



Note: 1. In the 4th address cycle, 0Yh is the last 4 bits and represents the group of blocks to be protected. There are always 12 Groups, so Y = 0000b-1011b: Y = 0000 protects Group0 = blks 0, 1, 2, 3; Y = 0001 protects Group1 = blks 4, 5, 6, 7; Y = 1011 protects Group11 = blks 44, 45, 46, 47.

Protection Command Details

To enable protection, four bus WRITE cycles set up the 4Ch, 03h, 1Dh, and 41h commands. Next, one bus WRITE cycle sets up the PAGE PROGRAM command (80h).

Then, five bus WRITE cycles are required to input the targeted block group information: 00h, 00h, 00h, 0Yh, 00h. In this 4th address cycle, 0Yh is the last 4 bits and represents the group of blocks to be protected. There are always 12 Groups, so Y = 0000b-1011b:

- Y = 0000 protects Group0 = blks 0, 1, 2, 3.
- Y = 0001 protects Group1 = blks 4, 5, 6, 7.
- Y = 1011 protects Group11 = blks 44, 45, 46, 47.

One bus cycle is required to issue the PAGE PROGRAM CONFIRM command. After tPROG, the targeted block groups are protected. The EXIT protection command (FFh) is issued to ensure the device exits protection mode.

(4Ch-03h-1Dh-41h)-80h-addr(00h-00h-00h-0Yh-00h)-10h-tPROG-FFh

The enable protection step is four bytes wide to prevent implementing involuntary protection. In addition, any spurious command/address/data cycles between each byte invalidates the entire process and the next PROGRAM command does not affect the block protection status. Likewise, any spurious command/address/data cycle between enable protection and setting up the PAGE PROGRAM command invalidates the entire protection command process.

If enable protection is followed by an operation other than the PROGRAM operation, such as a PAGE READ or BLOCK ERASE operation, this other operation is executed without affecting block protection status. Therefore, the PROTECT operation must still be executed to protect the block. The PROTECT operation is inhibited if WP# is LOW. Upon PROTECT operation failure, the status register reports a value of E1h. Upon PROTECT operation success, the status register reports value of E0h.

The following is an example of boot block protection:

Protect group 5 (blks20-23): (4Ch-03h-1Dh-41h)-80h-addr(00h-00h-00h-05h-00h)-10h-tPROG-FFh



Permanent Block Lock Disable Mode

The PROTECT command provides nonvolatile, irreversible protection of up to twelve groups (48 blocks total), these blocks are permanent locked once the PROTECT command is issued to them. The permanent block lock disable mode provides the command sequence to freeze the block lock status, it is highly recommended for customers to follow this operation to prevent unintentional or malicious changes but not limited to these scenarios:

- Only certain number of groups of blocks need to be permanently locked, the rest of the block groups do not need to be permanently locked
- Customer do not need permanent block lock feature, and all 48 blocks are normal blocks

In permanent block lock disable mode, the following program sequence is used to disable protection command to add more permanent locked block groups:

- SET FEATURE command (EFh) with feature address 90h and data value 10h-00h-00h-00h to enter permanent block lock disable mode
- PROGRAM command (80h-10h) with block/page address all "0", and data input 0x00
- READ STATUS command 70h to check the operation status and success

READ command also could be used in permanent block lock disable mode to check whether PROTECT command is disabled by reading out all "0"; all "1" indicates Protection command is not disabled.

If permanent block lock disable sequence is issued again to the part that has already been disabled, the part will be busy for ^tOBSY and exit with SR = 60h. The part will be busy for ^tOBSY_ECC when ECC is enabled.



One-Time Programmable (OTP) Operations

This Micron NAND Flash device offers a protected, one-time programmable NAND Flash memory area. 48 full pages of OTP data are available on the device, and the entire range is guaranteed to be good. The OTP area is accessible only through the OTP commands. Customers can use the OTP area any way they choose; typical uses include programming serial numbers or other data for permanent storage.

The OTP area leaves the factory in an unwritten state (all bits are 1s). Programming or partial-page programming enables the user to program only 0 bits in the OTP area. The OTP area cannot be erased, whether it is protected or not. Protecting the OTP area prevents further programming of that area.

Micron provides a unique way to program and verify data before permanently protecting it and preventing future changes. The OTP area is only accessible while in OTP operation mode. To set the device to OTP operation mode, issue the SET FEATURE (EFh) command to feature address 90h and write 01h to P1, followed by three cycles of 00h to P2-P4. For parameters to enter OTP mode, see Features Operations.

When the device is in OTP operation mode, all subsequent PAGE READ (00h-30h) and PROGRAM PAGE (80h-10h) commands are applied to the OTP area. The OTP area is assigned to page addresses 02h-31h. To program an OTP page, issue the PROGRAM PAGE (80h-10h) command. The pages must be programmed in the ascending order. Similarly, to read an OTP page, issue the PAGE READ (00h-30h) command.

Protecting the OTP is done by entering OTP protect mode. To set the device to OTP protect mode, issue the SET FEATURE (EFh) command to feature address 90h and write 03h to P1, followed by three cycles of 00h to P2-P4.

To determine whether the device is busy during an OTP operation, either monitor R/B# or use the READ STATUS (70h) command.

To exit OTP operation or protect mode, write 00h to P1 at feature address 90h.

Legacy OTP Commands

For legacy OTP commands, OTP DATA PROGRAM (A0h-10h), OTP DATA PROTECT (A5h-10h), and OTP DATA READ (AFh-30h).

OTP DATA PROGRAM (80h-10h)

The OTP DATA PROGRAM (80h-10h) command is used to write data to the pages within the OTP area. An OTP page allows only four partial-page programs. There is no ERASE operation for OTP pages.

PROGRAM PAGE enables programming into an offset of an OTP page using two bytes of the column address (CA[12:0]). The command is compatible with the RANDOM DATA INPUT (85h) command. The PROGRAM PAGE command will not execute if the OTP area has been protected.

To use the PROGRAM PAGE command, issue the 80h command. Issue n address cycles. The first two address cycles are the column address. For the remaining cycles, select a page in the range of 02h-00h through 31h-00h. Next, write n bytes of data. After data input is complete, issue the 10h command. The internal control logic automatically executes the proper programming algorithm and controls the necessary timing for programming and verification.



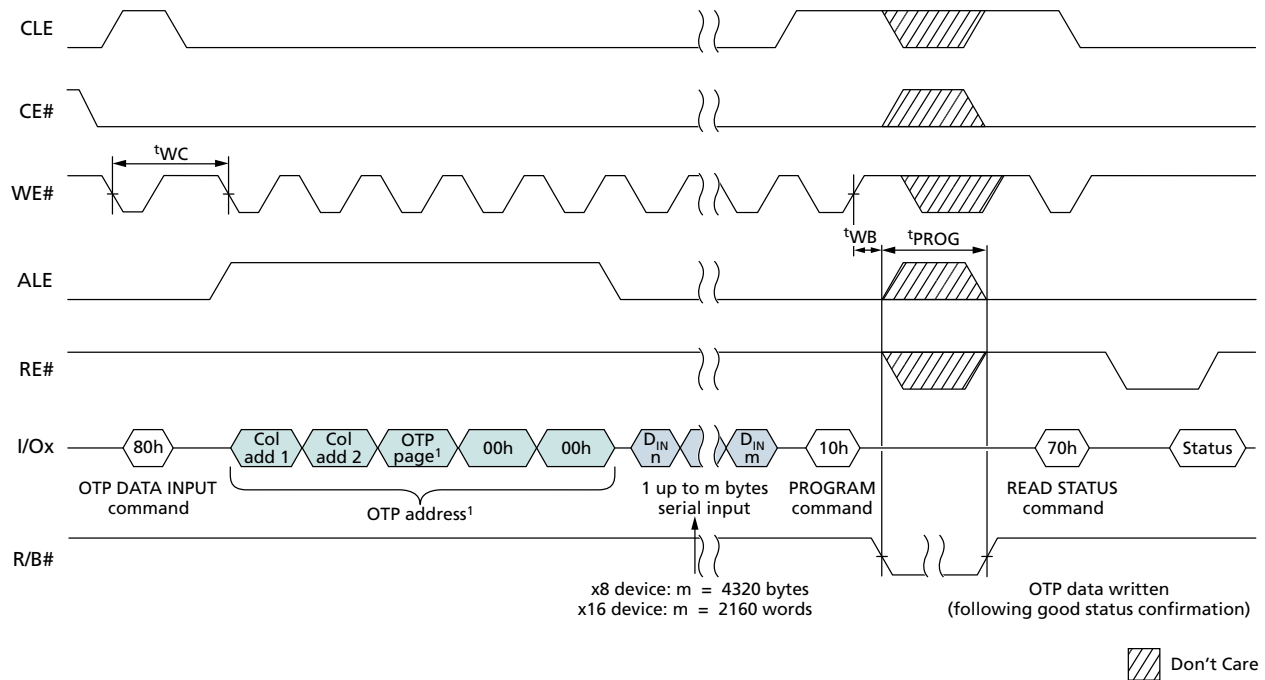
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP One-Time Programmable (OTP) Operations

R/B# goes LOW for the duration of the array programming time (t_{PROG}). The READ STATUS (70h) command is the only valid command for reading status in OTP operation mode. Bit 5 of the status register reflects the state of R/B#. When the device is ready, read bit 0 of the status register to determine whether the operation passed or failed (see Status Operations). Each OTP page can be programmed to 4 partial-page programming.

RANDOM DATA INPUT (85h)

After the initial OTP data set is input, additional data can be written to a new column address with the RANDOM DATA INPUT (85h) command. The RANDOM DATA INPUT command can be used any number of times in the same page prior to the OTP PAGE WRITE (10h) command being issued.

Figure 56: OTP DATA PROGRAM (After Entering OTP Operation Mode)

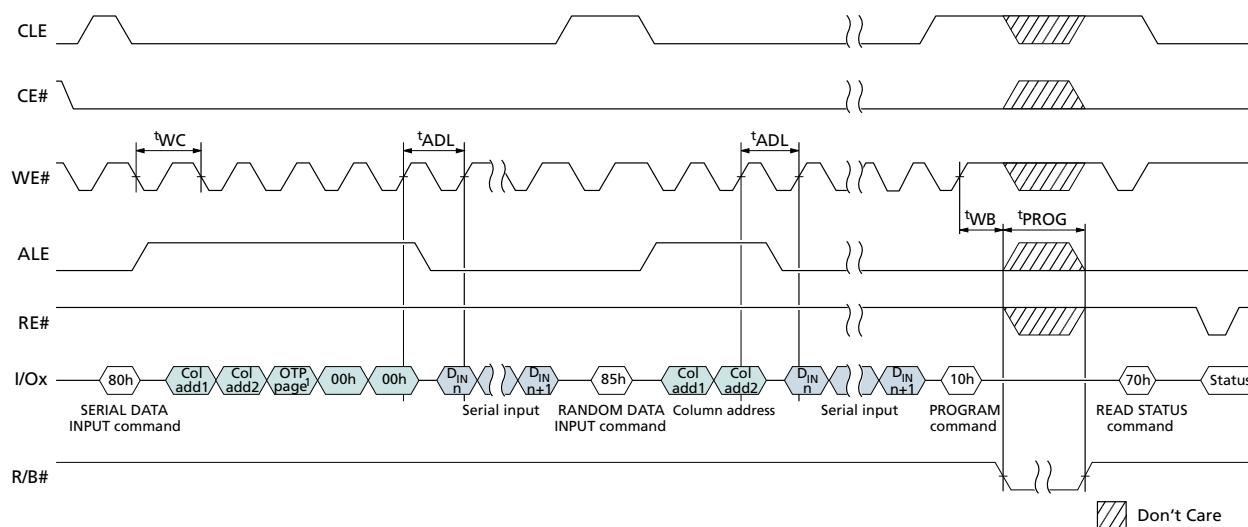


Note: 1. The OTP page must be within the 02h–31h range.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP One-Time Programmable (OTP) Operations

Figure 57: OTP DATA PROGRAM Operation with RANDOM DATA INPUT (After Entering OTP Operation Mode)



OTP DATA PROTECT (80h-10h)

The OTP area is protected on a block basis. To protect a block, set the device to OTP protect mode, then issue the PROGRAM PAGE (80h-10h) command and write OTP address 00h, 00h, 00h, 00h. To set the device to OTP protect mode, issue the SET FEATURE (EFh) command to 90h (feature address) and write 03h to P1, followed by three cycles of 00h to P2-P4.

After the data is protected, it cannot be programmed further. When the OTP area is protected, the pages within the area are no longer programmable and cannot be unprotected.

To use the PROGRAM PAGE command to protect the OTP area, issue the 80h command, followed by n address cycles, write 00h data, data cycle of 00h, followed by the 10h command. (An example of the address sequence is shown in the following figure.) If an OTP DATA PROGRAM command is issued after the OTP area has been protected, R/B# will go LOW for t_{OBSY} .

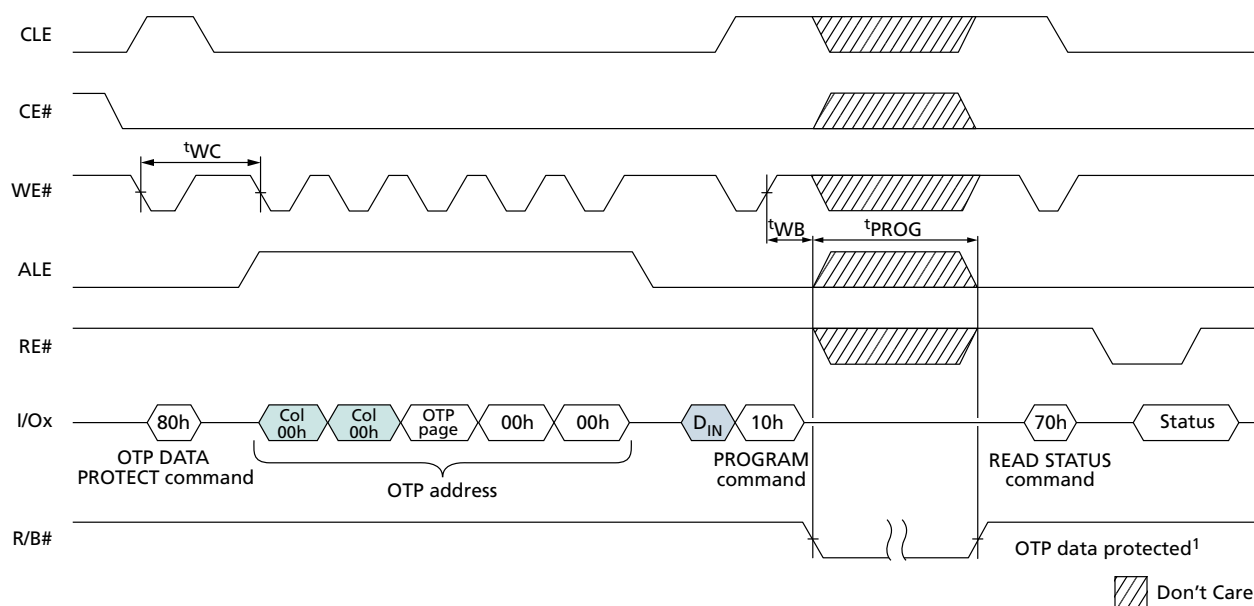
The READ STATUS (70h) command is the only valid command for reading status in OTP operation mode. Bit 5 of the status register reflects the state of R/B#.

When the device is ready, read bit 0 of the status register to determine whether the operation passed or failed (see Status Operations).



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP One-Time Programmable (OTP) Operations

Figure 58: OTP DATA PROTECT Operation (After Entering OTP Protect Mode)



Note: 1. OTP data is protected following a good status confirmation.

OTP DATA READ (00h-30h)

To read data from the OTP area, set the device to OTP operation mode, then issue the PAGE READ (00h-30h) command. Data can be read from OTP pages within the OTP area whether the area is protected or not.

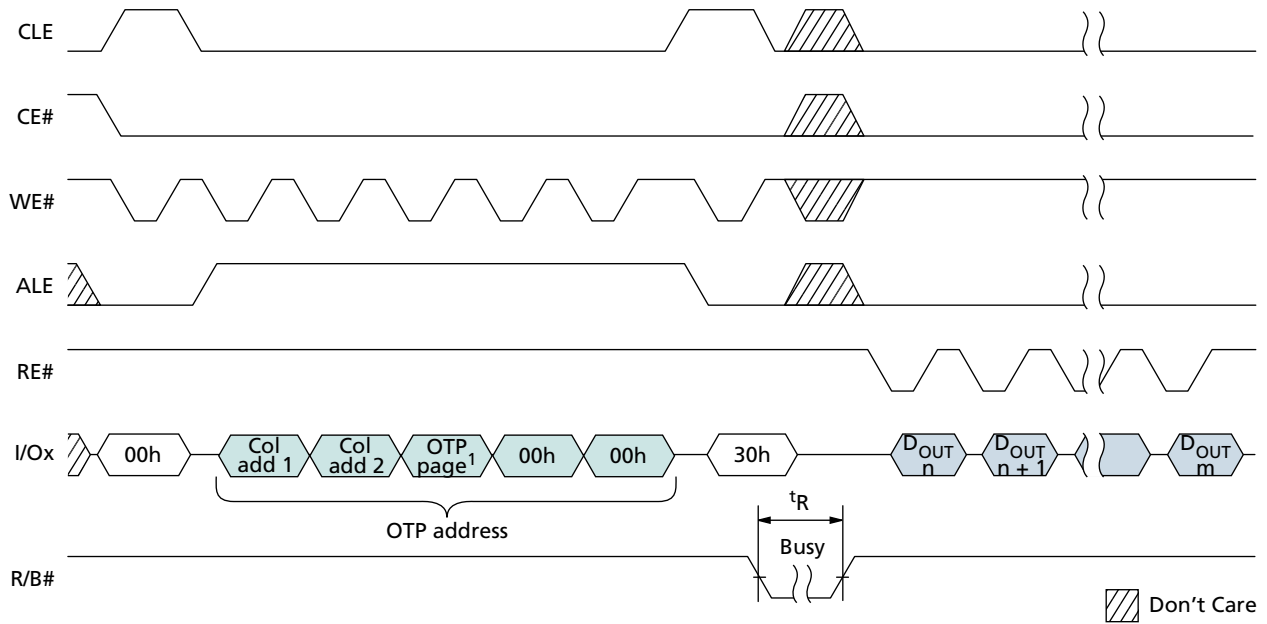
To use the PAGE READ command for reading data from the OTP area, issue the 00h command, and then issue five address cycles: for the first two cycles, the column address; and for the remaining address cycles, select a page in the range of 02h-00h-00h through 31h-00h-00h. Lastly, issue the 30h command. The PAGE READ CACHE MODE command is not supported on OTP pages.

R/B# goes LOW (\bar{R}) while the data is moved from the OTP page to the data register. The READ STATUS (70h) command is the only valid command for reading status in OTP operation mode. Bit 5 of the status register reflects the state of R/B# (see Status Operations).

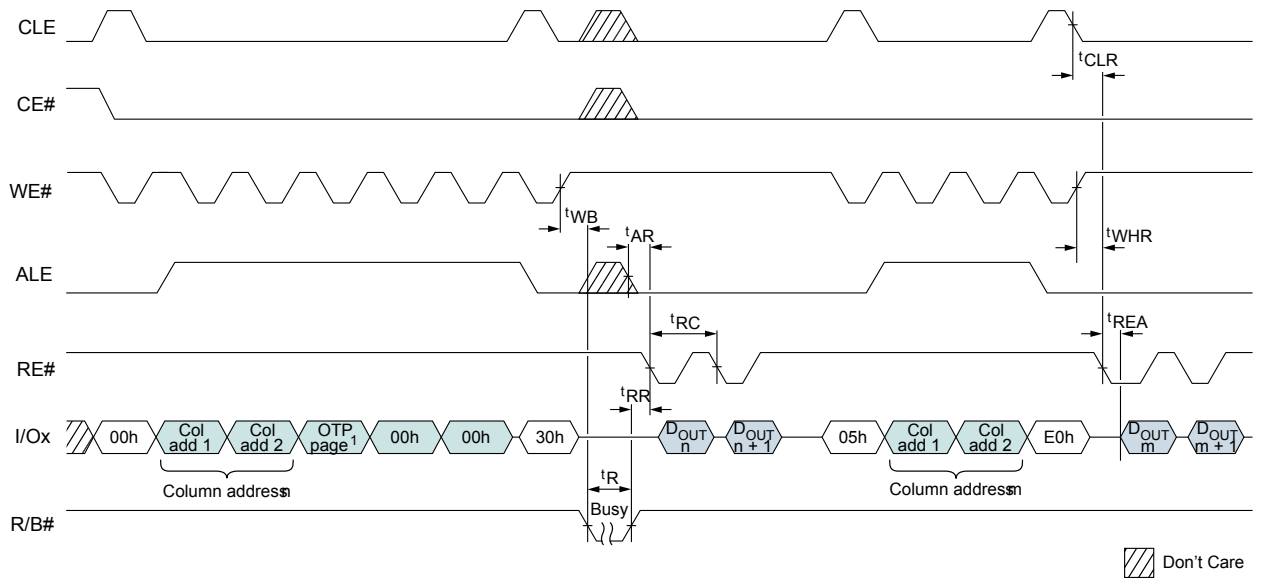
Normal READ operation timings apply to OTP read accesses. Additional pages within the OTP area can be selected by repeating the OTP DATA READ command.

The PAGE READ command is compatible with the RANDOM DATA OUTPUT (05h-E0h) command.

Only data on the current page can be read. Pulsing RE# outputs data sequentially.


Figure 59: OTP DATA READ


Note: 1. The OTP page must be within the 02h–31h range.

Figure 60: OTP DATA READ with RANDOM DATA READ Operation


Note: 1. The OTP page must be within the range 02h–31h.

ECC Protection

Internal ECC enables 9-bit detection and 8-bit correction in 512 bytes (x8) of main area and 16 bytes (x8) of spare area or 256 words (x16) of the main area and 8 words (x16) of



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP ECC Protection

spare area. During the busy time for PROGRAM operations, internal ECC generates parity bits when error detection is complete. During READ operations the device executes the internal ECC engine (9-bit detection and 8-bit error correction). When the READ operation is complete, read status bit 0 must be checked to determine whether errors larger than eight bits have occurred.

Following the READ STATUS command, the device must be returned to read mode by issuing the 00h command.

Limitations of internal ECC include the spare area, defined in the Spare Area Mapping (x8) and (x16) tables, and ECC parity areas that cannot be written to. Each ECC user area (referred to main and spare) must be written within one partial-page program so that the NAND device can calculate the proper ECC parity. The number of partial-page programs within a page cannot exceed four.

During a PROGRAM operation, the device calculates an ECC code on the 4K page in the cache register, before the page is written to the NAND Flash array. The ECC code is stored in the spare area of the page.

During a READ operation, the page data is read from the array to the cache register, where the ECC code is calculated and compared with the ECC code value read from the array. If a 1- to 8-bit error is detected, the error is corrected in the cache register. Only corrected data is output on the I/O bus. The ECC status bit indicates whether the error correction was successful. The Spare Area Mapping (x8) and (x16) tables that follow show the ECC protection scheme used throughout a page.

With internal ECC, the user must accommodate the following:

- Spare area definitions provided in the Spare Area Mapping table below.
- WRITES to ECC are supported for main and spare areas 0 and 1. WRITES to the ECC area are prohibited (see the Spare Area Mapping table below).
- When using partial-page programming, the following conditions must both be met: First, in the main user area and in user meta data area, single partial-page programming operations must be used (see the Spare Area Mapping table below). Second, within a page, the user can perform a maximum of four partial-page programming operations.

Table 26: Spare Area Mapping (x8)

Max Byte Address	Min Byte Address	ECC Protected	Area	Description
User Data				
1FFh	000h	Yes	Main 0	User data 0
3FFh	200h	Yes	Main 1	User data 1
5FFh	400h	Yes	Main 2	User data 2
7FFh	600h	Yes	Main 3	User data 3
9FFh	800h	Yes	Main 4	User data 4
BFFh	A00h	Yes	Main 5	User data 5
DFFh	C00h	Yes	Main 6	User data 6
FFFh	E00h	Yes	Main 7	User data 7
User Meta Data				


Table 26: Spare Area Mapping (x8) (Continued)

Max Byte Address	Min Byte Address	ECC Protected	Area	Description
100Fh	1000h	Yes	Spare 0	User meta data
101Fh	1010h	Yes	Spare 1	User meta data
102Fh	1020h	Yes	Spare 2	User meta data
103Fh	1030h	Yes	Spare 3	User meta data
104Fh	1040h	Yes	Spare 4	User meta data
105Fh	1050h	Yes	Spare 5	User meta data
106Fh	1060h	Yes	Spare 6	User meta data
107Fh	1070h	Yes	Spare 7	User meta data
ECC				
108Fh	1080h	Yes	Spare 0	ECC for main/spare 0
109Fh	1090h	Yes	Spare 1	ECC for main/spare 1
10AFh	10A0h	Yes	Spare 2	ECC for main/spare 2
10BFh	10B0h	Yes	Spare 3	ECC for main/spare 3
10CFh	10C0h	Yes	Spare 4	ECC for main/spare 4
10DFh	10D0h	Yes	Spare 5	ECC for main/spare 5
10EFh	10E0h	Yes	Spare 6	ECC for main/spare 6
10FFh	10F0h	Yes	Spare 7	ECC for main/spare 7

Table 27: Spare Area Mapping (x16)

Max Byte Address	Min Byte Address	ECC Protected	Area	Description
User Data				
0FFh	000h	Yes	Main 0	User data 0
1FFh	100h	Yes	Main 1	User data 1
2FFh	200h	Yes	Main 2	User data 2
3FFh	300h	Yes	Main 3	User data 3
4FFh	400h	Yes	Main 4	User data 4
5FFh	500h	Yes	Main 5	User data 5
6FFh	600h	Yes	Main 6	User data 6
7FFh	700h	Yes	Main 7	User data 7
User Meta Data				
807h	800h	Yes	Spare 0	User meta data
80Fh	808h	Yes	Spare 1	User meta data
817h	810h	Yes	Spare 2	User meta data
81Fh	818h	Yes	Spare 3	User meta data
827h	820h	Yes	Spare 4	User meta data


Table 27: Spare Area Mapping (×16) (Continued)

Max Byte Address	Min Byte Address	ECC Protected	Area	Description
82Fh	828h	Yes	Spare 5	User meta data
837h	830h	Yes	Spare 6	User meta data
83Fh	838h	Yes	Spare 7	User meta data
ECC				
847h	840h	Yes	Spare 0	ECC for main/spare 0
84Fh	848h	Yes	Spare 1	ECC for main/spare 1
857h	850h	Yes	Spare 2	ECC for main/spare 2
85Fh	858h	Yes	Spare 3	ECC for main/spare 3
867h	860h	Yes	Spare 4	ECC for main/spare 4
86Fh	868h	Yes	Spare 5	ECC for main/spare 5
877h	870h	Yes	Spare 6	ECC for main/spare 6
87Fh	878h	Yes	Spare 7	ECC for main/spare 7

Table 28: ECC Status

Bit 4	Bit 3	Bit 0	Description
0	0	0	No bit errors were detected.
0	0	1	More than 8 bits error were detected and not corrected.
0	1	0	4 to 6 bit errors were detected and corrected. Refresh is recommended.
0	1	1	Reserved
1	0	0	1 to 3 bit errors/page were detected and corrected.
1	0	1	Reserved
1	1	0	7 to 8 bit errors were detected and corrected. Refresh is required to guarantee data retention.
1	1	1	Reserved



Error Management

Each NAND Flash die (LUN) is specified to have a minimum number of valid blocks (NVB) of the total available blocks. This means the die (LUNs) could have blocks that are invalid when shipped from the factory. An invalid block is one that contains at least one page that has more bad bits than can be corrected by the minimum required ECC. Additional blocks can develop with use. However, the total number of available blocks per die (LUN) will not fall below NVB during the endurance life of the product.

Although NAND Flash memory devices could contain bad blocks, they can be used quite reliably in systems that provide bad block management and error-correction algorithms. This type of software environment ensures data integrity.

Internal circuitry isolates each block from other blocks, so the presence of a bad block does not affect the operation of the rest of the NAND Flash array.

NAND Flash devices are shipped from the factory erased. The factory identifies invalid blocks before shipping by attempting to program the bad block mark into every location in the first page of each invalid block. It may not be possible to program every location with the bad block mark. However, the first spare area location in each bad block is guaranteed to contain the bad block mark. This method is compliant with ONFI Factory Defect Mapping requirements.

System software should check the first spare area location on the first page of each block prior to performing any PROGRAM or ERASE operations on the NAND Flash device. A bad block table can then be created, enabling system software to map around these areas. Factory testing is performed under worst-case conditions. Because invalid blocks could be marginal, it may not be possible to recover this information if the block is erased.

Over time, some memory locations may fail to program or erase properly. In order to ensure that data is stored properly over the life of the NAND Flash device, the following precautions are required:

- Always check status after a PROGRAM or ERASE operation
- Under typical conditions, use the minimum required ECC (see table below)
- Use bad block management and wear-leveling algorithms

Table 29: Error Management Details

Description	Requirement
Minimum number of valid blocks (NVB) per LUN	2008
Total available blocks per LUN	2048
First spare area location	×8: byte 4096 ×16: word 2048
Bad block mark	×8: 00h ×16: 0000h
Minimum required ECC	8-bit ECC per 544 bytes of data
Minimum ECC with internal ECC enabled	8-bit ECC per 528 bytes (user data) + 16 bytes (parity data)



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications

Electrical Specifications

Stresses greater than those listed can cause permanent damage to the device. This is stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not guaranteed. Exposure to absolute maximum rating conditions for extended periods can affect reliability.

Table 30: Absolute Maximum Ratings

Parameter/Condition		Symbol	Min	Max	Unit
Voltage input	3.3V	V_{IN}	-0.6	+4.6	V
V_{CC} supply voltage	3.3V	V_{CC}	-0.6	+4.6	V
Storage temperature		T_{STG}	-65	+150	°C
Electrostatic discharge voltage		V_{ESD}	-2000	2000	V

Note: 1. All specified voltages are with respect to V_{SS} .

Table 31: Recommended Operating Conditions

Parameter/Condition		Symbol	Min	Typ	Max	Unit
V_{CC} supply voltage	1.8V	V_{CC}	1.7	1.8	1.95	V
	3.3V	V_{CC}	2.7	3.3	3.6	V
Ground supply voltage		V_{SS}	0	0	0	V
Operating temperature	Industrial	T_A	-40	–	+85	°C
	Automotive		-40	–	+105	°C

Notes: 1. 3.3V and 1.8V are separate line items.
2. All specified voltages are with respect to V_{SS} .

Table 32: Capacitance

Description	Symbol	Max	Unit	Notes
Input/output capacitance (I/O)	C_{IO}	8	pF	1, 2
Input capacitance	C_{IN} (4Gb)	6	pF	1, 2
Input capacitance	C_{IN} (8Gb)	9	pF	1, 2

Notes: 1. These parameters will be verified in device characterization.
2. Test conditions: $T_C = 25^\circ\text{C}$; $f = 1\text{ MHz}$; $V_{in} = 0\text{V}$.

Table 33: Test Conditions

Parameter	Value	Notes
Input pulse levels	0.0V to V_{CC}	
Input rise and fall times	5ns	
Input and output timing levels	$V_{CC}/2$	

**4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP
Electrical Specifications****Table 33: Test Conditions (Continued)**

Parameter	Value	Notes
Output load	1 TTL GATE and CL = 50pF (3.3V, 1.8V)	1

Note: 1. These parameters will be verify in device characterization.



Electrical Specifications – DC Characteristics and Operating Conditions

Table 34: DC Characteristics and Operating Conditions (3.3V)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit	Notes
Sequential read current ECC off	$t_{RC} = t_{RC} \text{ (MIN)}; CE\# = V_{IL};$ $I_{OUT} = 0\text{mA}$	I_{CC1}	–	15	20	mA	1
Sequential read current ECC on	$t_{RC} = t_{RC} \text{ (MIN)}; CE\# = V_{IL};$ $I_{OUT} = 0\text{mA}$	I_{CC1}	–	25	35	mA	1
Program current ECC off	–	I_{CC2}	–	15	20	mA	1
Program current ECC on	–	I_{CC2}	–	20	25	mA	1
Erase current	–	I_{CC3}	–	15	20	mA	1
Standby current (TTL)	$CE\# = V_{IH};$ $WP\# = 0V/V_{CC}$	I_{SB1}	–	–	1	mA	
Standby current (CMOS)	$CE\# = V_{CC} - 0.2V;$ $WP\# = 0V/V_{CC}$	I_{SB2}	–	20	100	μA	
Staggered power-up current	Rise time = 1ms Line capacitance = 0.1 μF	I_{ST}	–	–	10 per die	mA	2
Input leakage current	$V_{IN} = 0V \text{ to } V_{CC}$	I_{LI}	–	–	± 10	μA	
Output leakage current	$V_{OUT} = 0V \text{ to } V_{CC}$	I_{LO}	–	–	± 10	μA	
Input high voltage	$I/O[7:0], I/O[15:0],$ $CE\#, CLE, ALE, WE\#, RE\#,$ $WP\#, R/B\#$	V_{IH}	$0.8 \times V_{CC}$	–	$V_{CC} + 0.3$	V	
Input low voltage, all inputs	–	V_{IL}	-0.3	–	$0.2 \times V_{CC}$	V	
Output high voltage	$I_{OH} = -400\mu\text{A}$	V_{OH}	$0.67 \times V_{CC}$	–	–	V	3
Output low voltage	$I_{OL} = 2.1\text{mA}$	V_{OL}	–	–	0.4	V	3
Output low current	$V_{OL} = 0.4V$	$I_{OL} \text{ (R/B\#)}$	8	10	–	mA	4

- Notes:
1. Typical and maximum values are for single-plane operation only.
 2. Measurement is taken with 1ms averaging intervals and begins after V_{CC} reaches $V_{CC,min}$.
 3. $I_{OL} \text{ (R/B\#)}$ may need to be relaxed if R/B pull-down strength is not set to full.
 4. V_{OH} and V_{OL} may need to be relaxed if I/O drive strength is not set to full.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP

Electrical Specifications – DC Characteristics and Operating Conditions

Table 35: DC Characteristics and Operating Conditions (1.8V)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit	Notes
Sequential read current ECC off	$t_{RC} = t_{RC} \text{ (MIN)}; CE\# = V_{IL};$ $I_{OUT} = 0\text{mA}$	I_{CC1}	–	13	20	mA	1, 2
Sequential read current ECC on	$t_{RC} = t_{RC} \text{ (MIN)}; CE\# = V_{IL};$ $I_{OUT} = 0\text{mA}$	–	–	25	35	mA	1, 2
Program current ECC on	–	I_{CC2}	–	13	20	mA	1, 2
Program current ECC off	–	I_{CC2}	–	20	25	mA	1, 2
Erase current	–	I_{CC3}	–	15	20	mA	1, 2
Standby current (TTL)	$CE\# = V_{IH};$ $LOCK = WP\# = 0V/V_{CC}$	I_{SB1}	–	–	1	mA	
Standby current (CMOS)	$CE\# = V_{CC} - 0.2V;$ $LOCK = WP\# = 0V/V_{CC}$	I_{SB2}	–	15	50	μA	
Staggered power-up current	Rise time = 1ms Line capacitance = $0.1\mu\text{F}$	I_{ST}	–	–	10 per die	mA	3
Input leakage current	$V_{IN} = 0V \text{ to } V_{CC}$	I_{LI}	–	–	± 10	μA	
Output leakage current	$V_{OUT} = 0V \text{ to } V_{CC}$	I_{LO}	–	–	± 10	μA	
Input high voltage	$I/O[7:0], I/O[15:0],$ $CE\#, CLE, ALE, WE\#, RE\#,$ $WP\#, R/B\#, LOCK$	V_{IH}	$0.8 \times V_{CC}$	–	$V_{CC} + 0.3$	V	
Input low voltage, all inputs	–	V_{IL}	-0.3	–	$0.2 \times V_{CC}$	V	
Output high voltage	$I_{OH} = -100\mu\text{A}$	V_{OH}	$V_{CC} - 0.2$	–	–	V	4
Output low voltage	$I_{OL} = 100\mu\text{A}$	V_{OL}	–	–	0.2	V	4
Output low current	$V_{OL} = 0.2V$	$I_{OL} \text{ (R/B\#)}$	3	4	–	mA	5

- Notes:
1. Typical and maximum values are for single-plane operation only.
 2. Values are for single die operations. Values could be higher for interleaved die operations.
 3. Measurement is taken with 1ms averaging intervals and begins after V_{CC} reaches $V_{CC,min}$.
 4. Test conditions for V_{OH} and V_{OL} .
 5. DC characteristics may need to be relaxed if R/B# pull-down strength is not set to full.



Electrical Specifications – AC Characteristics and Operating Conditions

Table 36: AC Characteristics: Command, Data, and Address Input (3.3V)

Parameter	Symbol	Min	Max	Unit	Notes
ALE to data start	t_{ADL}	70	–	ns	1
ALE hold time	t_{ALH}	5	–	ns	
ALE setup time	t_{ALS}	10	–	ns	
CE# hold time	t_{CH}	5	–	ns	
CLE hold time	t_{CLH}	5	–	ns	
CLE setup time	t_{CLS}	10	–	ns	
CE# setup time	t_{CS}	15	–	ns	
Data hold time	t_{DH}	5	–	ns	
Data setup time	t_{DS}	7	–	ns	
WRITE cycle time	t_{WC}	20	–	ns	1
WE# pulse width HIGH	t_{WH}	7	–	ns	1
WE# pulse width	t_{WP}	10	–	ns	1
WP# transition to WE# LOW	t_{WW}	100	–	ns	

Note: 1. Timing for t_{ADL} begins in the address cycle, on the final rising edge of WE#, and ends with the first rising edge of WE# for data input.

Table 37: AC Characteristics: Command, Data, and Address Input (1.8V)

Parameter	Symbol	Min	Max	Unit	Notes
ALE to data start	t_{ADL}	100	–	ns	1
ALE hold time	t_{ALH}	5	–	ns	
ALE setup time	t_{ALS}	10	–	ns	
CE# hold time	t_{CH}	5	–	ns	
CLE hold time	t_{CLH}	5	–	ns	
CLE setup time	t_{CLS}	10	–	ns	
CE# setup time	t_{CS}	25	–	ns	
Data hold time	t_{DH}	5	–	ns	
Data setup time	t_{DS}	10	–	ns	
WRITE cycle time	t_{WC}	30	–	ns	1
WE# pulse width HIGH	t_{WH}	10	–	ns	1
WE# pulse width	t_{WP}	15	–	ns	1
WP# transition to WE# LOW	t_{WW}	100	–	ns	

Note: 1. Timing for t_{ADL} begins in the address cycle, on the final rising edge of WE#, and ends with the first rising edge of WE# for data input.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP

Electrical Specifications – AC Characteristics and Operating Conditions

Table 38: AC Characteristics: Normal Operation (3.3V)

Note 1 applies to all

Parameter	Symbol	Min	Max	Unit	Notes
ALE to RE# delay	t_{AR}	10	–	ns	
CE# access time	t_{CEA}	–	25	ns	
CE# HIGH to output High-Z	t_{CHZ}	–	30	ns	2
CLE to RE# delay	t_{CLR}	10	–	ns	
CE# HIGH to output hold	t_{COH}	15	–	ns	
Output High-Z to RE# LOW	t_{IR}	0	–	ns	
READ cycle time	t_{RC}	20	–	ns	
RE# access time	t_{REA}	–	16	ns	
RE# HIGH hold time	t_{REH}	7	–	ns	
RE# HIGH to output hold	t_{RHOH}	15	–	ns	
RE# HIGH to WE# LOW	t_{RHW}	100	–	ns	2
RE# HIGH to output High-Z	t_{RHZ}	–	100	ns	
RE# LOW to output hold	t_{RLOH}	5	–	ns	
RE# pulse width	t_{RP}	10	–	ns	
Ready to RE# LOW	t_{RR}	20	–	ns	
Reset time (READ/PROGRAM/ERASE)	t_{RST}	–	5/10/500	μ s	3
WE# HIGH to busy	t_{WB}	–	100	ns	4
WE# HIGH to RE# LOW	t_{WHR}	60	–	ns	
ALE to RE# delay	t_{AR}	10	–	ns	

- Notes:
1. AC characteristics may need to be relaxed if I/O drive strength is not set to “full.”
 2. Transition is measured ± 200 mV from steady-state voltage with load. This parameter is sampled and not 100% tested.
 3. The first time the RESET (FFh) command is issued while the device is idle, the device will go busy for a maximum of 1ms. Thereafter, the device goes busy for a maximum of 5 μ s.
 4. Do not issue a new command during t_{WB} , even if R/B# is ready.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP

Electrical Specifications – AC Characteristics and Operating Conditions

Table 39: AC Characteristics: Normal Operation (1.8V)

Note 1 applies to all

Parameter	Symbol	Min	Max	Unit	Notes
ALE to RE# delay	t_{AR}	10	–	ns	
CE# access time	t_{CEA}	–	30	ns	
CE# HIGH to output High-Z	t_{CHZ}	–	50	ns	2
CLE to RE# delay	t_{CLR}	10	–	ns	
CE# HIGH to output hold	t_{COH}	15	–	ns	
Output High-Z to RE# LOW	t_{IR}	0	–	ns	
READ cycle time	t_{RC}	30	–	ns	
RE# access time	t_{REA}	–	25	ns	
RE# HIGH hold time	t_{REH}	10	–	ns	
RE# HIGH to output hold	t_{RHOH}	15	–	ns	
RE# HIGH to WE# LOW	t_{RHW}	100	–	ns	2
RE# HIGH to output High-Z	t_{RHZ}	–	65	ns	
RE# pulse width	t_{RP}	15	–	ns	
Ready to RE# LOW	t_{RR}	20	–	ns	
Reset time (READ/PROGRAM/ERASE)	t_{RST}	–	7/13/600	μ s	3
WE# HIGH to busy	t_{WB}	–	100	ns	4
WE# HIGH to RE# LOW	t_{WHR}	80	–	ns	

- Notes:
1. AC characteristics may need to be relaxed if I/O drive strength is not set to “full.”
 2. Transition is measured ± 200 mV from steady-state voltage with load. This parameter is sampled and not 100% tested.
 3. The first time the RESET (FFh) command is issued while the device is idle, the device will go busy for a maximum of 1ms. Thereafter, the device goes busy for a maximum of 5 μ s.
 4. Do not issue a new command during t_{WB} , even if R/B# is ready.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications – Program/Erase Characteristics

Electrical Specifications – Program/Erase Characteristics

Table 40: Program/Erase Characteristics

Parameter	Symbol	Typ	Max	Unit	Notes
Number of partial-page programs (AIT)	NOP	–	4	cycles	1
Number of partial-page programs (AAT)		–	4	cycles	1
BLOCK ERASE operation time	t_{BERS}	2	10	ms	
Busy time for PROGRAM CACHE operation 3.3V V_{CC}	t_{CBSY}	3	600	μs	2
Cache read busy time	t_{RCBSY}	5	25	μs	
Cache read busy time ECC enabled 3.3V V_{CC}	t_{RCBSY_ECC}	80	115	μs	
Cache read busy time ECC enabled 1.8V V_{CC}		90	170	μs	
Busy time for SET FEATURES and GET FEATURES operations	t_{FEAT}	–	1	μs	
LAST PAGE PROGRAM operation time	t_{LPROG}	–	–	–	3
Busy time for OTP DATA PROGRAM operation if OTP is protected (ECC disabled)	t_{OBSY}	–	30	μs	
Busy time for OTP DATA PROGRAM operation if OTP is protected (ECC enabled), 3.3V	t_{OBSY_ECC}	–	75	μs	
Busy time for OTP DATA PROGRAM operation if OTP is protected (ECC enabled), 1.8V		–	90	μs	
Busy time for PROGRAM/ERASE on locked blocks	t_{LBSY}	–	3	μs	
PROGRAM PAGE operation time	t_{PROG}	200	600	μs	
PROGRAM PAGE ECC ON operation time	t_{PROG_ECC}	240	600	μs	
Power-on reset time	t_{POR}	–	1	ms	
READ PAGE operation time	t_R	–	25	μs	
READ PAGE operation time ECC enabled 3.3V V_{CC}	t_{R_ECC}	80	115	μs	
READ PAGE operation time ECC enabled 1.8V V_{CC}		90	170	μs	

- Notes:
1. Four total partial-page programs to the same page.
 2. t_{CBSY} (MAX) time depends on timing between internal program completion and data-in.
 3. $t_{LPROG} = t_{PROG}$ (last page) + t_{PROG} (last - 1 page) - command load time (last page) - address load time (last page) - data load time (last page).



Asynchronous Interface Timing Diagrams

Figure 61: RESET Operation

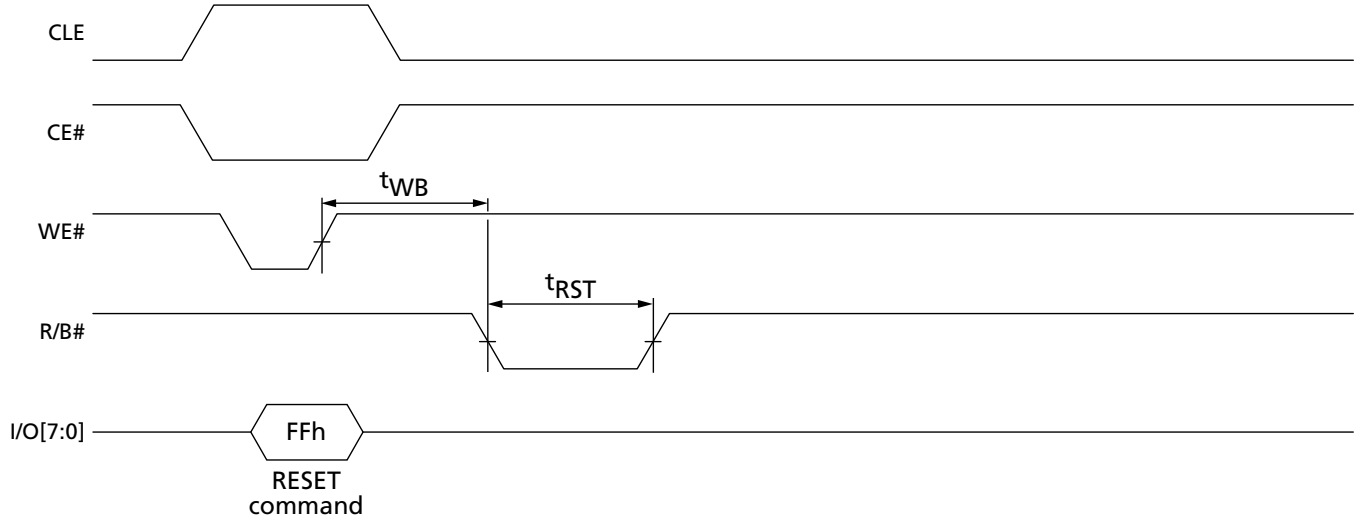
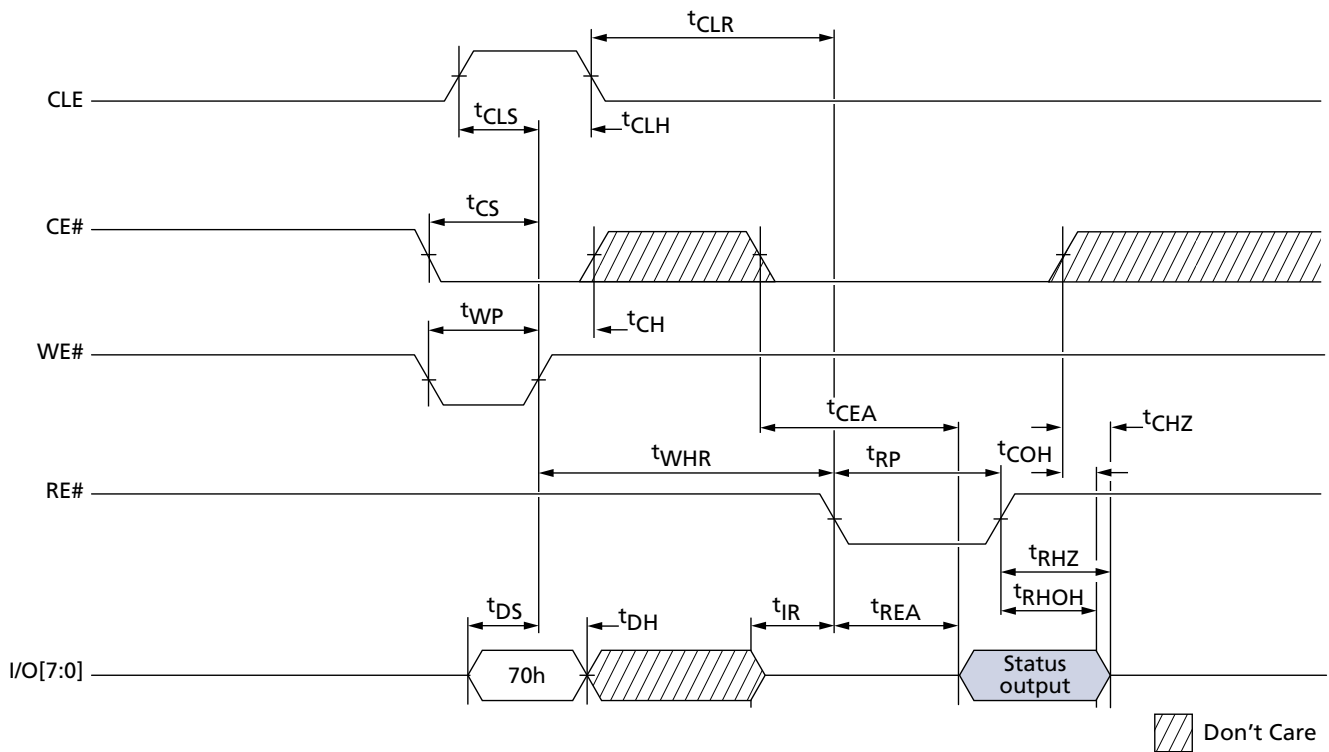


Figure 62: READ STATUS Cycle





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 63: READ STATUS ENHANCED Cycle

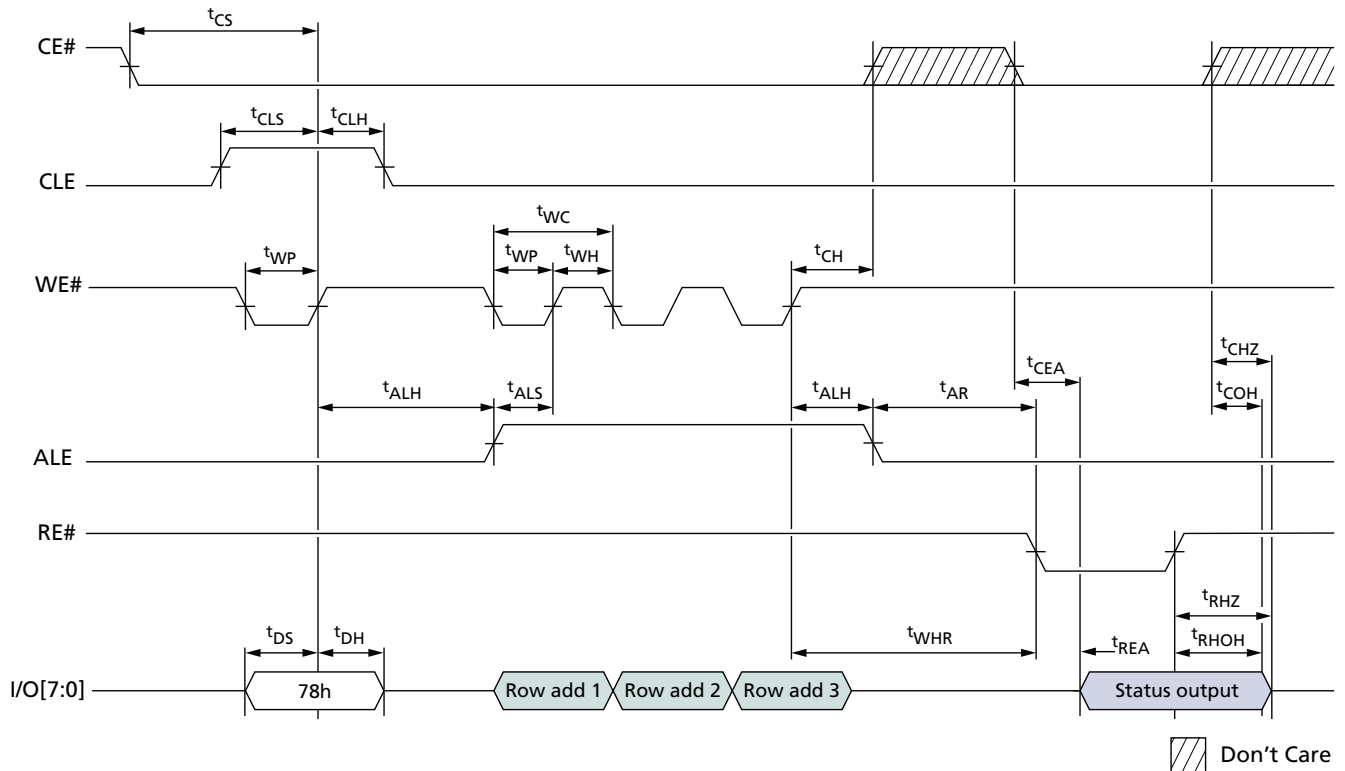
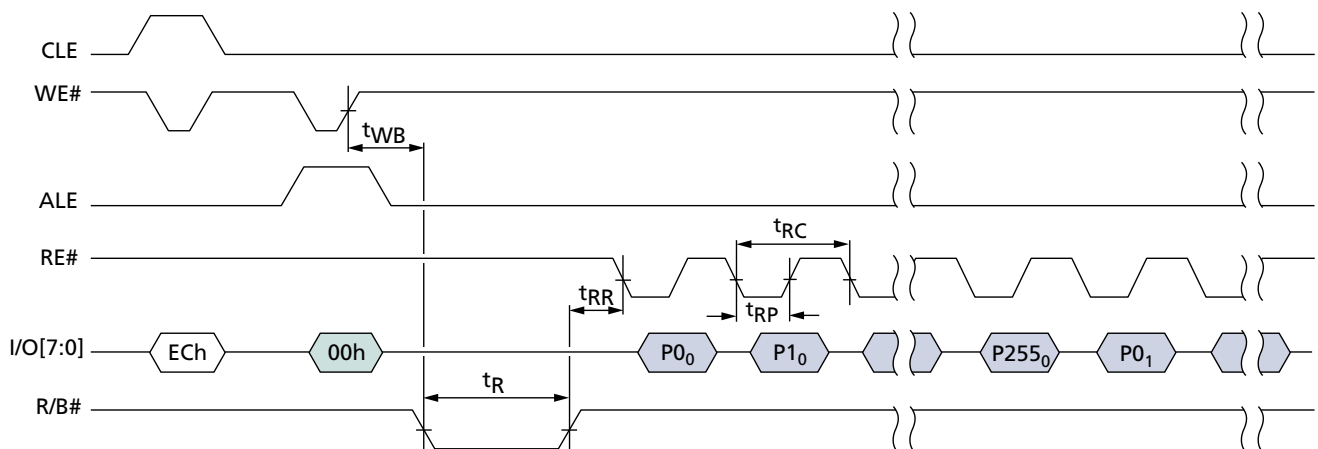


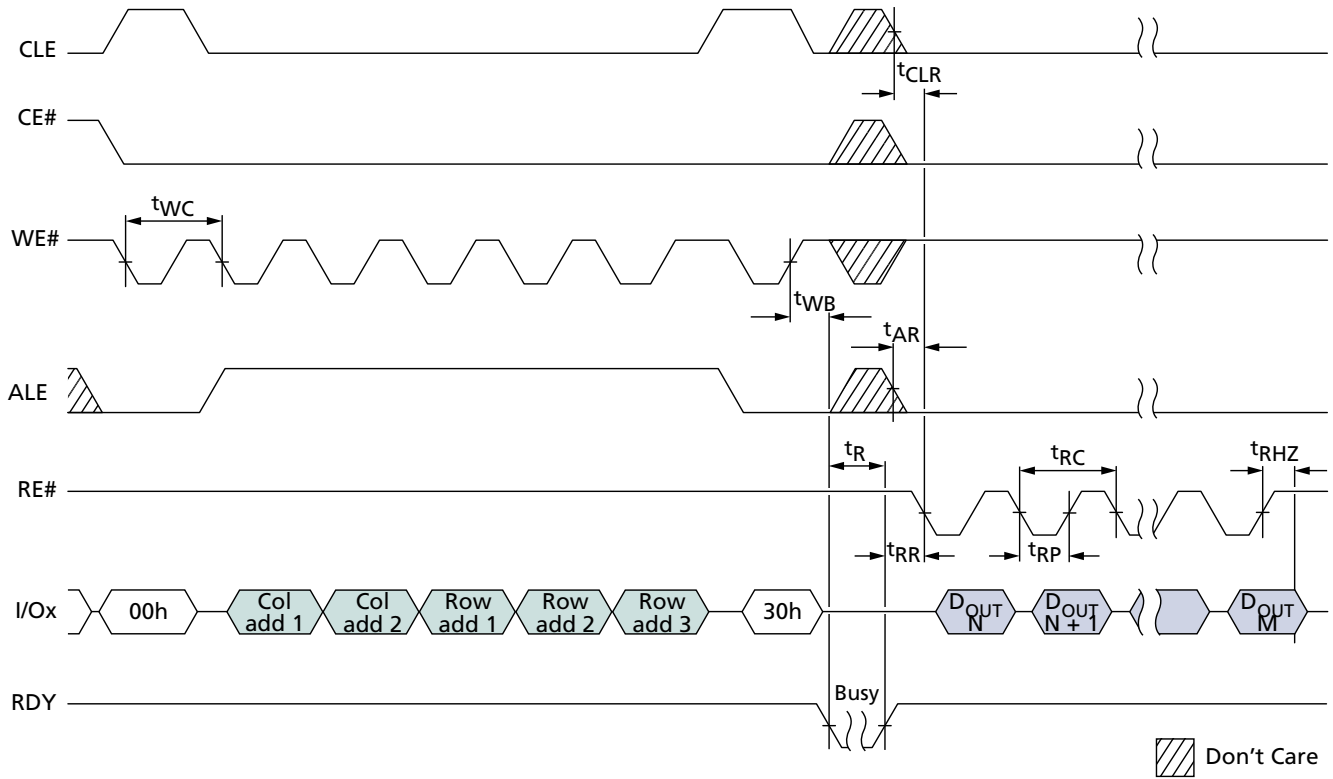
Figure 64: READ PARAMETER PAGE





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 65: READ PAGE





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 66: READ PAGE Operation with CE# "Don't Care"

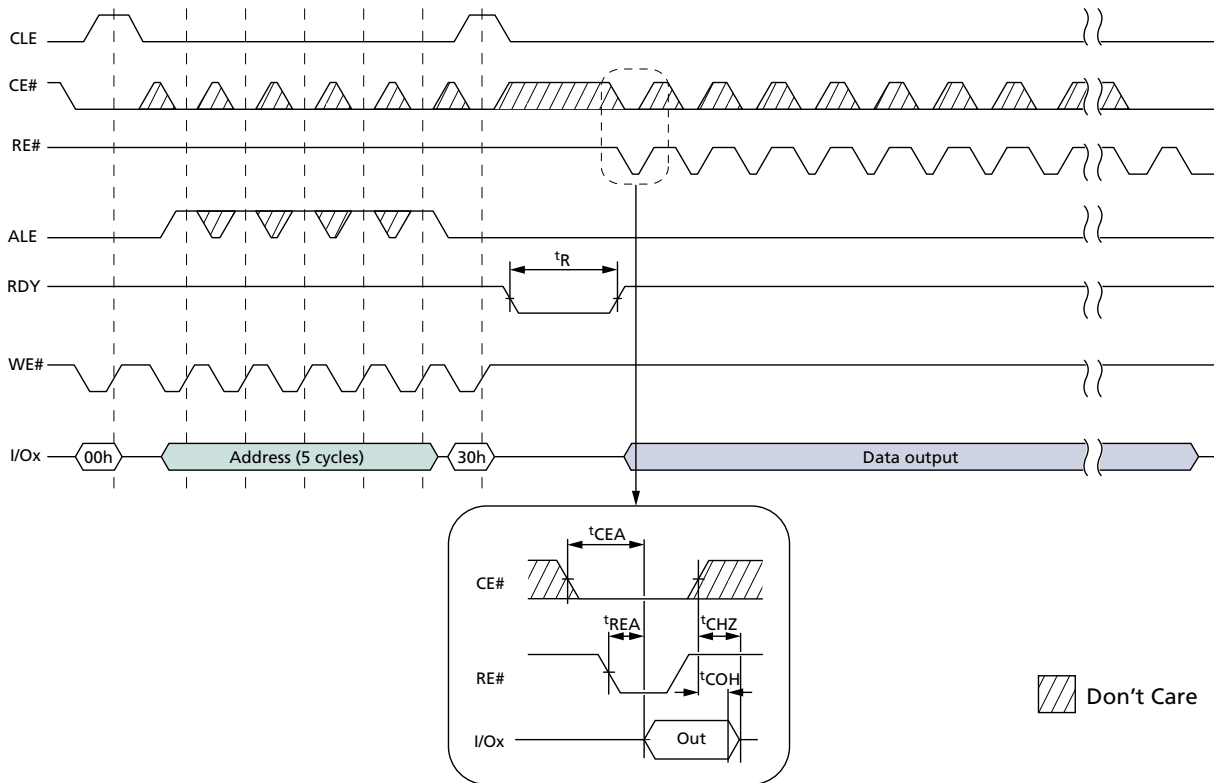
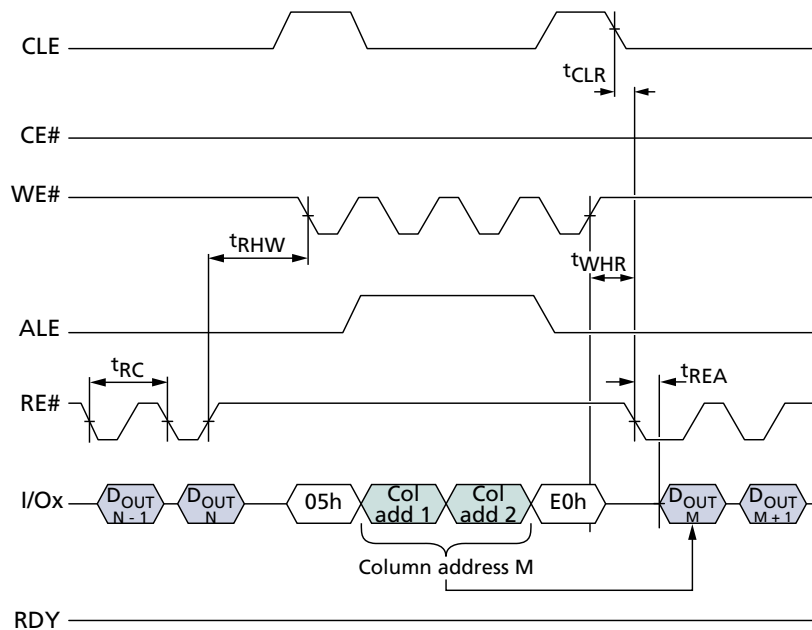


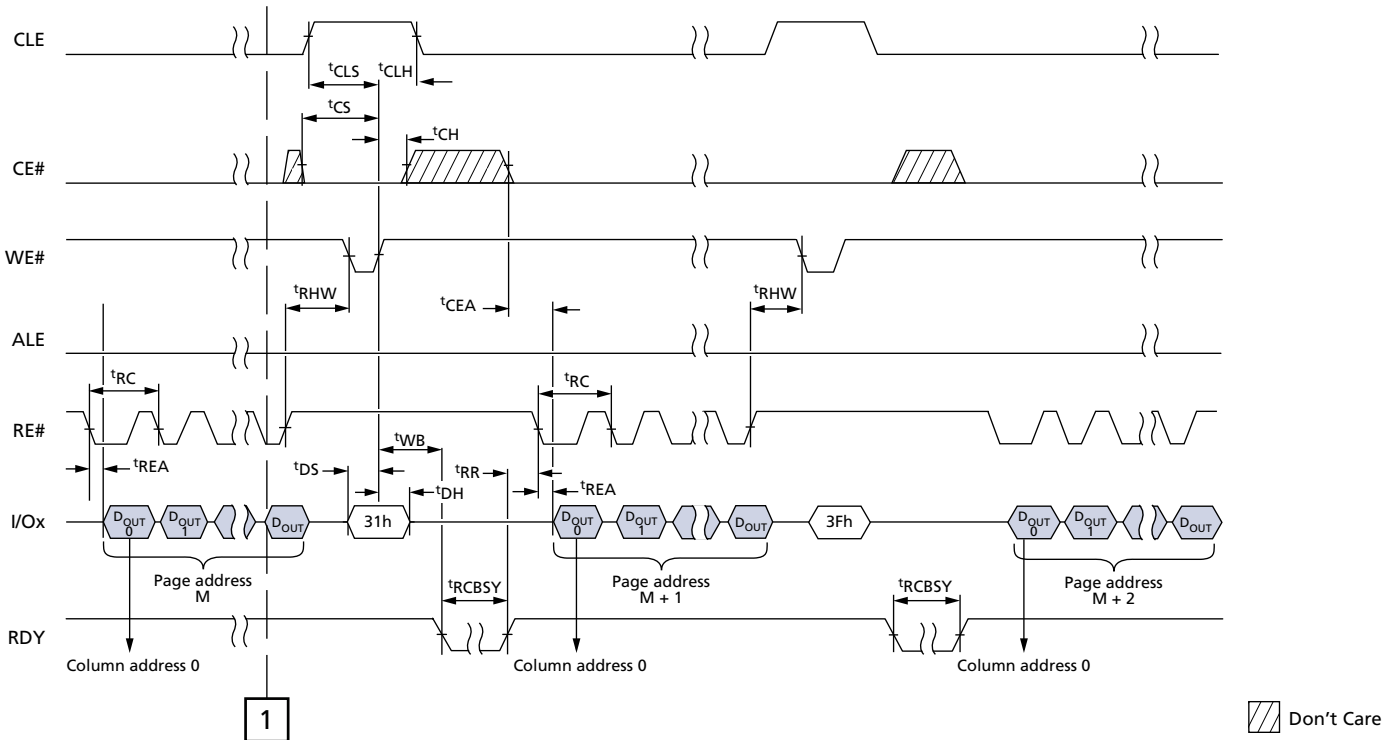
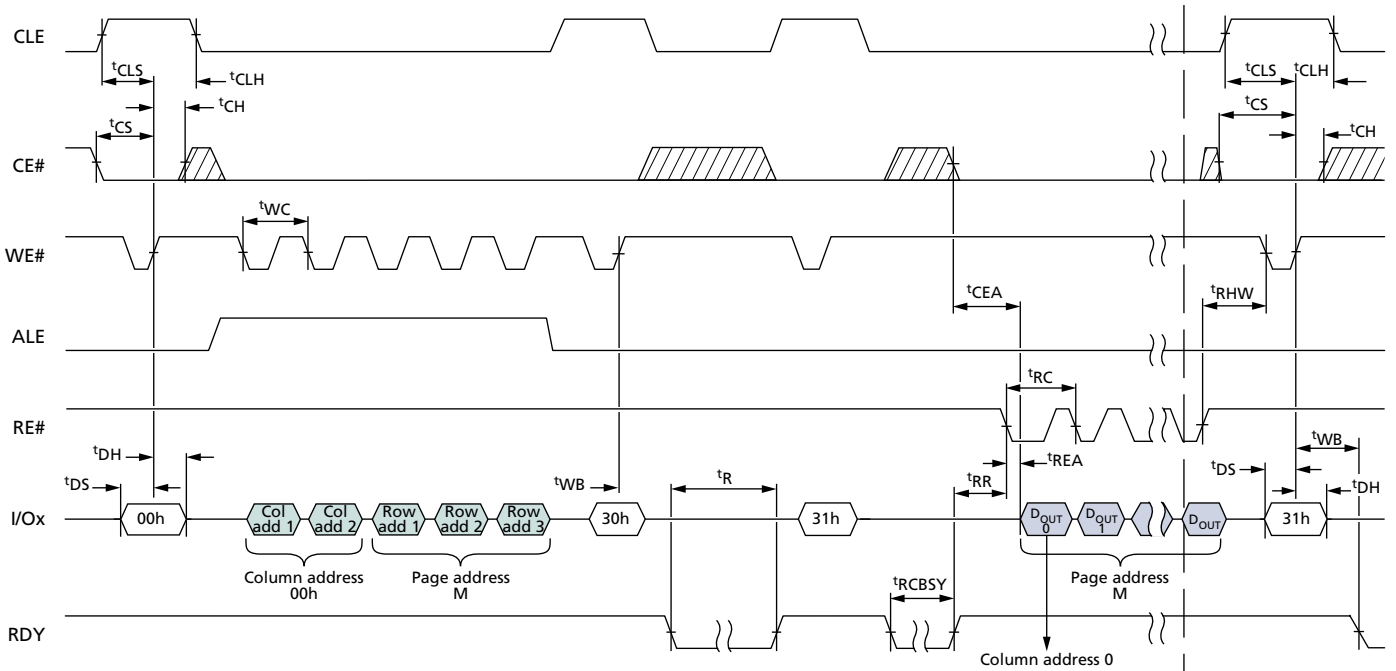
Figure 67: RANDOM DATA READ





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

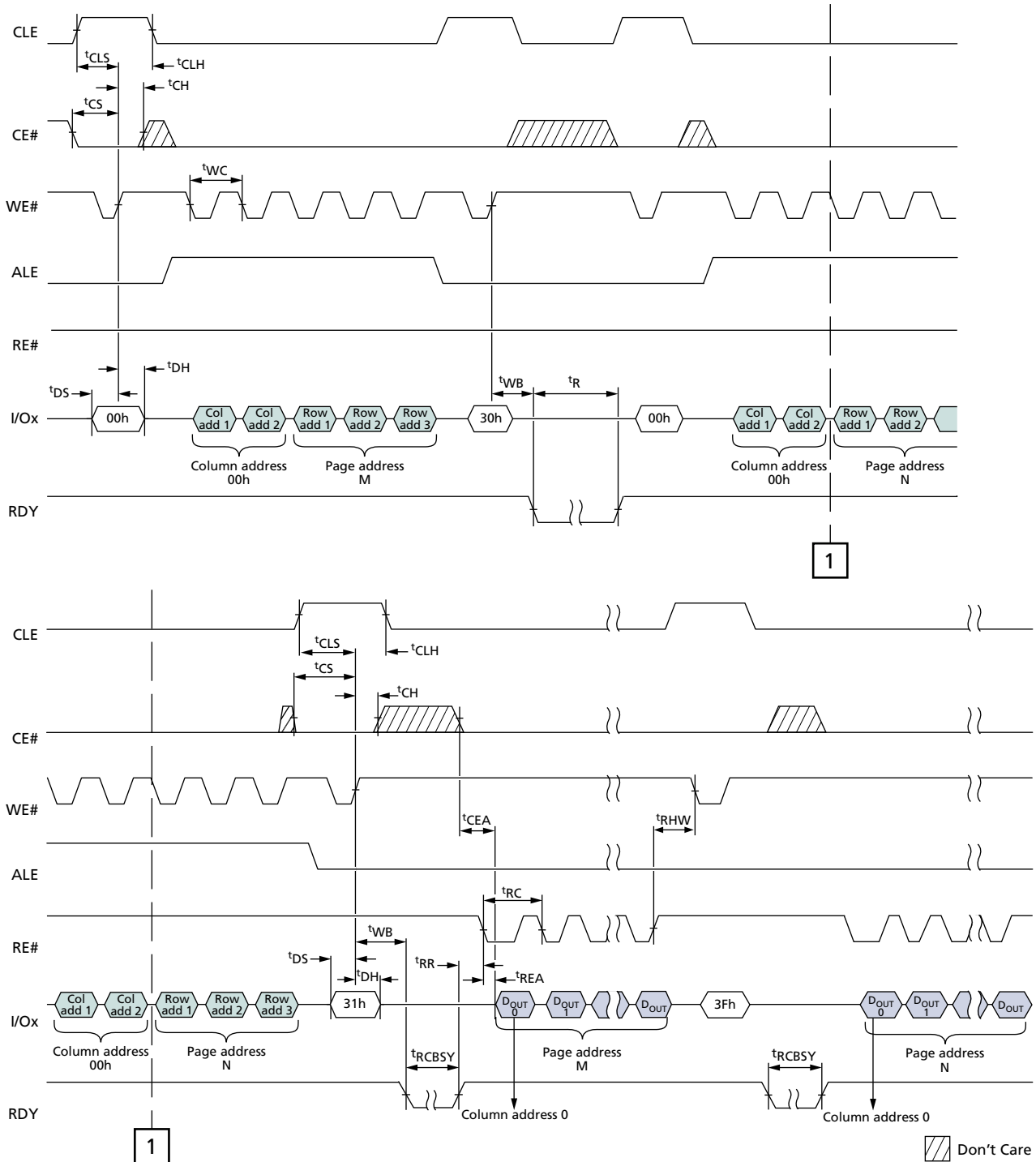
Figure 68: READ PAGE CACHE SEQUENTIAL





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 69: READ PAGE CACHE RANDOM





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 70: READ ID Operation

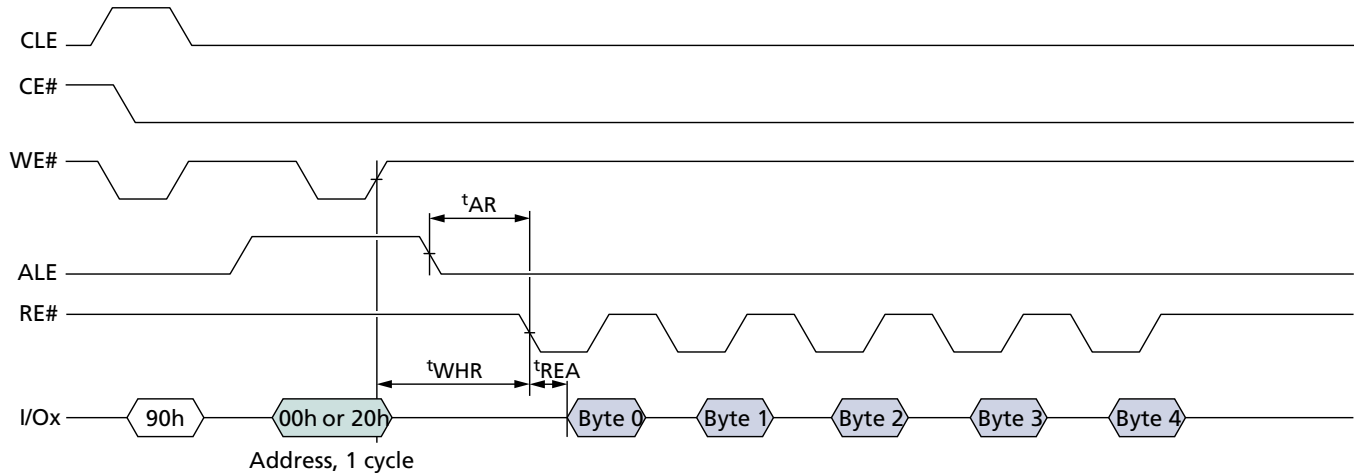
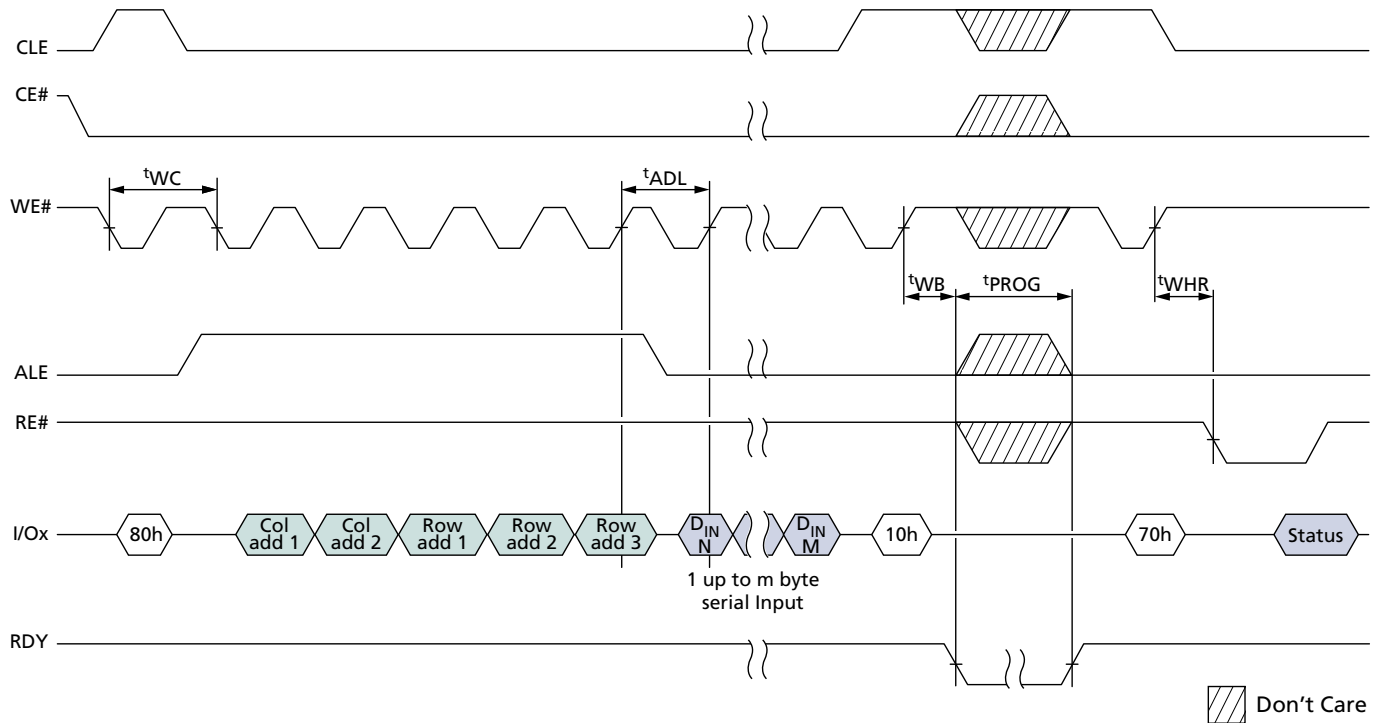


Figure 71: PROGRAM PAGE Operation





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 72: PROGRAM PAGE Operation with CE# "Don't Care"

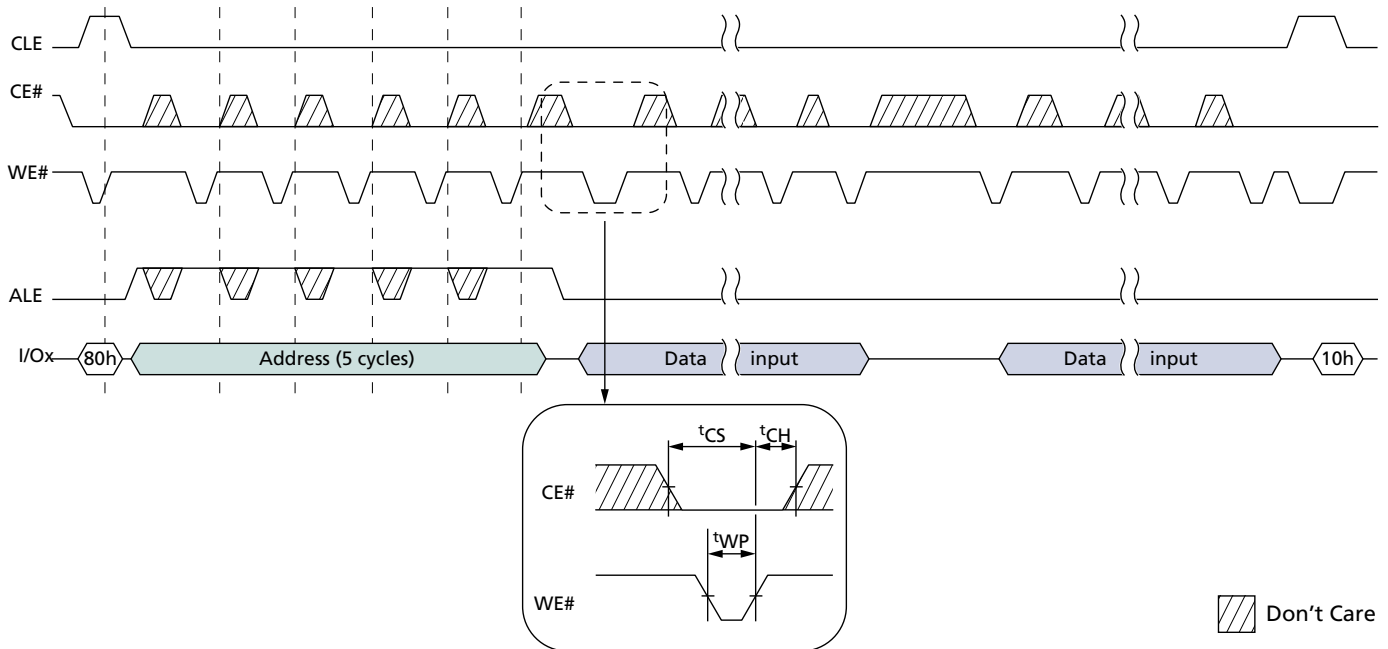
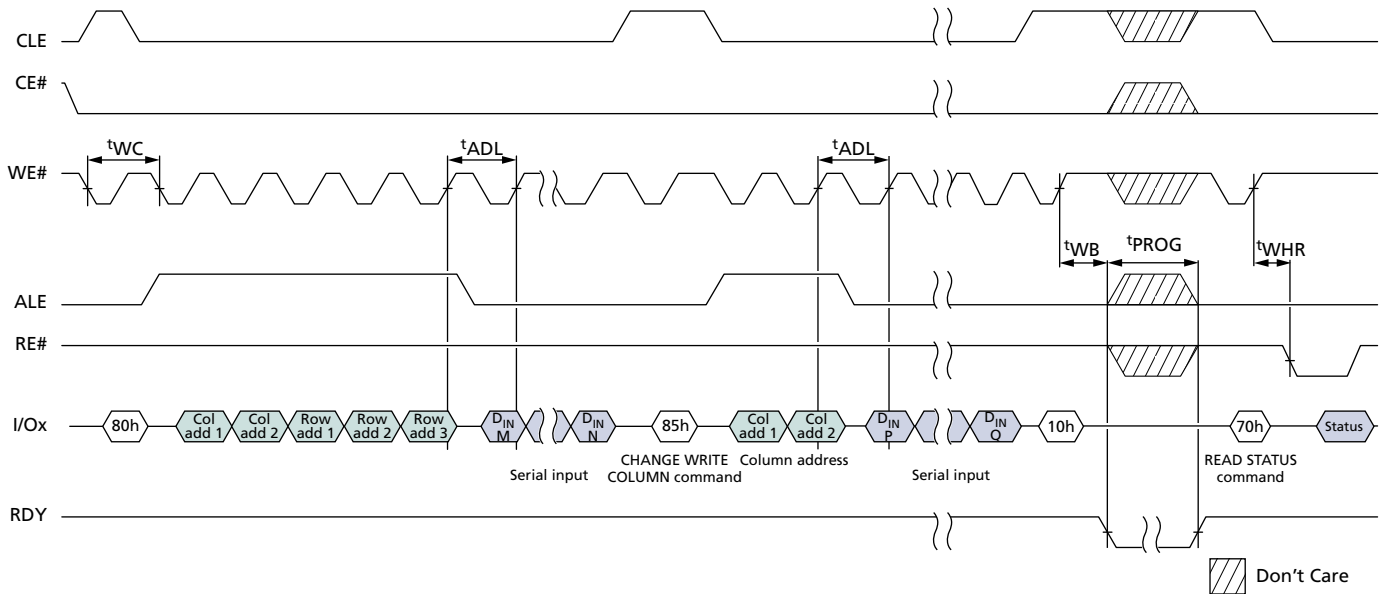


Figure 73: PROGRAM PAGE Operation with RANDOM DATA INPUT





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 74: PROGRAM PAGE CACHE

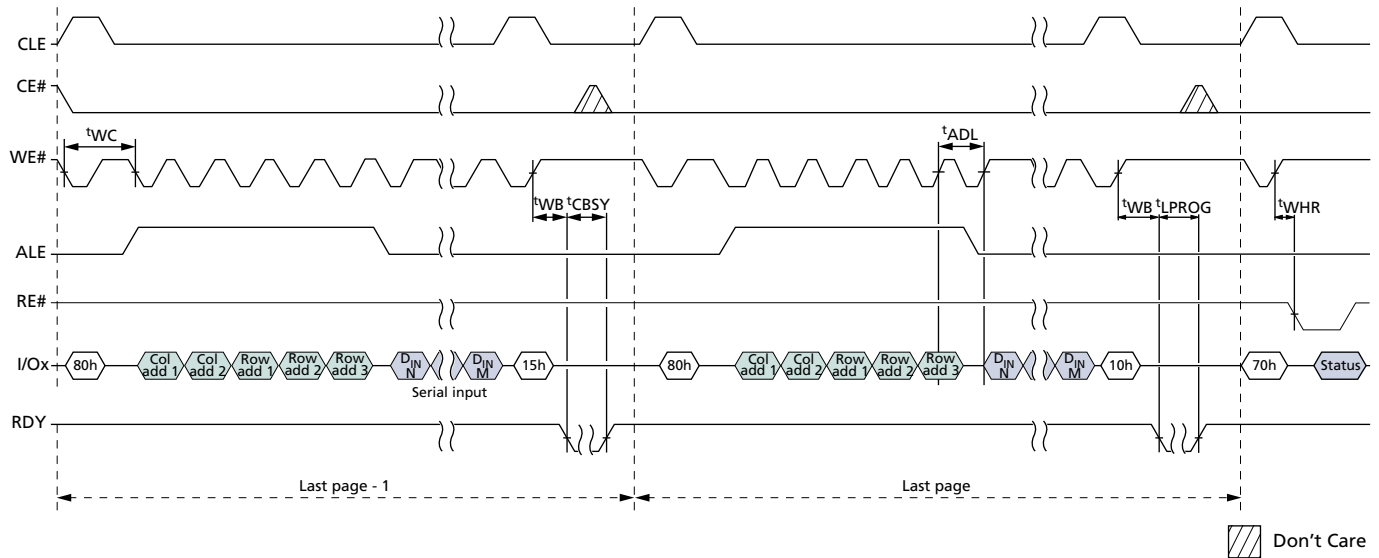
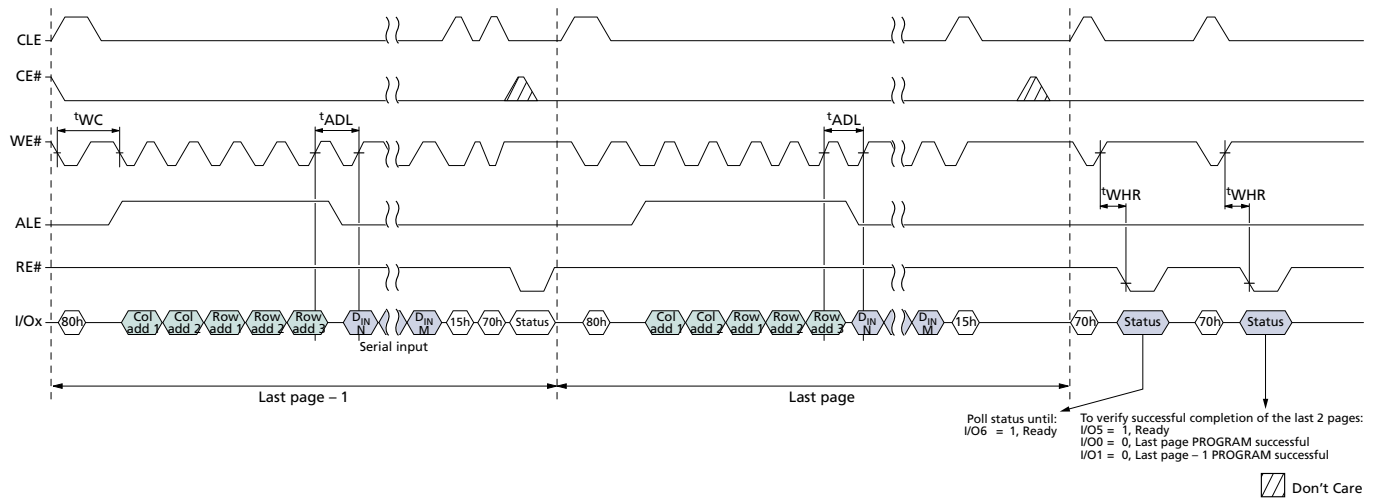


Figure 75: PROGRAM PAGE CACHE Ending on 15h





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Asynchronous Interface Timing Diagrams

Figure 76: INTERNAL DATA MOVE

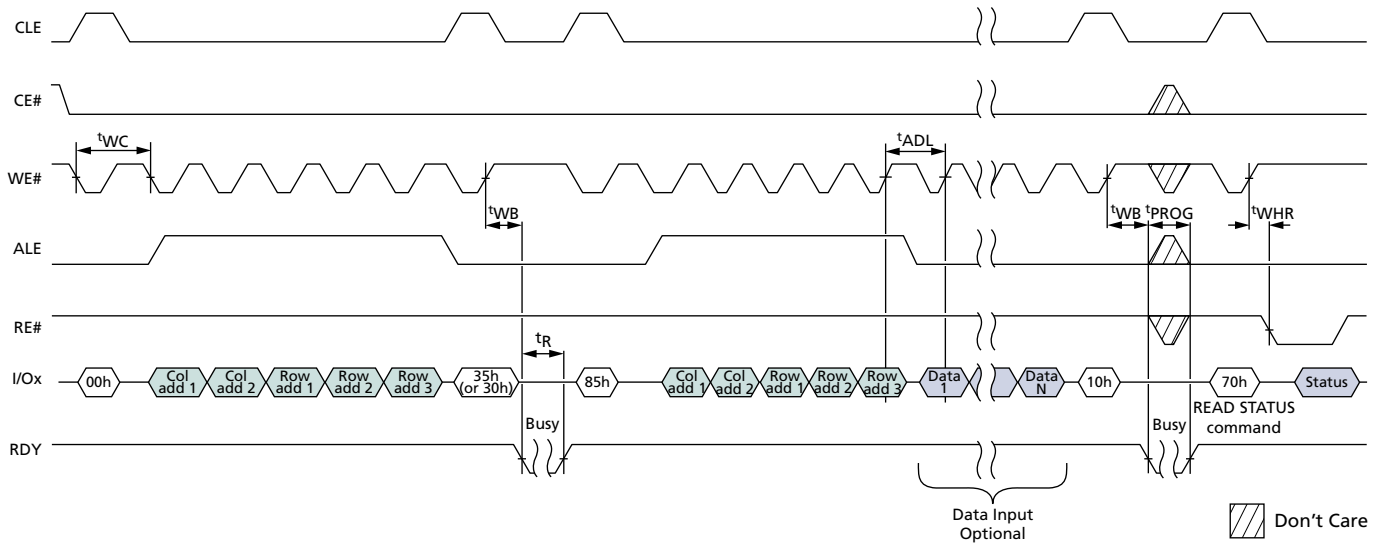
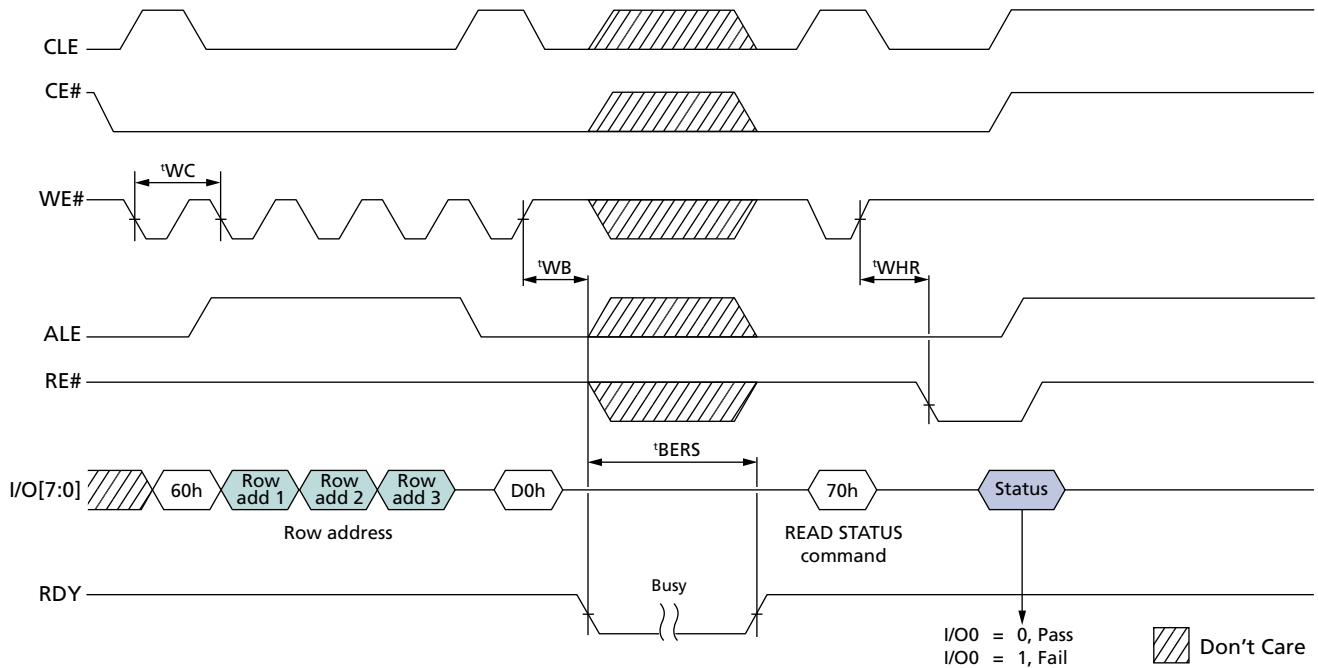


Figure 77: ERASE BLOCK Operation





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP
1Gb: x16, x32 Mobile LPDDR2 SDRAM

1Gb: x16, x32 Mobile LPDDR2 SDRAM

Features

- Ultra low-voltage core and I/O power supplies
 - $V_{DD2} = 1.14\text{--}1.30\text{V}$
 - $V_{DDCA}/V_{DDQ} = 1.14\text{--}1.30\text{V}$
 - $V_{DD1} = 1.70\text{--}1.95\text{V}$
- Clock frequency range
 - 533–10 MHz (data rate range: 1066–20 Mb/s/pin)
- Four-bit prefetch DDR architecture
- Eight internal banks for concurrent operation
- Multiplexed, double data rate, command/address inputs; commands entered on every CK edge
- Bidirectional/differential data strobe per byte of data (DQS/DQS#)
- Programmable READ and WRITE latencies (RL/WL)
- Programmable burst lengths: 4, 8, or 16
- Per-bank refresh for concurrent operation
- Partial-array self refresh (PASR)
- Deep power-down mode (DPD)
- Selectable output drive strength (DS)
- Clock stop capability

Table 41: S4 Configuration Addressing

Architecture	64 Meg x 16	32 Meg x 32	64 Meg x 32	64 Meg x 64
Die configuration	8 Meg x 16 x 8 banks	4 Meg x 32 x 8 banks	2 x 8 Meg x 16 x 8 banks	4 x 4 Meg x 32 x 8 banks
Row addressing	8K (A[12:0])	8K (A[12:0])	8K (A[12:0])	8K (A[12:0])
Column addressing	1K (A[9:0])	512 (A[8:0])	1K (A[9:0])	512 (A[8:0])
Number of die	1	1	2	4
Die per rank	1	1	2	2
Ranks per channel ¹	1	1	1	2

Note: 1. A channel is a complete LPDRAM interface, including command/address and data pins.

General Description

The 1Gb Mobile Low-Power DDR2 SDRAM (LPDDR2) is a high-speed CMOS, dynamic random-access memory containing 1,073,741,824 bits. The LPDDR2-S4 device is internally configured as an eight-bank DRAM. Each of the x16's 134,217,728-bit banks is organized as 8192 rows by 1024 columns by 16 bits. Each of the x32's 134,217,728-bit banks is organized as 8192 rows by 512 columns by 32 bits.

**4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP**
1Gb: x16, x32 Mobile LPDDR2 SDRAM**General Notes**

Throughout the data sheet, figures and text refer to DQs as “DQ.” DQ should be interpreted as any or all DQ collectively, unless specifically stated otherwise.

“DQS” and “CK” should be interpreted as DQS, DQS# and CK, CK# respectively, unless specifically stated otherwise. “BA” includes all BA pins used for a given density.

In timing diagrams, “CMD” is used as an indicator only. Actual signals occur on CA[9:0].

V_{REF} indicates V_{REFCA} and V_{REFDQ} .

Complete functionality may be described throughout the entire document. Any page or diagram may have been simplified to convey a topic and may not be inclusive of all requirements.

Any specific requirement takes precedence over a general statement.

Any functionality not specifically stated herein is considered undefined, illegal, is not supported, and will result in unknown operation.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP General Description

General Description

The 1Gb Mobile Low-Power DDR2 SDRAM (LPDDR2) is a high-speed CMOS, dynamic random-access memory containing 1,073,741,824 bits. The LPDDR2-S4 device is internally configured as an eight-bank DRAM. Each of the x16's 134,217,728-bit banks is organized as 8192 rows by 1024 columns by 16 bits. Each of the x32's 134,217,728-bit banks is organized as 8192 rows by 512 columns by 32 bits.

General Notes

Throughout the data sheet, figures and text refer to DQs as "DQ." DQ should be interpreted as any or all DQ collectively, unless specifically stated otherwise.

"DQS" and "CK" should be interpreted as DQS, DQS# and CK, CK# respectively, unless specifically stated otherwise. "BA" includes all BA pins used for a given density.

Complete functionality may be described throughout the entire document. Any page or diagram may have been simplified to convey a topic and may not be inclusive of all requirements.

Any specific requirement takes precedence over a general statement.

Any functionality not specifically stated herein is considered undefined, illegal, is not supported, and will result in unknown operation.



I_{DD} Specifications

Table 42: I_{DD} Specifications (32 Meg x 16)
 $V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14\text{--}1.30\text{V}; V_{DD1} = 1.70\text{--}1.95\text{V}$

Parameter	Supply	Clock Rate 533 MHz		Unit
		+85°C	+105°C	
I _{DD01}	V _{DD1}	6	6	mA
I _{DD02}	V _{DD2}	30	35	
I _{DD0,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD2P1}	V _{DD1}	600	600	μA
I _{DD2P2}	V _{DD2}	1600	1600	
I _{DD2P,in}	V _{DDCA} + V _{DDQ}	100	100	
I _{DD2PS1}	V _{DD1}	600	600	μA
I _{DD2PS2}	V _{DD2}	1600	1600	
I _{DD2PS,in}	V _{DDCA} + V _{DDQ}	100	100	
I _{DD2N1}	V _{DD1}	0.6	0.6	mA
I _{DD2N2}	V _{DD2}	20	20	
I _{DD2N,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD2NS1}	V _{DD1}	0.6	0.6	mA
I _{DD2NS2}	V _{DD2}	12	12	
I _{DD2NS,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD3P1}	V _{DD1}	1.4	1.4	mA
I _{DD3P2}	V _{DD2}	5	5	
I _{DD3P,in}	V _{DDCA} + V _{DDQ}	0.1	0.1	
I _{DD3PS1}	V _{DD1}	1.4	1.4	mA
I _{DD3PS2}	V _{DD2}	5	5	
I _{DD3PS,in}	V _{DDCA} + V _{DDQ}	0.1	0.1	
I _{DD3N1}	V _{DD1}	1.5	1.5	mA
I _{DD3N2}	V _{DD2}	22	24	
I _{DD3N,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD3NS1}	V _{DD1}	1.5	1.5	mA
I _{DD3NS2}	V _{DD2}	16	16	
I _{DD3NS,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD4R1}	V _{DD1}	2	2	mA
I _{DD4R2}	V _{DD2}	180	180	
I _{DD4R,in}	V _{DDCA}	2	2	
I _{DD4W1}	V _{DD1}	2	2	mA
I _{DD4W2}	V _{DD2}	200	200	
I _{DD4W,in}	V _{DDCA} + V _{DDQ}	1	1	



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP I_{DD} Specifications

Table 42: I_{DD} Specifications (32 Meg x 16) (Continued)
 $V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14\text{--}1.30\text{V}; V_{DD1} = 1.70\text{--}1.95\text{V}$

Parameter	Supply	Clock Rate 533 MHz		Unit
		+85°C	+105°C	
I _{DD51}	V _{DD1}	20	20	mA
I _{DD52}	V _{DD2}	70	70	
I _{DD5,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD5PB1}	V _{DD1}	2	2	mA
I _{DD5PB2}	V _{DD2}	23	23	
I _{DD5PB,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD5AB1}	V _{DD1}	2	2	mA
I _{DD5AB2}	V _{DD2}	23	23	
I _{DD5AB,in}	V _{DDCA} + V _{DDQ}	1	1	
I _{DD61}	V _{DD1}	–	–	Table 43
I _{DD62}	V _{DD2}	–	–	
I _{DD6,in}	V _{DDCA} + V _{DDQ}	–	–	
I _{DD81}	V _{DD1}	50	50	μA
I _{DD82}	V _{DD2}	50	50	
I _{DD8,in}	V _{DDCA} + V _{DDQ}	20	80	

Table 43: I_{DD6} Partial-Array Self Refresh Current (32 Meg x 16)
 $V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14\text{--}1.30\text{V}; V_{DD1} = 1.70\text{--}1.95\text{V}$

PASR	Supply	I _{DD6} Partial-Array Self Refresh Current		Unit
		–40°C to +85°C	+85°C to +105°C	
Full array	V _{DD1}	350	2100	μA
	V _{DD2}	2000	10700	
	V _{DDi}	30	30	
1/2 array	V _{DD1}	280	2000	
	V _{DD2}	1450	6200	
	V _{DDi}	30	30	
1/4 array	V _{DD1}	240	1800	
	V _{DD2}	1150	4000	
	V _{DDi}	30	30	
1/8 array	V _{DD1}	230	1700	
	V _{DD2}	1000	3000	
	V _{DDi}	30	30	

Note: 1. LPDDR2-S4 SDRAM devices support both bank-masking and segment-masking. I_{DD6} PASR currents are measured using bank-masking only.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP I_{DD} Specifications

Table 44: I_{DD} Specifications (64 Meg x 32)
 $V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14\text{--}1.30\text{V}; V_{DD1} = 1.70\text{--}1.95\text{V}$

Parameter	Supply	Clock Rate 533 MHz		Unit
		+85°C	+105°C	
I _{DD01}	V _{DD1}	12	12	mA
I _{DD02}	V _{DD2}	60	70	
I _{DD0,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD2P1}	V _{DD1}	1200	1200	μA
I _{DD2P2}	V _{DD2}	3200	3200	
I _{DD2P,in}	V _{DDCA} + V _{DDQ}	200	200	
I _{DD2PS1}	V _{DD1}	1200	1200	μA
I _{DD2PS2}	V _{DD2}	3200	3200	
I _{DD2PS,in}	V _{DDCA} + V _{DDQ}	200	200	
I _{DD2N1}	V _{DD1}	1.2	1.2	mA
I _{DD2N2}	V _{DD2}	40	40	
I _{DD2N,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD2NS1}	V _{DD1}	1.2	1.2	mA
I _{DD2NS2}	V _{DD2}	24	24	
I _{DD2NS,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD3P1}	V _{DD1}	2.8	2.8	mA
I _{DD3P2}	V _{DD2}	10	10	
I _{DD3P,in}	V _{DDCA} + V _{DDQ}	0.2	0.2	
I _{DD3PS1}	V _{DD1}	2.8	2.8	mA
I _{DD3PS2}	V _{DD2}	10	10	
I _{DD3PS,in}	V _{DDCA} + V _{DDQ}	0.2	0.2	
I _{DD3N1}	V _{DD1}	3	3	mA
I _{DD3N2}	V _{DD2}	44	48	
I _{DD3N,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD3NS1}	V _{DD1}	3	3	mA
I _{DD3NS2}	V _{DD2}	32	32	
I _{DD3NS,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD4R1}	V _{DD1}	4	4	mA
I _{DD4R2}	V _{DD2}	360	360	
I _{DD4R,in}	V _{DDCA}	4	4	
I _{DD4W1}	V _{DD1}	4	4	mA
I _{DD4W2}	V _{DD2}	400	400	
I _{DD4W,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD51}	V _{DD1}	40	40	mA
I _{DD52}	V _{DD2}	140	140	
I _{DD5,in}	V _{DDCA} + V _{DDQ}	2	2	



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP I_{DD} Specifications

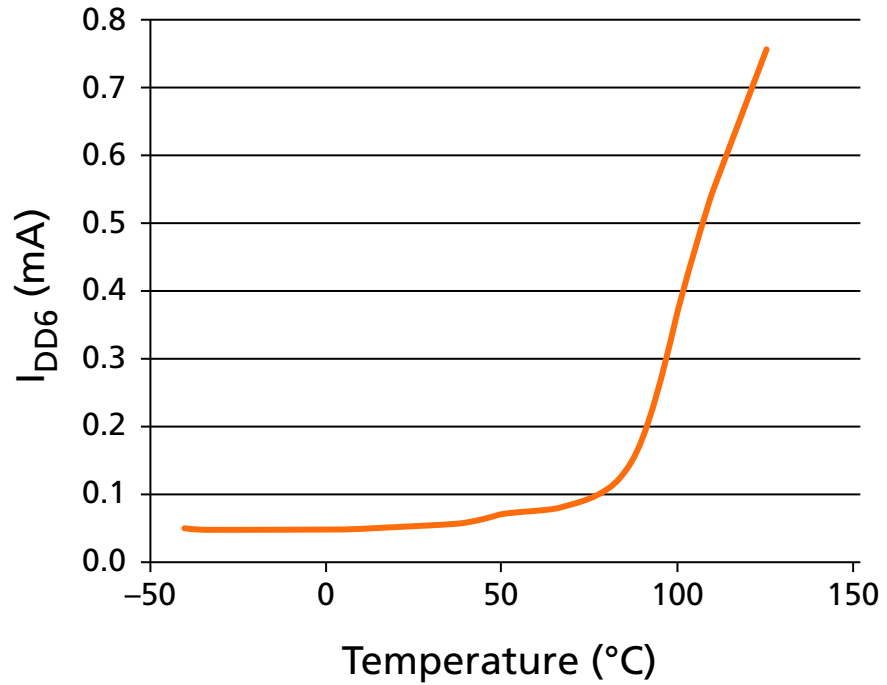
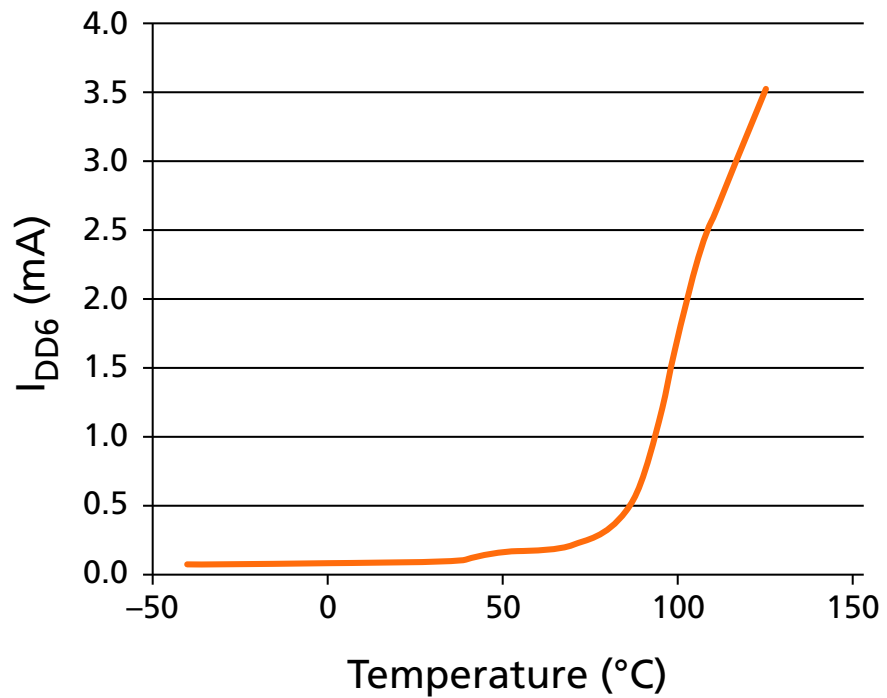
Table 44: I_{DD} Specifications (64 Meg x 32) (Continued)
 $V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14\text{--}1.30\text{V}; V_{DD1} = 1.70\text{--}1.95\text{V}$

Parameter	Supply	Clock Rate 533 MHz		Unit
		+85°C	+105°C	
I _{DD5PB1}	V _{DD1}	4	4	mA
I _{DD5PB2}	V _{DD2}	46	46	
I _{DD5PB,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD5AB1}	V _{DD1}	4	4	mA
I _{DD5AB2}	V _{DD2}	46	46	
I _{DD5AB,in}	V _{DDCA} + V _{DDQ}	2	2	
I _{DD61}	V _{DD1}	–	–	Table 45
I _{DD62}	V _{DD2}	–	–	
I _{DD6,in}	V _{DDCA} + V _{DDQ}	–	–	
I _{DD81}	V _{DD1}	100	100	μA
I _{DD82}	V _{DD2}	100	100	
I _{DD8,in}	V _{DDCA} + V _{DDQ}	40	160	

Table 45: I_{DD6} Partial-Array Self Refresh Current (64 Meg x 32)
 $V_{DD2}, V_{DDQ}, V_{DDCA} = 1.14\text{--}1.30\text{V}; V_{DD1} = 1.70\text{--}1.95\text{V}$

PASR	Supply	I _{DD6} Partial-Array Self Refresh Current		Unit
		–40°C to +85°C	+85°C to +105°C	
Full array	V _{DD1}	700	4200	μA
	V _{DD2}	4000	21400	
	V _{DDi}	60	60	
1/2 array	V _{DD1}	360	4000	
	V _{DD2}	2900	12400	
	V _{DDi}	60	60	
1/4 array	V _{DD1}	480	3600	
	V _{DD2}	2300	8000	
	V _{DDi}	60	60	
1/8 array	V _{DD1}	460	3400	
	V _{DD2}	2000	6000	
	V _{DDi}	60	60	

Note: 1. LPDDR2-S4 SDRAM devices support both bank-masking and segment-masking. I_{DD6} PASR currents are measured using bank-masking only.

**4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP
 I_{DD} Specifications****Figure 78: V_{DD1} Typical Self-Refresh Current vs. Temperature (Per Die)****Figure 79: V_{DD2} Typical Self-Refresh Current vs. Temperature (Per Die)**



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Functional Description

Functional Description

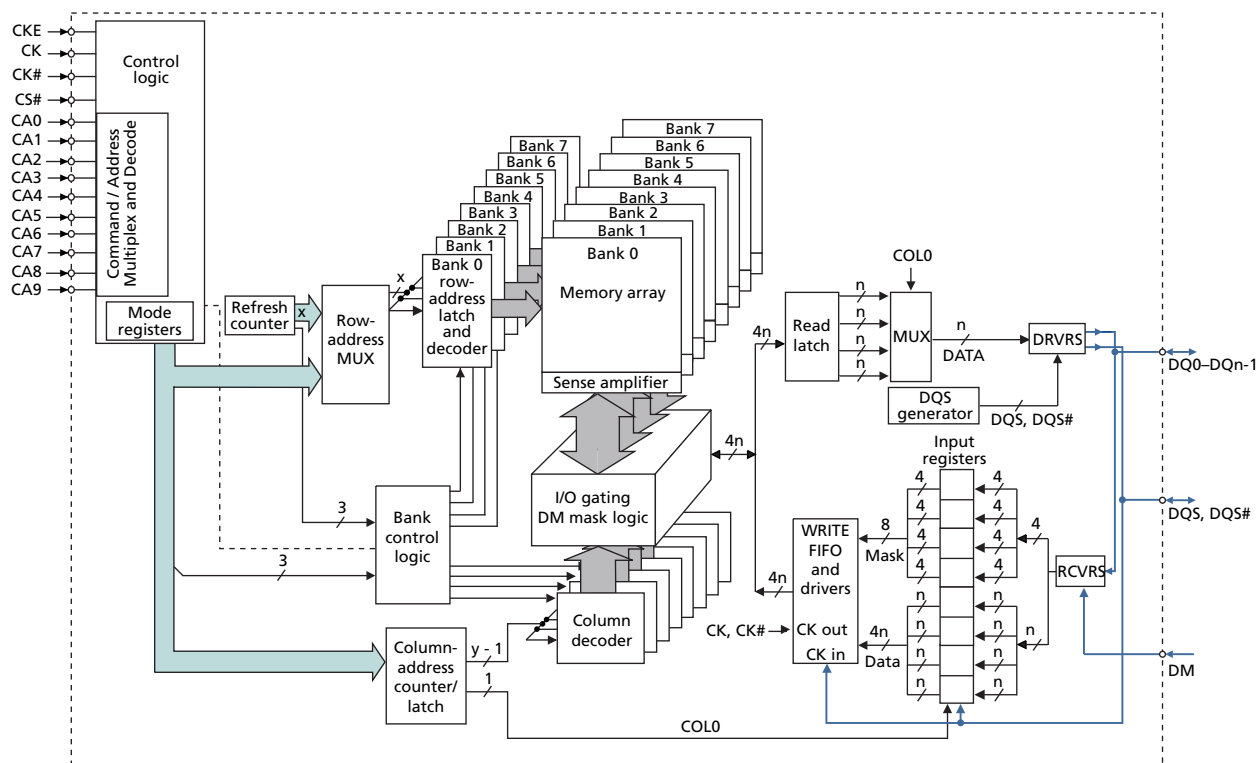
Mobile LPDDR2 is a high-speed SDRAM internally configured as a 4- or 8-bank memory device. LPDDR2 devices use a double data rate architecture on the command/address (CA) bus to reduce the number of input pins in the system. The 10-bit CA bus is used to transmit command, address, and bank information. Each command uses one clock cycle, during which command information is transferred on both the rising and falling edges of the clock.

LPDDR2-S4 devices use a double data rate architecture on the DQ pins to achieve high-speed operation. The double data rate architecture is essentially a $4n$ prefetch architecture with an interface designed to transfer two data bits per DQ every clock cycle at the I/O pins. A single read or write access for the LPDDR2-S4 effectively consists of a single $4n$ -bit-wide, one-clock-cycle data transfer at the internal SDRAM core and four corresponding n -bit-wide, one-half-clock-cycle data transfers at the I/O pins.

Read and write accesses are burst oriented; accesses start at a selected location and continue for a programmed number of locations in a programmed sequence.

Accesses begin with the registration of an ACTIVATE command followed by a READ or WRITE command. The address and BA bits registered coincident with the ACTIVATE command are used to select the row and bank to be accessed. The address bits registered coincident with the READ or WRITE command are used to select the bank and the starting column location for the burst access.

Figure 80: Functional Block Diagram





Power-Up

The following sequence must be used to power up the device. Unless specified otherwise, this procedure is mandatory (see Figure 81 (page 119)). Power-up and initialization by means other than those specified will result in undefined operation.

1. Voltage Ramp

While applying power (after T_a), CKE must be held LOW ($\leq 0.2 \times V_{DDCA}$), and all other inputs must be between V_{ILmin} and V_{IHmax} . The device outputs remain at High-Z while CKE is held LOW.

On or before the completion of the voltage ramp (T_b), CKE must be held LOW. DQ, DM, DQS, and DQS# voltage levels must be between V_{SSQ} and V_{DDQ} during voltage ramp to avoid latchup. CK, CK#, CS#, and CA input levels must be between V_{SSCA} and V_{DDCA} during voltage ramp to avoid latchup.

The following conditions apply for voltage ramp:

- T_a is the point when any power supply first reaches 300mV.
- Noted conditions apply between T_a and power-down (controlled or uncontrolled).
- T_b is the point at which all supply and reference voltages are within their defined operating ranges.
- Power ramp duration t_{INIT0} ($T_b - T_a$) must not exceed 20ms.
- For supply and reference voltage operating conditions, see the Recommended DC Operating Conditions table.
- The voltage difference between any of V_{SS} , V_{SSQ} , and V_{SSCA} pins must not exceed 100mV.

Voltage Ramp Completion

After T_a is reached:

- V_{DD1} must be greater than $V_{DD2} - 200mV$
- V_{DD1} and V_{DD2} must be greater than $V_{DDCA} - 200mV$
- V_{DD1} and V_{DD2} must be greater than $V_{DDQ} - 200mV$
- V_{REF} must always be less than all other supply voltages

Beginning at T_b , CKE must remain LOW for at least $t_{INIT1} = 100ns$, after which CKE can be asserted HIGH. The clock must be stable at least $t_{INIT2} = 5 \times t_{CK}$ prior to the first CKE LOW-to-HIGH transition (T_c). CKE, CS#, and CA inputs must observe setup and hold requirements (t_{IS} , t_{IH}) with respect to the first rising clock edge (and to subsequent falling and rising edges).

If any MRRs are issued, the clock period must be within the range defined for t_{CKb} (18ns to 100ns). MRWs can be issued at normal clock frequencies as long as all AC timings are met. Some AC parameters (for example, t_{DQSCK}) could have relaxed timings (such as t_{DQSCKb}) before the system is appropriately configured. While keeping CKE HIGH, NOP commands must be issued for at least $t_{INIT3} = 200\mu s$ (T_d).

2. RESET Command

After t_{INIT3} is satisfied, the MRW RESET command must be issued (T_d). An optional PRECHARGE ALL command can be issued prior to the MRW RESET command.

Wait at least t_{INIT4} while keeping CKE asserted and issuing NOP commands.



3. MRRs and Device Auto Initialization (DAI) Polling

After t_{INIT4} is satisfied (T_e), only MRR commands and power-down entry/exit commands are supported. After T_e , CKE can go LOW in alignment with power-down entry and exit specifications (see Power-Down).

The MRR command can be used to poll the DAI bit, which indicates when device auto initialization is complete; otherwise, the controller must wait a minimum of t_{INIT5} , or until the DAI bit is set, before proceeding.

Because the memory output buffers are not properly configured by T_e , some AC parameters must use relaxed timing specifications before the system is appropriately configured.

After the DAI bit (MR0, DAI) is set to zero by the memory device (DAI complete), the device is in the idle state (T_f). DAI status can be determined by issuing the MRR command to MR0.

The device sets the DAI bit no later than t_{INIT5} after the RESET command. The controller must wait at least t_{INIT5} or until the DAI bit is set before proceeding.

4. ZQ Calibration

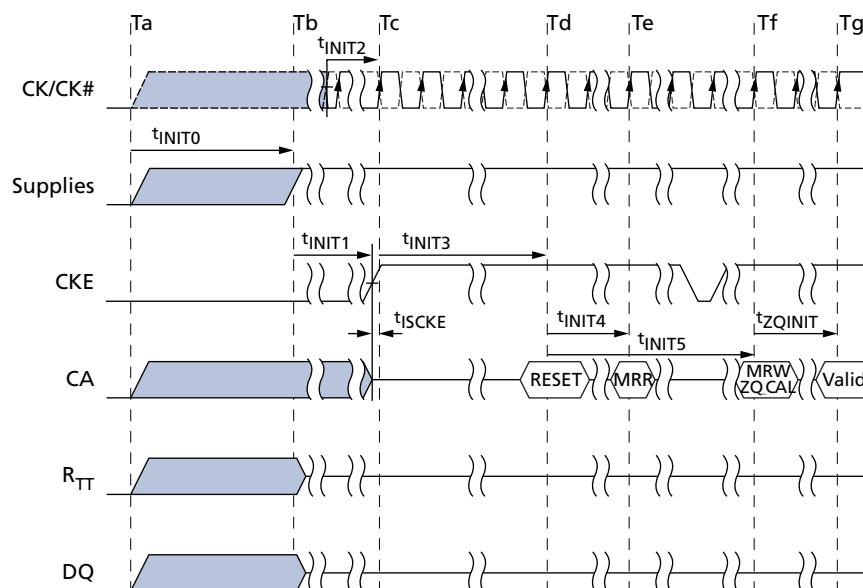
After t_{INIT5} (T_f), the MRW initialization calibration (ZQ calibration) command can be issued to the memory (MR10).

This command is used to calibrate output impedance over process, voltage, and temperature. In systems where more than one Mobile LPDDR2 device exists on the same bus, the controller must not overlap MRW ZQ calibration commands. The device is ready for normal operation after t_{ZQINIT} .

5. Normal Operation

After (T_g), MRW commands must be used to properly configure the memory (output buffer drive strength, latencies, etc.). Specifically, MR1, MR2, and MR3 must be set to configure the memory for the target frequency and memory configuration.

After the initialization sequence is complete, the device is ready for any valid command. After T_g , the clock frequency can be changed using the procedure described in Input Clock Frequency Changes and Stop Events.


Figure 81: Voltage Ramp and Initialization Sequence


Note: 1. High-Z on the CA bus indicates valid NOP.

Table 46: Initialization Timing Parameters

Parameter	Value		Unit	Comment
	Min	Max		
t_{INIT0}	–	20	ms	Maximum voltage ramp time
t_{INIT1}	100	–	ns	Minimum CKE LOW time after completion of voltage ramp
t_{INIT2}	5	–	t_{CK}	Minimum stable clock before first CKE HIGH
t_{INIT3}	200	–	μ s	Minimum idle time after first CKE assertion
t_{INIT4}	1	–	μ s	Minimum idle time after RESET command
t_{INIT5}	–	10	μ s	Maximum duration of device auto initialization
t_{ZQINIT}	1	–	μ s	ZQ initial calibration (S4 devices only)
t_{CKb}	18	100	ns	Clock cycle time during boot

Note: 1. The t_{INIT0} maximum specification is not a tested limit and should be used as a general guideline. For voltage ramp times exceeding t_{INIT0} MAX, please contact the factory.

Initialization After RESET (Without Voltage Ramp)

If the RESET command is issued before or after the power-up initialization sequence, the reinitialization procedure must begin at Td.

Power-Off

While powering off, CKE must be held LOW ($\leq 0.2 \times V_{DDCA}$); all other inputs must be between V_{ILmin} and V_{IHmax} . The device outputs remain at High-Z while CKE is held LOW.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

DQ, DM, DQS, and DQS# voltage levels must be between V_{SSQ} and V_{DDQ} during the power-off sequence to avoid latchup. CK, CK#, CS#, and CA input levels must be between V_{SSCA} and V_{DDCA} during the power-off sequence to avoid latchup.

Tx is the point where any power supply drops below the minimum value specified in the Recommended DC Operating Conditions table.

Tz is the point where all power supplies are below 300mV. After Tz, the device is powered off.

Required Power Supply Conditions Between Tx and Tz:

- V_{DD1} must be greater than $V_{DD2} - 200\text{mV}$
- V_{DD1} must be greater than $V_{DDCA} - 200\text{mV}$
- V_{DD1} must be greater than $V_{DDQ} - 200\text{mV}$
- V_{REF} must always be less than all other supply voltages

The voltage difference between V_{SS} , V_{SSQ} , and V_{SSCA} must not exceed 100mV.

For supply and reference voltage operating conditions, see Recommended DC Operating Conditions table.

Uncontrolled Power-Off

When an uncontrolled power-off occurs, the following conditions must be met:

- At Tx, when the power supply drops below the minimum values specified in the Recommended DC Operating Conditions table, all power supplies must be turned off and all power-supply current capacity must be at zero, except for any static charge remaining in the system.
- After Tz (the point at which all power supplies first reach 300mV), the device must power off. The time between Tx and Tz must not exceed t_{POFF} . During this period, the relative voltage between power supplies is uncontrolled. V_{DD1} and V_{DD2} must decrease with a slope lower than $0.5\text{ V}/\mu\text{s}$ between Tx and Tz.

An uncontrolled power-off sequence can occur a maximum of 400 times over the life of the device.

Table 47: Power-Off Timing

Parameter	Symbol	Min	Max	Unit
Maximum power-off ramp time	t_{POFF}	–	2	sec

Mode Register Definition

LPDDR2 devices contain a set of mode registers used for programming device operating parameters, reading device information and status, and for initiating special operations such as DQ calibration, ZQ calibration, and device reset.

Mode Register Assignments and Definitions

The MRR command is used to read from a register. The MRW command is used to write to a register. An “R” in the access column of the mode register assignment table indicates read-only; a “W” indicates write-only; “R/W” indicates read or write capable or enabled.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 48: Mode Register Assignments

Notes 1–5 apply to all parameters and conditions

MR#	MA[7:0]	Function	Access	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0	Link	
0	00h	Device info	R	RFU			RZQI		DNVI	DI	DAI	go to MR0	
1	01h	Device feature 1	W	nWR (for AP)			WC	BT	BL			go to MR1	
2	02h	Device feature 2	W	RFU			RL and WL					go to MR2	
3	03h	I/O config-1	W	RFU			DS					go to MR3	
4	04h	SDRAM refresh rate	R	TUF	RFU			Refresh rate				go to MR4	
5	05h	Basic config-1	R	LPDDR2 Manufacturer ID									go to MR5
6	06h	Basic config-2	R	Revision ID1									go to MR6
7	07h	Basic config-3	R	Revision ID2									go to MR7
8	08h	Basic config-4	R	I/O width		Density			Type				go to MR8
9	09h	Test mode	W	Vendor-specific test mode									go to MR9
10	0Ah	I/O calibration	W	Calibration code									go to MR10
11–15	0Bh ~ 0Fh	Reserved	–	RFU									go to MR11
16	10h	PASR_Bank	W	Bank mask									go to MR16
17	11h	PASR_Seg	W	Segment mask									go to MR17
18–19	12h–13h	Reserved	–	RFU									go to MR18
20–31	14h–1Fh	Reserved for NVM										MR20–MR30	
32	20h	DQ calibration pattern A	R	See Table 85 (page 167).									go to MR32
33–39	21h–27h	Do not use											go to MR33
40	28h	DQ calibration pattern B	R	See Table 85 (page 167).									go to MR40
41–47	29h–2Fh	Do not use											go to MR41
48–62	30h–3Eh	Reserved	–	RFU									go to MR48
63	3Fh	RESET	W	X									go to MR63
64–126	40h–7Eh	Reserved	–	RFU									go to MR64
127	7Fh	Do not use											go to MR127
128–190	80h–BEh	Reserved for vendor use		RVU									go to MR128
191	BFh	Do not use											go to MR191
192–254	C0h–FEh	Reserved for vendor use		RVU									go to MR192
255	FFh	Do not use											go to MR255

- Notes:
1. RFU bits must be set to 0 during MRW.
 2. RFU bits must be read as 0 during MRR.
 3. For READs to a write-only or RFU register, DQS will be toggled and undefined data is returned.
 4. RFU mode registers must not be written.
 5. WRITEs to read-only registers must have no impact on the functionality of the device.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 49: MR0 Device Information (MA[7:0] = 00h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU			RZQI		DNVI	DI	DAI

Table 50: MR0 Op-Code Bit Definitions

Notes 1–4 apply to all parameters and conditions

Register Information	Tag	Type	OP	Definition
Device auto initialization status	DAI	Read-only	OP0	0b: DAI complete
				1b: DAI in progress
Device information	DI	Read-only	OP1	0b
				1b: NVM
Data not valid information	DNVI	Read-only	OP2	0b: DNVI not supported
Built-in self test for RZQ information	RZQI	Read-only	OP[4:3]	00b: RZQ self test not supported
				01b: ZQ pin might be connected to V _{DDCA} or left floating
				10b: ZQ pin might be shorted to ground
				11b: ZQ pin self test complete; no error condition detected

- Notes:
1. If RZQI is supported, it will be set upon completion of the MRW ZQ initialization calibration.
 2. If ZQ is connected to V_{DDCA} to set default calibration, OP[4:3] must be set to 01. If ZQ is not connected to V_{DDCA}, either OP[4:3] = 01 or OP[4:3] = 10 could indicate a ZQ-pin assembly error. It is recommended that the assembly error be corrected.
 3. In the case of a possible assembly error (either OP[4:3] = 01 or OP[4:3] = 10, as defined above), the device will default to factory trim settings for R_{ON} and will ignore ZQ calibration commands. In either case, the system might not function as intended.
 4. If a ZQ self test returns a value of 11b, this indicates that the device has detected a resistor connection to the ZQ pin. Note that this result cannot be used to validate the ZQ resistor value, nor does it indicate that the ZQ resistor tolerance meets the specified limits (240 ohms ±1%).

Table 51: MR1 Device Feature 1 (MA[7:0] = 01h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
nWR (for AP)			WC	BT	BL		



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 52: MR1 Op-Code Bit Definitions

Feature	Type	OP	Definition	Notes
BL = burst length	Write-only	OP[2:0]	010b: BL4 (default)	
			011b: BL8	
			100b: BL16	
			All others: Reserved	
BT = burst type	Write-only	OP3	0b: Sequential (default)	
			1b: Interleaved	
WC = wrap control	Write-only	OP4	0b: Wrap (default)	
			1b: No wrap	
nWR = number of ^t WR clock cycles	Write-only	OP[7:5]	001b: nWR = 3 (default)	1
			010b: nWR = 4	
			011b: nWR = 5	
			100b: nWR = 6	
			101b: nWR = 7	
			110b: nWR = 8	
			All others: Reserved	

Note: 1. The programmed value in nWR register is the number of clock cycles that determines when to start internal precharge operation for a WRITE burst with AP enabled. It is determined by RU (^tWR/^tCK).

Table 53: Burst Sequence by Burst Length (BL), Burst Type (BT), and Wrap Control (WC)

Notes 1–5 apply to all parameters and conditions

Notes 1-5 apply to all parameters and conditions																						
BL	BT	C3	C2	C1	C0	WC	Burst Cycle Number and Burst Address Sequence															
							1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
4	Any	X	X	0b	0b	Wrap	0	1	2	3												
		X	X	1b	0b		2	3	0	1												
	Any	X	X	X	0b	No wrap	y	y + 1	y + 2	y + 3												
8	Seq	X	0b	0b	0b	Wrap	0	1	2	3	4	5	6	7								
		X	0b	1b	0b		2	3	4	5	6	7	0	1								
		X	1b	0b	0b		4	5	6	7	0	1	2	3								
		X	1b	1b	0b		6	7	0	1	2	3	4	5								
	Int	X	0b	0b	0b	Wrap	0	1	2	3	4	5	6	7								
		X	0b	1b	0b		2	3	0	1	6	7	4	5								
		X	1b	0b	0b		4	5	6	7	0	1	2	3								
		X	1b	1b	0b		6	7	4	5	2	3	0	1								
	Any	X	X	X	0b	No wrap	Illegal (not supported)															



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 53: Burst Sequence by Burst Length (BL), Burst Type (BT), and Wrap Control (WC) (Continued)

Notes 1–5 apply to all parameters and conditions

BL	BT	C3	C2	C1	C0	WC	Burst Cycle Number and Burst Address Sequence															
							1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
16	Seq	0b	0b	0b	0b	Wrap	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
		0b	0b	1b	0b		2	3	4	5	6	7	8	9	A	B	C	D	E	F	0	1
		0b	1b	0b	0b		4	5	6	7	8	9	A	B	C	D	E	F	0	1	2	3
		0b	1b	1b	0b		6	7	8	9	A	B	C	D	E	F	0	1	2	3	4	5
		1b	0b	0b	0b		8	9	A	B	C	D	E	F	0	1	2	3	4	5	6	7
		1b	0b	1b	0b		A	B	C	D	E	F	0	1	2	3	4	5	6	7	8	9
		1b	1b	0b	0b		C	D	E	F	0	1	2	3	4	5	6	7	8	9	A	B
		1b	1b	1b	0b		E	F	0	1	2	3	4	5	6	7	8	9	A	B	C	D
	Int	X	X	X	0b	No wrap	Illegal (not supported)															
	Any	X	X	X	0b		Illegal (not supported)															

- Notes:
1. C0 input is not present on CA bus. It is implied zero.
 2. For BL = 4, the burst address represents C[1:0].
 3. For BL = 8, the burst address represents C[2:0].
 4. For BL = 16, the burst address represents C[3:0].
 5. For no-wrap, BL4, the burst must not cross the page boundary or the sub-page boundary. The variable y can start at any address with C0 equal to 0, but must not start at any address shown in the following table.

Table 54: No-Wrap Restrictions

Width	64Mb	128Mb/256Mb	512Mb/1Gb/2Gb	4Gb/8Gb
Cannot cross full-page boundary				
x16	FE, FF, 00, 01	1FE, 1FF, 000, 001	3FE, 3FF, 000, 001	7FE, 7FF, 000, 001
x32	7E, 7F, 00, 01	FE, FF, 00, 01	1FE, 1FF, 000, 001	3FE, 3FF, 000, 001
Cannot cross sub-page boundary				
x16	7E, 7F, 80, 81	0FE, 0FF, 100, 101	1FE, 1FF, 200, 201	3FE, 3FF, 400, 401
x32	None	None	None	None

Note: 1. No-wrap BL = 4 data orders shown are prohibited.

Table 55: MR2 Device Feature 2 (MA[7:0] = 02h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU				RL and WL			



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 56: MR2 Op-Code Bit Definitions

Feature	Type	OP	Definition
RL and WL	Write-only	OP[3:0]	0001b: RL3/WL1 (default)
			0010b: RL4/WL2
			0011b: RL5/WL2
			0100b: RL6/WL3
			0101b: RL7/WL4
			0110b: RL8/WL4
			All others: Reserved

Table 57: MR3 I/O Configuration 1 (MA[7:0] = 03h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
RFU				DS			

Table 58: MR3 Op-Code Bit Definitions

Feature	Type	OP	Definition
DS	Write-only	OP[3:0]	0000b: Reserved
			0001b: 34.3 ohm typical
			0010b: 40 ohm typical (default)
			0011b: 48 ohm typical
			0100b: 60 ohm typical
			0101b: Reserved
			0110b: 80 ohm typical
			0111b: 120 ohm typical
			All others: Reserved

Table 59: MR4 Device Temperature (MA[7:0] = 04h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
TUF	RFU				SDRAM refresh rate		



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 60: MR4 Op-Code Bit Definitions

Notes 1–10 apply to all parameters and conditions

Feature	Type	OP	Definition
SDRAM refresh rate	Read-only	OP[2:0]	000b: SDRAM low temperature operating limit exceeded
			001b: $4 \times t_{REFI}$, $4 \times t_{REFIpb}$, $4 \times t_{REFW}$
			010b: $2 \times t_{REFI}$, $2 \times t_{REFIpb}$, $2 \times t_{REFW}$
			011b: $1 \times t_{REFI}$, $1 \times t_{REFIpb}$, $1 \times t_{REFW}$ ($\leq 85^{\circ}\text{C}$)
			100b: Reserved
			101b: $0.25 \times t_{REFI}$, $0.25 \times t_{REFIpb}$, $0.25 \times t_{REFW}$, do not derate SDRAM AC timing
			110b: $0.25 \times t_{REFI}$, $0.25 \times t_{REFIpb}$, $0.25 \times t_{REFW}$, derate SDRAM AC timing
			111b: SDRAM high temperature operating limit exceeded
Temperature update flag (TUF)	Read-only	OP7	0b: OP[2:0] value has not changed since last read of MR4
			1b: OP[2:0] value has changed since last read of MR4

- Notes:
1. A MODE REGISTER READ from MR4 will reset OP7 to 0.
 2. OP7 is reset to 0 at power-up.
 3. If OP2 = 1, the device temperature is greater than 85°C .
 4. OP7 is set to 1 if OP[2:0] has changed at any time since the last MR4 read.
 5. The device might not operate properly when OP[2:0] = 000b or 111b.
 6. For specified operating temperature range and maximum operating temperature, refer to the Operating Temperature Range table.
 7. LPDDR2 devices must be derated by adding 1.875ns to the following core timing parameters: t_{RCD} , t_{RC} , t_{RAS} , t_{RP} , and t_{RRD} . The t_{DQSCK} parameter must be derated as specified in AC Timing. Prevailing clock frequency specifications and related setup and hold timings remain unchanged.
 8. The recommended frequency for reading MR4 is provided in Temperature Sensor (page 164).
 9. While the AT grade product is guaranteed to operate from $T_{CASE} -40^{\circ}\text{C}$ to 105°C , the temperature sensor accuracy relative to this is not guaranteed. The temperature sensor embedded in the LPDDR2 device is not an accurate reflection of the DRAM T_{CASE} operating temperature. Sampling of the sensor has shown up to a $\pm 7^{\circ}\text{C}$ variance from actual T_{CASE} .
 10. The temperature sensor does not work above 105°C , but the functionalities here described in this datasheet are guaranteed for products range up to 125°C (AUT).

Table 61: MR5 Basic Configuration 1 (MA[7:0] = 05h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
LPDDR2 Manufacturer ID							

Table 62: MR5 Op-Code Bit Definitions

Feature	Type	OP	Definition
Manufacturer ID	Read-only	OP[7:0]	1111 1111b: Micron
			All others: Reserved



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 63: MR6 Basic Configuration 2 (MA[7:0] = 06h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Revision ID1							

Note: 1. MR6 is vendor-specific.

Table 64: MR6 Op-Code Bit Definitions

Feature	Type	OP	Definition
Revision ID1	Read-only	OP[7:0]	0000 0000b: Version A

Table 65: MR7 Basic Configuration 3 (MA[7:0] = 07h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Revision ID2							

Table 66: MR7 Op-Code Bit Definitions

Feature	Type	OP	Definition
Revision ID2	Read-only	OP[7:0]	0000 0000b: Version A

Note: 1. MR7 is vendor-specific.

Table 67: MR8 Basic Configuration 4 (MA[7:0] = 08h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
I/O width		Density				Type	

Table 68: MR8 Op-Code Bit Definitions

Feature	Type	OP	Definition
Type	Read-only	OP[1:0]	00b: S4 SDRAM
			01b: S2 SDRAM
			10b: NVM
			11b: Reserved



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 68: MR8 Op-Code Bit Definitions (Continued)

Feature	Type	OP	Definition
Density	Read-only	OP[5:2]	0000b: 64Mb
			0001b: 128Mb
			0010b: 256Mb
			0011b: 512Mb
			0100b: 1Gb
			0101b: 2Gb
			0110b: 4Gb
			0111b: 8Gb
			1000b: 16Gb
			1001b: 32Gb
			All others: Reserved
I/O width	Read-only	OP[7:6]	00b: x32
			01b: x16
			10b: x8
			11b: not used

Table 69: MR9 Test Mode (MA[7:0] = 09h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Vendor-specific test mode							

Table 70: MR10 Calibration (MA[7:0] = 0Ah)

	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
S4	Calibration code							

Table 71: MR10 Op-Code Bit Definitions

Notes 1–4 apply to all parameters and conditions

Feature	Type	OP	Definition
Calibration code	Write-only	OP[7:0]	0xFF: Calibration command after initialization
			0xAB: Long calibration
			0x56: Short calibration
			0xC3: ZQRESET
			All others: Reserved

- Notes:
1. Host processor must not write MR10 with reserved values.
 2. The device ignores calibration commands when a reserved value is written into MR10.
 3. See AC timing table for the calibration latency.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

4. If ZQ is connected to V_{SSCA} through R_{ZQ} , either the ZQ calibration function (see MRW ZQ Calibration Commands (page 169)) or default calibration (through the ZQRESET command) is supported. If ZQ is connected to V_{DDCA} , the device operates with default calibration, and ZQ calibration commands are ignored. In both cases, the ZQ connection must not change after power is supplied to the device.

Table 72: MR[11:15] Reserved (MA[7:0] = 0Bh–0Fh)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Reserved							

Table 73: MR16 PASR Bank Mask (MA[7:0] = 010h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Bank mask (4-bank or 8-bank)							

Table 74: MR16 Op-Code Bit Definitions

Feature	Type	OP	Definition
Bank[7:0] mask	Write-only	OP[7:0]	0b: refresh enable to the bank = unmasked (default)
			1b: refresh blocked = masked

Note: 1. For 4-bank devices, only OP[3:0] are used.

Table 75: MR17 PASR Segment Mask (MA[7:0] = 011h)

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
Segment mask							

Note: 1. This table applies for 1Gb to 8Gb devices only.

Table 76: MR17 PASR Segment Mask Definitions

Feature	Type	OP	Definition
Segment[7:0] mask	Write-only	OP[7:0]	0b: refresh enable to the segment: = unmasked (default)
			1b: refresh blocked: = masked

Table 77: MR17 PASR Row Address Ranges in Masked Segments

Segment	OP	Segment Mask	1Gb	2Gb, 4Gb	8Gb
			R[12:10]	R[13:11]	R[14:12]
0	0	XXXXXXXX1	000b		
1	1	XXXXXXXX1X	001b		
2	2	XXXXXX1XX	010b		



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Mode Register Definition

Table 77: MR17 PASR Row Address Ranges in Masked Segments (Continued)

Segment	OP	Segment Mask	1Gb	2Gb, 4Gb	8Gb
			R[12:10]	R[13:11]	R[14:12]
3	3	XXXX1XXX	011b		
4	4	XXX1XXXX	100b		
5	5	XX1XXXXX	101b		
6	6	X1XXXXXX	110b		
7	7	1XXXXXXX	111b		

Note: 1. X is "Don't Care" for the designated segment.

Table 78: Reserved Mode Registers

Mode Register	MA	Address	Restriction	OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
MR[18:19]	MA[7:0]	12h–13h	RFU	Reserved							
MR[20:31]		14h–1Fh	NVM ¹								
MR[33:39]		21h–27h	DNU ¹								
MR[41:47]		29h–2Fh									
MR[48:62]		30h–3Eh	RFU								
MR[64:126]		40h–7Eh	RFU								
MR127		7Fh	DNU								
MR[128:190]		80h–BEh	RVU ¹								
MR191		BFh	DNU								
MR[192:254]		C0h–FEh	RVU								
MR255		FFh	DNU								

Note: 1. NVM = nonvolatile memory use only; DNU = Do not use; RVU = Reserved for vendor use.

Table 79: MR63 RESET (MA[7:0] = 3Fh) – MRW Only

OP7	OP6	OP5	OP4	OP3	OP2	OP1	OP0
X							

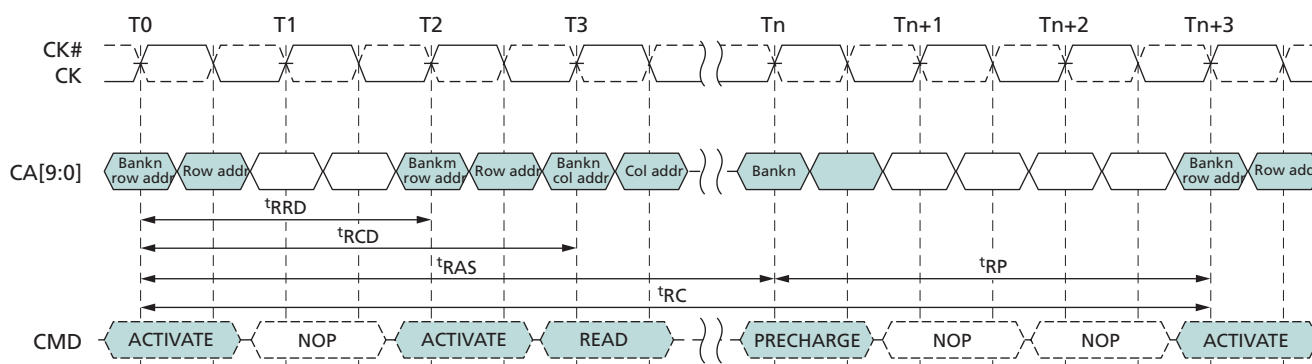
Note: 1. For additional information on MRW RESET see MODE REGISTER WRITE Command (page 168).



ACTIVATE Command

The ACTIVATE command is issued by holding CS# LOW, CA0 LOW, and CA1 HIGH at the rising edge of the clock. The bank addresses BA[2:0] are used to select the desired bank. Row addresses are used to determine which row to activate in the selected bank. The ACTIVATE command must be applied before any READ or WRITE operation can be executed. The device can accept a READ or WRITE command at t_{RCD} after the ACTIVATE command is issued. After a bank has been activated, it must be precharged before another ACTIVATE command can be applied to the same bank. The bank active and precharge times are defined as t_{RAS} and t_{RP} , respectively. The minimum time interval between successive ACTIVATE commands to the same bank is determined by the RAS cycle time of the device (t_{RC}). The minimum time interval between ACTIVATE commands to different banks is t_{RRD} .

Figure 82: ACTIVATE Command



- Notes:
1. $t_{RCD} = 3$, $t_{RP} = 3$, $t_{RRD} = 2$.
 2. A PRECHARGE ALL command uses t_{RPab} timing, and a single-bank PRECHARGE command uses t_{RPpb} timing. In this figure, t_{RP} is used to denote either an all-bank PRECHARGE or a single-bank PRECHARGE.

8-Bank Device Operation

Two rules regarding 8-bank device operation must be observed. One rule restricts the number of sequential ACTIVATE commands that can be issued; the second provides additional RAS precharge time for a PRECHARGE ALL command.

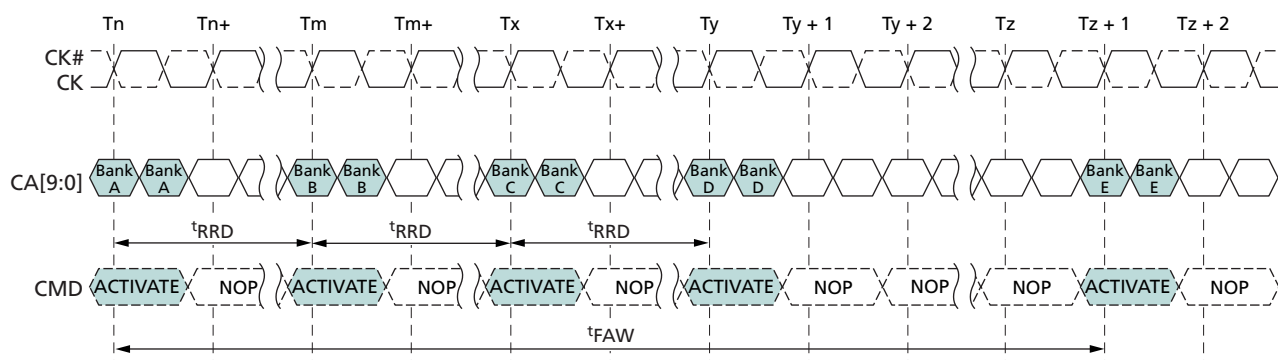
The 8-Bank Device Sequential Bank Activation Restriction: No more than four banks can be activated (or refreshed, in the case of REFpb) in a rolling t_{FAW} window. To convert to clocks, divide $t_{FAW}[ns]$ by $t_{CK}[ns]$, and round up to the next integer value. For example, if $RU(t_{FAW}/t_{CK})$ is 10 clocks, and an ACTIVATE command is issued in clock n , no more than three further ACTIVATE commands can be issued at or between clock $n + 1$ and $n + 9$. REFpb also counts as bank activation for purposes of t_{FAW} .

The 8-Bank Device PRECHARGE ALL Provision: t_{RP} for a PRECHARGE ALL command must equal t_{RPab} , which is greater than t_{RPpb} .



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Read and Write Access Modes

Figure 83: t_{FAW} Timing (8-Bank Devices)



Note: 1. Exclusively for 8-bank devices.

Read and Write Access Modes

After a bank is activated, a READ or WRITE command can be issued with CS# LOW, CA0 HIGH, and CA1 LOW at the rising edge of the clock. CA2 must also be defined at this time to determine whether the access cycle is a READ operation (CA2 HIGH) or a WRITE operation (CA2 LOW). A single READ or WRITE command initiates a burst READ or burst WRITE operation on successive clock cycles.

A new burst access must not interrupt the previous 4-bit burst operation when BL = 4. When BL = 8 or BL = 16, READs can be interrupted by READs and WRITEs can be interrupted by WRITEs, provided that the interrupt occurs on a 4-bit boundary and that t_{CCD} is met.

Burst READ Command

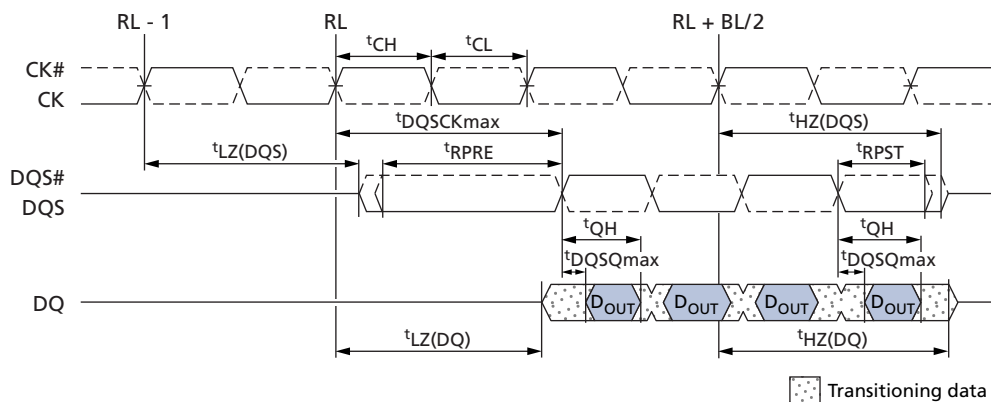
The burst READ command is initiated with CS# LOW, CA0 HIGH, CA1 LOW, and CA2 HIGH at the rising edge of the clock. The command address bus inputs, CA5r–CA6r and CA1f–CA9f, determine the starting column address for the burst. The read latency (RL) is defined from the rising edge of the clock on which the READ command is issued to the rising edge of the clock from which the t_{DQSCK} delay is measured. The first valid data is available $RL \times t_{CK} + t_{DQSCK} + t_{DQSQ}$ after the rising edge of the clock when the READ command is issued. The data strobe output is driven LOW t_{RPRE} before the first valid rising strobe edge. The first bit of the burst is synchronized with the first rising edge of the data strobe. Each subsequent data-out appears on each DQ pin, edge-aligned with the data strobe. The RL is programmed in the mode registers.

Pin input timings for the data strobe are measured relative to the crosspoint of DQS and its complement, DQS#.



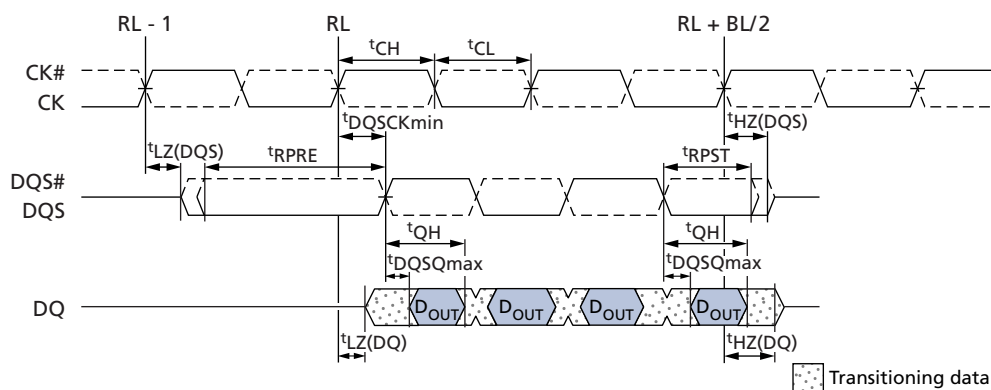
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst READ Command

Figure 84: READ Output Timing – t_{DQSCK} (MAX)



- Notes:
1. t_{DQSCK} can span multiple clock periods.
 2. An effective burst length of 4 is shown.

Figure 85: READ Output Timing – t_{DQSCK} (MIN)



- Note:
1. An effective burst length of 4 is shown.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst READ Command

Figure 86: Burst READ – RL = 5, BL = 4, $t_{DQSCK} > t_{CK}$

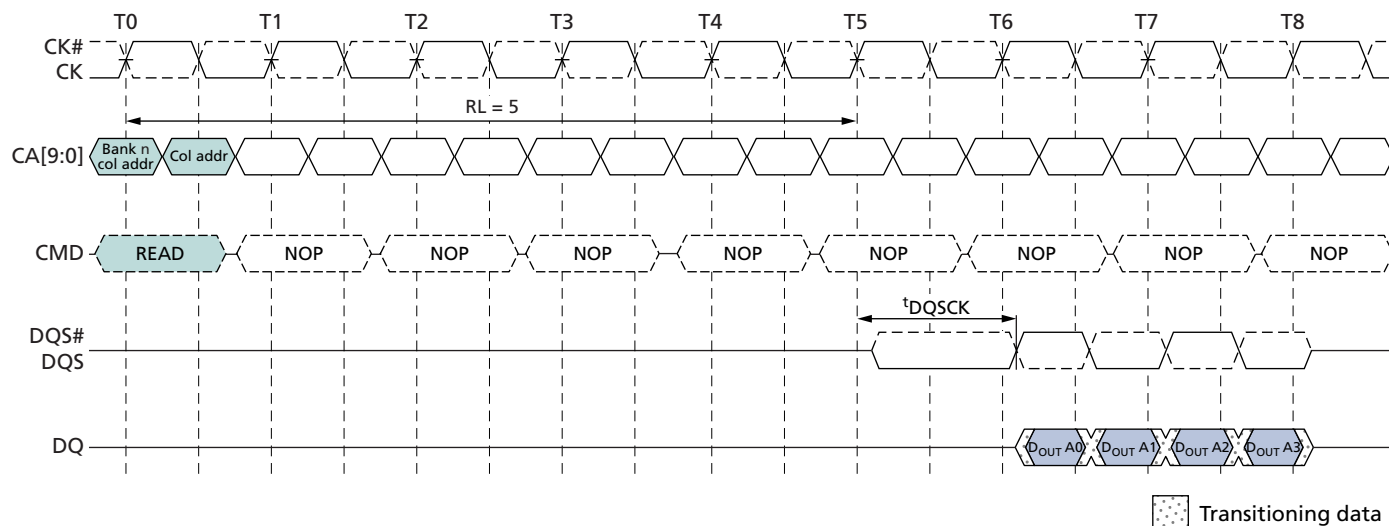
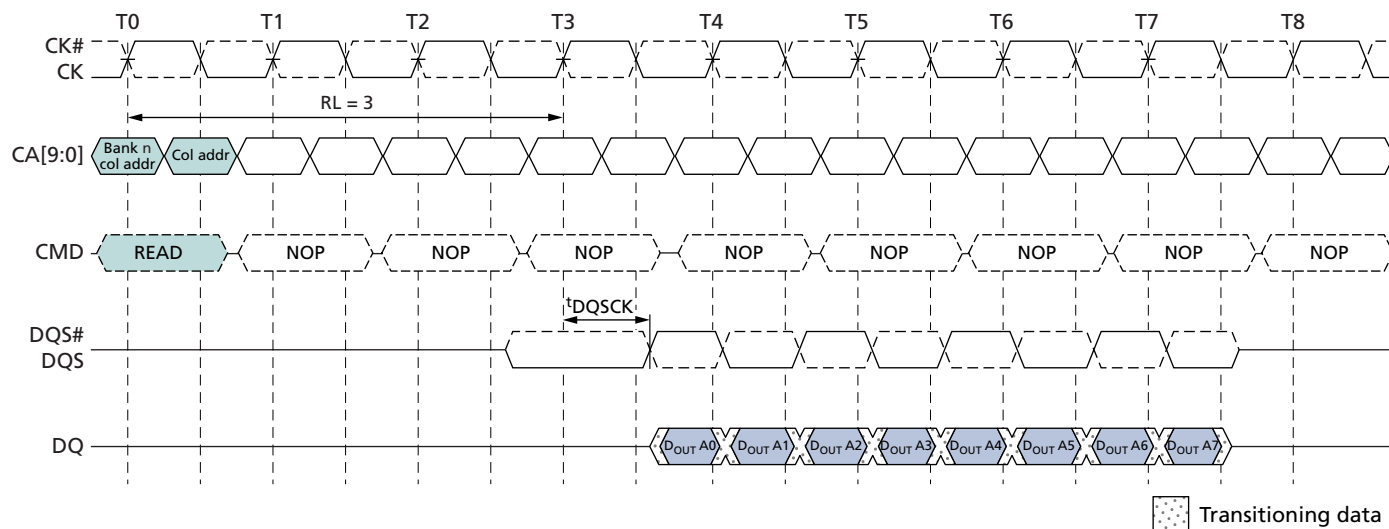


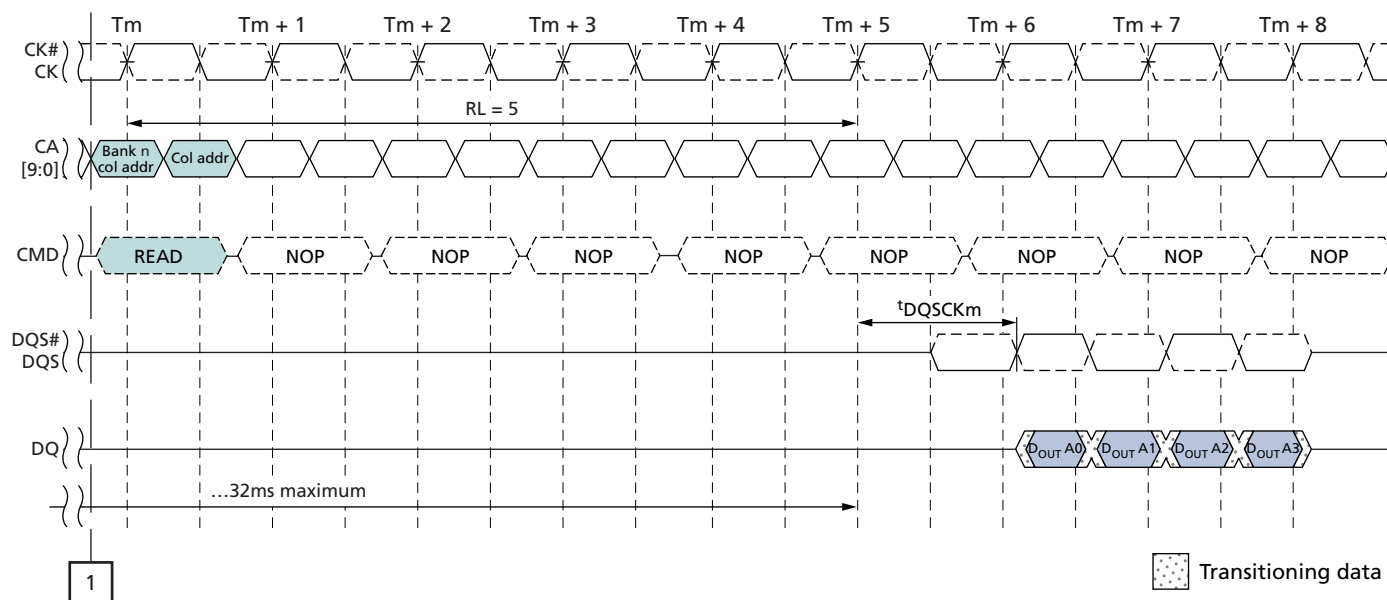
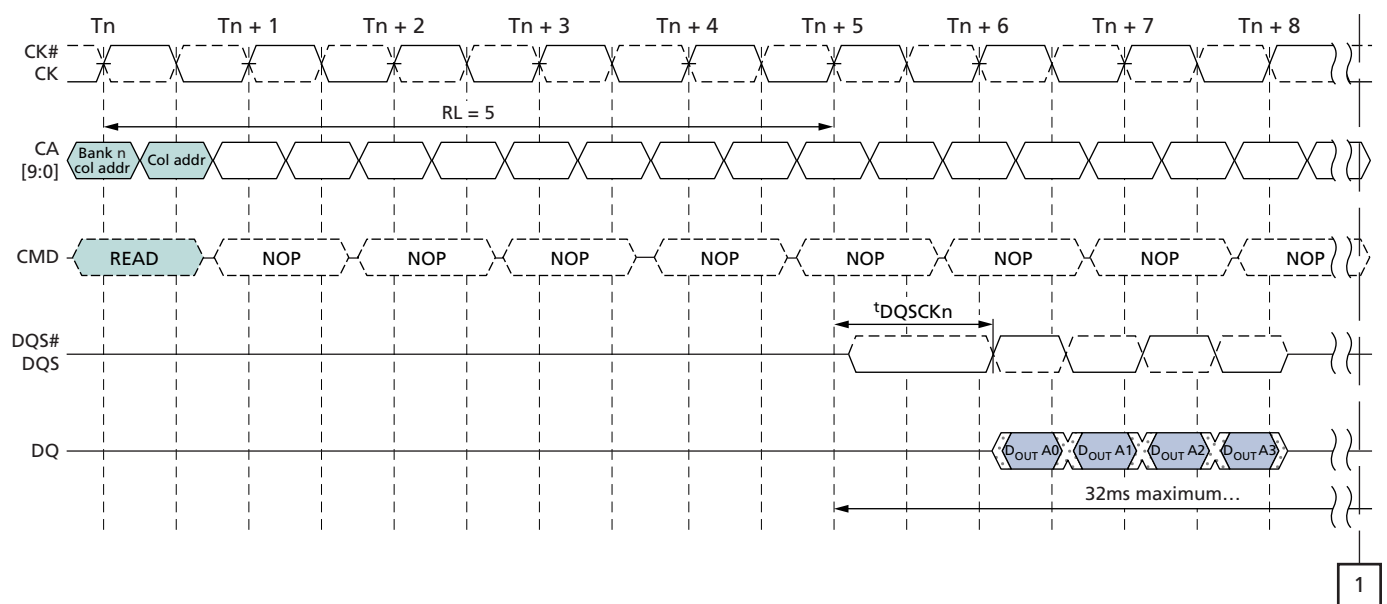
Figure 87: Burst READ – RL = 3, BL = 8, $t_{DQSCK} < t_{CK}$





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst READ Command

Figure 88: t_{DQSKDL} Timing

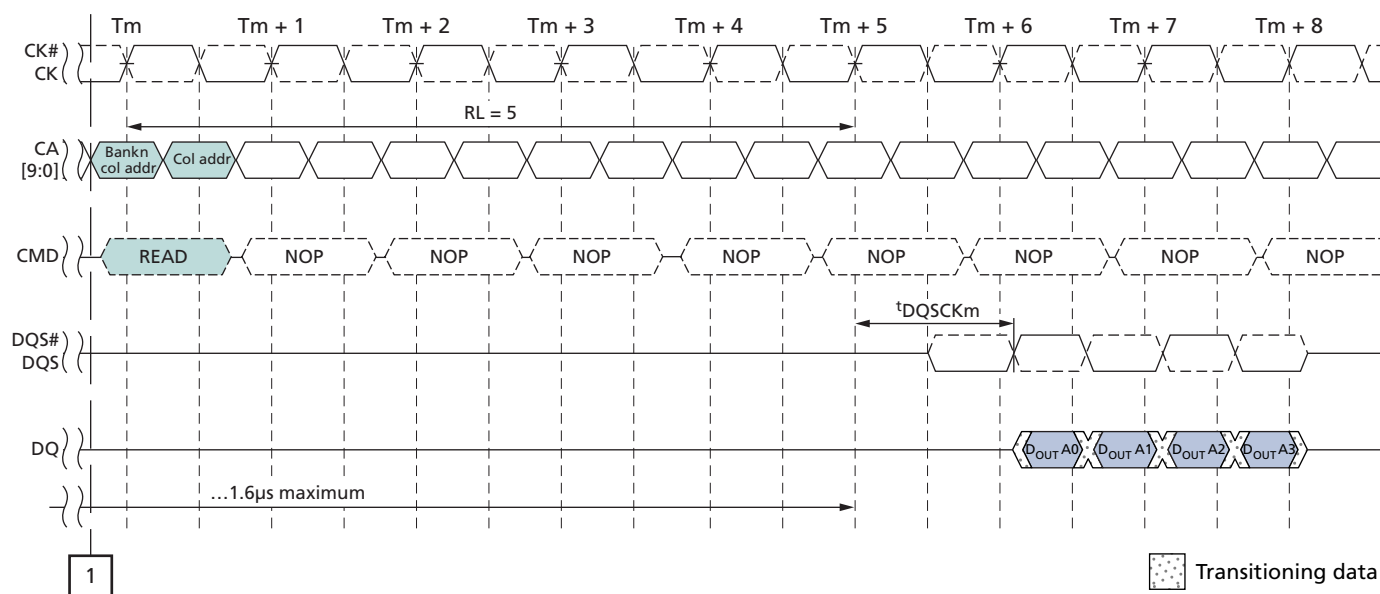
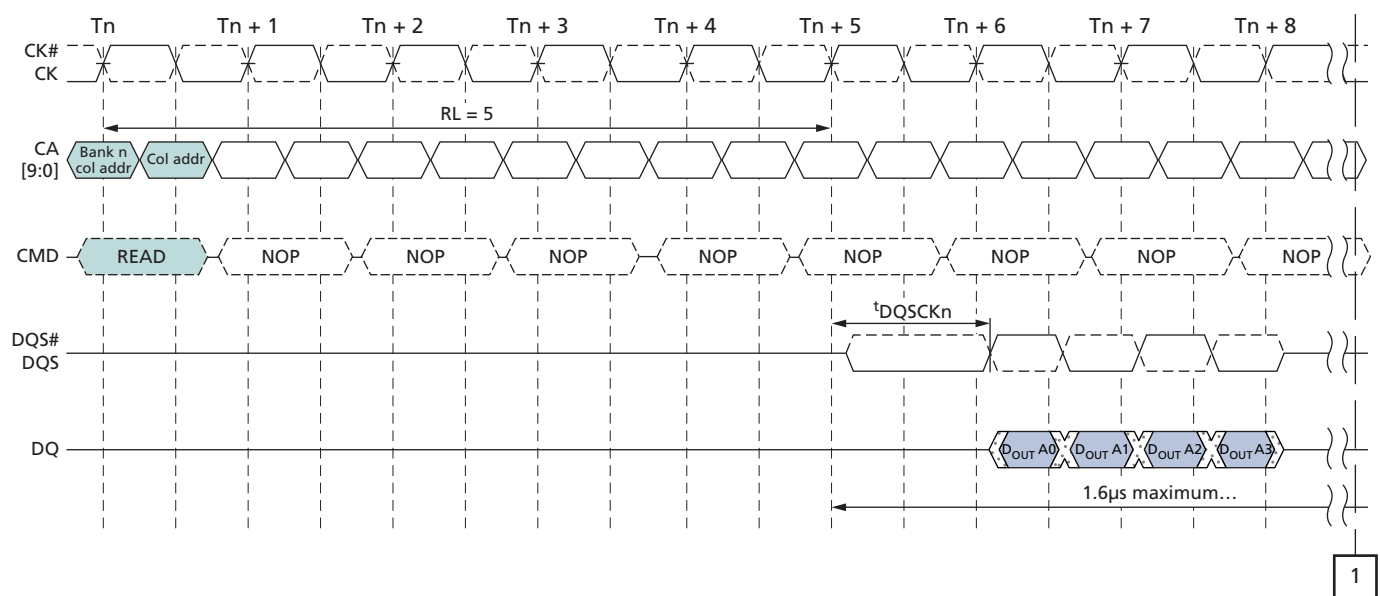


- Notes:
1. $t_{DQSKDL} = (t_{DQSKn} - t_{DQSKm})$.
 2. $t_{DQSKDL} (MAX)$ is defined as the maximum of ABS ($t_{DQSKn} - t_{DQSKm}$) for any (t_{DQSKn} , t_{DQSKm}) pair within any 32ms rolling window.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst READ Command

Figure 89: t_{DQSKDM} Timing

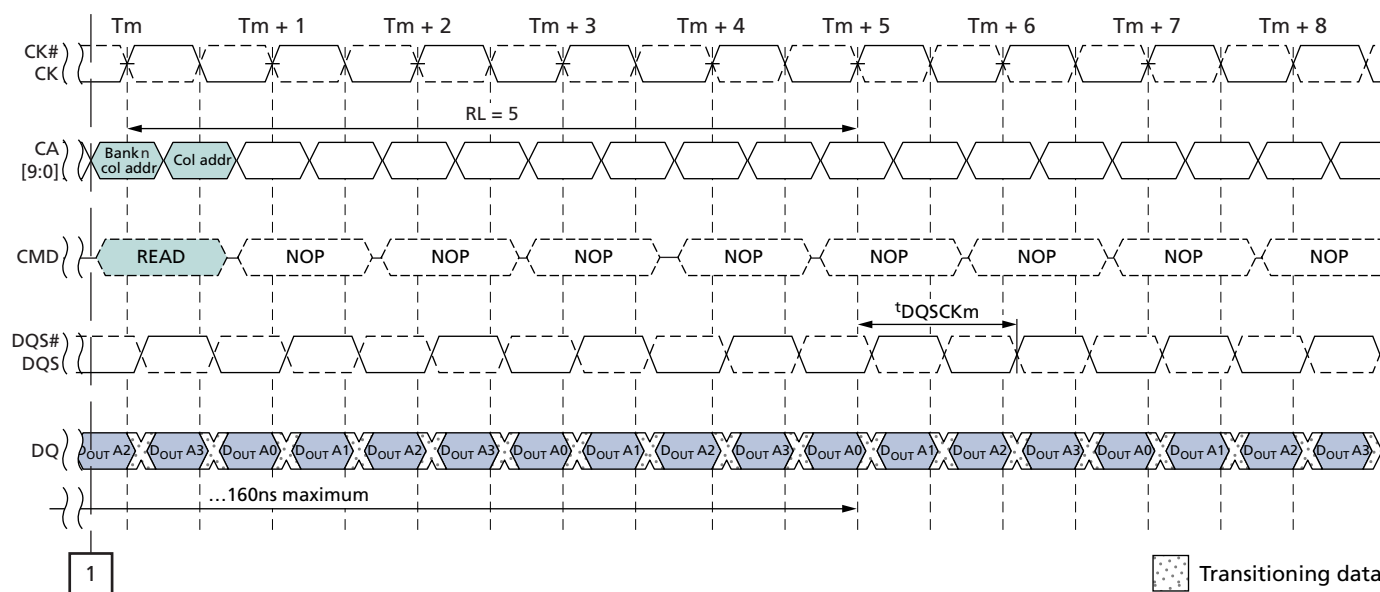
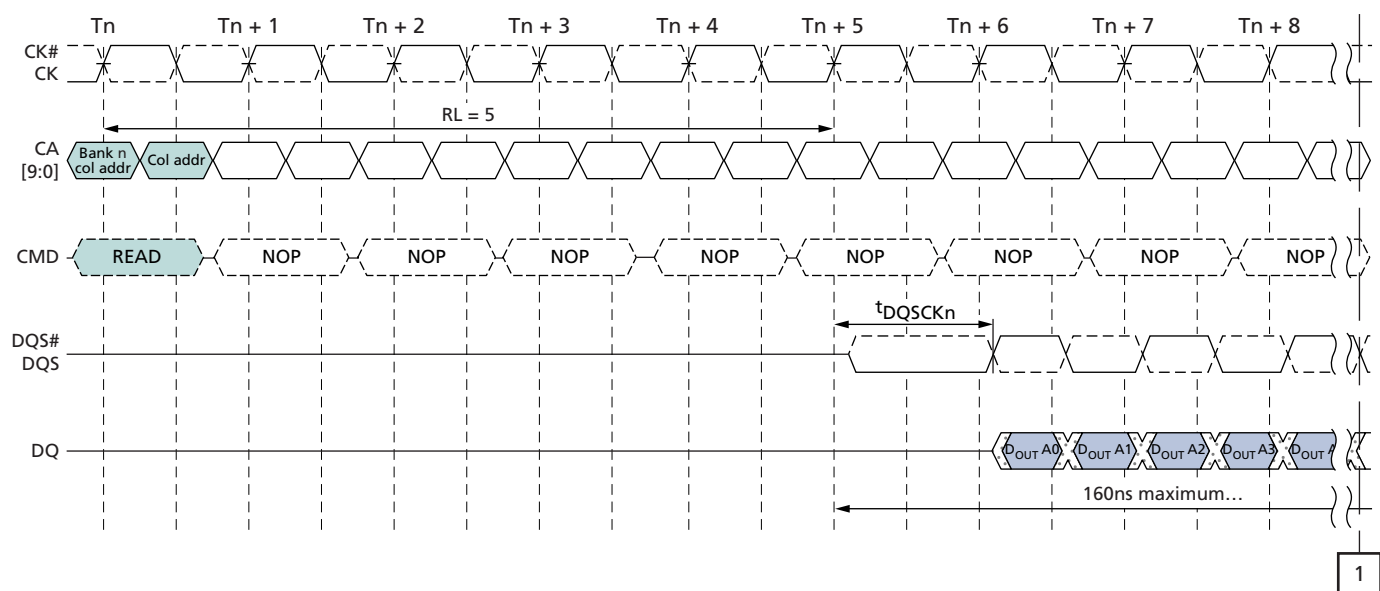


- Notes:
1. $t_{DQSKDM} = (t_{DQSKn} - t_{DQSKm})$.
 2. $t_{DQSKDM} (MAX)$ is defined as the maximum of ABS ($t_{DQSKn} - t_{DQSKm}$) for any (t_{DQSKn} , t_{DQSKm}) pair within any 1.6μs rolling window.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst READ Command

Figure 90: t_{DQCKDS} Timing

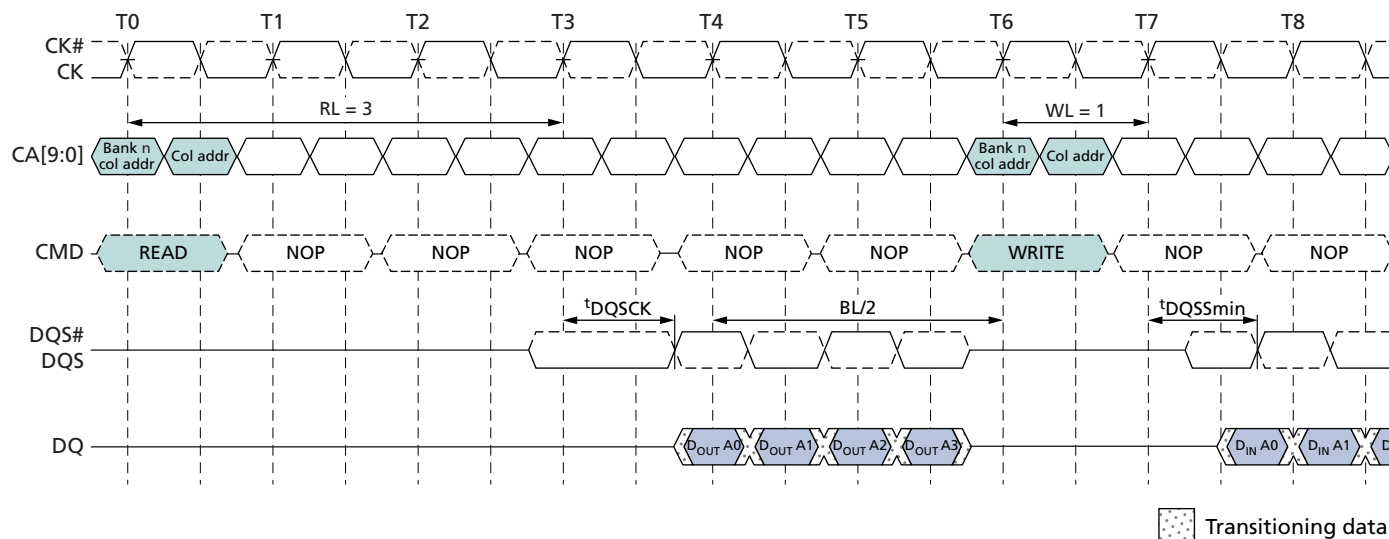


- Notes:
1. $t_{DQCKDS} = (t_{DQCKn} - t_{DQCKm})$.
 2. $t_{DQCKDS} (MAX)$ is defined as the maximum of ABS ($t_{DQCKn} - t_{DQCKm}$) for any (t_{DQCKn} , t_{DQCKm}) pair for READs within a consecutive burst, within any 160ns rolling window.



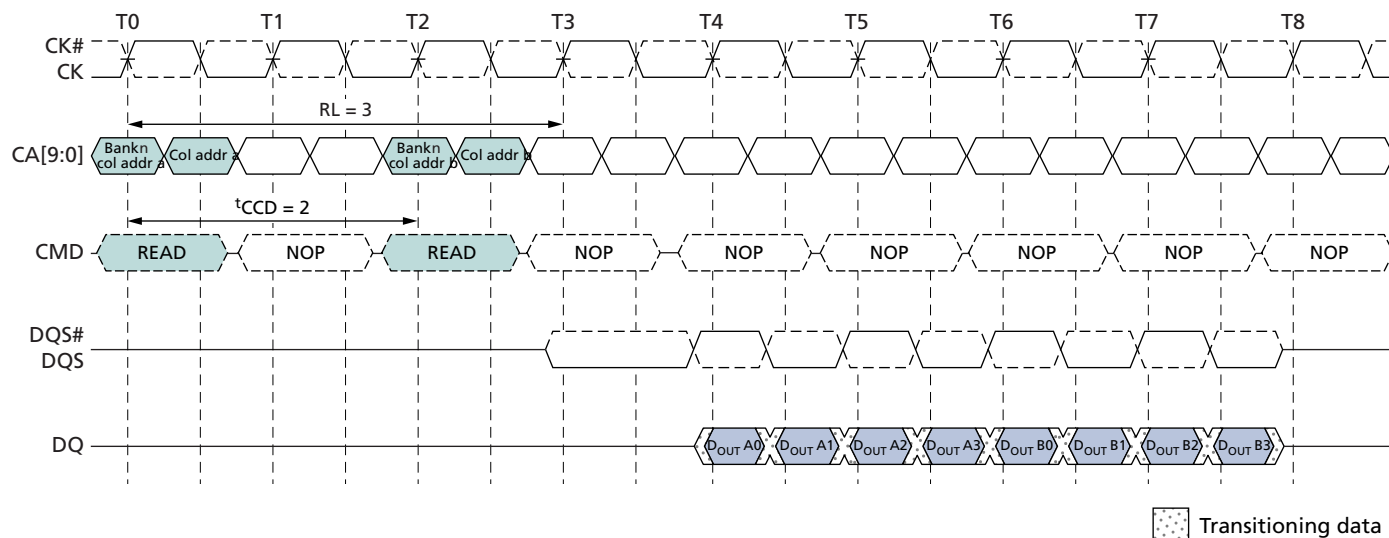
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst READ Command

Figure 91: Burst READ Followed by Burst WRITE – RL = 3, WL = 1, BL = 4



The minimum time from the burst READ command to the burst WRITE command is defined by the read latency (RL) and the burst length (BL). Minimum READ-to-WRITE latency is $RL + RU(t_{DQSCK}(MAX)/t_{CK}) + BL/2 + 1 - WL$ clock cycles. Note that if a READ burst is truncated with a burst TERMINATE (BST) command, the effective burst length of the truncated READ burst should be used for BL when calculating the minimum READ-to-WRITE delay.

Figure 92: Seamless Burst READ – RL = 3, BL = 4, $t_{CCD} = 2$



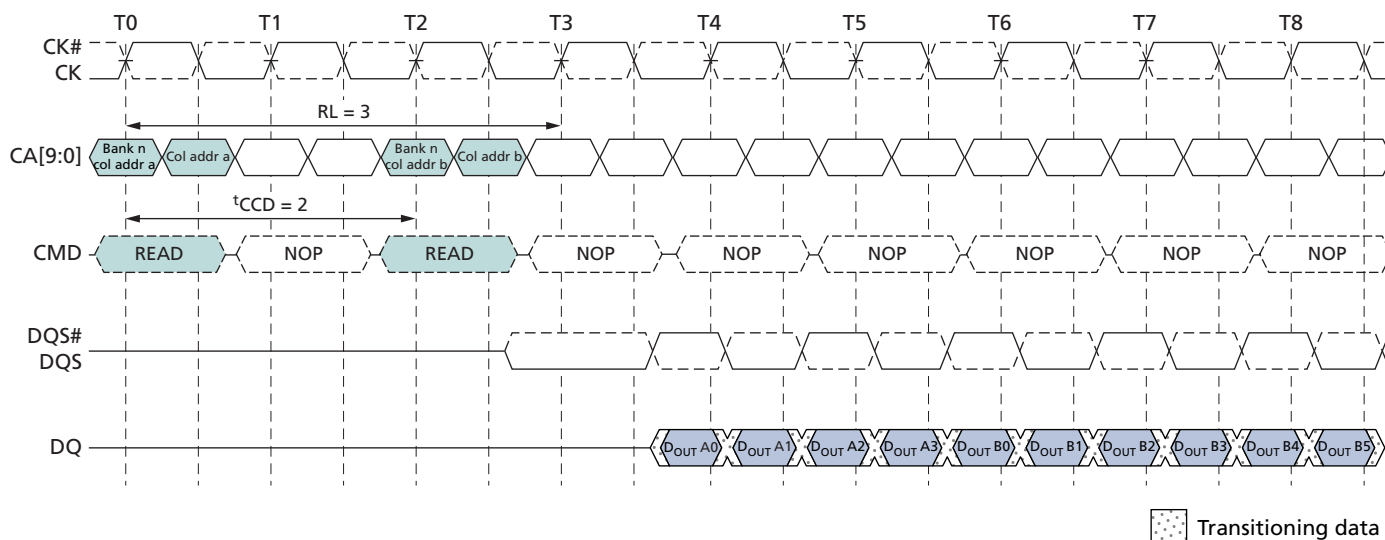
A seamless burst READ operation is supported by enabling a READ command at every other clock cycle for BL = 4 operation, every fourth clock cycle for BL = 8 operation, and every eighth clock cycle for BL = 16 operation. This operation is supported as long as the banks are activated, whether the accesses read the same or different banks.



READs Interrupted by a READ

A burst READ can be interrupted by another READ with a 4-bit burst boundary, provided that t_{CCD} is met.

Figure 93: READ Burst Interrupt Example – $RL = 3$, $BL = 8$, $t_{CCD} = 2$



Note: 1. READs can only be interrupted by other READs or the BST command.

Burst WRITE Command

The burst WRITE command is initiated with CS# LOW, CA0 HIGH, CA1 LOW, and CA2 LOW at the rising edge of the clock. The command address bus inputs, CA5r–CA6r and CA1f–CA9f, determine the starting column address for the burst. Write latency (WL) is defined from the rising edge of the clock on which the WRITE command is issued to the rising edge of the clock from which the t_{DQSS} delay is measured. The first valid data must be driven $WL \times t_{CK} + t_{DQSS}$ from the rising edge of the clock from which the WRITE command is issued. The data strobe signal (DQS) must be driven LOW t_{WPRE} prior to data input. The burst cycle data bits must be applied to the DQ pins t_{DS} prior to the associated edge of the DQS and held valid until t_{DH} after that edge. Burst data is sampled on successive edges of the DQS until the 4-, 8-, or 16-bit burst length is completed. After a burst WRITE operation, t_{WR} must be satisfied before a PRECHARGE command to the same bank can be issued.

Pin input timings are measured relative to the crosspoint of DQS and its complement, DQS#.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst WRITE Command

Figure 94: Data Input (WRITE) Timing

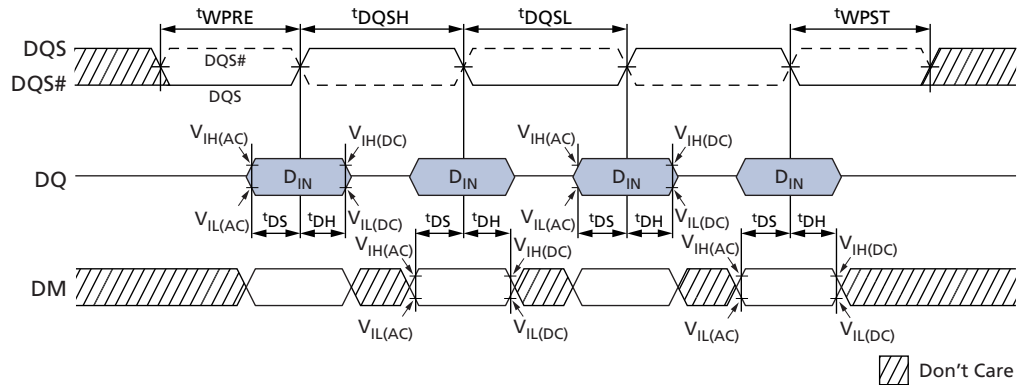
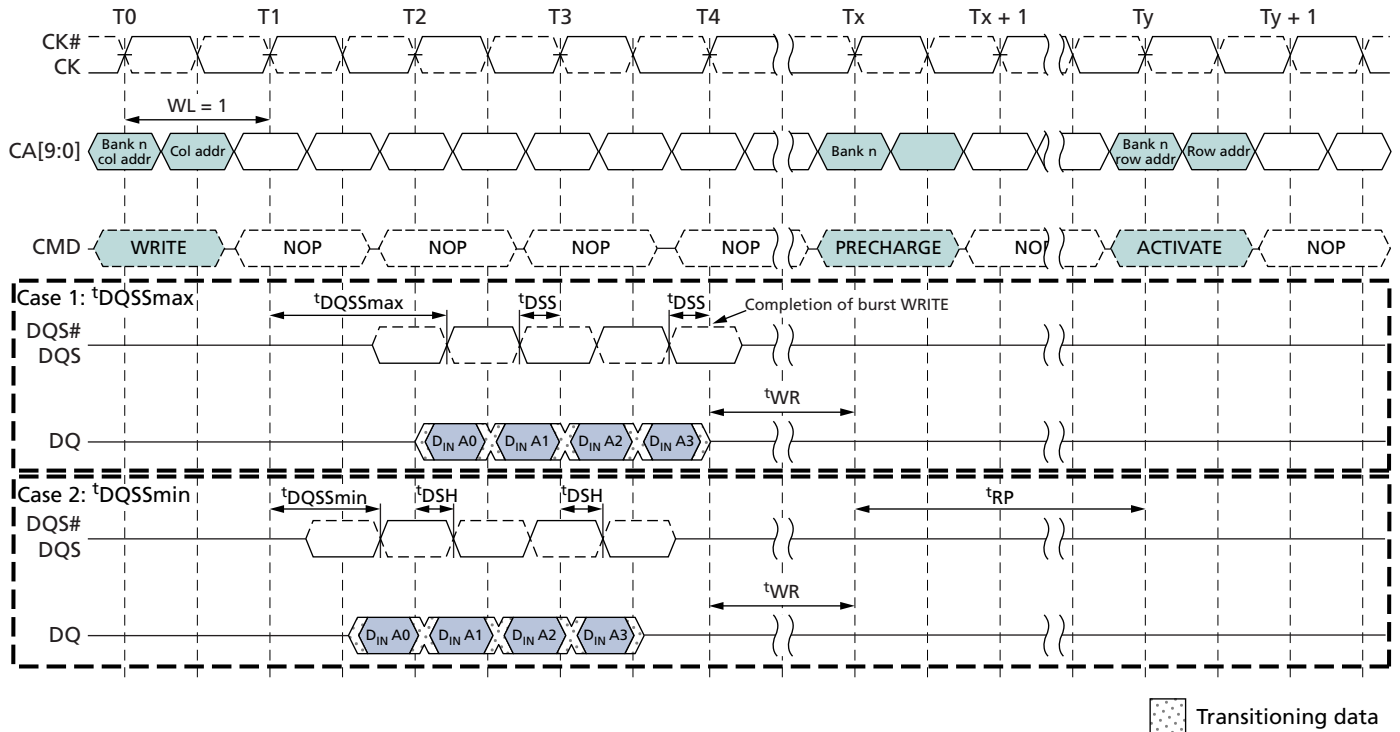


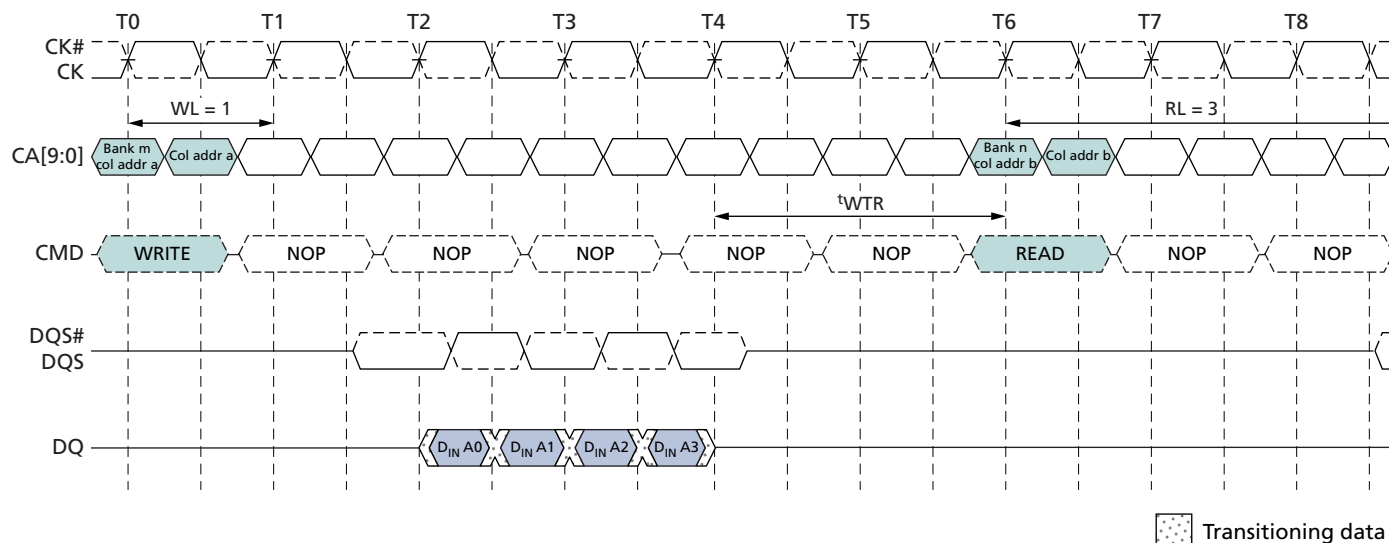
Figure 95: Burst WRITE – WL = 1, BL = 4





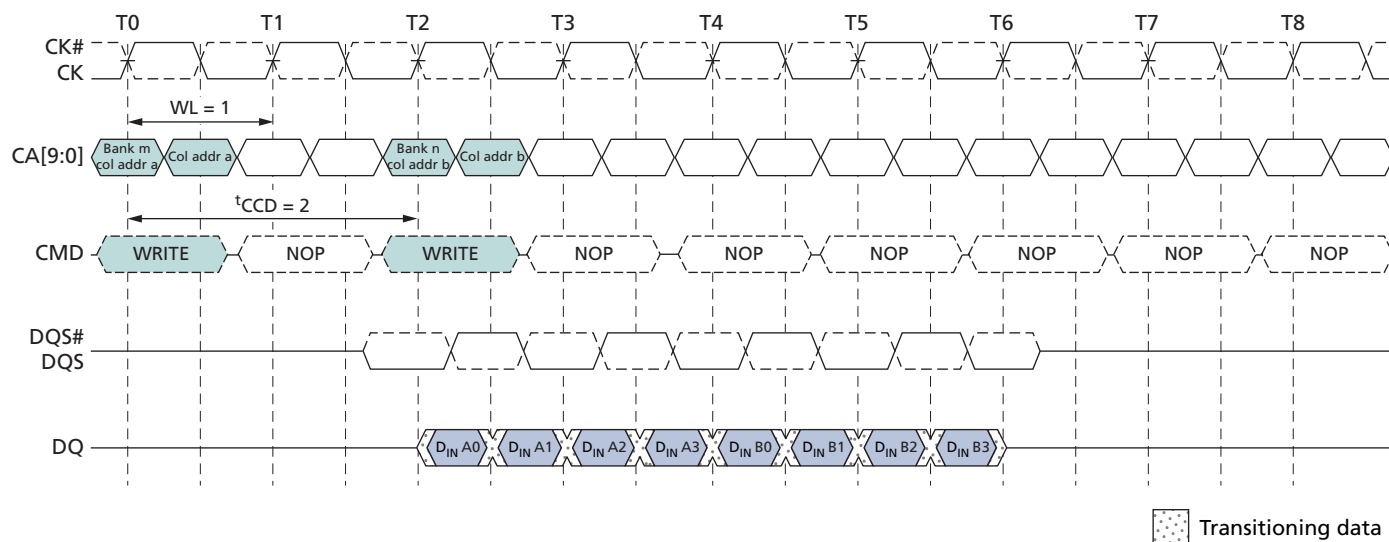
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Burst WRITE Command

Figure 96: Burst WRITE Followed by Burst READ – RL = 3, WL = 1, BL = 4



- Notes:
1. The minimum number of clock cycles from the burst WRITE command to the burst READ command for any bank is $[WL + 1 + BL/2 + RU(t_{WTR}/t_{CK})]$.
 2. t_{WTR} starts at the rising edge of the clock after the last valid input data.
 3. If a WRITE burst is truncated with a BST command, the effective burst length of the truncated WRITE burst should be used as BL to calculate the minimum WRITE-to-READ delay.

Figure 97: Seamless Burst WRITE – WL = 1, BL = 4, $t_{CCD} = 2$



- Note:
1. The seamless burst WRITE operation is supported by enabling a WRITE command every other clock for BL = 4 operation, every four clocks for BL = 8 operation, or every eight clocks for BL = 16 operation. This operation is supported for any activated bank.



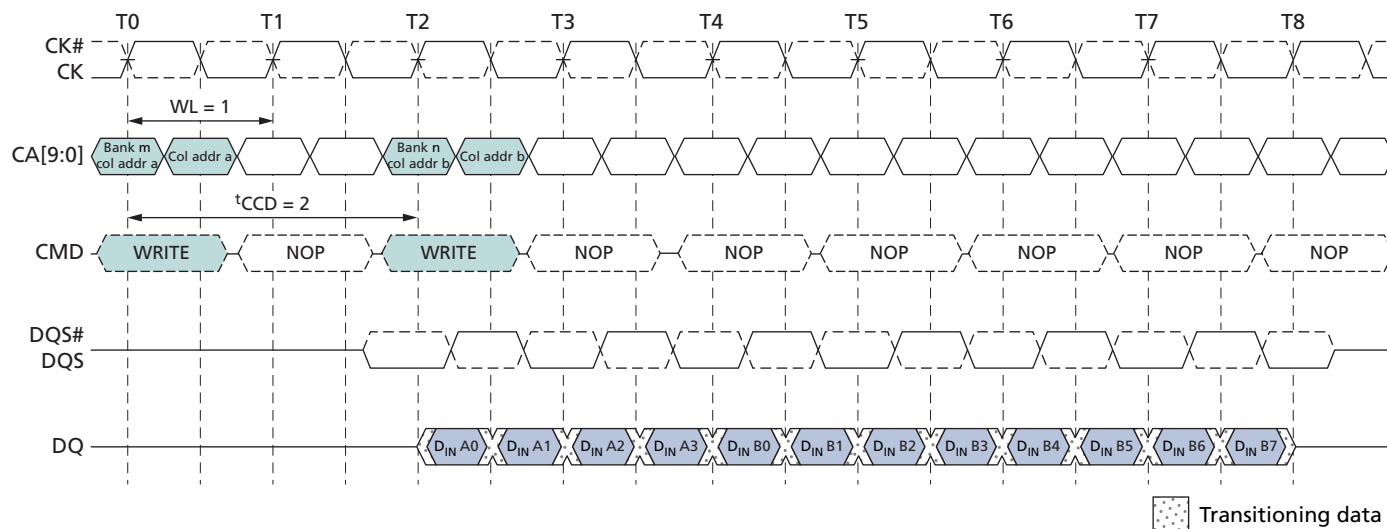
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP BURST TERMINATE Command

WRITES Interrupted by a WRITE

A burst WRITE can only be interrupted by another WRITE with a 4-bit burst boundary, provided that t_{CCD} (MIN) is met.

A WRITE burst interrupt can occur on even clock cycles after the initial WRITE command, provided that t_{CCD} (MIN) is met.

Figure 98: WRITE Burst Interrupt Timing – WL = 1, BL = 8, $t_{CCD} = 2$



- Notes:
1. WRITES can only be interrupted by other WRITES or the BST command.
 2. The effective burst length of the first WRITE equals two times the number of clock cycles between the first WRITE and the interrupting WRITE.

BURST TERMINATE Command

The BURST TERMINATE (BST) command is initiated with CS# LOW, CA0 HIGH, CA1 HIGH, CA2 LOW, and CA3 LOW at the rising edge of the clock. A BST command can only be issued to terminate an active READ or WRITE burst. Therefore, a BST command can only be issued up to and including $BL/2 - 1$ clock cycles after a READ or WRITE command. The effective burst length of a READ or WRITE command truncated by a BST command is as follows:

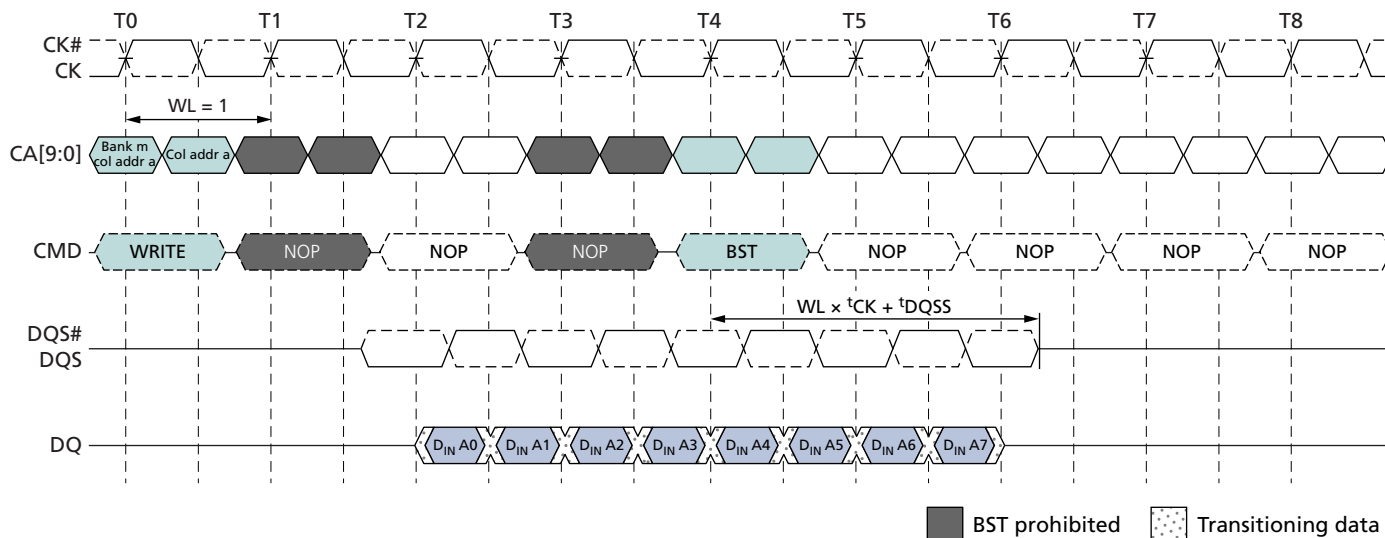
- Effective burst length = $2 \times (\text{number of clock cycles from the READ or WRITE command to the BST command})$.
- If a READ or WRITE burst is truncated with a BST command, the effective burst length of the truncated burst should be used for BL when calculating the minimum READ-to-WRITE or WRITE-to-READ delay.
- The BST command only affects the most recent READ or WRITE command. The BST command truncates an ongoing READ burst $RL \times t_{CK} + t_{DQSK} + t_{DQSQ}$ after the rising edge of the clock where the BST command is issued. The BST command truncates an ongoing WRITE burst $WL \times t_{CK} + t_{DQSS}$ after the rising edge of the clock where the BST command is issued.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP BURST TERMINATE Command

- The 4-bit prefetch architecture enables BST command assertion on even clock cycles following a WRITE or READ command. The effective burst length of a READ or WRITE command truncated by a BST command is thus an integer multiple of four.

Figure 99: Burst WRITE Truncated by BST – WL = 1, BL = 16

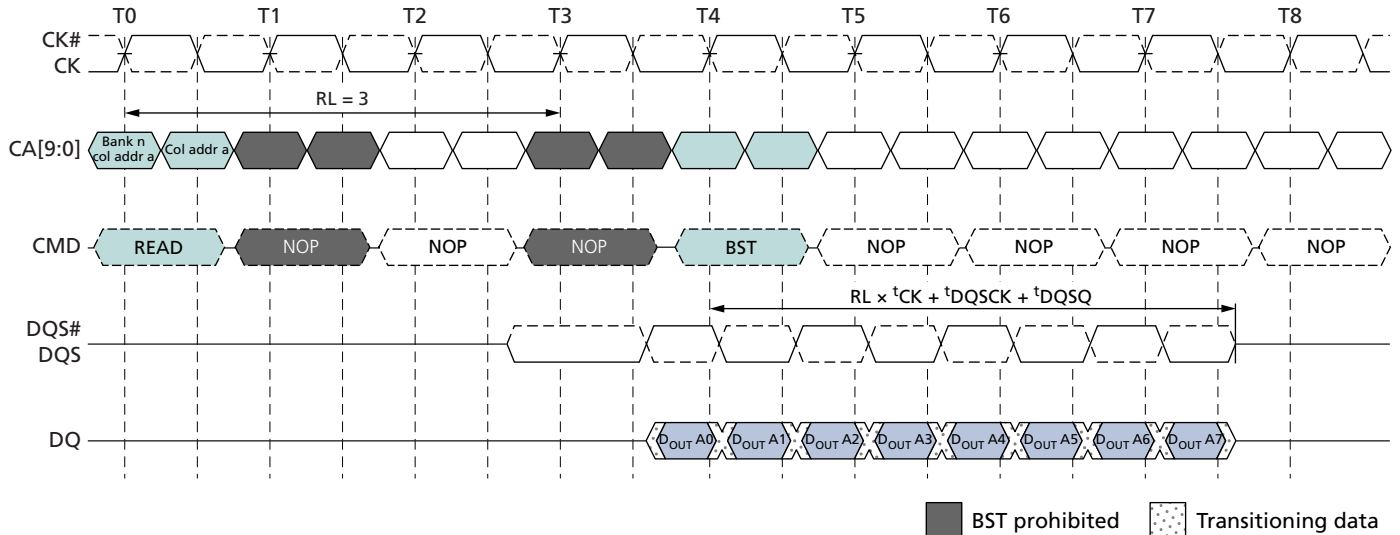


- Notes:
1. The BST command truncates an ongoing WRITE burst $WL \times t_{CK} + t_{DQSS}$ after the rising edge of the clock where the BST command is issued.
 2. BST can only be issued an even number of clock cycles after the WRITE command.
 3. Additional BST commands are not supported after T4 and must not be issued until after the next READ or WRITE command.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Write Data Mask

Figure 100: Burst READ Truncated by BST – RL = 3, BL = 16



- Notes:
1. The BST command truncates an ongoing READ burst ($RL \times t_{CK} + t_{DQSCK} + t_{DQSQ}$) after the rising edge of the clock where the BST command is issued.
 2. BST can only be issued an even number of clock cycles after the READ command.
 3. Additional BST commands are not supported after T4 and must not be issued until after the next READ or WRITE command.

Write Data Mask

On LPDDR2 devices, one write data mask (DM) pin for each data byte (DQ) is supported, consistent with the implementation on LPDDR SDRAM. Each DM can mask its respective DQ for any given cycle of the burst. Data mask timings match data bit timing, but are inputs only. Internal data mask loading is identical to data bit loading to ensure matched system timing.

Figure 101: Data Mask Timing

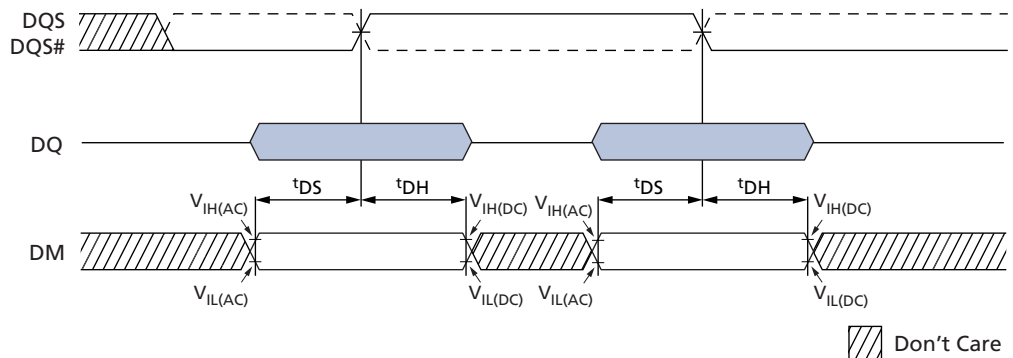
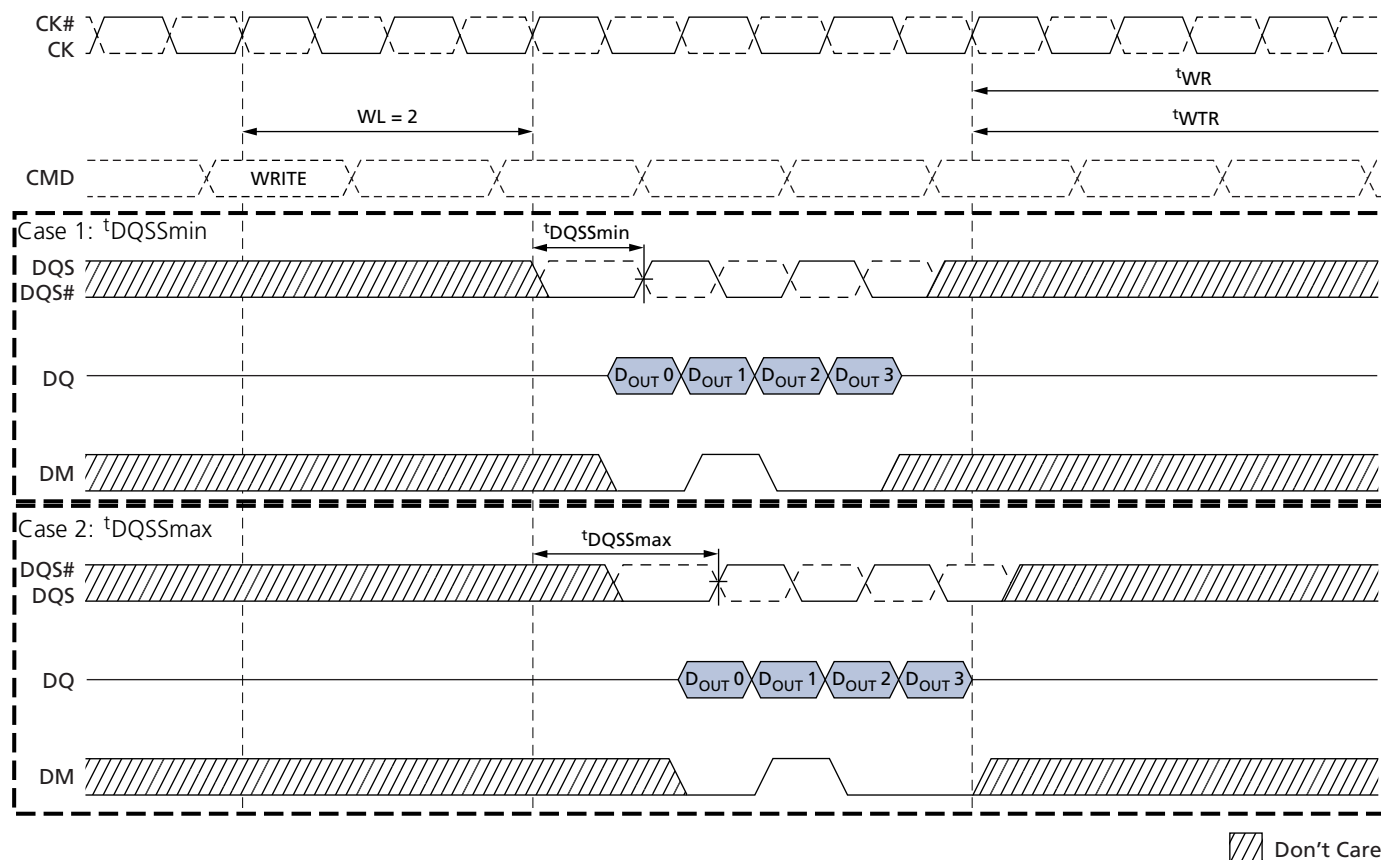



Figure 102: Write Data Mask – Second Data Bit Masked


Note: 1. For the data mask function, WL = 2, BL = 4 is shown; the second data bit is masked.

PRECHARGE Command

The PRECHARGE command is used to precharge or close a bank that has been activated. The PRECHARGE command is initiated with CS# LOW, CA0 HIGH, CA1 HIGH, CA2 LOW, and CA3 HIGH at the rising edge of the clock. The PRECHARGE command can be used to precharge each bank independently or all banks simultaneously. For 4-bank devices, the AB flag and bank address bits BA0 and BA1 are used to determine which bank(s) to precharge. For 8-bank devices, the AB flag and the bank address bits BA0, BA1, and BA2 are used to determine which bank(s) to precharge. The precharged bank(s) will be available for subsequent row access t_{RPab} after an all bank PRECHARGE command is issued, or t_{RPpb} after a single-bank PRECHARGE command is issued.

To ensure that 8-bank devices can meet the instantaneous current demand required to operate, the row precharge time (t_{RP}) for an all bank PRECHARGE in 8-bank devices (t_{RPab}) will be longer than the row precharge time for a single-bank PRECHARGE (t_{RPpb}). For 4-bank devices, t_{RPab} is equal to t_{RPpb} .

ACTIVATE to PRECHARGE timing is shown in ACTIVATE Command.


Table 80: Bank Selection for PRECHARGE by Address Bits

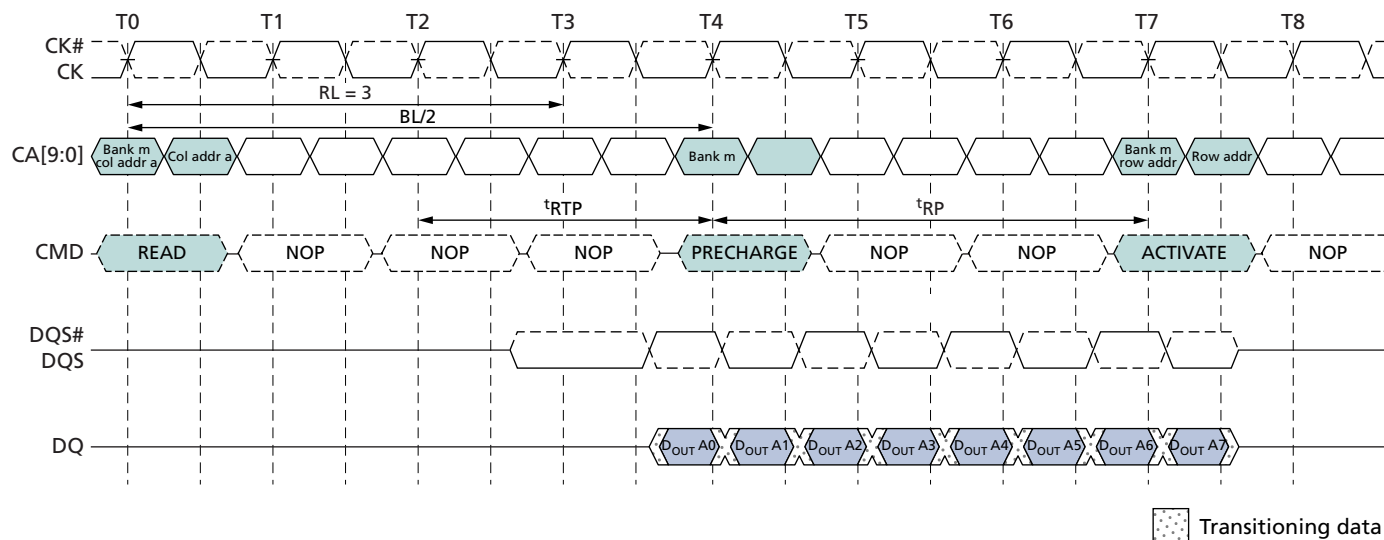
AB (CA4r)	BA2 (CA9r)	BA1 (CA8r)	BA0 (CA7r)	Precharged Bank(s) 4-Bank Device	Precharged Bank(s) 8-Bank Device
0	0	0	0	Bank 0 only	Bank 0 only
0	0	0	1	Bank 1 only	Bank 1 only
0	0	1	0	Bank 2 only	Bank 2 only
0	0	1	1	Bank 3 only	Bank 3 only
0	1	0	0	Bank 0 only	Bank 4 only
0	1	0	1	Bank 1 only	Bank 5 only
0	1	1	0	Bank 2 only	Bank 6 only
0	1	1	1	Bank 3 only	Bank 7 only
1	Don't Care	Don't Care	Don't Care	All banks	All banks

READ Burst Followed by PRECHARGE

For the earliest possible precharge, the PRECHARGE command can be issued BL/2 clock cycles after a READ command. A new bank ACTIVATE command can be issued to the same bank after the row precharge time (t_{RP}) has elapsed. A PRECHARGE command cannot be issued until after t_{RAS} is satisfied.

The minimum READ-to-PRECHARGE time (t_{RTP}) must also satisfy a minimum analog time from the rising clock edge that initiates the last 4-bit prefetch of a READ command. t_{RTP} begins BL/2 - 2 clock cycles after the READ command.

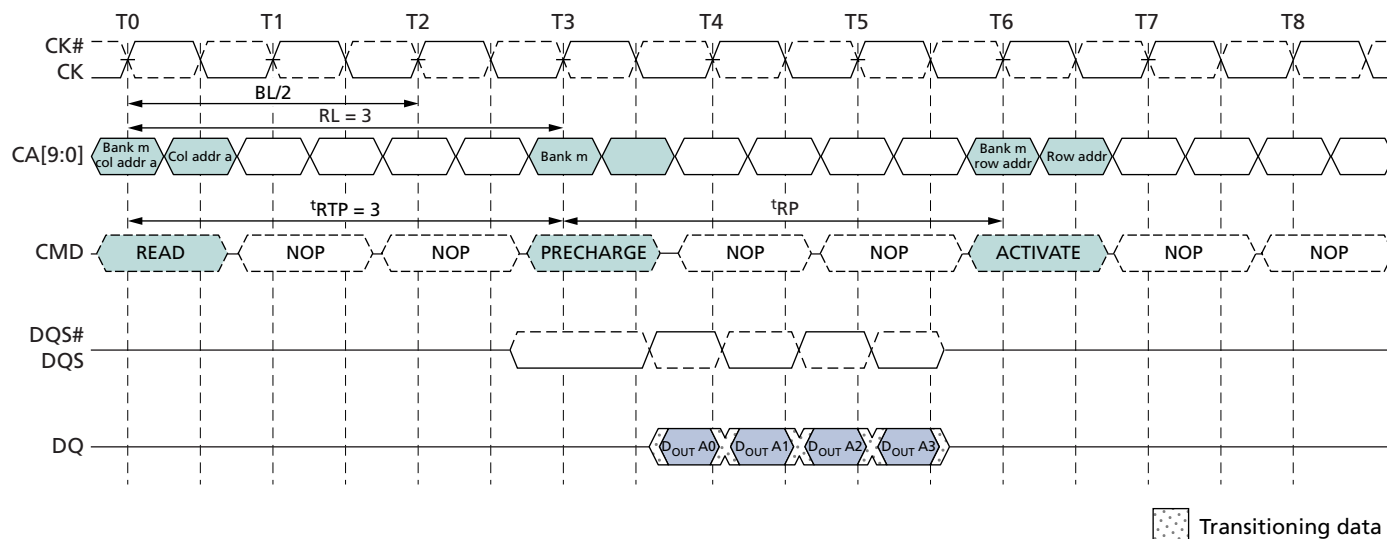
If the burst is truncated by a BST command, the effective BL value is used to calculate when t_{RTP} begins.

Figure 103: READ Burst Followed by PRECHARGE – RL = 3, BL = 8, $RU(t_{RTP(MIN)}/t_{CK}) = 2$




4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP PRECHARGE Command

Figure 104: READ Burst Followed by PRECHARGE – RL = 3, BL = 4, $RU(t_{RTP(MIN)}/t_{CK}) = 3$



WRITE Burst Followed by PRECHARGE

For WRITE cycles, a WRITE recovery time (t_{WR}) must be provided before a PRECHARGE command can be issued. t_{WR} delay is referenced from the completion of the burst WRITE. The PRECHARGE command must not be issued prior to the t_{WR} delay. For WRITE-to-PRECHARGE timings, see the PRECHARGE and Auto Precharge Clarification table.

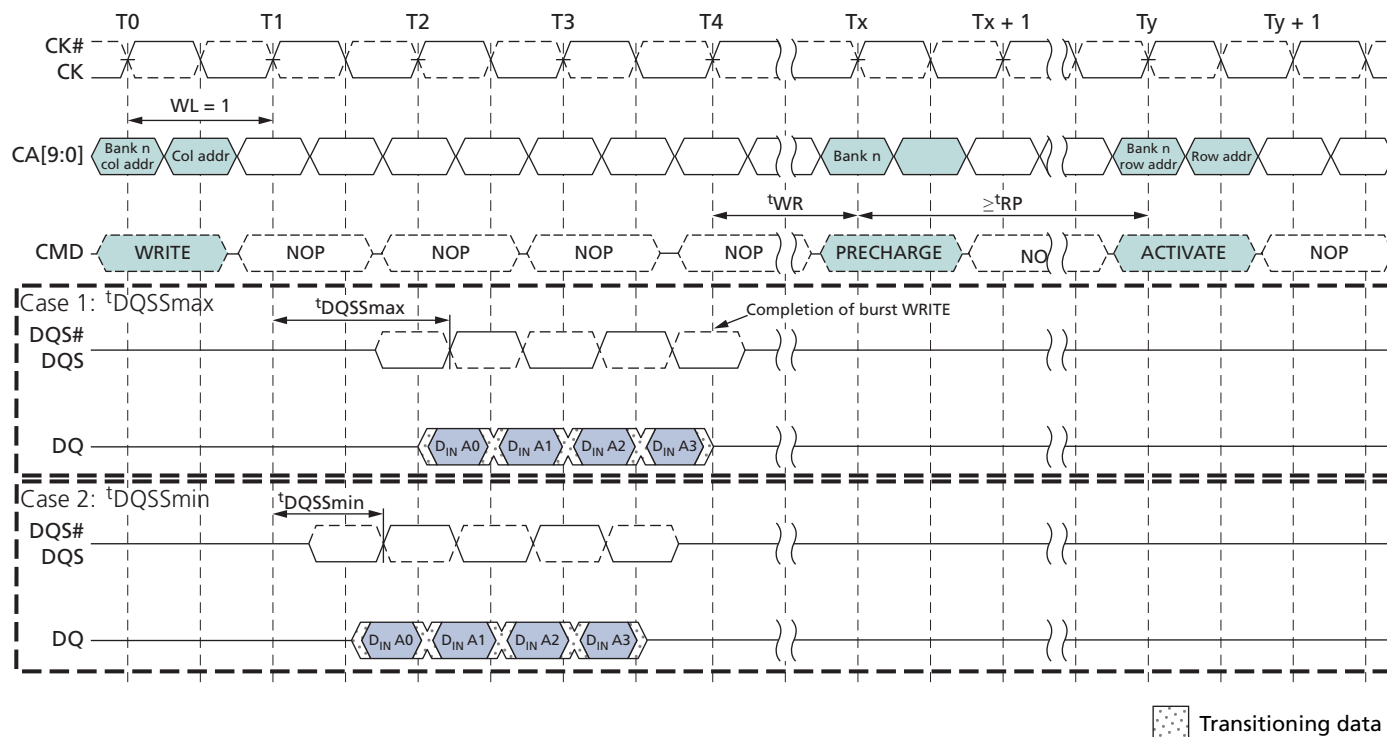
These devices write data to the array in prefetch quadruples (prefetch = 4). An internal WRITE operation can only begin after a prefetch group has been completely latched.

The minimum WRITE-to-PRECHARGE time for commands to the same bank is $WL + BL/2 + 1 + RU(t_{WR}/t_{CK})$ clock cycles. For untruncated bursts, BL is the value set in the mode register. For truncated bursts, BL is the effective burst length.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP PRECHARGE Command

Figure 105: WRITE Burst Followed by PRECHARGE – WL = 1, BL = 4



Auto Precharge

Before a new row can be opened in an active bank, the active bank must be precharged using either the PRECHARGE command or the auto precharge function. When a READ or WRITE command is issued to the device, the auto precharge bit (AP) can be set to enable the active bank to automatically begin precharge at the earliest possible moment during the burst READ or WRITE cycle.

If AP is LOW when the READ or WRITE command is issued, then normal READ or WRITE burst operation is executed and the bank remains active at the completion of the burst.

If AP is HIGH when the READ or WRITE command is issued, the auto precharge function is engaged. This feature enables the PRECHARGE operation to be partially or completely hidden during burst READ cycles (dependent upon READ or WRITE latency), thus improving system performance for random data access.

READ Burst with Auto Precharge

If AP (CA0f) is HIGH when a READ command is issued, the READ with auto precharge function is engaged.

These devices start an auto precharge on the rising edge of the clock BL/2 or BL/2 - 2 + RU (tRTP/tCK) clock cycles later than the READ with auto precharge command, whichever is greater. For auto precharge calculations, see the PRECHARGE and Auto Precharge Clarification table.

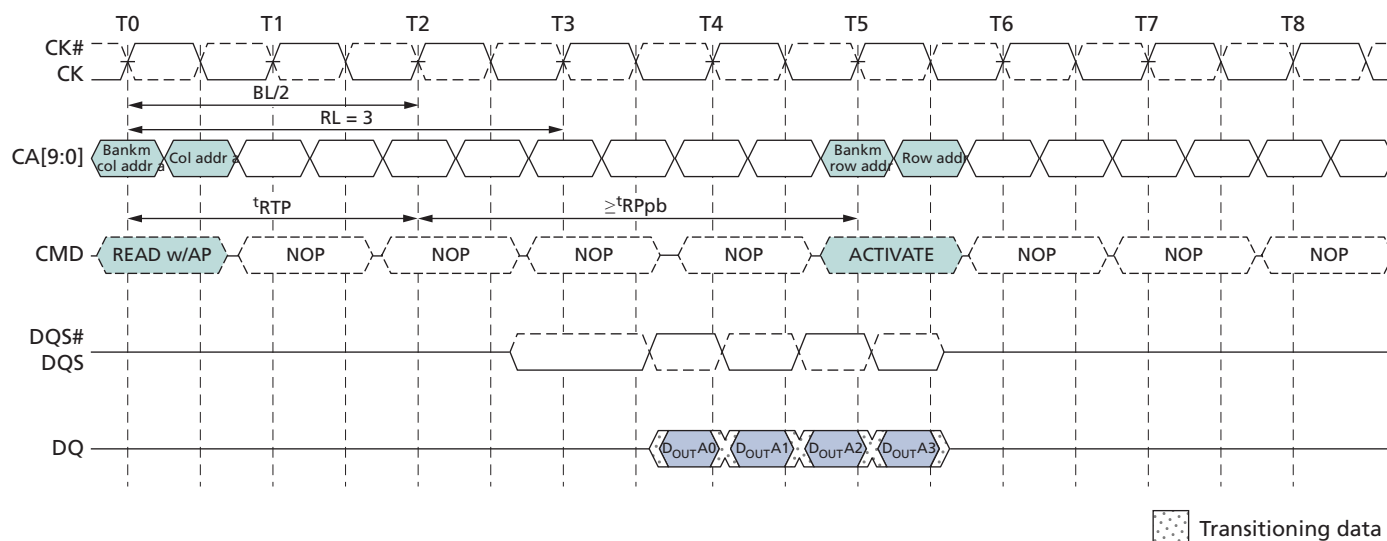


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP PRECHARGE Command

Following an auto precharge operation, an ACTIVATE command can be issued to the same bank if the following two conditions are satisfied simultaneously:

- The RAS precharge time (t_{RP}) has been satisfied from the clock at which the auto precharge begins.
- The RAS cycle time (t_{RC}) from the previous bank activation has been satisfied.

Figure 106: READ Burst with Auto Precharge – RL = 3, BL = 4, $RU(t_{RTP(MIN)}/t_{CK}) = 2$



WRITE Burst with Auto Precharge

If AP (CA0f) is HIGH when a WRITE command is issued, the WRITE with auto precharge function is engaged. The device starts an auto precharge at the clock rising edge t_{WR} cycles after the completion of the burst WRITE.

Following a WRITE with auto precharge, an ACTIVATE command can be issued to the same bank if the following two conditions are met:

- The RAS precharge time (t_{RP}) has been satisfied from the clock at which the auto precharge begins.
- The RAS cycle time (t_{RC}) from the previous bank activation has been satisfied.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP PRECHARGE Command

Figure 107: WRITE Burst with Auto Precharge – WL = 1, BL = 4

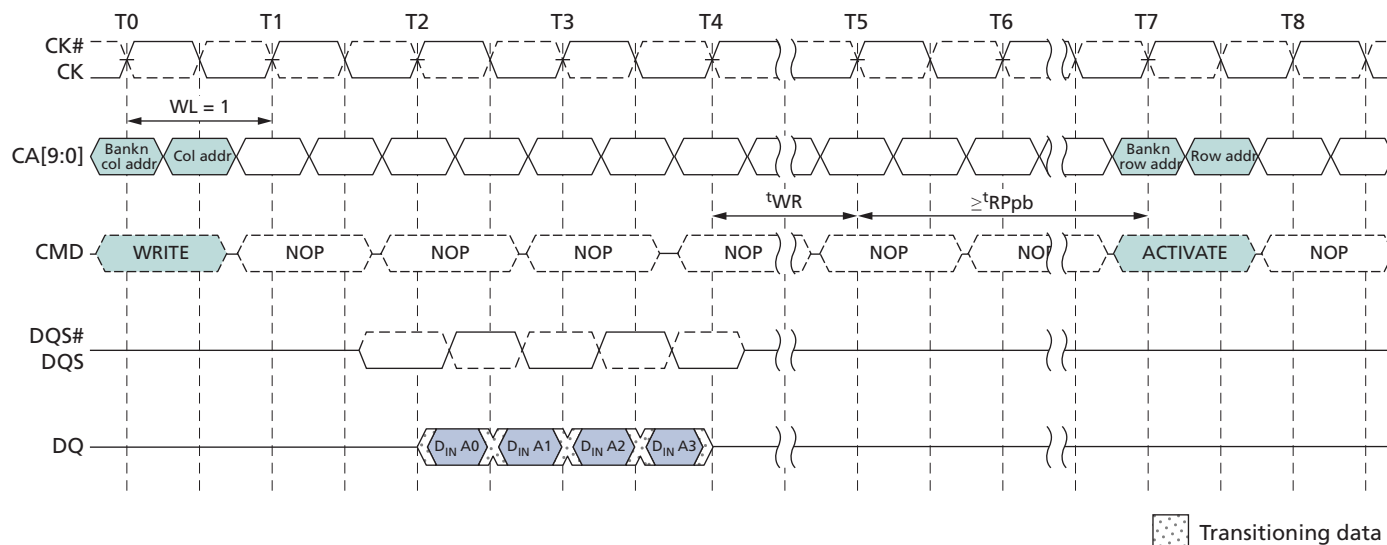


Table 81: PRECHARGE and Auto Precharge Clarification

From Command	To Command	Minimum Delay Between Commands	Unit	Notes
READ	PRECHARGE to same bank as READ	$BL/2 + \text{MAX}(2, RU(t_{RTP}/t_{CK})) - 2$	CLK	1
	PRECHARGE ALL	$BL/2 + \text{MAX}(2, RU(t_{RTP}/t_{CK})) - 2$	CLK	1
BST	PRECHARGE to same bank as READ	1	CLK	1
	PRECHARGE ALL	1	CLK	1
READ w/AP	PRECHARGE to same bank as READ w/AP	$BL/2 + \text{MAX}(2, RU(t_{RTP}/t_{CK})) - 2$	CLK	1, 2
	PRECHARGE ALL	$BL/2 + \text{MAX}(2, RU(t_{RTP}/t_{CK})) - 2$	CLK	1
	ACTIVATE to same bank as READ w/AP	$BL/2 + \text{MAX}(2, RU(t_{RTP}/t_{CK})) - 2 + RU(t_{RPpb}/t_{CK})$	CLK	1
	WRITE or WRITE w/AP (same bank)	Illegal	CLK	3
	WRITE or WRITE w/AP (different bank)	$RL + BL/2 + RU(t_{DQSCKmax}/t_{CK}) - WL + 1$	CLK	3
	READ or READ w/AP (same bank)	Illegal	CLK	3
	READ or READ w/AP (different bank)	$BL/2$	CLK	3
WRITE	PRECHARGE to same bank as WRITE	$WL + BL/2 + RU(t_{WR}/t_{CK}) + 1$	CLK	1
	PRECHARGE ALL	$WL + BL/2 + RU(t_{WR}/t_{CK}) + 1$	CLK	1
BST	PRECHARGE to same bank as WRITE	$WL + RU(t_{WR}/t_{CK}) + 1$	CLK	1
	PRECHARGE ALL	$WL + RU(t_{WR}/t_{CK}) + 1$	CLK	1



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP REFRESH Command

Table 81: PRECHARGE and Auto Precharge Clarification (Continued)

From Command	To Command	Minimum Delay Between Commands	Unit	Notes
WRITE w/AP	PRECHARGE to same bank as WRITE w/AP	$WL + BL/2 + RU(t_{WR}/t_{CK}) + 1$	CLK	1, 2
	PRECHARGE ALL	$WL + BL/2 + RU(t_{WR}/t_{CK}) + 1$	CLK	1
	ACTIVATE to same bank as WRITE w/AP	$WL + BL/2 + RU(t_{WR}/t_{CK}) + 1 + RU(t_{RPpb}/t_{CK})$	CLK	1
	WRITE or WRITE w/AP (same bank)	Illegal	CLK	3
	WRITE or WRITE w/AP (different bank)	BL/2	CLK	3
	READ or READ w/AP (same bank)	Illegal	CLK	3
	READ or READ w/AP (different bank)	$WL + BL/2 + RU(t_{WTR}/t_{CK}) + 1$	CLK	3
PRECHARGE	PRECHARGE to same bank as PRECHARGE	1	CLK	1
	PRECHARGE ALL	1	CLK	1
PRECHARGE ALL	PRECHARGE	1	CLK	1
	PRECHARGE ALL	1	CLK	1

- Notes:
1. For a given bank, the PRECHARGE period should be counted from the latest PRECHARGE command—either a one-bank PRECHARGE or PRECHARGE ALL—issued to that bank. The PRECHARGE period is satisfied after t_{RP} , depending on the latest PRECHARGE command issued to that bank.
 2. Any command issued during the specified minimum delay time is illegal.
 3. After READ with auto precharge, seamless READ operations to different banks are supported. After WRITE with auto precharge, seamless WRITE operations to different banks are supported. READ with auto precharge and WRITE with auto precharge must not be interrupted or truncated.

REFRESH Command

The REFRESH command is initiated with CS# LOW, CA0 LOW, CA1 LOW, and CA2 HIGH at the rising edge of the clock. Per-bank REFRESH is initiated with CA3 LOW at the rising edge of the clock. All-bank REFRESH is initiated with CA3 HIGH at the rising edge of the clock. Per-bank REFRESH is only supported in devices with eight banks.

A per-bank REFRESH command (REFpb) performs a per-bank REFRESH operation to the bank scheduled by the bank counter in the memory device. The bank sequence for per-bank REFRESH is fixed to be a sequential round-robin: 0-1-2-3-4-5-6-7-0-1-.... The bank count is synchronized between the controller and the SDRAM by resetting the bank count to zero. Synchronization can occur upon issuing a RESET command or at every exit from self refresh.

A bank must be idle before it can be refreshed. The controller must track the bank being refreshed by the per-bank REFRESH command.

The REFpb command must not be issued to the device until the following conditions have been met:

- t_{RFCab} has been satisfied after the prior REFab command
- t_{RFCpb} has been satisfied after the prior REFpb command
- t_{RP} has been satisfied after the prior PRECHARGE command to that bank



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP REFRESH Command

- t_{RRD} has been satisfied after the prior ACTIVATE command (if applicable, for example after activating a row in a different bank than the one affected by the REFpb command)

The target bank is inaccessible during per-bank REFRESH cycle time (t_{RFCpb}), however, other banks within the device are accessible and can be addressed during the cycle. During the REFpb operation, any of the banks other than the one being refreshed can be maintained in an active state or accessed by a READ or WRITE command.

When the per-bank REFRESH cycle has completed, the affected bank will be in the idle state.

After issuing REFpb, the following conditions must be met:

- t_{RFCpb} must be satisfied before issuing a REFab command
- t_{RFCpb} must be satisfied before issuing an ACTIVATE command to the same bank
- t_{RRD} must be satisfied before issuing an ACTIVATE command to a different bank
- t_{RFCpb} must be satisfied before issuing another REFpb command

An all-bank REFRESH command (REFab) issues a REFRESH command to all banks. All banks must be idle when REFab is issued (for instance, by issuing a PRECHARGE ALL command prior to issuing an all-bank REFRESH command). REFab also synchronizes the bank count between the controller and the SDRAM to zero. The REFab command must not be issued to the device until the following conditions have been met:

- t_{RFCab} has been satisfied following the prior REFab command
- t_{RFCpb} has been satisfied following the prior REFpb command
- t_{RP} has been satisfied following the prior PRECHARGE commands

After an all-bank REFRESH cycle has completed, all banks will be idle. After issuing REFab:

- t_{RFCab} latency must be satisfied before issuing an ACTIVATE command
- t_{RFCab} latency must be satisfied before issuing a REFab or REFpb command

Table 82: REFRESH Command Scheduling Separation Requirements

Symbol	Minimum Delay From	To	Notes
t_{RFCab}	REFab	REFab	
		ACTIVATE command to any bank	
		REFpb	
t_{RFCpb}	REFpb	REFab	
		ACTIVATE command to same bank as REFpb	
		REFpb	



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP REFRESH Command

Table 82: REFRESH Command Scheduling Separation Requirements (Continued)

Symbol	Minimum Delay From	To	Notes
t_{RRD}	REFpb	ACTIVATE command to a different bank than REFpb	
	ACTIVATE	REFpb	1
		ACTIVATE command to a different bank than the prior ACTIVATE command	

Note: 1. A bank must be in the idle state before it is refreshed, so REFpb is prohibited following an ACTIVATE command. REFpb is supported only if it affects a bank that is in the idle state.

Mobile LPDDR2 devices provide significant flexibility in scheduling REFRESH commands as long as the required boundary conditions are met (see the t_{SRF} Definition figure).

In the most straightforward implementations, a REFRESH command should be scheduled every t_{REFI} . In this case, self refresh can be entered at any time.

Users may choose to deviate from this regular refresh pattern, for instance, to enable a period in which no refresh is required. For example, using a 1Gb LPDDR2 device, the user can choose to issue a refresh burst of multi REFRESH commands at the maximum supported rate (limited by t_{REFBW}), followed by an extended period without issuing any REFRESH commands, until the refresh window is complete. The maximum supported time without REFRESH commands is calculated as follows: $t_{REFW} - (R/8) \times t_{REFBW} = t_{REFW} - R \times 4 \times t_{RfCab}$.

For example, a 1Gb device at $T_C \leq 85^\circ\text{C}$ can be operated without a refresh for up to 32ms - $4096 \times 4 \times 130\text{ns} \approx 30\text{ms}$.

Both the regular and the burst/pause patterns can satisfy refresh requirements if they are repeated in every 32ms window. It is critical to satisfy the refresh requirement in *every* rolling refresh window during refresh pattern transitions. The supported transition from a burst pattern to a regular distributed pattern is shown in the Supported Transition from Repetitive REFRESH Burst figure. If this transition occurs immediately after the burst refresh phase, all rolling t_{REFW} intervals will meet the minimum required number of REFRESH commands.

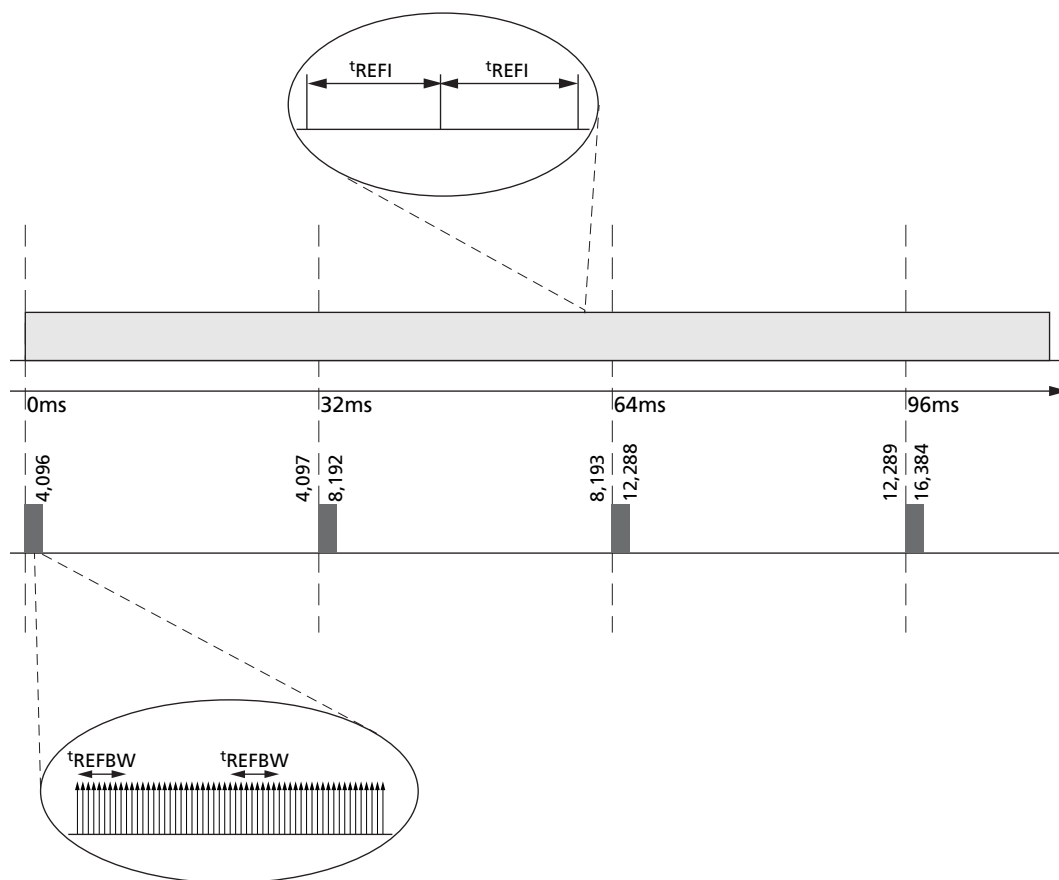
A nonsupported transition is shown in Figure 110 (page 156). In this example, the regular refresh pattern starts after the completion of the pause phase of the burst/pause refresh pattern. For several rolling t_{REFW} intervals, the minimum number of REFRESH commands is not satisfied.

Understanding this pattern transition is extremely important, even when only one pattern is employed. In self refresh mode, a regular distributed refresh pattern must be assumed. Micron recommends entering self refresh mode immediately following the burst phase of a burst/pause refresh pattern; upon exiting self refresh, begin with the burst phase (see the Recommended Self Refresh Entry and Exit figure).



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP REFRESH Command

Figure 108: Regular Distributed Refresh Pattern

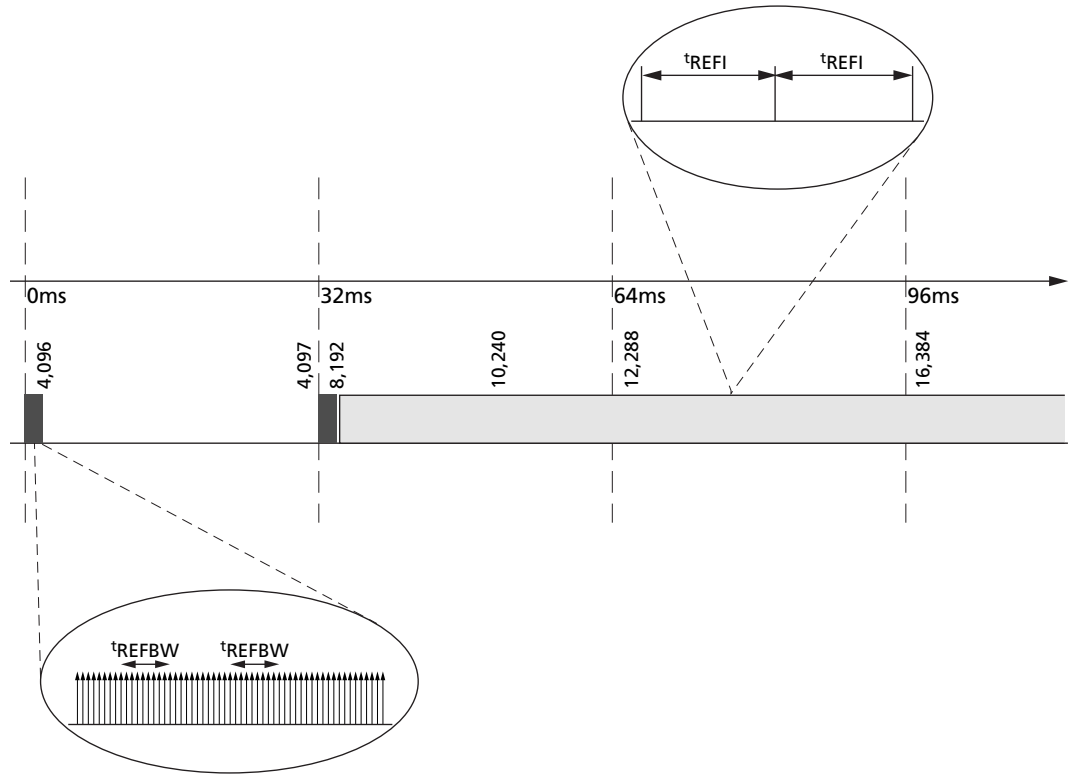


- Notes:
1. Compared to repetitive burst REFRESH with subsequent REFRESH pause.
 2. As an example, in a 1Gb LPDDR2 device at $T_C \leq 85^\circ\text{C}$, the distributed refresh pattern has one REFRESH command per $7.8\mu\text{s}$; the burst refresh pattern has one REFRESH command per $0.52\mu\text{s}$, followed by $\approx 30\text{ms}$ without any REFRESH command.
 3. As the nature of a DRAM scaling effect, the maximum burst of 4096 REFRESH commands could affect data retention of the DRAM. Memory controller may limit the maximum burst count to 8 REFRESH commands as similar to LPDDR3 and/or LPDDR4.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP REFRESH Command

Figure 109: Supported Transition from Repetitive REFRESH Burst

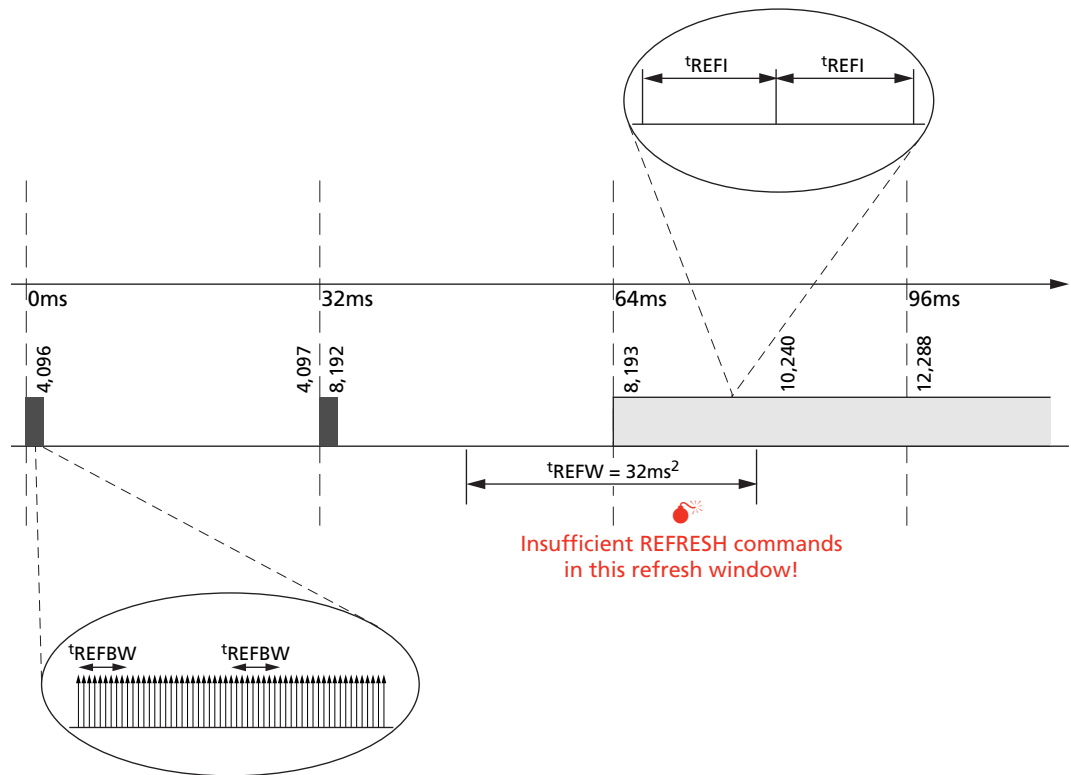


- Notes:
1. Shown with subsequent REFRESH pause to regular distributed refresh pattern.
 2. As an example, in a 1Gb LPDDR2 device at $T_C \leq 85^\circ\text{C}$, the distributed refresh pattern has one REFRESH command per $7.8\mu\text{s}$; the burst refresh pattern has one REFRESH command per $0.52\mu\text{s}$, followed by $\approx 30\text{ms}$ without any REFRESH command.
 3. As the nature of a DRAM scaling effect, the maximum burst of 4096 REFRESH commands could affect data retention of the DRAM. Memory controller may limit the maximum burst count to 8 REFRESH commands as similar to LPDDR3 and/or LPDDR4.

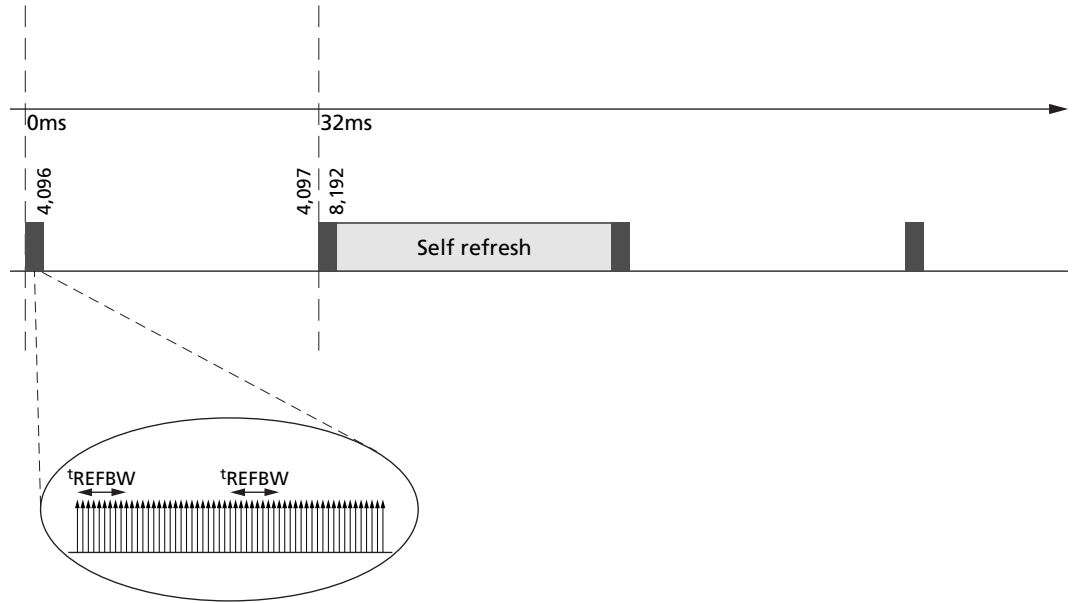


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP REFRESH Command

Figure 110: Nonsupported Transition from Repetitive REFRESH Burst



- Notes:
1. Shown with subsequent REFRESH pause to regular distributed refresh pattern.
 2. There are only ≈ 2048 REFRESH commands in the indicated t_{REFW} window. This does not provide the required minimum number of REFRESH commands (R).


Figure 111: Recommended Self Refresh Entry and Exit


Note: 1. In conjunction with a burst/pause refresh pattern.

REFRESH Requirements

1. Minimum Number of REFRESH Commands

Mobile LPDDR2 requires a minimum number, R , of REFRESH (REFab) commands within any rolling refresh window ($t_{REFW} = 32 \text{ ms}$ @ $MR4[2:0] = 011$ or $T_C \leq 85^\circ\text{C}$). For actual values per density and the resulting average refresh interval (t_{REFI}), see Refresh Requirements.

For t_{REFW} and t_{REFI} refresh multipliers at different $MR4$ settings, see the $MR4$ Device Temperature ($MA[7:0] = 04h$) table.

For devices supporting per-bank REFRESH, a REFab command can be replaced by a full cycle of eight REFpb commands.

2. Burst REFRESH Limitation

To limit current consumption, a maximum of eight REFab commands can be issued in any rolling t_{REFBW} ($t_{REFBW} = 4 \times 8 \times t_{RFCab}$). This condition does not apply if REFpb commands are used.

3. REFRESH Requirements and Self Refresh

If any time within a refresh window is spent in self refresh mode, the number of required REFRESH commands in that window is reduced to the following:

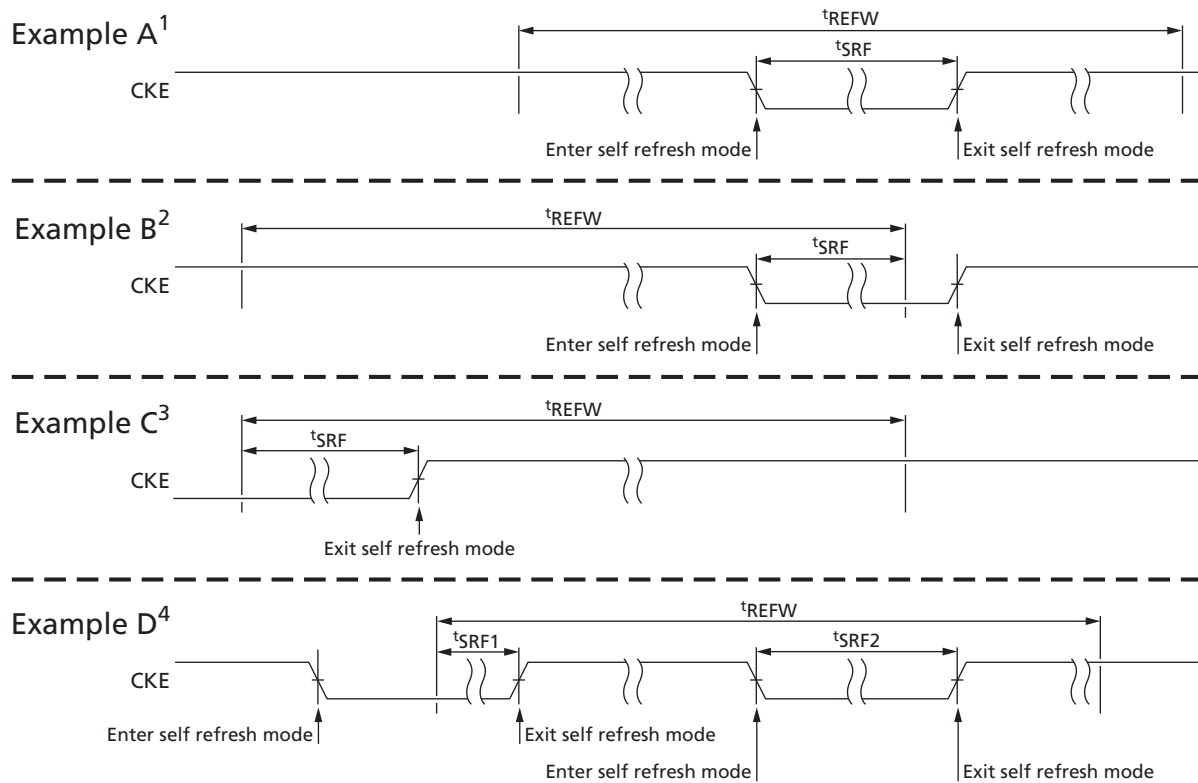
$$R' = RU \left(\frac{t_{SRF}}{t_{REFI}} \right) = R - RU \left(R \times \frac{t_{SRF}}{t_{REFW}} \right)$$

Where RU represents the round-up function.



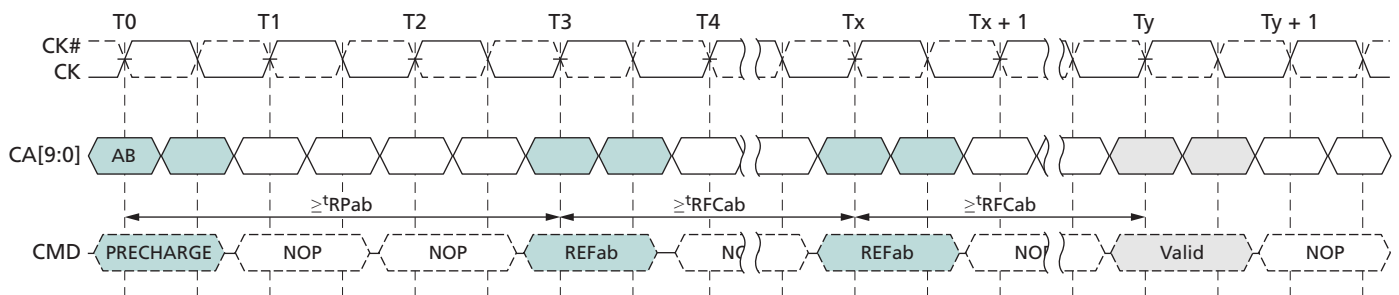
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP REFRESH Command

Figure 112: t_{SRF} Definition



- Notes:
1. Time in self refresh mode is fully enclosed in the refresh window (t_{REFW}).
 2. At self refresh entry.
 3. At self refresh exit.
 4. Several intervals in self refresh during one t_{REFW} interval. In this example, $t_{SRF} = t_{SRF1} + t_{SRF2}$.

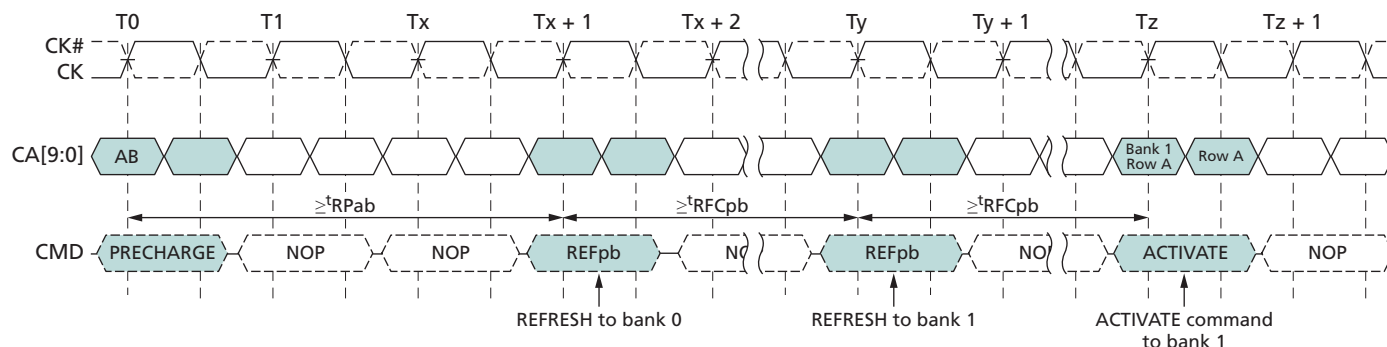
Figure 113: All-Bank REFRESH Operation





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP SELF REFRESH Operation

Figure 114: Per-Bank REFRESH Operation



- Notes:
1. Prior to T0, the REFpb bank counter points to bank 0.
 2. Operations to banks other than the bank being refreshed are supported during the t_{RFCpb} period.

SELF REFRESH Operation

The SELF REFRESH command can be used to retain data in the array, even if the rest of the system is powered down. When in the self refresh mode, the device retains data without external clocking. The device has a built-in timer to accommodate SELF REFRESH operation. The SELF REFRESH command is executed by taking CKE LOW, CS# LOW, CA0 LOW, CA1 LOW, and CA2 HIGH at the rising edge of the clock.

CKE must be HIGH during the clock cycle preceding a SELF REFRESH command. A NOP command must be driven in the clock cycle following the SELF REFRESH command. After the power-down command is registered, CKE must be held LOW to keep the device in self refresh mode.

Mobile LPDDR2 devices can operate in self refresh mode in both the standard and extended temperature ranges. These devices also manage self refresh power consumption when the operating temperature changes, resulting in the lowest possible power consumption across the operating temperature range. See I_{DD6} Partial-Array Self Refresh Current Table for details.

After the device has entered self refresh mode, all external signals other than CKE are “Don’t Care.” For proper self refresh operation, power supply pins (V_{DD1} , V_{DD2} , V_{DDQ} , and V_{DDCA}) must be at valid levels. V_{DDQ} can be turned off during self refresh. If V_{DDQ} is turned off, V_{REFDQ} must also be turned off. Prior to exiting self refresh, both V_{DDQ} and V_{REFDQ} must be within their respective minimum/maximum operating ranges (see the Single-Ended AC and DC Input Levels for DQ and DM table). V_{REFDQ} can be at any level between 0 and V_{DDQ} ; V_{REFCA} can be at any level between 0 and V_{DDCA} during self refresh.

Before exiting self refresh, V_{REFDQ} and V_{REFCA} must be within specified limits (see AC and DC Logic Input Measurement Levels for Single-Ended Signals (page 195)). After entering self refresh mode, the device initiates at least one all-bank REFRESH command internally during t_{CKESR} . The clock is internally disabled during SELF REFRESH operation to save power. The device must remain in self refresh mode for at least t_{CKESR} . The user can change the external clock frequency or halt the external clock one clock after



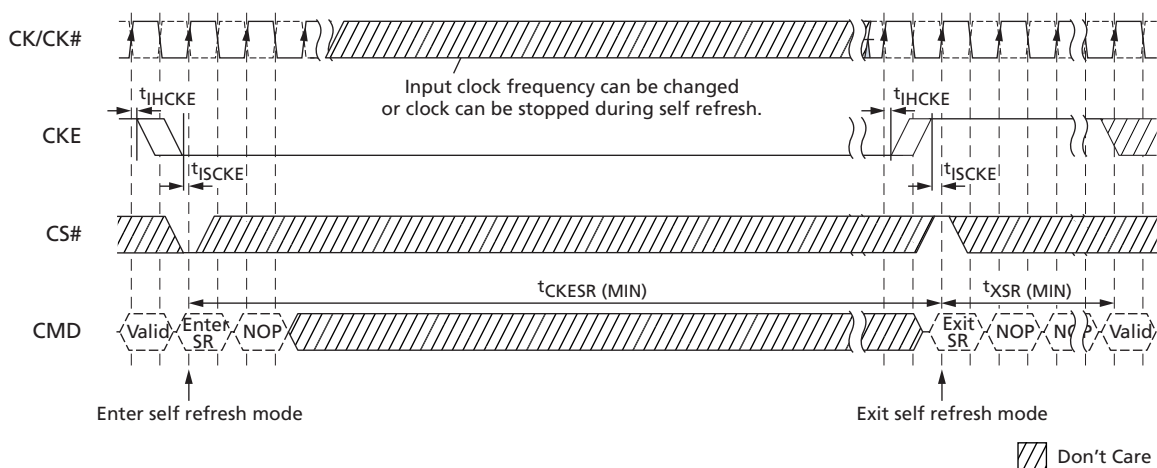
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP SELF REFRESH Operation

self refresh entry is registered; however, the clock must be restarted and stable before the device can exit SELF REFRESH operation.

Exiting self refresh requires a series of commands. First, the clock must be stable prior to CKE returning HIGH. After the self refresh exit is registered, a minimum delay, at least equal to the self refresh exit interval (t_{XSR}), must be satisfied before a valid command can be issued to the device. This provides completion time for any internal refresh in progress. For proper operation, CKE must remain HIGH throughout t_{XSR} . NOP commands must be registered on each rising clock edge during t_{XSR} .

Using self refresh mode introduces the possibility that an internally timed refresh event could be missed when CKE is driven HIGH for exit from self refresh mode. Upon exiting self refresh, at least one REFRESH command (one all-bank command or eight per-bank commands) must be issued before issuing a subsequent SELF REFRESH command.

Figure 115: SELF REFRESH Operation



- Notes:
1. Input clock frequency can be changed or stopped during self refresh, provided that upon exiting self-refresh, a minimum of two cycles of stable clocks are provided, and the clock frequency is between the minimum and maximum frequencies for the particular speed grade.
 2. The device must be in the all banks idle state prior to entering self refresh mode.
 3. t_{XSR} begins at the rising edge of the clock after CKE is driven HIGH.
 4. A valid command can be issued only after t_{XSR} is satisfied. NOPs must be issued during t_{XSR} .

Partial-Array Self Refresh – Bank Masking

Devices in densities of 64Mb–512Mb are comprised of four banks; densities of 1Gb and higher are comprised of eight banks. Each bank can be configured independently whether or not a SELF REFRESH operation will occur in that bank. One 8-bit mode register (accessible via the MRW command) is assigned to program the bank-masking status of each bank up to eight banks. For bank masking bit assignments, see the MR16 PASR Bank Mask (MA[7:0] = 010h) and MR16 Op-Code Bit Definitions tables.

The mask bit to the bank enables or disables a refresh operation of the entire memory space within the bank. If a bank is masked using the bank mask register, a REFRESH operation to the entire bank is blocked and bank data retention is not guaranteed in self



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP SELF REFRESH Operation

refresh mode. To enable a REFRESH operation to a bank, the corresponding bank mask bit must be programmed as “unmasked.” When a bank mask bit is unmasked, the array space being refreshed within that bank is determined by the programmed status of the segment mask bits.

Partial-Array Self Refresh – Segment Masking

Programming segment mask bits is similar to programming bank mask bits. For densities 1Gb and higher, eight segments are used for masking (see the MR17 PASR Segment Mask (MA[7:0] = 011h) and MR17 PASR Segment Mask Definitions tables). A mode register is used for programming segment mask bits up to eight bits. For densities less than 1Gb, segment masking is not supported.

When the mask bit to an address range (represented as a segment) is programmed as “masked,” a REFRESH operation to that segment is blocked. Conversely, when a segment mask bit to an address range is unmasked, refresh to that segment is enabled.

A segment masking scheme can be used in place of or in combination with a bank masking scheme. Each segment mask bit setting is applied across all banks. For segment masking bit assignments, see the tables noted above.

Table 83: Bank and Segment Masking Example

	Segment Mask (MR17)	Bank 0	Bank 1	Bank 2	Bank 3	Bank 4	Bank 5	Bank 6	Bank 7
Bank Mask (MR16)		0	1	0	0	0	0	0	1
Segment 0	0	–	M	–	–	–	–	–	M
Segment 1	0	–	M	–	–	–	–	–	M
Segment 2	1	M	M	M	M	M	M	M	M
Segment 3	0	–	M	–	–	–	–	–	M
Segment 4	0	–	M	–	–	–	–	–	M
Segment 5	0	–	M	–	–	–	–	–	M
Segment 6	0	–	M	–	–	–	–	–	M
Segment 7	1	M	M	M	M	M	M	M	M

Note: 1. This table provides values for an 8-bank device with REFRESH operations masked to banks 1 and 7, and segments 2 and 7.

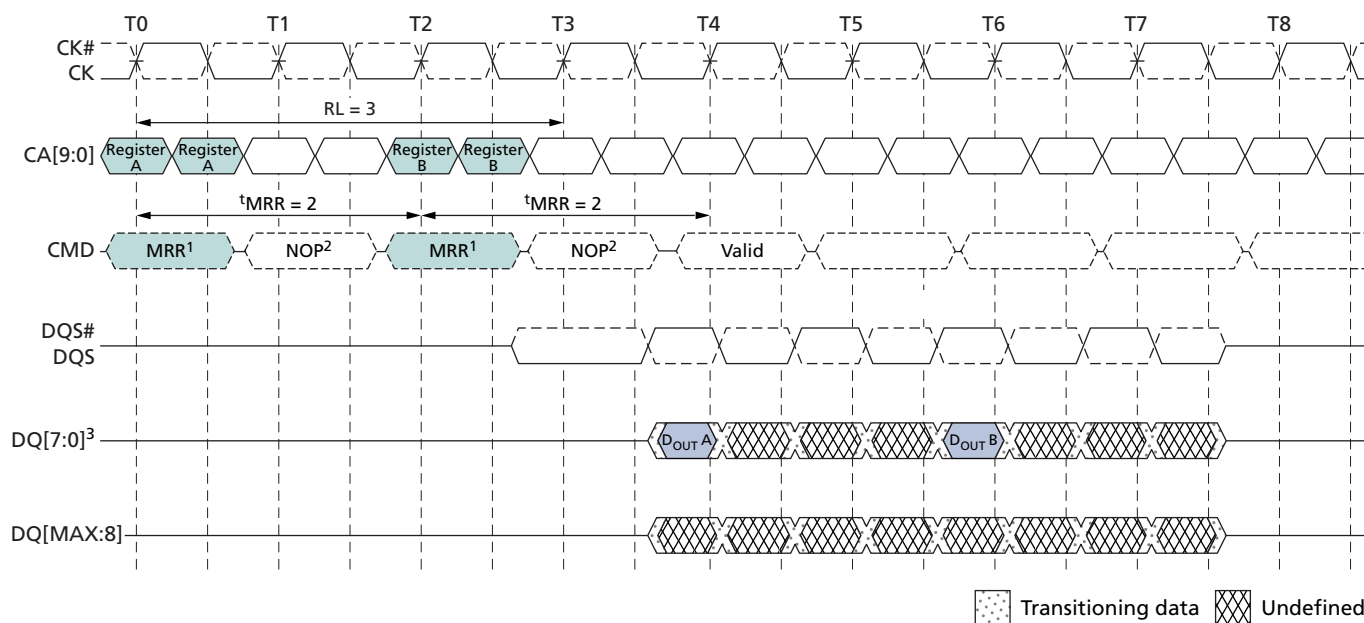


MODE REGISTER READ

The MODE REGISTER READ (MRR) command is used to read configuration and status data from SDRAM mode registers. The MRR command is initiated with CS# LOW, CA0 LOW, CA1 LOW, CA2 LOW, and CA3 HIGH at the rising edge of the clock. The mode register is selected by CA1f–CA0f and CA9r–CA4r. The mode register contents are available on the first data beat of DQ[7:0] after $RL \times {}^tCK + {}^tDQSCK + {}^tDQSQ$ and following the rising edge of the clock where MRR is issued. Subsequent data beats contain valid but undefined content, except in the case of the DQ calibration function, where subsequent data beats contain valid content as described in the Data Calibration Pattern Description table. All DQS are toggled for the duration of the mode register READ burst.

The MRR command has a burst length of four. MRR operation (consisting of the MRR command and the corresponding data traffic) must not be interrupted. The MRR command period (tMRR) is two clock cycles.

Figure 116: MRR Timing – $RL = 3$, ${}^tMRR = 2$



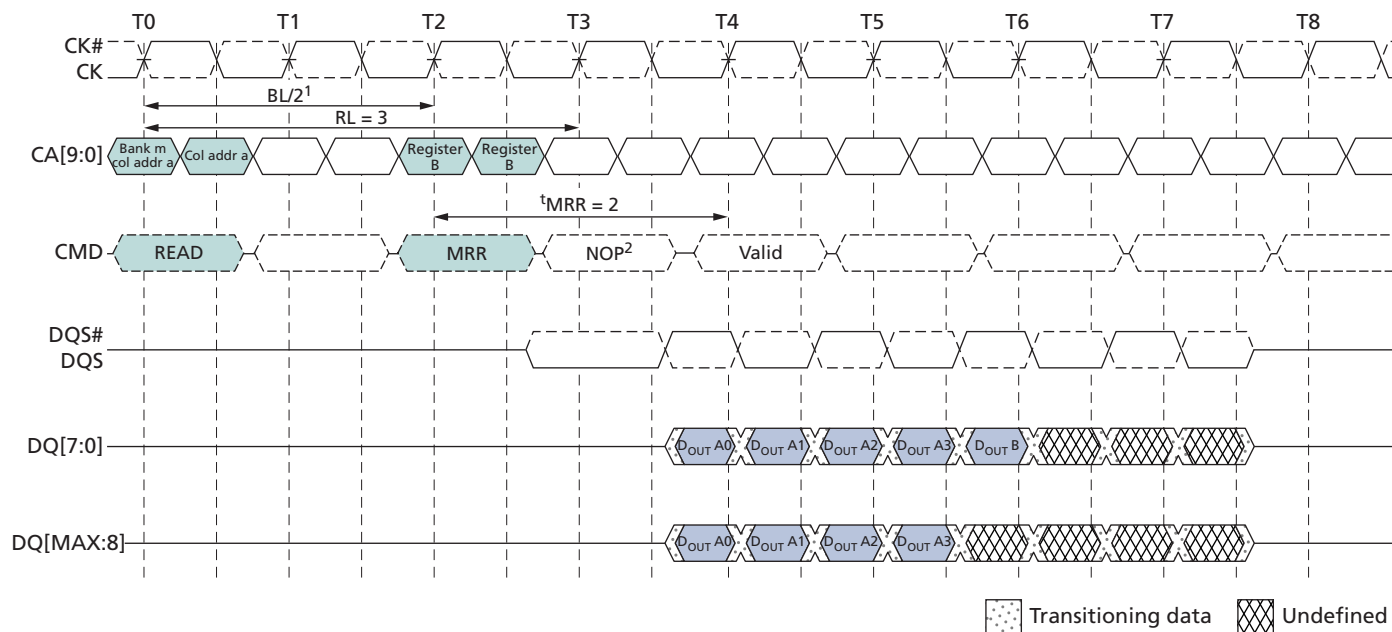
- Notes:
1. MRRs to DQ calibration registers MR32 and MR40 are described in Data Calibration.
 2. Only the NOP command is supported during tMRR .
 3. Mode register data is valid only on DQ[7:0] on the first beat. Subsequent beats contain valid but undefined data. DQ[MAX:8] contain valid but undefined data for the duration of the MRR burst.
 4. Minimum MRR to write latency is $RL + RU({}^tDQSCK_{max}/{}^tCK) + 4/2 + 1 - WL$ clock cycles.
 5. Minimum MRR to MRW latency is $RL + RU({}^tDQSCK_{max}/{}^tCK) + 4/2 + 1$ clock cycles.

READ bursts and WRITE bursts cannot be truncated by MRR. Following a READ command, the MRR command must not be issued before $BL/2$ clock cycles have completed. Following a WRITE command, the MRR command must not be issued before $WL + 1 + BL/2 + RU({}^tWTR/{}^tCK)$ clock cycles have completed. If a READ or WRITE burst is truncated with a BST command, the effective burst length of the truncated burst should be used for the BL value.

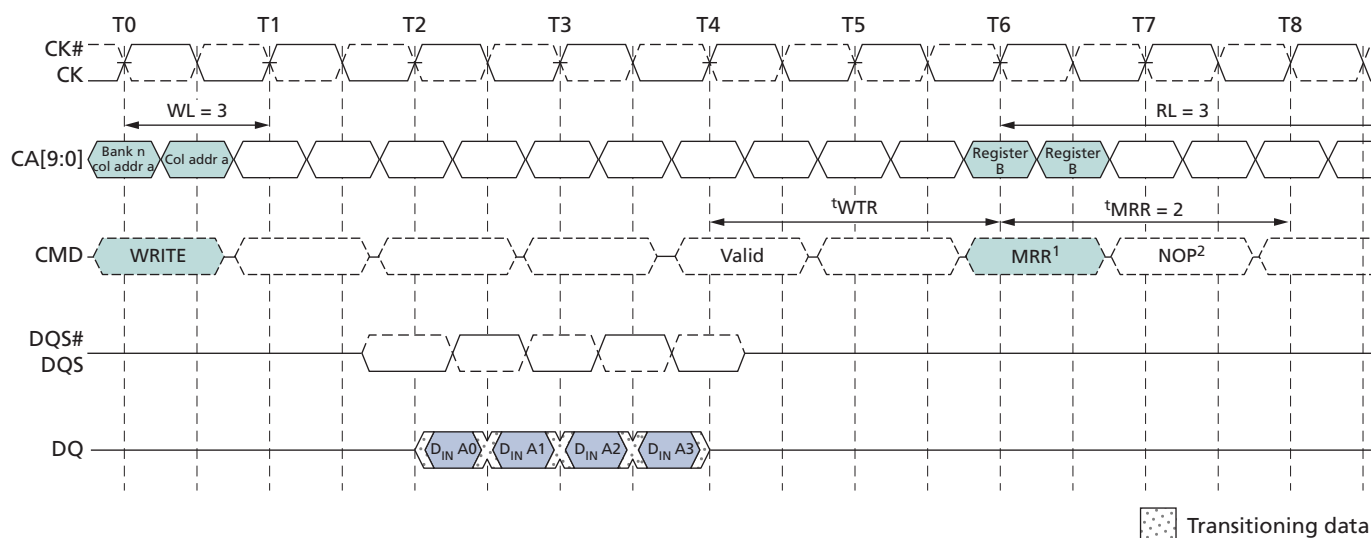


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP MODE REGISTER READ

Figure 117: READ to MRR Timing – RL = 3, $t_{MRR} = 2$



- Notes:
1. The minimum number of clock cycles from the burst READ command to the MRR command is $BL/2$.
 2. Only the NOP command is supported during t_{MRR} .


Figure 118: Burst WRITE Followed by MRR – RL = 3, WL = 1, BL = 4


- Notes:
1. The minimum number of clock cycles from the burst WRITE command to the MRR command is $[WL + 1 + BL/2 + RU(t_{WTR}/t_{CK})]$.
 2. Only the NOP command is supported during t_{MRR} .

Temperature Sensor

Mobile LPDDR2 devices feature a temperature sensor whose status can be read from MR4. This sensor can be used to determine an appropriate refresh rate, determine whether AC timing derating is required in the extended temperature range, and/or monitor the operating temperature. Either the temperature sensor or the device operating temperature can be used to determine whether operating temperature requirements are being met (see Operating Temperature Range table).

Temperature sensor data can be read from MR4 using the mode register read protocol. Upon exiting self-refresh or power-down, the device temperature status bits will be no older than t_{TSI} .

When using the temperature sensor, the actual device case temperature may be higher than the operating temperature specification that applies for the standard or extended temperature ranges (see table noted above). For example, T_{CASE} could be above 85°C when MR4[2:0] equals 011b.

To ensure proper operation using the temperature sensor, applications must accommodate the parameters in the temperature sensor definitions table.


Table 84: Temperature Sensor Definitions and Operating Conditions

Parameter	Description	Symbol	Min/Max	Value	Unit
System temperature gradient	Maximum temperature gradient experienced by the memory device at the temperature of interest over a range of 2°C	TempGradient	MAX	System-dependent	°C/s
MR4 READ interval	Time period between MR4 READs from the system	ReadInterval	MAX	System-dependent	ms
Temperature sensor interval	Maximum delay between internal updates of MR4	^t TSI	MAX	32	ms
System response delay	Maximum response time from an MR4 READ to the system response	SysRespDelay	MAX	System-dependent	ms
Device temperature margin	Margin above maximum temperature to support controller response	TempMargin	MAX	2	°C

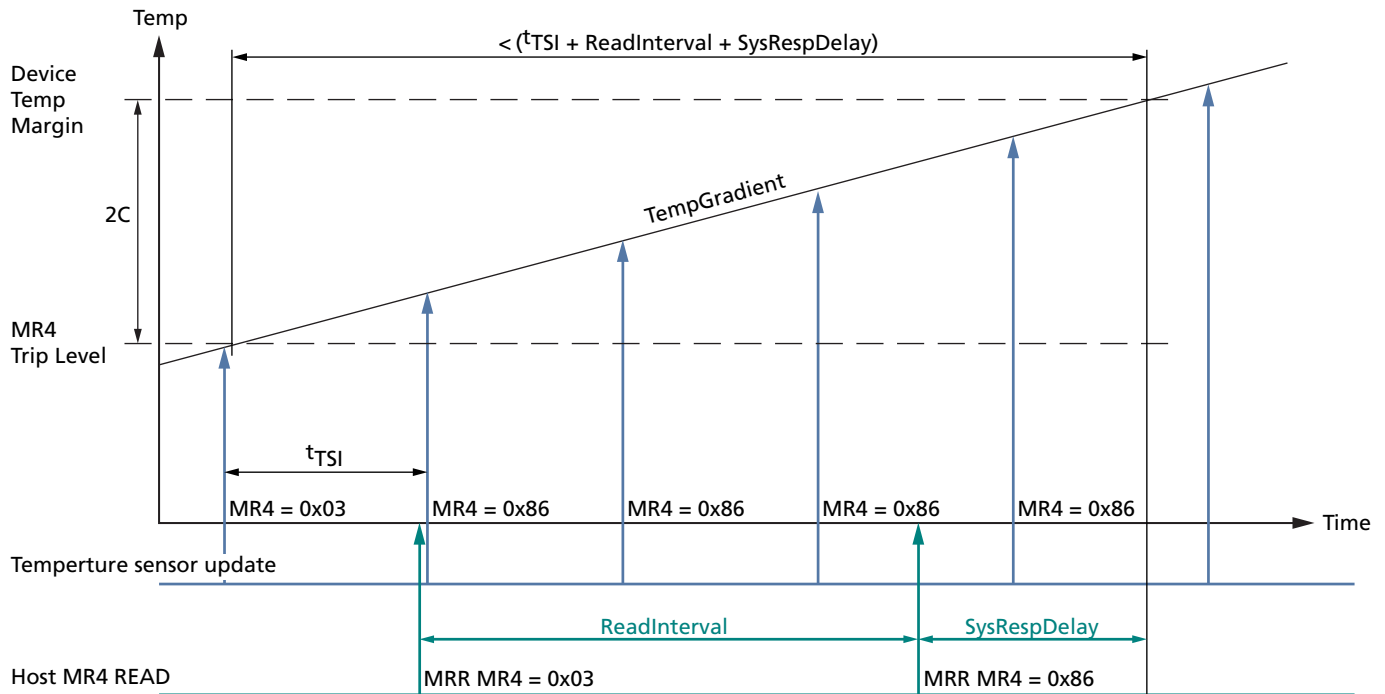
Mobile LPDDR2 devices accommodate the temperature margin between the point at which the device temperature enters the extended temperature range and the point at which the controller reconfigures the system accordingly. To determine the required MR4 polling frequency, the system must use the maximum TempGradient and the maximum response time of the system according to the following equation:

$$\text{TempGradient} \times (\text{ReadInterval} + {}^t\text{TSI} + \text{SysRespDelay}) \leq 2^\circ\text{C}$$

For example, if TempGradient is 10°C/s and the SysRespDelay is 1ms:

$$\frac{10^\circ\text{C}}{\text{s}} \times (\text{ReadInterval} + 32\text{ms} + 1\text{ms}) \leq 2^\circ\text{C}$$

In this case, ReadInterval must not exceed 167ms.


Figure 119: Temperature Sensor Timing


DQ Calibration

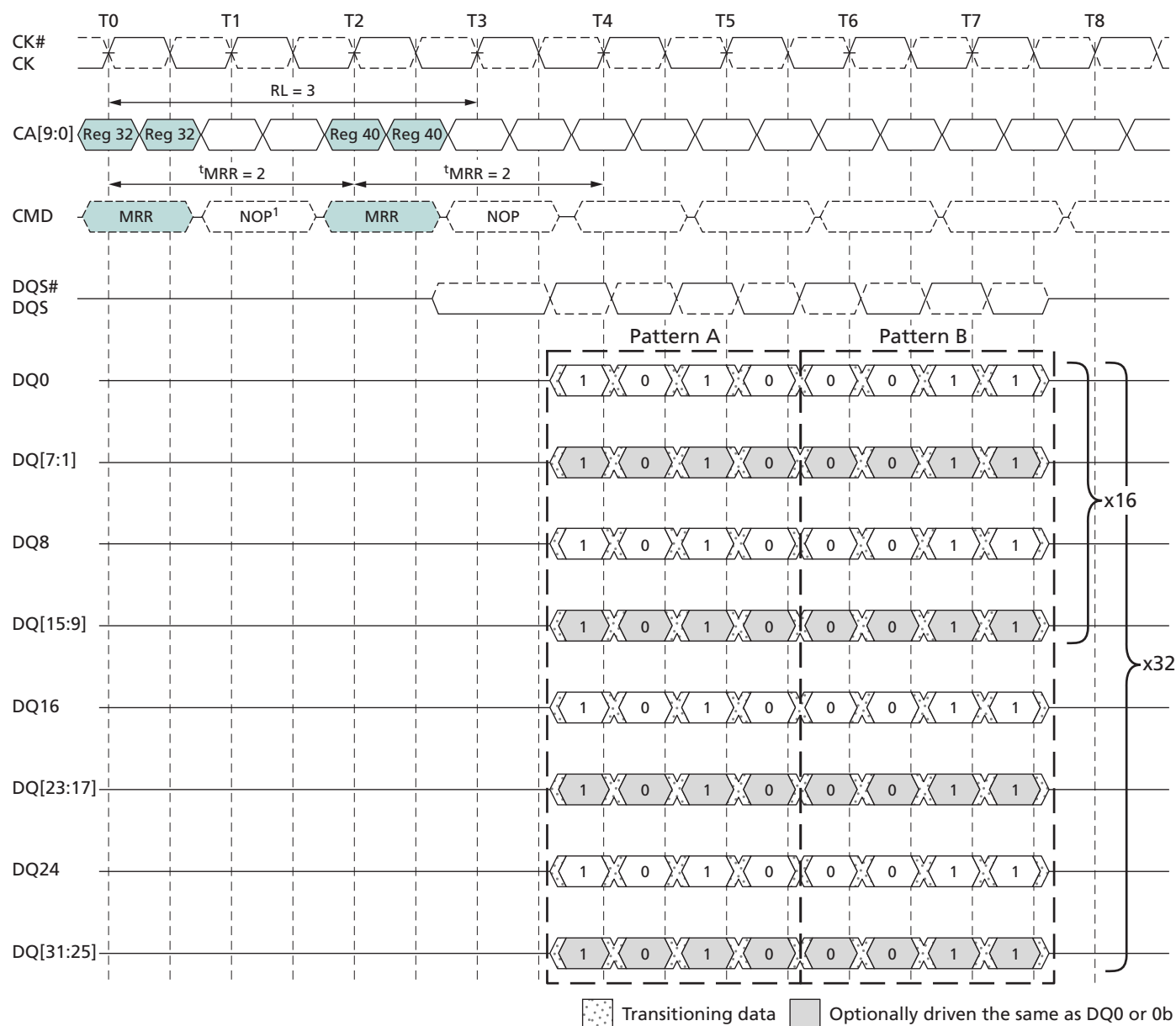
Mobile LPDDR2 devices feature a DQ calibration function that outputs one of two pre-defined system timing calibration patterns. For x16 devices, pattern A (MRR to MRR32) and pattern B (MRR to MRR40) will return the specified pattern on DQ0 and DQ8; x32 devices return the specified pattern on DQ0, DQ8, DQ16, and DQ24.

For x16 devices, DQ[7:1] and DQ[15:9] drive the same information as DQ0 during the MRR burst. For x32 devices, DQ[7:1], DQ[15:9], DQ[23:17] and DQ[31:25] drive the same information as DQ0 during the MRR burst. MRR DQ calibration commands can occur only in the idle state.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP MODE REGISTER READ

Figure 120: MR32 and MR40 DQ Calibration Timing – RL = 3, $t_{MRR} = 2$



Note: 1. Only the NOP command is supported during t_{MRR} .

Table 85: Data Calibration Pattern Description

Pattern	MR#	Bit Time 0	Bit Time 1	Bit Time 2	Bit Time 3	Description
Pattern A	MR32	1	0	1	0	Reads to MR32 return DQ calibration pattern A
Pattern B	MR40	0	0	1	1	Reads to MR40 return DQ calibration pattern B



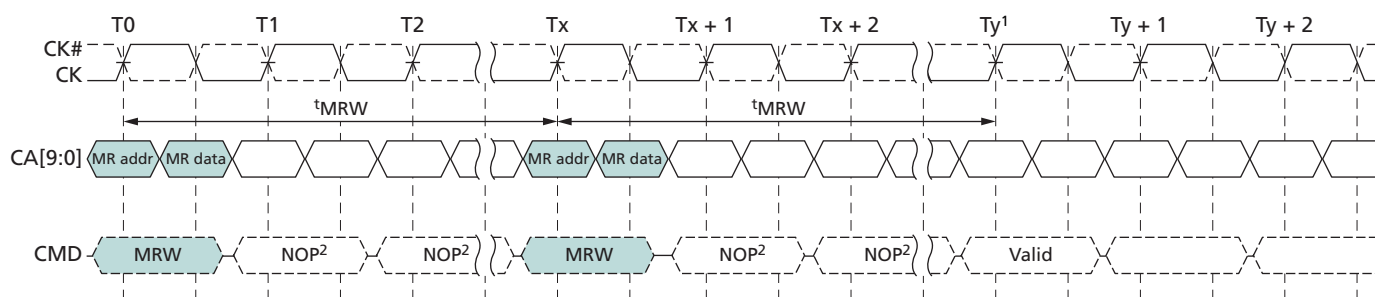
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP MODE REGISTER WRITE Command

MODE REGISTER WRITE Command

The MODE REGISTER WRITE (MRW) command is used to write configuration data to the mode registers. The MRW command is initiated with CS# LOW, CA0 LOW, CA1 LOW, CA2 LOW, and CA3 LOW at the rising edge of the clock. The mode register is selected by CA1f–CA0f, CA9r–CA4r. The data to be written to the mode register is contained in CA9f–CA2f. The MRW command period is defined by t_{MRW} . MRWs to read-only registers have no impact on the functionality of the device.

MRW can only be issued when all banks are in the idle precharge state. One method of ensuring that the banks are in this state is to issue a PRECHARGE ALL command.

Figure 121: MODE REGISTER WRITE Timing – RL = 3, $t_{MRW} = 5$



- Notes:
1. At time T_y , the device is in the idle state.
 2. Only the NOP command is supported during t_{MRW} .

Table 86: Truth Table for MRR and MRW

Current State	Command	Intermediate State	Next State
All banks idle	MRR	Reading mode register, all banks idle	All banks idle
	MRW	Writing mode register, all banks idle	All banks idle
	MRW (RESET)	Resetting, device auto initialization	All banks idle
Bank(s) active	MRR	Reading mode register, bank(s) idle	Bank(s) active
	MRW	Not allowed	Not allowed
	MRW (RESET)	Not allowed	Not allowed

MRW RESET Command

The MRW RESET command brings the device to the device auto initialization (resetting) state in the power-on initialization sequence (see 2. RESET Command under Power-Up (page 117)). The MRW RESET command can be issued from the idle state. This command resets all mode registers to their default values. Only the NOP command is supported during t_{INIT4} . After MRW RESET, boot timings must be observed until the device initialization sequence is complete and the device is in the idle state. Array data is undefined after the MRW RESET command has completed.

For MRW RESET timing, see Figure 81 (page 119).



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP MODE REGISTER WRITE Command

MRW ZQ Calibration Commands

The MRW command is used to initiate a ZQ calibration command that calibrates output driver impedance across process, temperature, and voltage. LPDDR2-S4 devices support ZQ calibration. To achieve tighter tolerances, proper ZQ calibration must be performed.

There are four ZQ calibration commands and related timings: 'ZQINIT, 'ZQRESET, 'ZQCL, and 'ZQCS. 'ZQINIT is used for initialization calibration; 'ZQRESET is used for resetting ZQ to the default output impedance; 'ZQCL is used for long calibration(s); and 'ZQCS is used for short calibration(s). See the MR10 Calibration (MA[7:0] = 0Ah) table for ZQ calibration command code definitions.

ZQINIT must be performed for LPDDR2 devices. ZQINIT provides an output impedance accuracy of $\pm 15\%$. After initialization, the ZQ calibration long (ZQCL) can be used to recalibrate the system to an output impedance accuracy of $\pm 15\%$. A ZQ calibration short (ZQCS) can be used periodically to compensate for temperature and voltage drift in the system.

ZQRESET resets the output impedance calibration to a default accuracy of $\pm 30\%$ across process, voltage, and temperature. This command is used to ensure output impedance accuracy to $\pm 30\%$ when ZQCS and ZQCL commands are not used.

One ZQCS command can effectively correct at least 1.5% (ZQ correction) of output impedance errors within 'ZQCS for all speed bins, assuming the maximum sensitivities specified in Table 117 and Table 118 are met. The appropriate interval between ZQCS commands can be determined using these tables and system-specific parameters.

Mobile LPDDR2 devices are subject to temperature drift rate ($T_{\text{driftrate}}$) and voltage drift rate ($V_{\text{driftrate}}$) in various applications. To accommodate drift rates and calculate the necessary interval between ZQCS commands, apply the following formula:

$$\frac{ZQ_{\text{correction}}}{(T_{\text{sens}} \times T_{\text{driftrate}}) + (V_{\text{sens}} \times V_{\text{driftrate}})}$$

Where $T_{\text{sens}} = \text{MAX}(dR_{\text{ONdT}})$ and $V_{\text{sens}} = \text{MAX}(dR_{\text{ONdV}})$ define temperature and voltage sensitivities.

For example, if $T_{\text{sens}} = 0.75\%/^{\circ}\text{C}$, $V_{\text{sens}} = 0.20\%/mV$, $T_{\text{driftrate}} = 1^{\circ}\text{C/sec}$, and $V_{\text{driftrate}} = 15\text{ mV/sec}$, then the interval between ZQCS commands is calculated as:

$$\frac{1.5}{(0.75 \times 1) + (0.20 \times 15)} = 0.4s$$

A ZQ calibration command can only be issued when the device is in the idle state with all banks precharged.

No other activities can be performed on the data bus during calibration periods ('ZQINIT, 'ZQCL, or 'ZQCS). The quiet time on the data bus helps to accurately calibrate output impedance. There is no required quiet time after the ZQRESET command. If multiple devices share a single ZQ resistor, only one device can be calibrating at any given time. After calibration is complete, the ZQ ball circuitry is disabled to reduce power consumption.

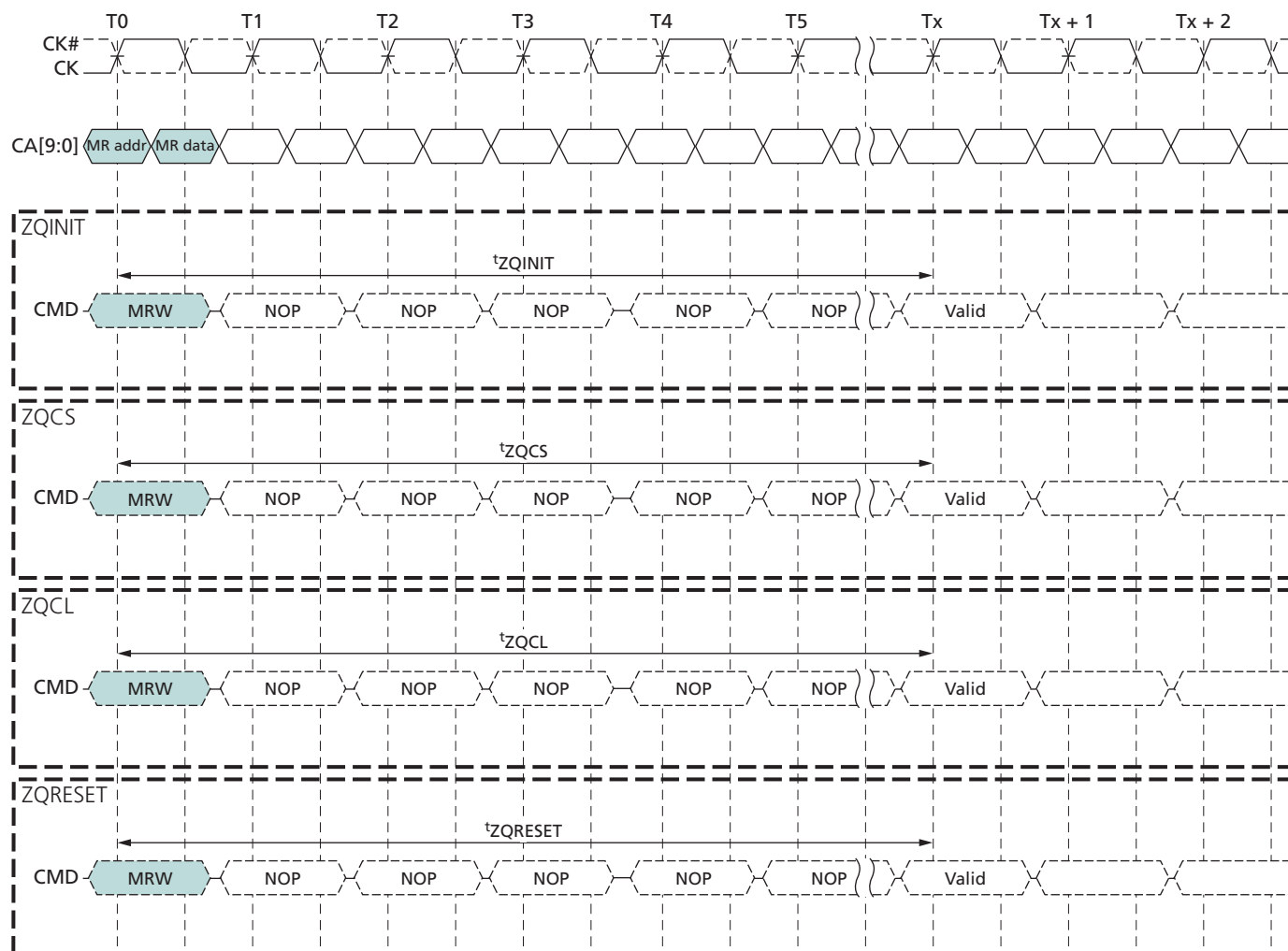
In systems sharing a ZQ resistor between devices, the controller must prevent 'ZQINIT, 'ZQCS, and 'ZQCL overlap between the devices. ZQRESET overlap is acceptable. If the



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP MODE REGISTER WRITE Command

ZQ resistor is absent from the system, ZQ must be connected to V_{DDCA} . In this situation, the device must ignore ZQ calibration commands and the device will use the default calibration settings.

Figure 122: ZQ Timings



- Notes:
1. Only the NOP command is supported during ZQ calibrations.
 2. CKE must be registered HIGH continuously during the calibration period.
 3. All devices connected to the DQ bus should be High-Z during the calibration process.



ZQ External Resistor Value, Tolerance, and Capacitive Loading

To use the ZQ calibration function, a 240 ohm ($\pm 1\%$ tolerance) external resistor must be connected between the ZQ pin and ground. A single resistor can be used for each device or one resistor can be shared between multiple devices if the ZQ calibration timings for each device do not overlap. The total capacitive loading on the ZQ pin must be limited (see the Input/Output Capacitance table).

Power-Down

Power-down is entered synchronously when CKE is registered LOW and CS# is HIGH at the rising edge of clock. A NOP command must be driven in the clock cycle following power-down entry. CKE must not go LOW while MRR, MRW, READ, or WRITE operations are in progress. CKE can go LOW while any other operations, such as ACTIVATE, PRECHARGE, auto precharge, or REFRESH are in progress, but the power-down I_{DD} specification will not be applied until such operations are complete.

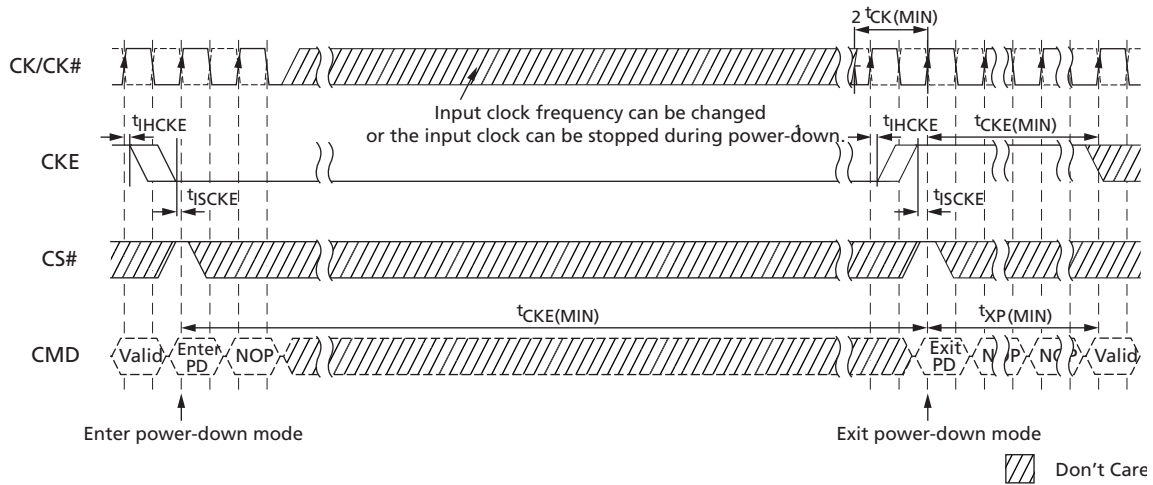
Idle power-down mode refers to a power-down occurring when all banks are idle; active power-down mode refers to a power-down occurring when there is a row active in any bank.

Entering power-down deactivates the input and output buffers, excluding CK, CK#, and CKE. In power-down mode, CKE must be held LOW; all other input signals are “Don’t Care.” CKE LOW must be maintained until t_{CKE} is satisfied. V_{REFCA} must be maintained at a valid level during power-down.

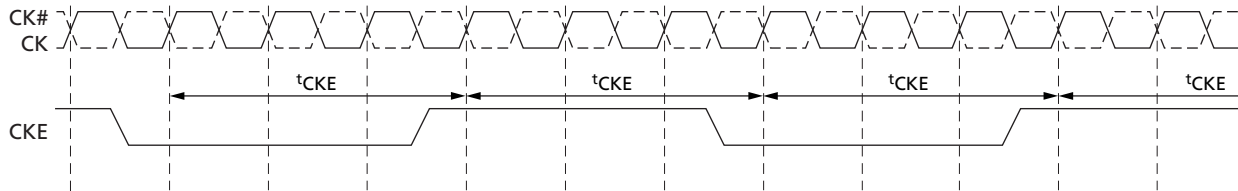
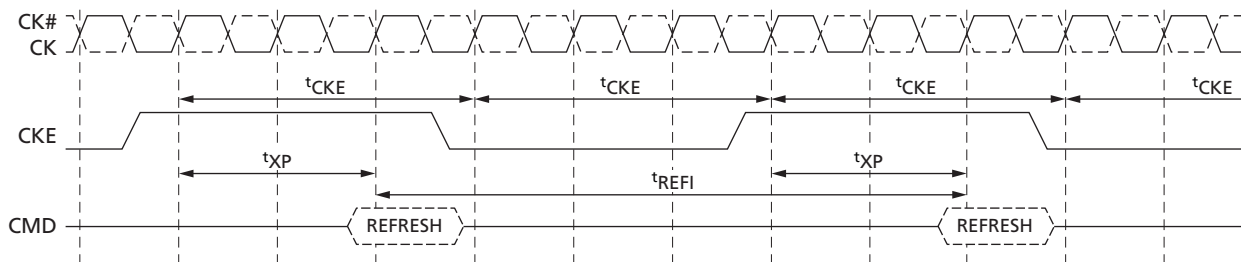
V_{DDQ} can be turned off during power-down. If V_{DDQ} is turned off, V_{REFDQ} must also be turned off. Prior to exiting power-down, both V_{DDQ} and V_{REFDQ} must be within their respective minimum/maximum operating ranges (see AC and DC Operating Conditions).

No refresh operations are performed in power-down mode. The maximum duration in power-down mode is only limited by the refresh requirements outlined in REFRESH Command.

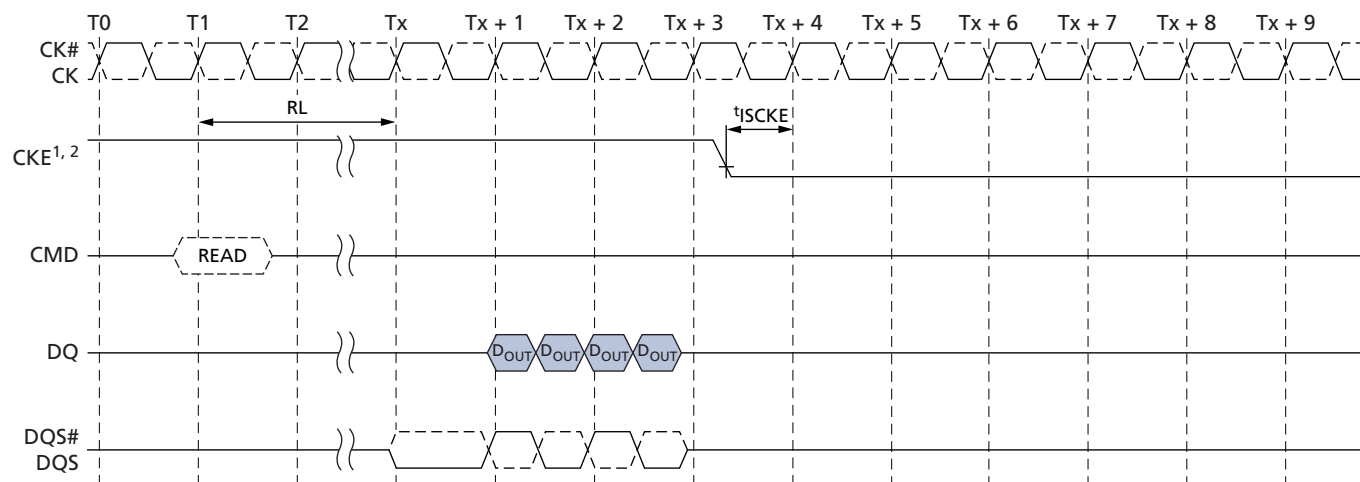
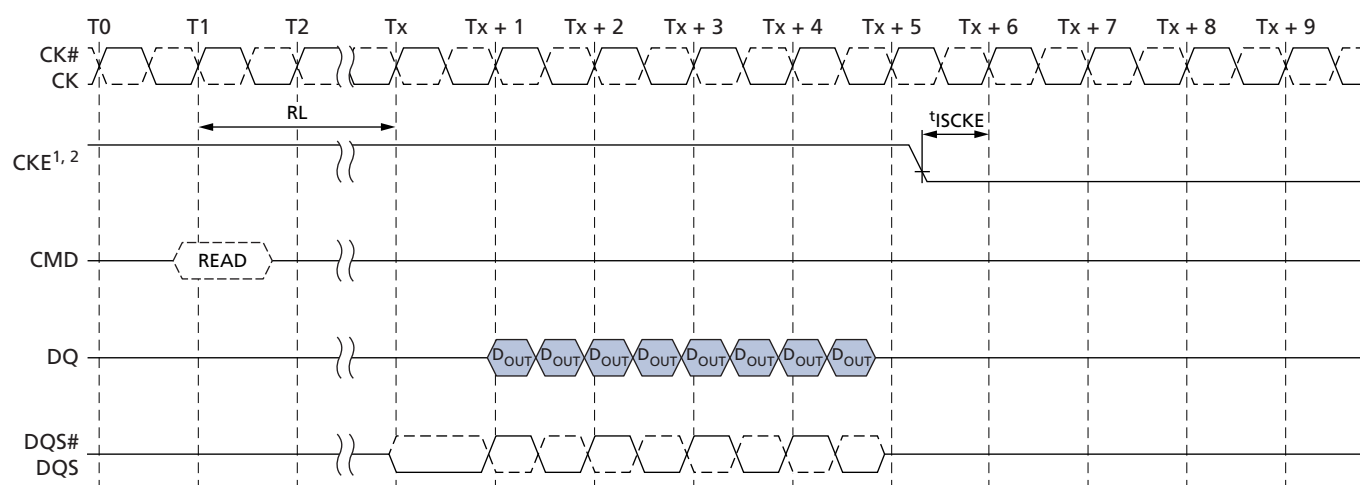
The power-down state is exited when CKE is registered HIGH. The controller must drive CS# HIGH in conjunction with CKE HIGH when exiting the power-down state. CKE HIGH must be maintained until t_{CKE} is satisfied. A valid, executable command can be applied with power-down exit latency t_{XP} after CKE goes HIGH. Power-down exit latency is defined in the AC Timing section.


Figure 123: Power-Down Entry and Exit Timing


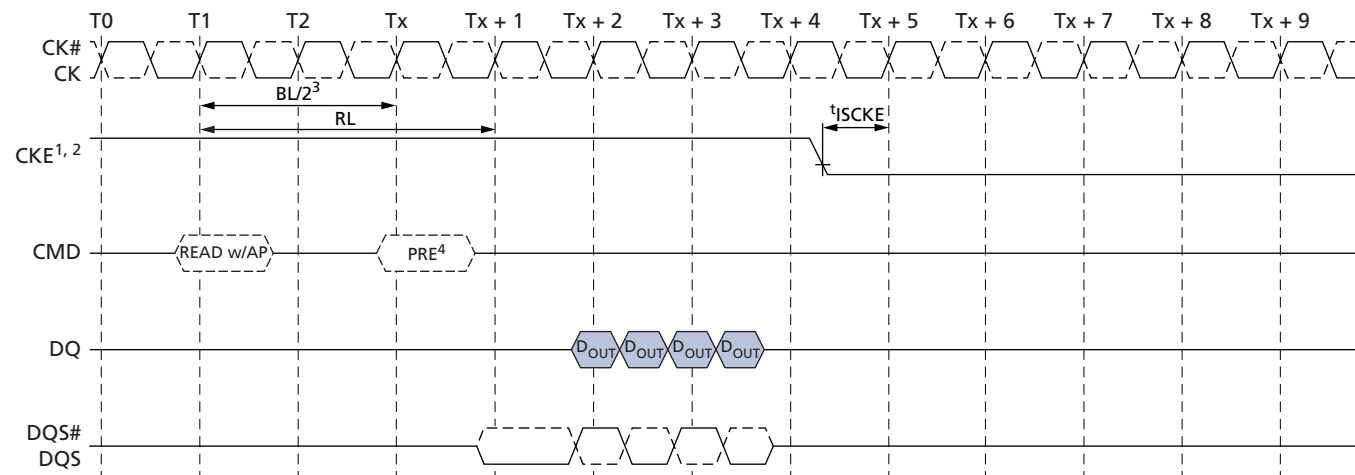
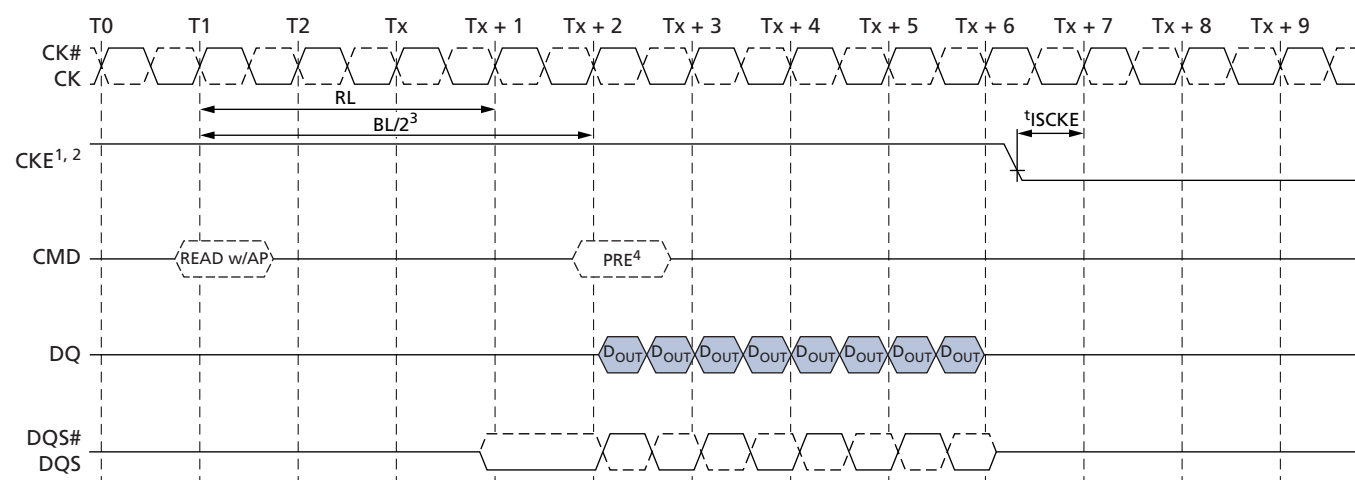
Note: 1. Input clock frequency can be changed or the input clock stopped during power-down, provided that the clock frequency is between the minimum and maximum specified frequencies for the speed grade in use, and that prior to power-down exit, a minimum of two stable clocks complete.

Figure 124: CKE Intensive Environment

Figure 125: REFRESH-to-REFRESH Timing in CKE Intensive Environments


Note: 1. The pattern shown can repeat over an extended period of time. With this pattern, all AC and DC timing and voltage specifications with temperature and voltage drift are ensured.


Figure 126: READ to Power-Down Entry
BL = 4

BL = 8


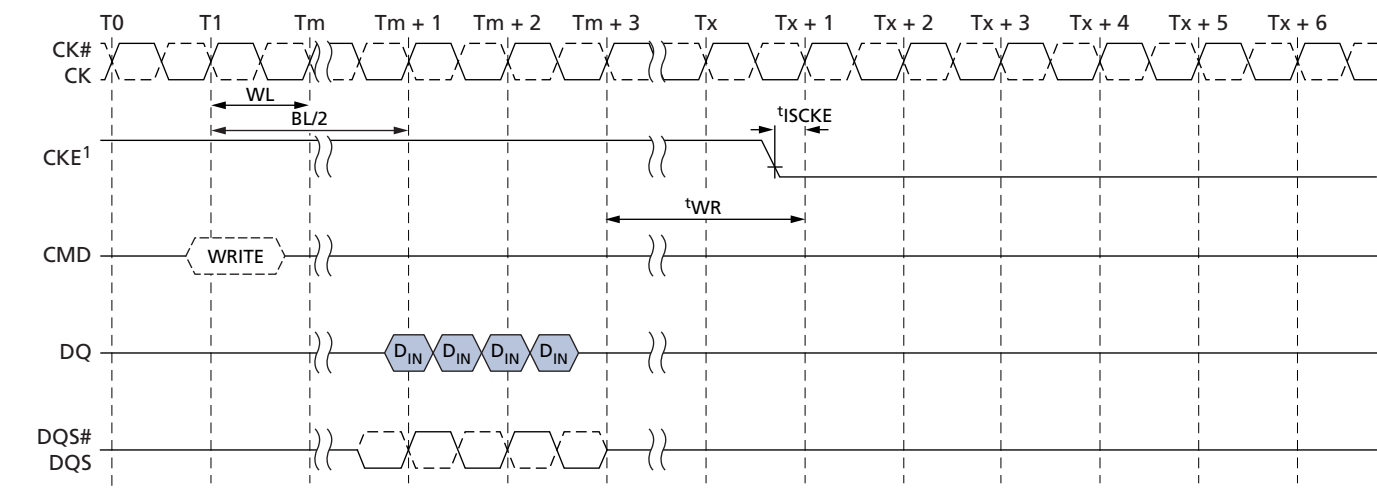
- Notes:
1. CKE must be held HIGH until the end of the burst operation.
 2. CKE can be registered LOW at $(RL + RU(t_{DQSCK}(MAX)/t_{CK}) + BL/2 + 1)$ clock cycles after the clock on which the READ command is registered.


Figure 127: READ with Auto Precharge to Power-Down Entry
BL = 4

BL = 8


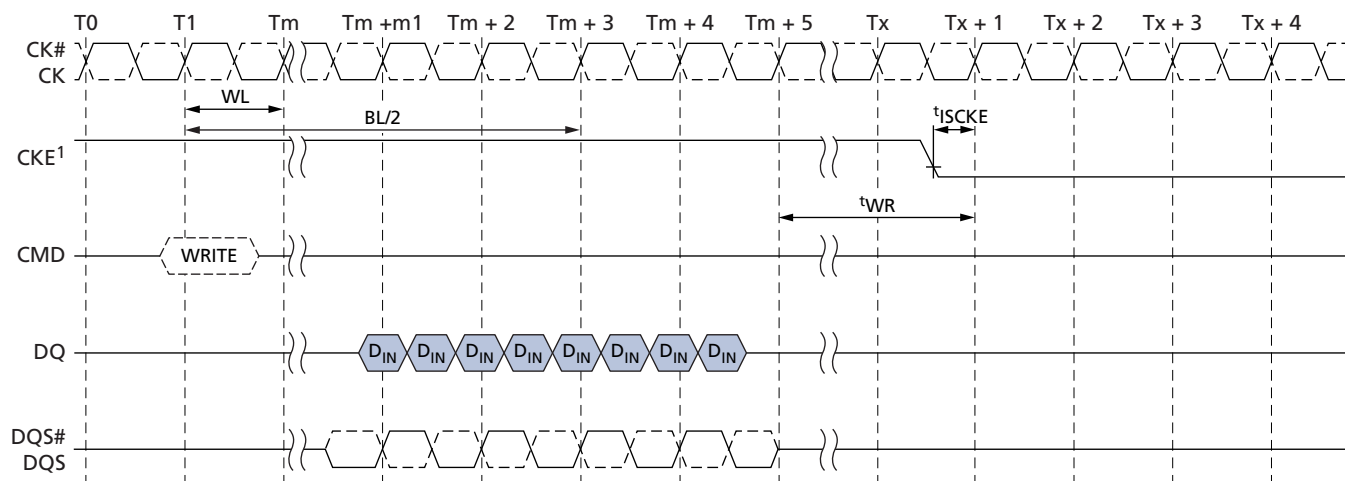
- Notes:
1. CKE must be held HIGH until the end of the burst operation.
 2. CKE can be registered LOW at $(RL + RU(t_{DQSCK}/t_{CK}) + BL/2 + 1)$ clock cycles after the clock on which the READ command is registered.
 3. $BL/2$ with $t_{RTP} = 7.5\text{ns}$ and $t_{RAS}(\text{MIN})$ is satisfied.
 4. Start internal PRECHARGE.


Figure 128: WRITE to Power-Down Entry

BL = 4



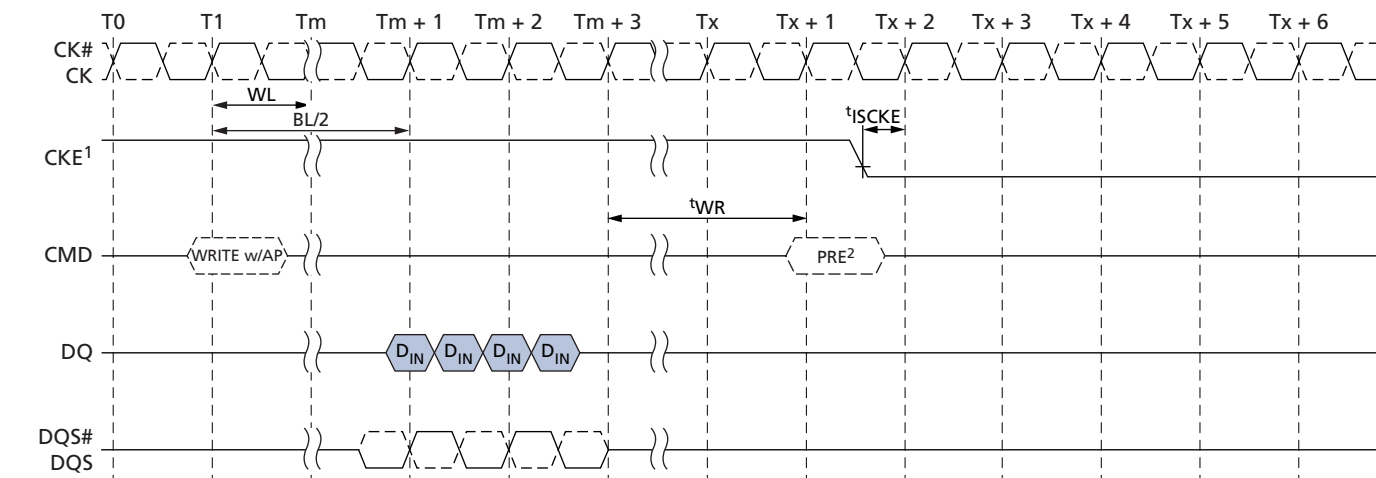
BL = 8



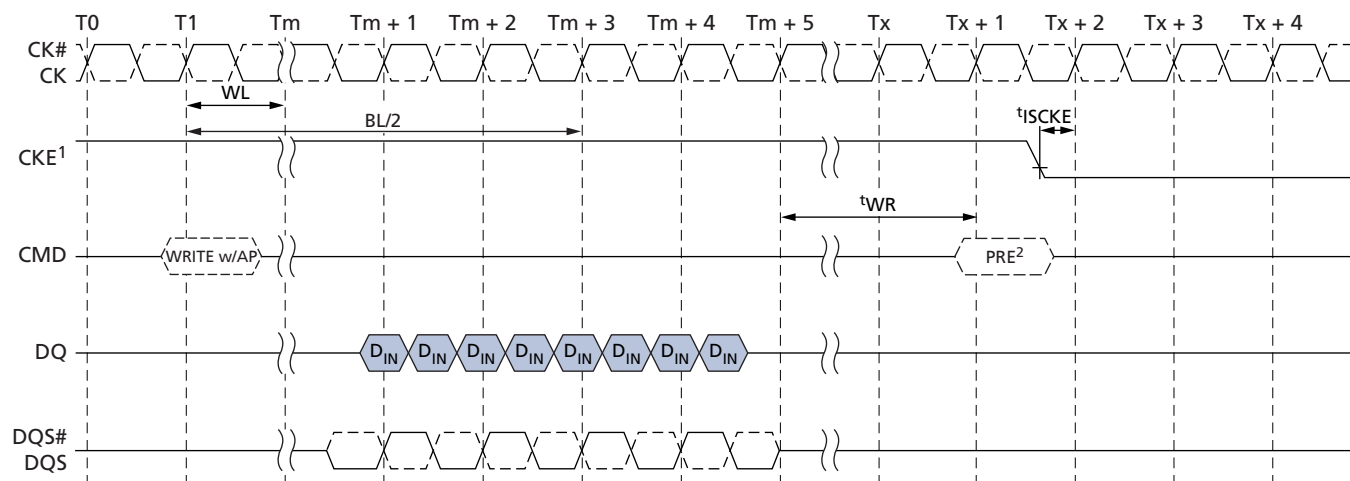
Note: 1. CKE can be registered LOW at $(WL + 1 + BL/2 + RU(t_{WR}/t_{CK}))$ clock cycles after the clock on which the WRITE command is registered.


Figure 129: WRITE with Auto Precharge to Power-Down Entry

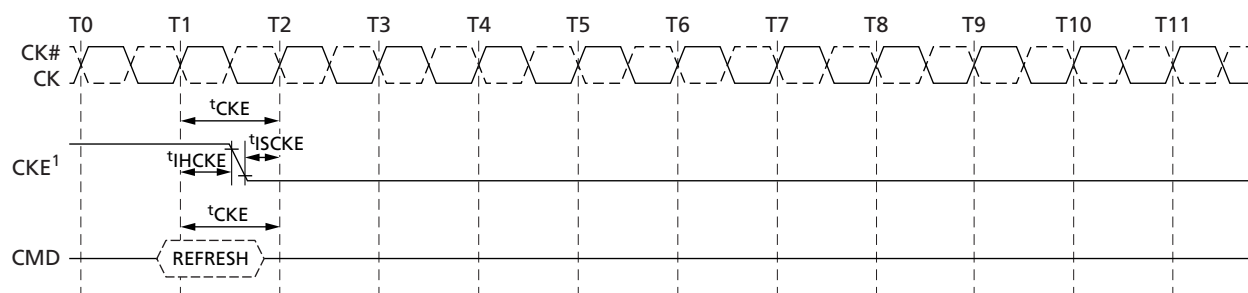
BL = 4



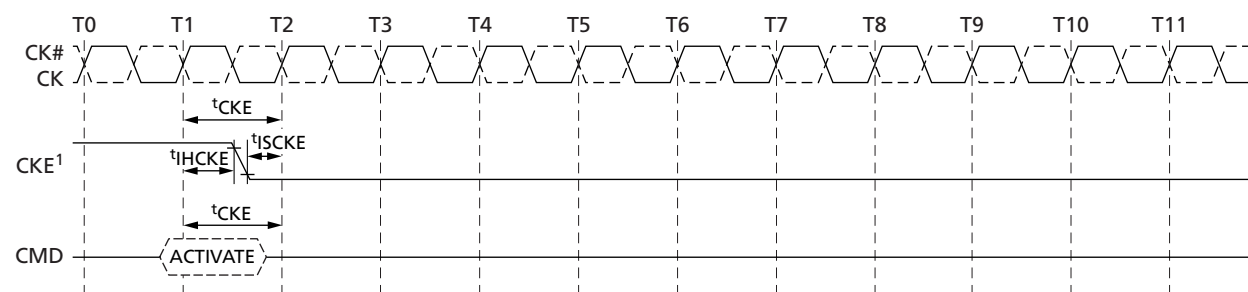
BL = 8



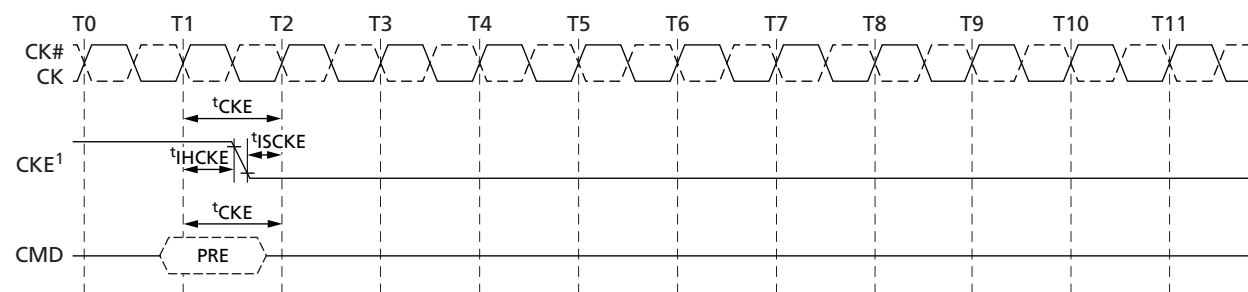
- Notes:
1. CKE can be registered LOW at $(WL + 1 + BL/2 + RU(t_{WR}/t_{CK} + 1))$ clock cycles after the WRITE command is registered.
 2. Start internal PRECHARGE.


Figure 130: REFRESH Command to Power-Down Entry


Note: 1. CKE can go LOW t_{IHCKE} after the clock on which the REFRESH command is registered.

Figure 131: ACTIVATE Command to Power-Down Entry


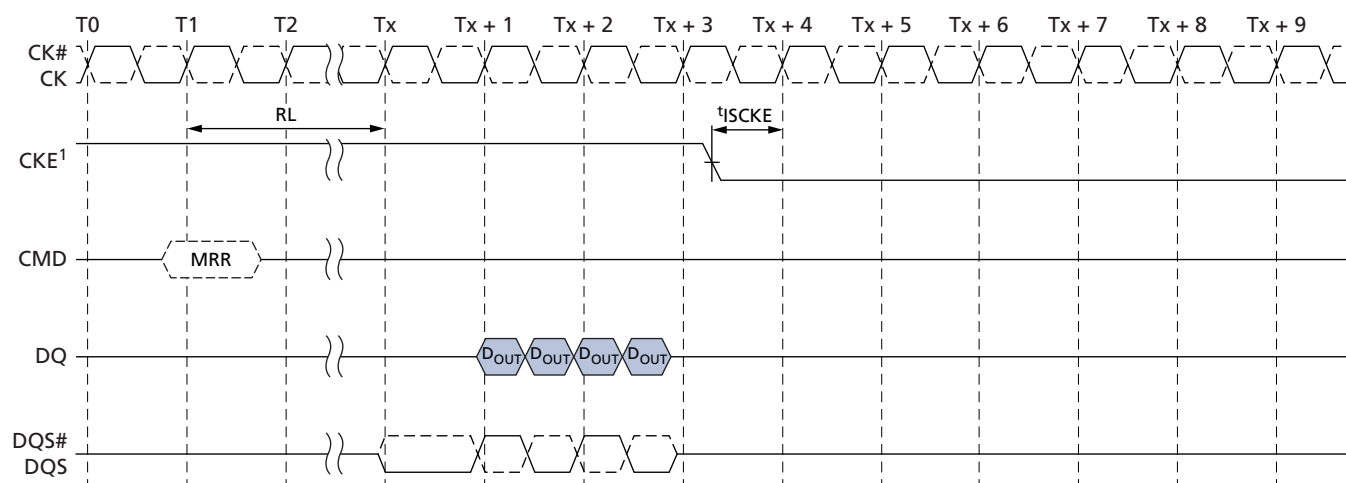
Note: 1. CKE can go LOW at t_{IHCKE} after the clock on which the ACTIVATE command is registered.

Figure 132: PRECHARGE Command to Power-Down Entry


Note: 1. CKE can go LOW t_{IHCKE} after the clock on which the PRECHARGE command is registered.

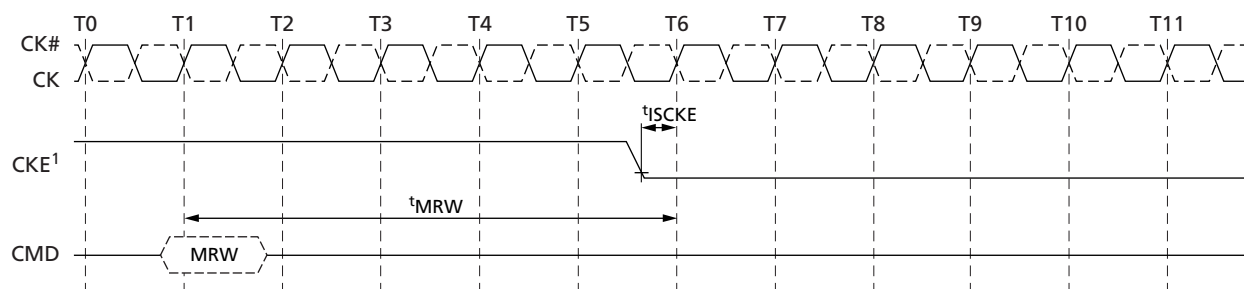
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Deep Power-Down

Figure 133: MRR Command to Power-Down Entry



Note: 1. CKE can be registered LOW at (RL + RU(^tDQCK/^tCK) + BL/2 + 1) clock cycles after the clock on which the MRR command is registered.

Figure 134: MRW Command to Power-Down Entry



Note: 1. CKE can be registered LOW ^tMRW after the clock on which the MRW command is registered.

Deep Power-Down

Deep power-down (DPD) is entered when CKE is registered LOW with CS# LOW, CA0 HIGH, CA1 HIGH, and CA2 LOW at the rising edge of the clock. The NOP command must be driven in the clock cycle following power-down entry. CKE must not go LOW while MRR or MRW operations are in progress. CKE can go LOW while other operations such as ACTIVATE, auto precharge, PRECHARGE, or REFRESH are in progress; however, deep power-down I_{DD} specifications will not be applied until those operations complete. The contents of the array will be lost upon entering DPD mode.

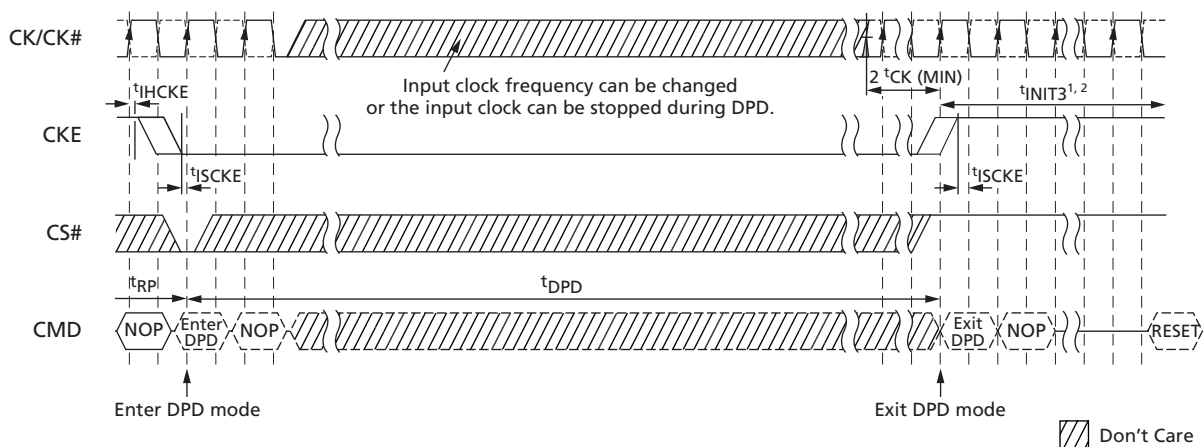
In DPD mode, all input buffers except CKE, all output buffers, and the power supply to internal circuitry are disabled within the device. V_{REFDQ} can be at any level between 0 and V_{DDQ} , and V_{REFCA} can be at any level between 0 and V_{DDCA} during DPD. All power supplies (including V_{REF}) must be within the specified limits prior to exiting DPD (see AC and DC Operating Conditions).



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Input Clock Frequency Changes and Stop Events

To exit DPD, CKE must be HIGH, t_{ISCKE} must be complete, and the clock must be stable. To resume operation, the device must be fully reinitialized using the power-up initialization sequence.

Figure 135: Deep Power-Down Entry and Exit Timing



- Notes:
1. The initialization sequence can start at any time after $T_x + 1$.
 2. t_{INIT3} and $T_x + 1$ refer to timings in the initialization sequence. For details, see Mode Register Definition.

Input Clock Frequency Changes and Stop Events

Input Clock Frequency Changes and Clock Stop with CKE LOW

During CKE LOW, Mobile LPDDR2 devices support input clock frequency changes and clock stop under the following conditions:

- Refresh requirements are met
- Only REFab or REFpb commands can be in process
- Any ACTIVATE or PRECHARGE commands have completed prior to changing the frequency
- Related timing conditions, t_{RCD} and t_{RP} , have been met prior to changing the frequency
- The initial clock frequency must be maintained for a minimum of two clock cycles after CKE goes LOW
- The clock satisfies $t_{\text{CH}}(\text{abs})$ and $t_{\text{CL}}(\text{abs})$ for a minimum of two clock cycles prior to CKE going HIGH

For input clock frequency changes, $t_{\text{CK}}(\text{MIN})$ and $t_{\text{CK}}(\text{MAX})$ must be met for each clock cycle.

After the input clock frequency is changed and CKE is held HIGH, additional MRW commands may be required to set the WR, RL, etc. These settings may require adjustment to meet minimum timing requirements at the target clock frequency.

For clock stop, CK is held LOW and CK# is held HIGH.



Input Clock Frequency Changes and Clock Stop with CKE HIGH

During CKE HIGH, LPDDR2 devices support input clock frequency changes and clock stop under the following conditions:

- REFRESH requirements are met
- Any ACTIVATE, READ, WRITE, PRECHARGE, MRW, or MRR commands must have completed, including any associated data bursts, prior to changing the frequency
- Related timing conditions, t_{RCD} , t_{WR} , t_{WRA} , t_{RP} , t_{MRW} , and t_{MRR} , etc., are met
- CS# must be held HIGH
- Only REFab or REFpb commands can be in process

The device is ready for normal operation after the clock satisfies $t_{CH(abs)}$ and $t_{CL(abs)}$ for a minimum of $2 \times t_{CK} + t_{XP}$.

For input clock frequency changes, $t_{CK(MIN)}$ and $t_{CK(MAX)}$ must be met for each clock cycle.

After the input clock frequency is changed, additional MRW commands may be required to set the WR, RL, etc. These settings may require adjustment to meet minimum timing requirements at the target clock frequency.

For clock stop, CK is held LOW and CK# is held HIGH.

NO OPERATION Command

The NO OPERATION (NOP) command prevents the device from registering any unwanted commands issued between operations. A NOP command can only be issued at clock cycle N when the CKE level is constant for clock cycle N-1 and clock cycle N. The NOP command has two possible encodings: CS# HIGH at the clock rising edge N, and CS# LOW with CA0, CA1, CA2 HIGH at the clock rising edge N.

The NOP command will not terminate a previous operation that is still in process, such as a READ burst or WRITE burst cycle.

Simplified Bus Interface State Diagram

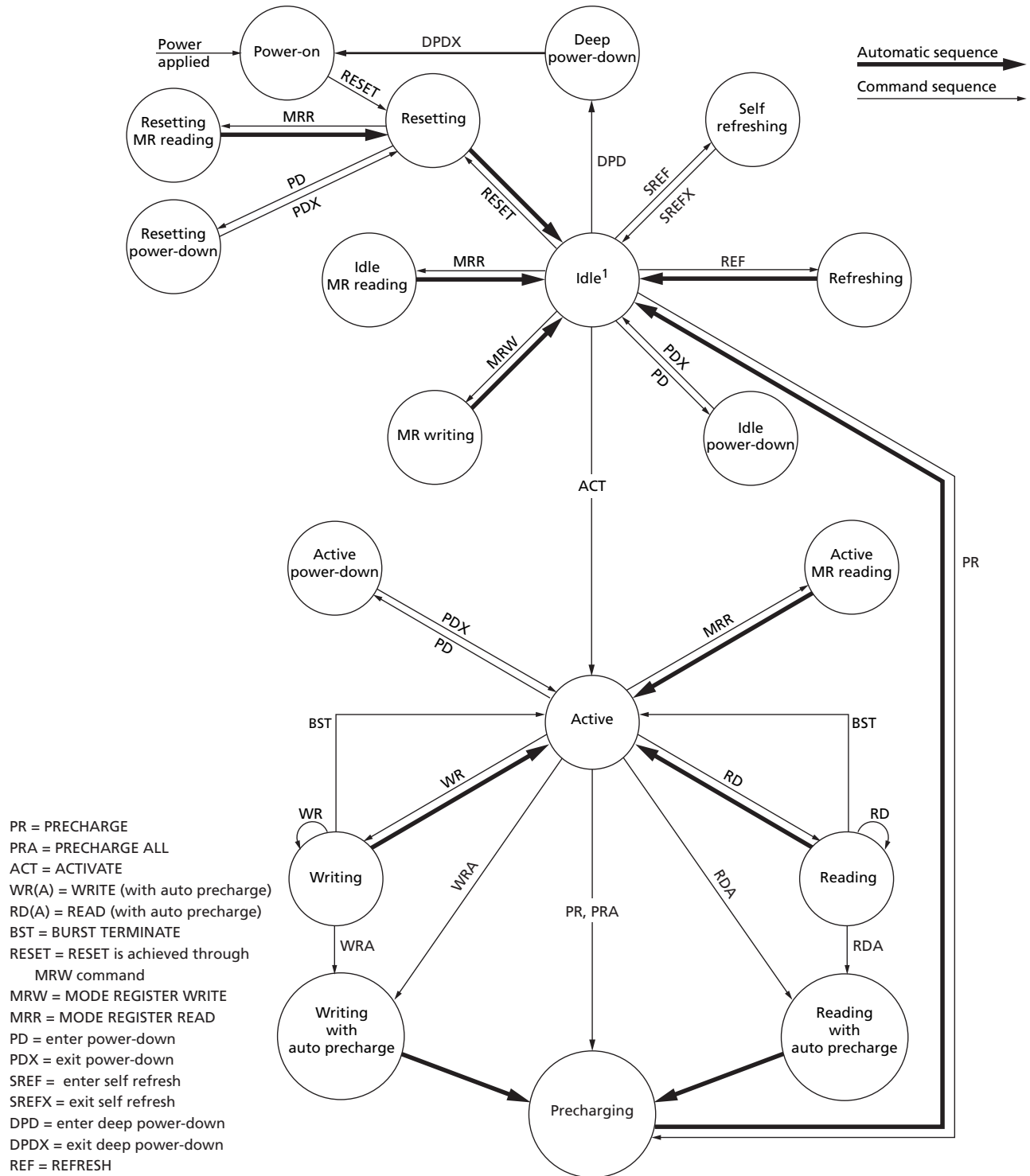
The state diagram (see Figure 136 (page 181)) provides a simplified illustration of the bus interface, supported state transitions, and the commands that control them. For a complete description of device behavior, use the information provided in the state diagram with the truth tables and timing specifications.

The truth tables describe device behavior and applicable restrictions when considering the actual state of all banks.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP NO OPERATION Command

Figure 136: Simplified Bus Interface State Diagram



Note: 1. All banks are precharged in the idle state.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Truth Tables

Truth Tables

Truth tables provide complementary information to the state diagram. They also clarify device behavior and applicable restrictions when considering the actual state of the banks.

Unspecified operations and timings are illegal. To ensure proper operation after an illegal event, the device must be powered down and then restarted using the specified initialization sequence before normal operation can continue.

Table 87: Command Truth Table

Notes 1–11 apply to all parameters conditions









Command	Command Pins			CA Pins										CK Edge
	CKE		CS#	CA0	CA1	CA2	CA3	CA4	CA5	CA6	CA7	CA8	CA9	
	CK(n-1)	CK(n)												
MRW	H	H	L	L	L	L	L	MA0	MA1	MA2	MA3	MA4	MA5	
	H	H	X	MA6	MA7	OP0	OP1	OP2	OP3	OP4	OP5	OP6	OP7	
MRR	H	H	L	L	L	L	H	MA0	MA1	MA2	MA3	MA4	MA5	
	H	H	X	MA6	MA7	X								
REFRESH (per bank)	H	H	L	L	L	H	L	X						
	H	H	X	X										
REFRESH (all banks)	H	H	L	L	L	H	H	X						
	H	H	X	X										
Enter self refresh	H	L	L	L	L	H	X							
	X	L	X	X										
ACTIVATE (bank)	H	H	L	L	H	R8	R9	R10	R11	R12	BA0	BA1	BA2	
	H	H	X	R0	R1	R2	R3	R4	R5	R6	R7	R13	R14	
WRITE (bank)	H	H	L	H	L	L	RFU	RFU	C1	C2	BA0	BA1	BA2	
	H	H	X	AP	C3	C4	C5	C6	C7	C8	C9	C10	C11	
READ (bank)	H	H	L	H	L	H	RFU	RFU	C1	C2	BA0	BA1	BA2	
	H	H	X	AP	C3	C4	C5	C6	C7	C8	C9	C10	C11	
PRECHARGE (bank)	H	H	L	H	H	L	H	AB	X	X	BA0	BA1	BA2	
	H	H	X	X										
BST	H	H	L	H	H	L	L	X						
	H	H	X	X										
Enter DPD	H	L	L	H	H	L	X							
	X	L	X	X										
NOP	H	H	L	H	H	H	X							
	H	H	X	X										
Maintain PD, SREF, DPD, (NOP)	L	L	L	H	H	H	X							
	L	L	X	X										



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Truth Tables

Table 87: Command Truth Table (Continued)

Notes 1–11 apply to all parameters conditions

Command	Command Pins			CA Pins										CK Edge
	CKE		CS#	CA0	CA1	CA2	CA3	CA4	CA5	CA6	CA7	CA8	CA9	
	CK(n-1)	CK(n)												
NOP	H	H	H	X										
	H	H	X	X										
Maintain PD, SREF, DPD, (NOP)	L	L	H	X										
	L	L	X	X										
Enter power-down	H	L	H	X										
	X	L	X	X										
Exit PD, SREF, DPD	L	H	H	X										
	X	H	X	X										

- Notes:
1. All commands are defined by the current state of CS#, CA0, CA1, CA2, CA3, and CKE at the rising edge of the clock.
 2. Bank addresses (BA) determine which bank will be operated upon.
 3. AP HIGH during a READ or WRITE command indicates that an auto precharge will occur to the bank associated with the READ or WRITE command.
 4. X indicates a "Don't Care" state, with a defined logic level, either HIGH (H) or LOW (L).
 5. Self refresh exit and DPD exit are asynchronous.
 6. V_{REF} must be between 0 and V_{DDQ} during self refresh and DPD operation.
 7. CA_{xr} refers to command/address bit "x" on the rising edge of clock.
 8. CA_{xf} refers to command/address bit "x" on the falling edge of clock.
 9. CS# and CKE are sampled on the rising edge of the clock.
 10. Per-bank refresh is only supported in devices with eight banks.
 11. The least-significant column address C0 is not transmitted on the CA bus, and is inferred to be zero.

Table 88: CKE Truth Table

Notes 1–5 apply to all parameters and conditions; L = LOW, H = HIGH, X = "Don't Care"

Current State	CKEn-1	CKEn	CS#	Command <i>n</i>	Operation <i>n</i>	Next State	Notes
Active power-down	L	L	X	X	Maintain active power-down	Active power-down	
	L	H	H	NOP	Exit active power-down	Active	6, 7
Idle power-down	L	L	X	X	Maintain idle power-down	Idle power-down	
	L	H	H	NOP	Exit idle power-down	Idle	6, 7
Resetting idle power-down	L	L	X	X	Maintain resetting power-down	Resetting power-down	
	L	H	H	NOP	Exit resetting power-down	Idle or resetting	6, 7, 8



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Truth Tables

Table 88: CKE Truth Table (Continued)

Notes 1–5 apply to all parameters and conditions; L = LOW, H = HIGH, X = “Don’t Care”

Current State	CKEn-1	CKEn	CS#	Command <i>n</i>	Operation <i>n</i>	Next State	Notes
Deep power-down	L	L	X	X	Maintain deep power-down	Deep power-down	
	L	H	H	NOP	Exit deep power-down	Power-on	9
Self refresh	L	L	X	X	Maintain self refresh	Self refresh	
	L	H	H	NOP	Exit self refresh	Idle	10, 11
Bank(s) active	H	L	H	NOP	Enter active power-down	Active power-down	
All banks idle	H	L	H	NOP	Enter idle power-down	Idle power-down	
	H	L	L	Enter self refresh	Enter self refresh	Self refresh	
	H	L	L	DPD	Enter deep power-down	Deep power-down	
Resetting	H	L	H	NOP	Enter resetting power-down	Resetting power-down	
Other states	H	H	Refer to the command truth table				

- Notes:
1. Current state = the state of the device immediately prior to the clock rising edge *n*.
 2. All states and sequences not shown are illegal or reserved unless explicitly described elsewhere in this document.
 3. CKEn = the logic state of CKE at clock rising edge *n*; CKEn-1 was the state of CKE at the previous clock edge.
 4. CS# = the logic state of CS# at the clock rising edge *n*.
 5. Command *n* = the command registered at clock edge *n*, and operation *n* is a result of command *n*.
 6. Power-down exit time (t_{XP}) must elapse before any command other than NOP is issued.
 7. The clock must toggle at least twice prior to the t_{XP} period.
 8. Upon exiting the resetting power-down state, the device will return to the idle state if t_{INIT5} has expired.
 9. The DPD exit procedure must be followed as described in Deep Power Down.
 10. Self refresh exit time (t_{XSR}) must elapse before any command other than NOP is issued.
 11. The clock must toggle at least twice prior to the t_{XSR} time.

Table 89: Current State Bank *n* to Command to Bank *n* Truth Table

Notes 1–5 apply to all parameters and conditions

Current State	Command	Operation	Next State	Notes
Any	NOP	Continue previous operation	Current state	



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Truth Tables

Table 89: Current State Bank *n* to Command to Bank *n* Truth Table (Continued)

Notes 1–5 apply to all parameters and conditions

Current State	Command	Operation	Next State	Notes
Idle	ACTIVATE	Select and activate row	Active	6
	Refresh (per bank)	Begin to refresh	Refreshing (per bank)	7
	Refresh (all banks)	Begin to refresh	Refreshing (all banks)	8
	MRW	Load value to mode register	MR writing	8
	MRR	Read value from mode register	Idle, MR reading	
	RESET	Begin device auto initialization	Resetting	8, 9
	PRECHARGE	Deactivate row(s) in bank or banks	Precharging	10, 11
Row active	READ	Select column and start read burst	Reading	
	WRITE	Select column and start write burst	Writing	
	MRR	Read value from mode register	Active MR reading	
	PRECHARGE	Deactivate row(s) in bank or banks	Precharging	10
Reading	READ	Select column and start new read burst	Reading	12, 13
	WRITE	Select column and start write burst	Writing	12, 13, 14
	BST	Read burst terminate	Active	15
Writing	WRITE	Select column and start new write burst	Writing	12, 13
	READ	Select column and start read burst	Reading	12, 13, 16
	BST	Write burst terminate	Active	15
Power-on	MRW RESET	Begin device auto initialization	Resetting	8, 10
Resetting	MRR	Read value from mode register	Resetting MR reading	

- Notes:
1. Values in this table apply when both $CKEn-1$ and $CKEn$ are HIGH, and after t_{XSR} or t_{XP} has been met, if the previous state was power-down.
 2. All states and sequences not shown are illegal or reserved.
 3. Current state definitions:

Idle: The bank or banks have been precharged, and t_{RP} has been met.

Active: A row in the bank has been activated, and t_{RCD} has been met. No data bursts or accesses and no register accesses are in progress.

Reading: A READ burst has been initiated with auto precharge disabled and has not yet terminated or been terminated.

Writing: A WRITE burst has been initiated with auto precharge disabled and has not yet terminated or been terminated.

4. The states listed below must not be interrupted by a command issued to the same bank. NOP commands or supported commands to the other bank must be issued on any clock edge occurring during these states. Supported commands to the other banks are determined by that bank's current state, and the definitions given in the following table.

Precharge: Starts with registration of a PRECHARGE command and ends when t_{RP} is met. After t_{RP} is met, the bank is in the idle state.

Row activate: Starts with registration of an ACTIVATE command and ends when t_{RCD} is met. After t_{RCD} is met, the bank is in the active state.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Truth Tables

READ with AP enabled: Starts with registration of a READ command with auto pre-charge enabled and ends when t_{RP} is met. After t_{RP} is met, the bank is in the idle state.

WRITE with AP enabled: Starts with registration of a WRITE command with auto pre-charge enabled and ends when t_{RP} is met. After t_{RP} is met, the bank is in the idle state.

5. The states listed below must not be interrupted by any executable command. NOP commands must be applied to each rising clock edge during these states.

Refresh (per bank): Starts with registration of a REFRESH (per bank) command and ends when t_{RFCpb} is met. After t_{RFCpb} is met, the bank is in the idle state.

Refresh (all banks): Starts with registration of a REFRESH (all banks) command and ends when t_{RFCab} is met. After t_{RFCab} is met, the device is in the all banks idle state.

Idle MR reading: Starts with registration of the MRR command and ends when t_{MRR} is met. After t_{MRR} is met, the device is in the all banks idle state.

Resetting MR reading: Starts with registration of the MRR command and ends when t_{MRR} is met. After t_{MRR} is met, the device is in the all banks idle state.

Active MR reading: Starts with registration of the MRR command and ends when t_{MRR} is met. After t_{MRR} is met, the bank is in the active state.

MR writing: Starts with registration of the MRW command and ends when t_{MRW} is met. After t_{MRW} is met, the device is in the all banks idle state.

Precharging all: Starts with registration of a PRECHARGE ALL command and ends when t_{RP} is met. After t_{RP} is met, the device is in the all banks idle state.

6. There are no restrictions to the number of ACTIVATE commands to a given row in a refresh period provided DRAM timing specifications are not violated. However, specific attempts to bypass Rowhammer circuits may result in data disturb.
7. Bank-specific; requires that the bank is idle and no bursts are in progress.
8. Not bank-specific; requires that all banks are idle and no bursts are in progress.
9. Not bank-specific.
10. This command may or may not be bank specific. If all banks are being precharged, they must be in a valid state for precharging.
11. If a PRECHARGE command is issued to a bank in the idle state, t_{RP} still applies.
12. A command other than NOP should not be issued to the same bank while a burst READ or burst WRITE with auto precharge is enabled.
13. The new READ or WRITE command could be auto precharge enabled or auto precharge disabled.
14. A WRITE command can be issued after the completion of the READ burst; otherwise, a BST must be issued to end the READ prior to asserting a WRITE command.
15. Not bank-specific. The BST command affects the most recent READ/WRITE burst started by the most recent READ/WRITE command, regardless of bank.
16. A READ command can be issued after completion of the WRITE burst; otherwise, a BST must be used to end the WRITE prior to asserting another READ command.

Table 90: Current State Bank n to Command to Bank m Truth Table

Notes 1–6 apply to all parameters and conditions

Current State of Bank n	Command to Bank m	Operation	Next State for Bank m	Notes
Any	NOP	Continue previous operation	Current state of bank m	
Idle	Any	Any command supported to bank m	–	7



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Truth Tables

Table 90: Current State Bank *n* to Command to Bank *m* Truth Table (Continued)

Notes 1–6 apply to all parameters and conditions

Current State of Bank <i>n</i>	Command to Bank <i>m</i>	Operation	Next State for Bank <i>m</i>	Notes
Row activating, active, or pre-charging	ACTIVATE	Select and activate row in bank <i>m</i>	Active	8
	READ	Select column and start READ burst from bank <i>m</i>	Reading	9
	WRITE	Select column and start WRITE burst to bank <i>m</i>	Writing	9
	PRECHARGE	Deactivate row(s) in bank or banks	Precharging	10
	MRR	READ value from mode register	Idle MR reading or active MR reading	11, 12, 13
	BST	READ or WRITE burst terminates an on-going READ/WRITE from/to bank <i>m</i>	Active	7
Reading (auto precharge disabled)	READ	Select column and start READ burst from bank <i>m</i>	Reading	9
	WRITE	Select column and start WRITE burst to bank <i>m</i>	Writing	9, 14
	ACTIVATE	Select and activate row in bank <i>m</i>	Active	
	PRECHARGE	Deactivate row(s) in bank or banks	Precharging	10
Writing (auto precharge disabled)	READ	Select column and start READ burst from bank <i>m</i>	Reading	9, 15
	WRITE	Select column and start WRITE burst to bank <i>m</i>	Writing	9
	ACTIVATE	Select and activate row in bank <i>m</i>	Active	
	PRECHARGE	Deactivate row(s) in bank or banks	Precharging	10
Reading with auto precharge	READ	Select column and start READ burst from bank <i>m</i>	Reading	9, 16
	WRITE	Select column and start WRITE burst to bank <i>m</i>	Writing	9, 14, 16
	ACTIVATE	Select and activate row in bank <i>m</i>	Active	
	PRECHARGE	Deactivate row(s) in bank or banks	Precharging	10
Writing with auto precharge	READ	Select column and start READ burst from bank <i>m</i>	Reading	9, 15, 16
	WRITE	Select column and start WRITE burst to bank <i>m</i>	Writing	9, 16
	ACTIVATE	Select and activate row in bank <i>m</i>	Active	
	PRECHARGE	Deactivate row(s) in bank or banks	Precharging	10
Power-on	MRW RESET	Begin device auto initialization	Resetting	17, 18
Resetting	MRR	Read value from mode register	Resetting MR reading	

- Notes:
1. This table applies when: the previous state was self refresh or power-down; after ^tXSR or ^tXP has been met; and both CKEn -1 and CKEn are HIGH.
 2. All states and sequences not shown are illegal or reserved.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Truth Tables

3. Current state definitions:

Idle: The bank has been precharged and t_{RP} has been met.

Active: A row in the bank has been activated, t_{RCD} has been met, no data bursts or accesses and no register accesses are in progress.

Read: A READ burst has been initiated with auto precharge disabled and the READ has not yet terminated or been terminated.

Write: A WRITE burst has been initiated with auto precharge disabled and the WRITE has not yet terminated or been terminated.

4. Refresh, self refresh, and MRW commands can only be issued when all banks are idle.
5. A BST command cannot be issued to another bank; it applies only to the bank represented by the current state.
6. The states listed below must not be interrupted by any executable command. NOP commands must be applied during each clock cycle while in these states:

Idle MRR: Starts with registration of the MRR command and ends when t_{MRR} has been met. After t_{MRR} is met, the device is in the all banks idle state.

Reset MRR: Starts with registration of the MRR command and ends when t_{MRR} has been met. After t_{MRR} is met, the device is in the all banks idle state.

Active MRR: Starts with registration of the MRR command and ends when t_{MRR} has been met. After t_{MRR} is met, the bank is in the active state.

MRW: Starts with registration of the MRW command and ends when t_{MRW} has been met. After t_{MRW} is met, the device is in the all banks idle state.
7. BST is supported only if a READ or WRITE burst is ongoing.
8. t_{RRD} must be met between the ACTIVATE command to bank n and any subsequent ACTIVATE command to bank m .
9. READs or WRITEs listed in the command column include READs and WRITEs with or without auto precharge enabled.
10. This command may or may not be bank-specific. If all banks are being precharged, they must be in a valid state for precharging.
11. MRR is supported in the row-activating state.
12. MRR is supported in the precharging state.
13. The next state for bank m depends on the current state of bank m (idle, row-activating, precharging, or active).
14. A WRITE command can be issued after the completion of the READ burst; otherwise a BST must be issued to end the READ prior to asserting a WRITE command.
15. A READ command can be issued after the completion of the WRITE burst; otherwise, a BST must be issued to end the WRITE prior to asserting another READ command.
16. A READ with auto precharge enabled or a WRITE with auto precharge enabled can be followed by any valid command to other banks provided that the timing restrictions in the PRECHARGE and Auto Precharge Clarification table are met.
17. Not bank-specific; requires that all banks are idle and no bursts are in progress.
18. RESET command is achieved through MODE REGISTER WRITE command.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications

Table 91: DM Truth Table

Functional Name	DM	DQ	Notes
Write enable	L	Valid	1
Write inhibit	H	X	1

Note: 1. Used to mask write data, and is provided simultaneously with the corresponding input data.

Electrical Specifications

Absolute Maximum Ratings

Stresses greater than those listed below may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this document is not implied. Exposure to absolute maximum rating conditions for extended periods may adversely affect reliability.

Table 92: Absolute Maximum DC Ratings

Parameter	Symbol	Min	Max	Unit	Notes
V _{DD1} supply voltage relative to V _{SS}	V _{DD1}	-0.4	+2.3	V	1
V _{DD2} supply voltage relative to V _{SS}	V _{DD2} (1.2V)	-0.4	+1.6	V	1
V _{DDCA} supply voltage relative to V _{SSCA}	V _{DDCA}	-0.4	+1.6	V	1, 2
V _{DDQ} supply voltage relative to V _{SSQ}	V _{DDQ}	-0.4	+1.6	V	1, 3
Voltage on any ball relative to V _{SS}	V _{IN} , V _{OUT}	-0.4	+1.6	V	
Storage temperature	T _{STG}	-55	+125	°C	4

- Notes:
- See 1. Voltage Ramp under Power-Up.
 - V_{REFCA} 0.6 ≤ V_{DDCA}; however, V_{REFCA} may be ≥ V_{DDCA} provided that V_{REFCA} ≤ 300mV.
 - V_{REFDQ} 0.6 ≤ V_{DDQ}; however, V_{REFDQ} may be ≥ V_{DDQ} provided that V_{REFDQ} ≤ 300mV.
 - Storage temperature is the case surface temperature on the center/top side of the device. For measurement conditions, refer to the JE51-2 standard.

Input/Output Capacitance

Table 93: Input/Output Capacitance

Note 1 applies to all parameters and conditions

Parameter	Symbol	LPDDR2 1066-466		LPDDR2 400-200		Unit	Notes
		MIN	MAX	MIN	MAX		
Input capacitance, CK and CK#	C _{CK}	1.0	2.0	1.0	2.0	pF	2, 3
Input capacitance delta, CK and CK#	C _{DCK}	0	0.20	0	0.25	pF	2, 3, 4
Input capacitance, all other input-only pins	C _I	1.0	2.0	1.0	2.0	pF	2, 3, 5



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications – I_{DD} Specifications and Conditions

Table 93: Input/Output Capacitance (Continued)

Note 1 applies to all parameters and conditions

Parameter	Symbol	LPDDR2 1066-466		LPDDR2 400-200		Unit	Notes
		MIN	MAX	MIN	MAX		
Input capacitance delta, all other input-only pins	C _{DI}	-0.40	+0.40	-0.50	+0.50	pF	2, 3, 6
Input/output capacitance, DQ, DM, DQS, DQS#	C _{IO}	1.25	2.5	1.25	2.5	pF	2, 3, 7, 8
Input/output capacitance delta, DQS, DQS#	C _{DDQS}	0	0.25	0	0.30	pF	2, 3, 8, 9
Input/output capacitance delta, DQ, DM	C _{DIO}	-0.5	+0.5	-0.6	+0.6	pF	2, 3, 8, 10
Input/output capacitance ZQ	C _{ZQ}	0	2.5	0	2.5	pF	2, 3, 11

- Notes:
1. T_C -40°C to +105°C; V_{DDQ} = 1.14–1.3V; V_{DDCA} = 1.14–1.3V; V_{DD1} = 1.7–1.95V; V_{DD2} = 1.14–1.3V.
 2. This parameter applies to die devices only (does not include package capacitance).
 3. This parameter is not subject to production testing. It is verified by design and characterization. The capacitance is measured according to JEP147 (procedure for measuring input capacitance using a vector network analyzer), with V_{DD1}, V_{DD2}, V_{DDQ}, V_{SS}, V_{SSCA}, and V_{SSQ} applied; all other pins are left floating.
 4. Absolute value of C_{CK} - C_{CK#}.
 5. C_I applies to CS#, CKE, and CA[9:0].
 6. C_{DI} = C_I - 0.5 × (C_{CK} + C_{CK#}).
 7. DM loading matches DQ and DQS.
 8. MR3 I/O configuration drive strength OP[3:0] = 0001b (34.3 ohm typical).
 9. Absolute value of C_{DQS} and C_{DQS#}.
 10. C_{DIO} = C_{IO} - 0.5 × (C_{DQS} + C_{DQS#}) in byte-lane.
 11. Maximum external load capacitance on ZQ pin: 5pF.

Electrical Specifications – I_{DD} Specifications and Conditions

The following definitions and conditions are used in the I_{DD} measurement tables unless stated otherwise:

- LOW: V_{IN} ≤ V_{IL(DC)max}
- HIGH: V_{IN} ≥ V_{IH(DC)min}
- STABLE: Inputs are stable at a HIGH or LOW level
- SWITCHING: See the following three tables

Table 94: Switching for CA Input Signals

Notes 1–3 apply to all parameters and conditions

	CK Rising/ CK#Falling	CK Falling/ CK# Rising	CK Rising/ CK#Falling	CK Falling/ CK# Rising	CK Rising/ CK#Falling	CK Falling/ CK# Rising	CK Rising/ CK#Falling	CK Falling/ CK# Rising
Cycle	N		N + 1		N + 2		N + 3	
CS#	HIGH		HIGH		HIGH		HIGH	
CA0	H	L	L	L	L	H	H	H



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications – I_{DD} Specifications and Conditions

Table 94: Switching for CA Input Signals (Continued)

Notes 1–3 apply to all parameters and conditions

	CK Rising/ CK#Falling	CK Falling/ CK# Rising	CK Rising/ CK#Falling	CK Falling/ CK# Rising	CK Rising/ CK#Falling	CK Falling/ CK# Rising	CK Rising/ CK#Falling	CK Falling/ CK# Rising
CA1	H	H	H	L	L	L	L	H
CA2	H	L	L	L	L	H	H	H
CA3	H	H	H	L	L	L	L	H
CA4	H	L	L	L	L	H	H	H
CA5	H	H	H	L	L	L	L	H
CA6	H	L	L	L	L	H	H	H
CA7	H	H	H	L	L	L	L	H
CA8	H	L	L	L	L	H	H	H
CA9	H	H	H	L	L	L	L	H

- Notes:
1. CS# must always be driven HIGH.
 2. For each clock cycle, 50% of the CA bus is changing between HIGH and LOW.
 3. The noted pattern (N, N + 1, N + 2, N + 3...) is used continuously during I_{DD} measurement for I_{DD} values that require switching on the CA bus.

Table 95: Switching for I_{DD4R}

Clock	CKE	CS#	Clock Cycle Number	Command	CA[2:0]	CA[9:3]	All DQ
Rising	H	L	N	Read_Rising	HLH	LHLHLHL	L
Falling	H	L	N	Read_Falling	LLL	LLLLLLL	L
Rising	H	H	N + 1	NOP	LLL	LLLLLLL	H
Falling	H	H	N + 1	NOP	HLH	LHLHLHL	L
Rising	H	L	N + 2	Read_Rising	HLH	LHLHLHL	H
Falling	H	L	N + 2	Read_Falling	LLL	HHHHHHH	H
Rising	H	H	N + 3	NOP	LLL	HHHHHHH	H
Falling	H	H	N + 3	NOP	HLH	LHLHLHL	L

- Notes:
1. Data strobe (DQS) is changing between HIGH and LOW with every clock cycle.
 2. The noted pattern (N, N + 1...) is used continuously during I_{DD} measurement for I_{DD4R}.

Table 96: Switching for I_{DD4W}

Clock	CKE	CS#	Clock Cycle Number	Command	CA[2:0]	CA[9:3]	All DQ
Rising	H	L	N	Write_Rising	LLH	LHLHLHL	L
Falling	H	L	N	Write_Falling	LLL	LLLLLLL	L
Rising	H	H	N + 1	NOP	LLL	LLLLLLL	H
Falling	H	H	N + 1	NOP	HLH	LHLHLHL	L
Rising	H	L	N + 2	Write_Rising	LLH	LHLHLHL	H



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications – I_{DD} Specifications and Conditions

Table 96: Switching for I_{DD4W} (Continued)

Clock	CKE	CS#	Clock Cycle Number	Command	CA[2:0]	CA[9:3]	All DQ
Falling	H	L	N + 2	Write_Falling	LLL	HHHHHHH	H
Rising	H	H	N + 3	NOP	LLL	HHHHHHH	H
Falling	H	H	N + 3	NOP	HLH	LHLHLHL	L

- Notes:
1. Data strobe (DQS) is changing between HIGH and LOW with every clock cycle.
 2. Data masking (DM) must always be driven LOW.
 3. The noted pattern (N, N + 1...) is used continuously during I_{DD} measurement for I_{DD4W}.

Table 97: I_{DD} Specification Parameters and Operating Conditions

Notes 1–3 apply to all parameters and conditions

Parameter/Condition	Symbol	Power Supply	Notes
Operating one bank active-precharge current (SDRAM): ^t CK = ^t CKmin; ^t RC = ^t RCmin; CKE is HIGH; CS# is HIGH between valid commands; CA bus inputs are switching; Data bus inputs are stable	I _{DD01}	V _{DD1}	
	I _{DD02}	V _{DD2}	
	I _{DD0in}	V _{DDCA} , V _{DDQ}	4
Idle power-down standby current: ^t CK = ^t CKmin; CKE is LOW; CS# is HIGH; All banks are idle; CA bus inputs are switching; Data bus inputs are stable	I _{DD2P1}	V _{DD1}	
	I _{DD2P2}	V _{DD2}	
	I _{DD2P,in}	V _{DDCA} , V _{DDQ}	4
Idle power-down standby current with clock stop: CK = LOW, CK# = HIGH; CKE is LOW; CS# is HIGH; All banks are idle; CA bus inputs are stable; Data bus inputs are stable	I _{DD2PS1}	V _{DD1}	
	I _{DD2PS2}	V _{DD2}	
	I _{DD2PS,in}	V _{DDCA} , V _{DDQ}	4
Idle non-power-down standby current: ^t CK = ^t CKmin; CKE is HIGH; CS# is HIGH; All banks are idle; CA bus inputs are switching; Data bus inputs are stable	I _{DD2N1}	V _{DD1}	
	I _{DD2N2}	V _{DD2}	
	I _{DD2N,in}	V _{DDCA} , V _{DDQ}	4
Idle non-power-down standby current with clock stopped: CK = LOW; CK# = HIGH; CKE is HIGH; CS# is HIGH; All banks are idle; CA bus inputs are stable; Data bus inputs are stable	I _{DD2NS1}	V _{DD1}	
	I _{DD2NS2}	V _{DD2}	
	I _{DD2NS,in}	V _{DDCA} , V _{DDQ}	4
Active power-down standby current: ^t CK = ^t CKmin; CKE is LOW; CS# is HIGH; One bank is active; CA bus inputs are switching; Data bus inputs are stable	I _{DD3P1}	V _{DD1}	
	I _{DD3P2}	V _{DD2}	
	I _{DD3P,in}	V _{DDCA} , V _{DDQ}	4
Active power-down standby current with clock stop: CK = LOW, CK# = HIGH; CKE is LOW; CS# is HIGH; One bank is active; CA bus inputs are stable; Data bus inputs are stable	I _{DD3PS1}	V _{DD1}	
	I _{DD3PS2}	V _{DD2}	
	I _{DD3PS,in}	V _{DDCA} , V _{DDQ}	4
Active non-power-down standby current: ^t CK = ^t CKmin; CKE is HIGH; CS# is HIGH; One bank is active; CA bus inputs are switching; Data bus inputs are stable	I _{DD3N1}	V _{DD1}	
	I _{DD3N2}	V _{DD2}	
	I _{DD3N,in}	V _{DDCA} , V _{DDQ}	4
Active non-power-down standby current with clock stopped: CK = LOW, CK# = HIGH; CKE is HIGH; CS# is HIGH; One bank is active; CA bus inputs are stable; Data bus inputs are stable	I _{DD3NS1}	V _{DD1}	
	I _{DD3NS2}	V _{DD2}	
	I _{DD3NS,in}	V _{DDCA} , V _{DDQ}	4



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Electrical Specifications – I_{DD} Specifications and Conditions

Table 97: I_{DD} Specification Parameters and Operating Conditions (Continued)

Notes 1–3 apply to all parameters and conditions

Parameter/Condition	Symbol	Power Supply	Notes
Operating burst READ current: $t_{CK} = t_{CKmin}$; CS# is HIGH between valid commands; One bank is active; BL = 4; RL = RL (MIN); CA bus inputs are switching; 50% data change each burst transfer	I _{DD4R1}	V _{DD1}	
	I _{DD4R2}	V _{DD2}	
	I _{DD4R,in}	V _{DDCA}	
	I _{DD4RQ}	V _{DDQ}	5
Operating burst WRITE current: $t_{CK} = t_{CKmin}$; CS# is HIGH between valid commands; One bank is active; BL = 4; WL = WLmin; CA bus inputs are switching; 50% data change each burst transfer	I _{DD4W1}	V _{DD1}	
	I _{DD4W2}	V _{DD2}	
	I _{DD4W,in}	V _{DDCA} , V _{DDQ}	4
All-bank REFRESH burst current: $t_{CK} = t_{CKmin}$; CKE is HIGH between valid commands; $t_{RC} = t_{RFCabmin}$; Burst refresh; CA bus inputs are switching; Data bus inputs are stable	I _{DD51}	V _{DD1}	
	I _{DD52}	V _{DD2}	
	I _{DD5IN}	V _{DDCA} , V _{DDQ}	4
All-bank REFRESH average current: $t_{CK} = t_{CKmin}$; CKE is HIGH between valid commands; $t_{RC} = t_{REFI}$; CA bus inputs are switching; Data bus inputs are stable	I _{DD5AB1}	V _{DD1}	
	I _{DD5AB2}	V _{DD2}	
	I _{DD5AB,in}	V _{DDCA} , V _{DDQ}	4
Per-bank REFRESH average current: $t_{CK} = t_{CKmin}$; CKE is HIGH between valid commands; $t_{RC} = t_{REFI}/8$; CA bus inputs are switching; Data bus inputs are stable	I _{DD5PB1}	V _{DD1}	6
	I _{DD5PB2}	V _{DD2}	6
	I _{DD5PB,in}	V _{DDCA} , V _{DDQ}	4, 6
Self refresh current (–40°C to +85°C): CK = LOW, CK# = HIGH; CKE is LOW; CA bus inputs are stable; Data bus inputs are stable; Maximum 1x self refresh rate	I _{DD61}	V _{DD1}	7
	I _{DD62}	V _{DD2}	7
	I _{DD6IN}	V _{DDCA} , V _{DDQ}	4, 7
Self refresh current (+85°C to +105°C): CK = LOW, CK# = HIGH; CKE is LOW; CA bus inputs are stable; Data bus inputs are stable	I _{DD6ET1}	V _{DD1}	7, 8
	I _{DD6ET2}	V _{DD2}	7, 8
	I _{DD6ET,in}	V _{DDCA} , V _{DDQ}	4, 7, 8
Self refresh current (+105°C to +125°C): Not available.			9
Deep power-down current: CK = LOW, CK# = HIGH; CKE is LOW; CA bus inputs are stable; Data bus inputs are stable	I _{DD81}	V _{DD1}	8
	I _{DD82}	V _{DD2}	8
	I _{DD8IN}	V _{DDCA} , V _{DDQ}	4, 8

- Notes:
1. I_{DD} values are the maximum of the distribution of the arithmetic mean.
 2. I_{DD} current specifications are tested after the device is properly initialized.
 3. The 1x self refresh rate is the rate at which the device is refreshed internally during self refresh, before going into the extended temperature range.
 4. Measured currents are the sum of V_{DDQ} and V_{DDCA}.
 5. Guaranteed by design with output reference load and R_{ON} = 40 ohm.
 6. Per-bank REFRESH is only applicable for LPDDR2-S4 device densities 1Gb or higher.
 7. This is the general definition that applies to full-array self refresh.
 8. I_{DD6ET} and I_{DD8} are typical values, are sampled only, and are not tested.
 9. When TC > 105°C, self-refresh mode is not available.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC and DC Operating Conditions

AC and DC Operating Conditions

Operation or timing that is not specified is illegal. To ensure proper operation, the device must be initialized properly.

Table 98: Recommended DC Operating Conditions

Symbol	LPDDR2-S4B			Power Supply	Unit
	Min	Typ	Max		
V_{DD1}^1	1.70	1.80	1.95	Core power 1	V
V_{DD2}	1.14	1.20	1.30	Core power 2	V
V_{DDCA}	1.14	1.20	1.30	Input buffer power	V
V_{DDQ}	1.14	1.20	1.30	I/O buffer power	V

Note: 1. V_{DD1} uses significantly less power than V_{DD2} .

Table 99: Input Leakage Current

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input leakage current: For CA, CKE, CS#, CK, CK#; Any input $0V \leq V_{IN} \leq V_{DDCA}$; (All other pins not under test = 0V)	I_L	-2	2	μA	1
V_{REF} supply leakage current: $V_{REFDQ} = V_{DDQ}/2$, or $V_{REFCA} = V_{DDCA}/2$; (All other pins not under test = 0V)	I_{VREF}	-1	1	μA	2

- Notes:
- Although DM is for input only, the DM leakage must match the DQ and DQS/DQS# output leakage specification.
 - The minimum limit requirement is for testing purposes. The leakage current on V_{REFCA} and V_{REFDQ} pins should be minimal.

Table 100: Operating Temperature Range

Parameter/Condition	Symbol	Min	Max	Unit
IT temperature range	T_{CASE}^1	-40	+85	$^{\circ}C$
AT temperature range		-40	+105	$^{\circ}C$
UT temperature range		-40	+125	$^{\circ}C$

- Notes:
- Operating temperature is the case surface temperature at the center of the top side of the device. For measurement conditions, refer to the JESD51-2 standard.
 - Some applications require operation in the maximum case temperature range, between 85°C and 105°C. For some LPDDR2 devices, derating may be necessary to operate in this range (see the MR4 Device Temperature (MA[7:0] = 04h) table).
 - Either the device operating temperature or the temperature sensor can be used to set an appropriate refresh rate, determine the need for AC timing derating, and/or monitor the operating temperature (see Temperature Sensor). When using the temperature sensor, the actual device case temperature may be higher than the T_{CASE} rating that applies for the operating temperature range. For example, T_{CASE} could be above 85°C when the temperature sensor indicates a temperature of less than 85°C.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC and DC Logic Input Measurement Levels for Single-Ended Signals

4. UT option use based on automotive usage model. Please contact Micron sales representative if you have questions.

AC and DC Logic Input Measurement Levels for Single-Ended Signals

Table 101: Single-Ended AC and DC Input Levels for CA and CS# Inputs

Symbol	Parameter	LPDDR2-1066 to LPDDR2-466		LPDDR2-400 to LPDDR2-200		Unit	Notes
		Min	Max	Min	Max		
$V_{IHCA(AC)}$	AC input logic HIGH	$V_{REF} + 0.220$	Note 2	$V_{REF} + 0.300$	Note 2	V	1, 2
$V_{ILCA(AC)}$	AC input logic LOW	Note 2	$V_{REF} - 0.220$	Note 2	$V_{REF} - 0.300$	V	1, 2
$V_{IHCA(DC)}$	DC input logic HIGH	$V_{REF} + 0.130$	V_{DDCA}	$V_{REF} + 0.200$	V_{DDCA}	V	1
$V_{ILCA(DC)}$	DC input logic LOW	V_{SSCA}	$V_{REF} - 0.130$	V_{SSCA}	$V_{REF} - 0.200$	V	1
$V_{REFCA(DC)}$	Reference voltage for CA and CS# inputs	$0.49 \times V_{DDCA}$	$0.51 \times V_{DDCA}$	$0.49 \times V_{DDCA}$	$0.51 \times V_{DDCA}$	V	3, 4

- Notes:
1. For CA and CS# input-only pins. $V_{REF} = V_{REFCA(DC)}$.
 2. See Overshoot and Undershoot Definition.
 3. The AC peak noise on V_{REFCA} could prevent V_{REFCA} from deviating more than $\pm 1\% V_{DDCA}$ from $V_{REFCA(DC)}$ (for reference, approximately $\pm 12mV$).
 4. For reference, approximately $V_{DDCA}/2 \pm 12mV$.

Table 102: Single-Ended AC and DC Input Levels for CKE

Symbol	Parameter	Min	Max	Unit	Notes
V_{IHCKE}	CKE input HIGH level	$0.8 \times V_{DDCA}$	Note 1	V	1
V_{ILCKE}	CKE input LOW level	Note 1	$0.2 \times V_{DDCA}$	V	1

- Note:
1. See Overshoot and Undershoot Definition.

Table 103: Single-Ended AC and DC Input Levels for DQ and DM

Symbol	Parameter	LPDDR2-1066 to LPDDR2-466		LPDDR2-400 to LPDDR2-200		Unit	Notes
		Min	Max	Min	Max		
$V_{IHDQ(AC)}$	AC input logic HIGH	$V_{REF} + 0.220$	Note 2	$V_{REF} + 0.300$	Note 2	V	1, 2
$V_{ILDQ(AC)}$	AC input logic LOW	Note 2	$V_{REF} - 0.220$	Note 2	$V_{REF} - 0.300$	V	1, 2
$V_{IHDQ(DC)}$	DC input logic HIGH	$V_{REF} + 0.130$	V_{DDQ}	$V_{REF} + 0.200$	V_{DDQ}	V	1
$V_{ILDQ(DC)}$	DC input logic LOW	V_{SSQ}	$V_{REF} - 0.130$	V_{SSQ}	$V_{REF} - 0.200$	V	1
$V_{REFDQ(DC)}$	Reference voltage for DQ and DM inputs	$0.49 \times V_{DDQ}$	$0.51 \times V_{DDQ}$	$0.49 \times V_{DDQ}$	$0.51 \times V_{DDQ}$	V	3, 4

- Notes:
1. For DQ input-only pins. $V_{REF} = V_{REFDQ(DC)}$.
 2. See Overshoot and Undershoot Definition.
 3. The AC peak noise on V_{REFDQ} could prevent V_{REFDQ} from deviating more than $\pm 1\% V_{DDQ}$ from $V_{REFDQ(DC)}$ (for reference, approximately $\pm 12mV$).
 4. For reference, approximately $V_{DDQ}/2 \pm 12mV$.

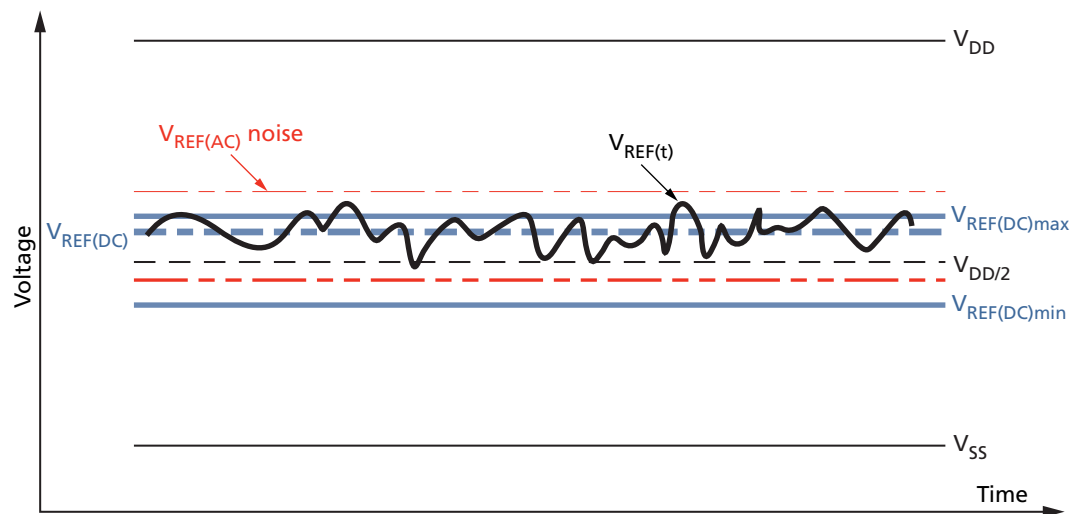


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC and DC Logic Input Measurement Levels for Single-Ended Signals

V_{REF} Tolerances

The DC tolerance limits and AC noise limits for the reference voltages V_{REFCA} and V_{REFDQ} are illustrated below. This figure shows a valid reference voltage $V_{REF}(t)$ as a function of time. V_{DD} is used in place of V_{DDCA} for V_{REFCA} , and V_{DDQ} for V_{REFDQ} . $V_{REF(DC)}$ is the linear average of $V_{REF}(t)$ over a very long period of time (for example, 1 second) and is specified as a fraction of the linear average of V_{DDQ} or V_{DDCA} , also over a very long period of time (for example, 1 second). This average must meet the MIN/MAX requirements in Table 101 (page 195). Additionally, $V_{REF}(t)$ can temporarily deviate from $V_{REF(DC)}$ by no more than $\pm 1\% V_{DD}$. $V_{REF}(t)$ cannot track noise on V_{DDQ} or V_{DDCA} if doing so would force V_{REF} outside these specifications.

Figure 137: V_{REF} DC Tolerance and V_{REF} AC Noise Limits



The voltage levels for setup and hold time measurements $V_{IH(AC)}$, $V_{IH(DC)}$, $V_{IL(AC)}$, and $V_{IL(DC)}$ are dependent on V_{REF} .

V_{REF} DC variations affect the absolute voltage a signal must reach to achieve a valid HIGH or LOW, as well as the time from which setup and hold times are measured. When V_{REF} is outside the specified levels, devices will function correctly with appropriate timing deratings as long as:

- V_{REF} is maintained between $0.44 \times V_{DDQ}$ (or V_{DDCA}) and $0.56 \times V_{DDQ}$ (or V_{DDCA}), and
- the controller achieves the required single-ended AC and DC input levels from instantaneous V_{REF} (see Table 101 (page 195)).

System timing and voltage budgets must account for V_{REF} deviations outside this range.

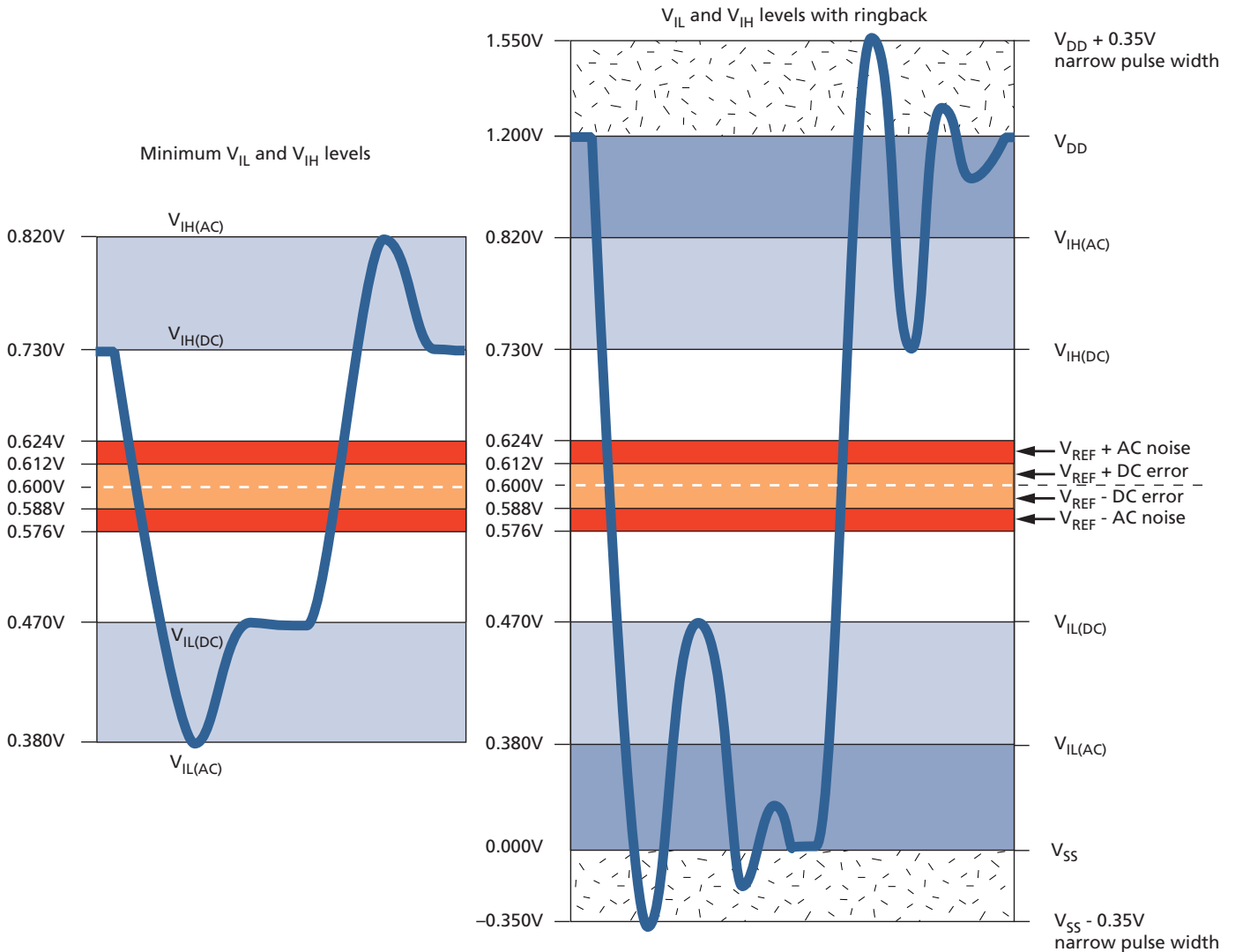
The setup/hold specification and derating values must include time and voltage associated with V_{REF} AC noise. Timing and voltage effects due to AC noise on V_{REF} up to the specified limit ($\pm 1\% V_{DD}$) are included in LPDDR2 timings and their associated deratings.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC and DC Logic Input Measurement Levels for Single-Ended Signals

Input Signal

Figure 138: LPDDR2-466 to LPDDR2-1066 Input Signal



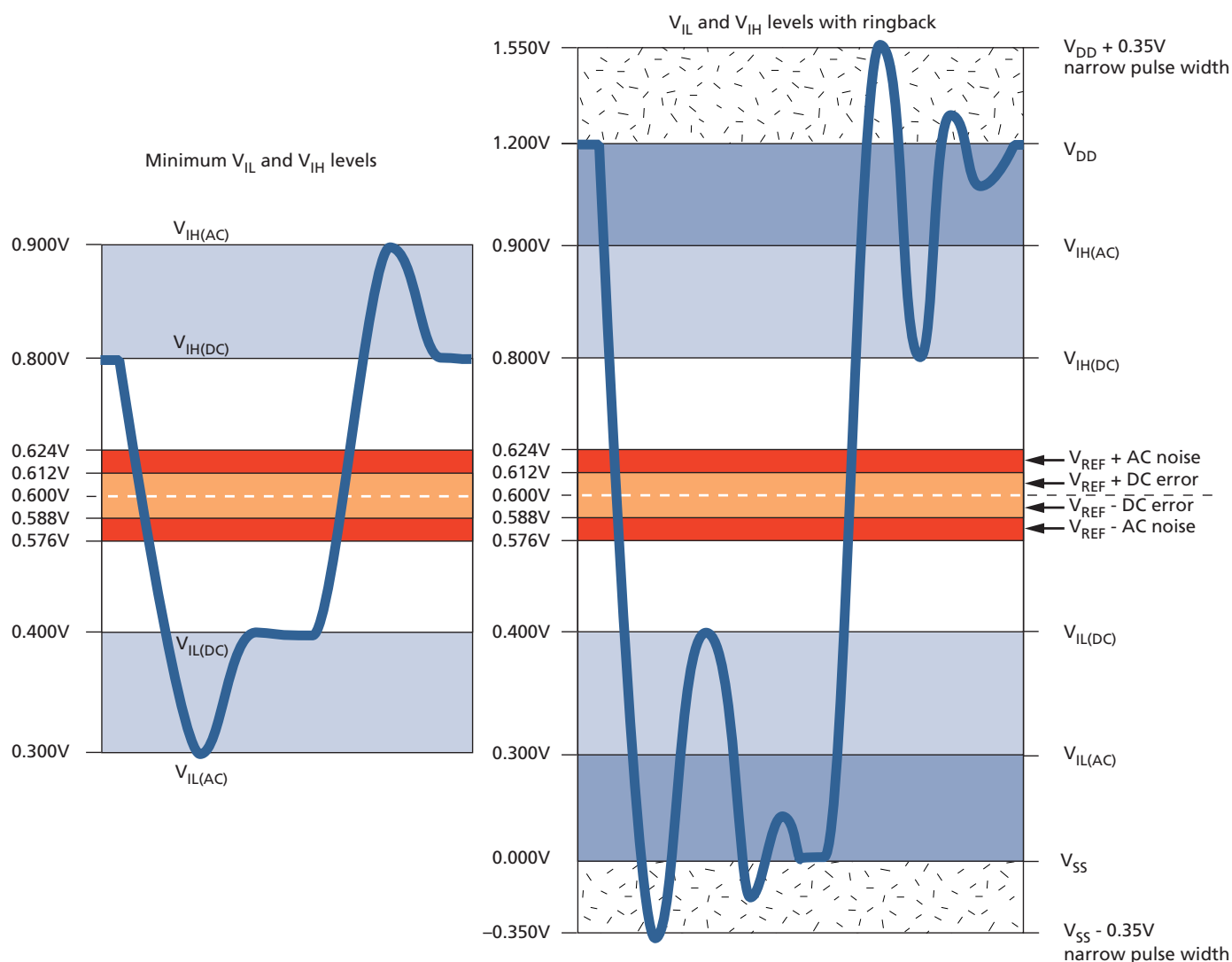
- Notes:
1. Numbers reflect typical values.
 2. For CA[9:0], CK, CK#, and CS# V_{DD} stands for V_{DDCA} . For DQ, DM, DQS, and DQS#, V_{DD} stands for V_{DDQ} .
 3. For CA[9:0], CK, CK#, and CS# V_{SS} stands for V_{SSCA} . For DQ, DM, DQS, and DQS#, V_{SS} stands for V_{SSQ} .



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP

AC and DC Logic Input Measurement Levels for Single-Ended Signals

Figure 139: LPDDR2-200 to LPDDR2-400 Input Signal



- Notes:
1. Numbers reflect typical values.
 2. For CA[9:0], CK, CK#, and CS# V_{DD} stands for V_{DDCA} . For DQ, DM, DQS, and DQS#, V_{DD} stands for V_{DDQ} .
 3. For CA[9:0], CK, CK#, and CS# V_{SS} stands for V_{SSCA} . For DQ, DM, DQS, and DQS#, V_{SS} stands for V_{SSQ} .



AC and DC Logic Input Measurement Levels for Differential Signals

Figure 140: Differential AC Swing Time and t_{DVAC}

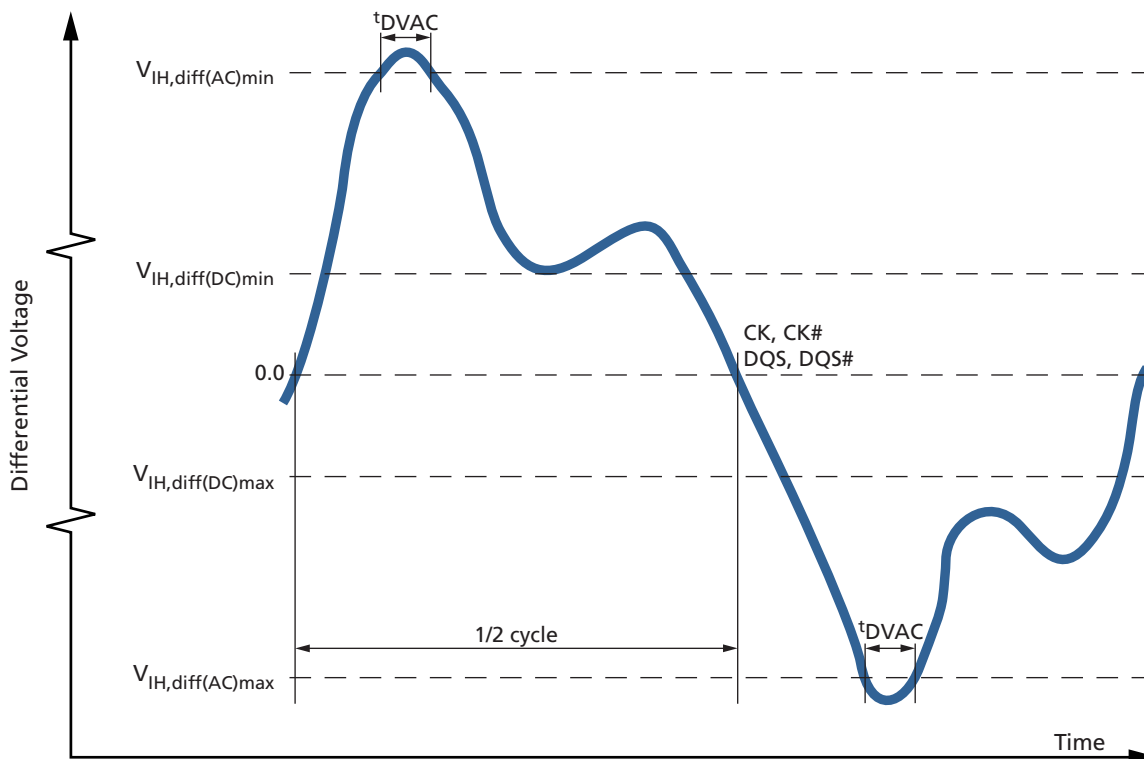


Table 104: Differential AC and DC Input Levels

For CK and CK#, $V_{REF} = V_{REFCA(DC)}$; For DQS and DQS# $V_{REF} = V_{REFDQ(DC)}$

Symbol	Parameter	LPDDR2-1066 to LPDDR2-466		LPDDR2-400 to LPDDR2-200		Unit	Notes
		Min	Max	Min	Max		
$V_{IH,diff(AC)}$	Differential input HIGH AC	$2 \times (V_{IH(AC)} - V_{REF})$	Note 1	$2 \times (V_{IH(AC)} - V_{REF})$	Note 1	V	2
$V_{IL,diff(AC)}$	Differential input LOW AC	Note 1	$2 \times (V_{REF} - V_{IL(AC)})$	Note 1	$2 \times (V_{REF} - V_{IL(AC)})$	V	2
$V_{IH,diff(DC)}$	Differential input HIGH	$2 \times (V_{IH(DC)} - V_{REF})$	Note 1	$2 \times (V_{IH(DC)} - V_{REF})$	Note 1	V	3
$V_{IL,diff(DC)}$	Differential input LOW	Note 1	$2 \times (V_{REF} - V_{IL(DC)})$	Note 1	$2 \times (V_{REF} - V_{IL(DC)})$	V	3

Notes: 1. These values are not defined, however the single-ended signals CK, CK#, DQS, and DQS# must be within the respective limits ($V_{IH(DC)max}$, $V_{IL(DC)min}$) for single-ended signals and must comply with the specified limitations for overshoot and undershoot (see Overshoot and Undershoot Definition).



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC and DC Logic Input Measurement Levels for Differential Signals

- For CK and CK#, use $V_{IH}/V_{IL(AC)}$ of CA and V_{REFCA} ; for DQS and DQS#, use $V_{IH}/V_{IL(AC)}$ of DQ and V_{REFDQ} . If a reduced AC HIGH or AC LOW is used for a signal group, the reduced voltage level also applies.
- Used to define a differential signal slew rate.

Table 105: CK/CK# and DQS/DQS# Time Requirements Before Ringback (t_{DVAC})

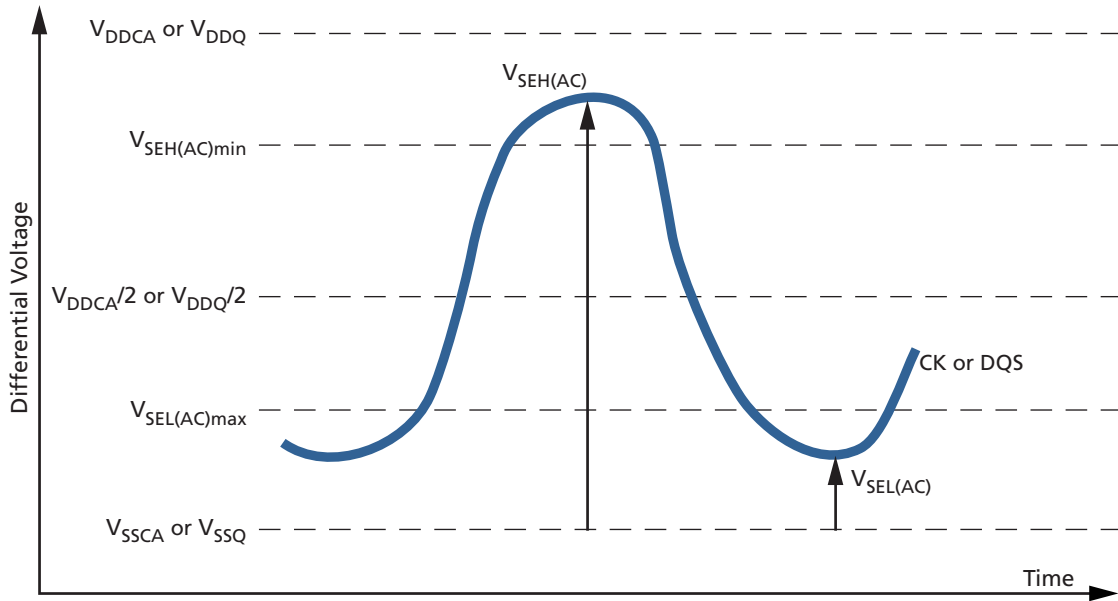
Slew Rate (V/ns)	t_{DVAC} (ps) at $V_{IH}/V_{ILdiff(AC)} = 440mV$	t_{DVAC} (ps) at $V_{IH}/V_{ILdiff(AC)} = 600mV$
	Min	Min
> 4.0	175	75
4.0	170	57
3.0	167	50
2.0	163	38
1.8	162	34
1.6	161	29
1.4	159	22
1.2	155	13
1.0	150	0
< 1.0	150	0

Single-Ended Requirements for Differential Signals

Each individual component of a differential signal (CK, CK#, DQS, and DQS#) must also comply with certain requirements for single-ended signals.

CK and CK# must meet $V_{SEH(AC)min}/V_{SEL(AC)max}$ in every half cycle. DQS, DQS# must meet $V_{SEH(AC)min}/V_{SEL(AC)max}$ in every half cycle preceding and following a valid transition.

The applicable AC levels for CA and DQ differ by speed bin.


Figure 141: Single-Ended Requirements for Differential Signals


Note that while CA and DQ signal requirements are referenced to V_{REF} , the single-ended components of differential signals also have a requirement with respect to $V_{DDQ}/2$ for DQS, and $V_{DDCA}/2$ for CK.

The transition of single-ended signals through the AC levels is used to measure setup time. For single-ended components of differential signals, the requirement to reach $V_{SEL(AC)max}$ or $V_{SEH(AC)min}$ has no bearing on timing. This requirement does, however, add a restriction on the common mode characteristics of these signals (see "Single-Ended AC and DC Input Levels for CA and CS# Inputs" for CK/CK# single-ended requirements, and "Single-Ended AC and DC Input Levels for DQ and DM" for DQ and DQM single-ended requirements).

Table 106: Single-Ended Levels for CK, CK#, DQS, DQS#

Symbol	Parameter	LPDDR2-1066 to LPDDR2-466		LPDDR2-400 to LPDDR2-200		Unit	Notes
		Min	Max	Min	Max		
$V_{SEH(AC)}$	Single-ended HIGH level for strobes	$(V_{DDQ}/2) + 0.220$	Note 1	$(V_{DDQ}/2) + 0.300$	Note 1	V	2, 3
	Single-ended HIGH level for CK, CK#	$(V_{DDCA}/2) + 0.220$	Note 1	$(V_{DDCA}/2) + 0.300$	Note 1	V	2, 3
$V_{SEL(AC)}$	Single-ended LOW level for strobes	Note 1	$(V_{DDQ}/2) - 0.220$	Note 1	$(V_{DDQ}/2) - 0.300$	V	2, 3
	Single-ended LOW level for CK, CK#	Note 1	$(V_{DDCA}/2) - 0.220$	Note 1	$(V_{DDCA}/2) - 0.300$	V	2, 3

Notes: 1. These values are not defined, however, the single-ended signals CK, CK#, DQS0, DQS#0, DQS1, DQS#1, DQS2, DQS#2, DQS3, DQS#3 must be within the respective limits $(V_{IH(DC)max}/V_{IL(DC)min})$ for single-ended signals, and must comply with the specified limitations for overshoot and undershoot (See Overshoot and Undershoot Definition).



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC and DC Logic Input Measurement Levels for Differential Signals

- For CK and CK#, use $V_{SEH}/V_{SEL(AC)}$ of CA; for strobes (DQS[3:0] and DQS#[3:0]), use $V_{IH}/V_{IL(AC)}$ of DQ.
- $V_{IH(AC)}$ and $V_{IL(AC)}$ for DQ are based on V_{REFDQ} ; $V_{SEH(AC)}$ and $V_{SEL(AC)}$ for CA are based on V_{REFCA} . If a reduced AC HIGH or AC LOW is used for a signal group, the reduced level applies.

Differential Input Crosspoint Voltage

To ensure tight setup and hold times as well as output skew parameters with respect to clock and strobe, each crosspoint voltage of differential input signals (CK, CK#, DQS, and DQS#) must meet the specifications in Table 106 (page 201). The differential input crosspoint voltage (V_{IX}) is measured from the actual crosspoint of the true signal and its complement to the midlevel between V_{DD} and V_{SS} .

Figure 142: V_{IX} Definition

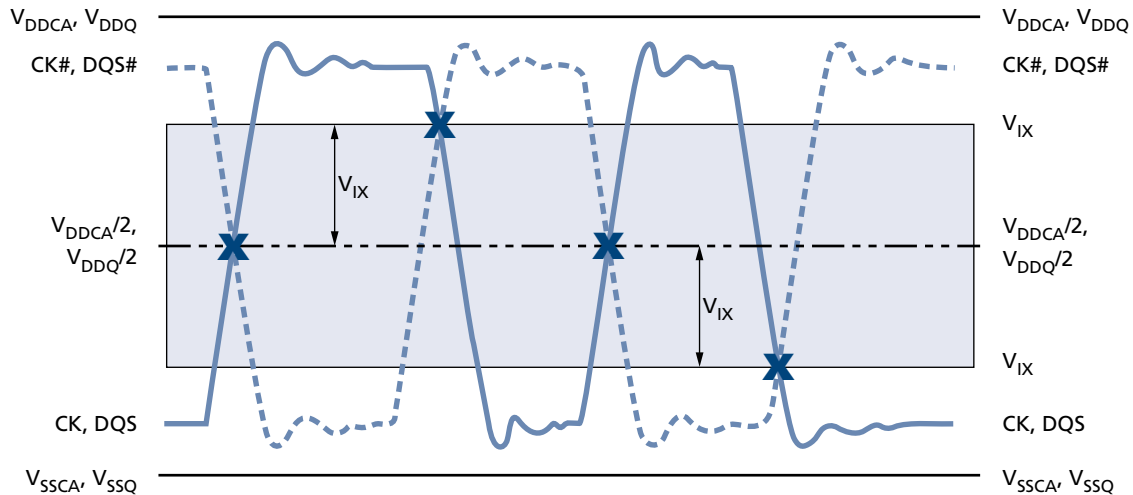


Table 107: Crosspoint Voltage for Differential Input Signals (CK, CK#, DQS, DQS#)

Symbol	Parameter	LPDDR2-1066 to LPDDR2-200		Unit	Notes
		Min	Max		
$V_{IXCA(AC)}$	Differential input crosspoint voltage relative to $V_{DDCA}/2$ for CK and CK#	-120	120	mV	1, 2
$V_{IXDQ(AC)}$	Differential input crosspoint voltage relative to $V_{DDQ}/2$ for DQS and DQS#	-120	120	mV	1, 2

- Notes:
- The typical value of $V_{IX(AC)}$ is expected to be about $0.5 \times V_{DD}$ of the transmitting device, and it is expected to track variations in V_{DD} . $V_{IX(AC)}$ indicates the voltage at which differential input signals must cross.
 - For CK and CK#, $V_{REF} = V_{REFCA(DC)}$. For DQS and DQS#, $V_{REF} = V_{REFDQ(DC)}$.

Input Slew Rate



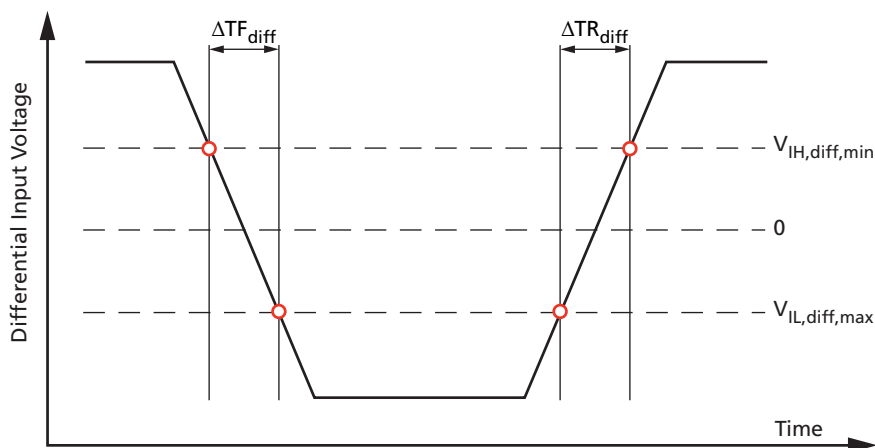
4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Characteristics and Operating Conditions

Table 108: Differential Input Slew Rate Definition

Description	Measured ¹		Defined by
	From	To	
Differential input slew rate for rising edge (CK/CK# and DQS/DQS#)	$V_{IL,diff,max}$	$V_{IH,diff,min}$	$[V_{IH,diff,min} - V_{IL,diff,max}] / \Delta TR_{diff}$
Differential input slew rate for falling edge (CK/CK# and DQS/DQS#)	$V_{IH,diff,min}$	$V_{IL,diff,max}$	$[V_{IH,diff,min} - V_{IL,diff,max}] / \Delta TF_{diff}$

Note: 1. The differential signals (CK/CK# and DQS/DQS#) must be linear between these thresholds.

Figure 143: Differential Input Slew Rate Definition for CK, CK#, DQS, and DQS#



Output Characteristics and Operating Conditions

Table 109: Single-Ended AC and DC Output Levels

Symbol	Parameter	Value	Unit	Notes
$V_{OH(AC)}$	AC output HIGH measurement level (for output slew rate)	$V_{REF} + 0.12$	V	
$V_{OL(AC)}$	AC output LOW measurement level (for output slew rate)	$V_{REF} - 0.12$	V	
$V_{OH(DC)}$	DC output HIGH measurement level (for I-V curve linearity)	$0.9 \times V_{DDQ}$	V	1
$V_{OL(DC)}$	DC output LOW measurement level (for I-V curve linearity)	$0.1 \times V_{DDQ}$	V	2
I_{OZ}	Output leakage current (DQ, DM, DQS, DQS#); DQ, DQS, DQS# are disabled; $0V \leq V_{OUT} \leq V_{DDQ}$	MIN	-5	μA
		MAX	+5	μA
MMpupd	Delta output impedance between pull-up and pull-down for DQ/DM	MIN	-15	%
		MAX	+15	%

Notes: 1. $I_{OH} = -0.1mA$.
2. $I_{OL} = 0.1mA$.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Characteristics and Operating Conditions

Table 110: Differential AC and DC Output Levels

Symbol	Parameter	Value	Unit
$V_{OHdiff(AC)}$	AC differential output HIGH measurement level (for output SR)	$+0.2 \times V_{DDQ}$	V
$V_{OLdiff(AC)}$	AC differential output LOW measurement level (for output SR)	$-0.2 \times V_{DDQ}$	V

Single-Ended Output Slew Rate

With the reference load for timing measurements, the output slew rate for falling and rising edges is defined and measured between $V_{OL(AC)}$ and $V_{OH(AC)}$ for single-ended signals.

Table 111: Single-Ended Output Slew Rate Definition

Description	Measured		Defined by
	From	To	
Single-ended output slew rate for rising edge	$V_{OL(AC)}$	$V_{OH(AC)}$	$[V_{OH(AC)} - V_{OL(AC)}] / \Delta TR_{SE}$
Single-ended output slew rate for falling edge	$V_{OH(AC)}$	$V_{OL(AC)}$	$[V_{OH(AC)} - V_{OL(AC)}] / \Delta TF_{SE}$

Note: 1. Output slew rate is verified by design and characterization and may not be subject to production testing.

Figure 144: Single-Ended Output Slew Rate Definition

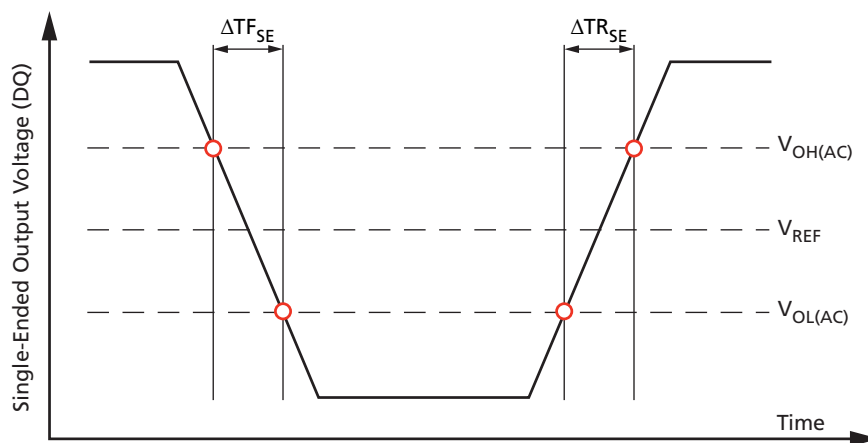


Table 112: Single-Ended Output Slew Rate

Notes 1–5 apply to all parameters conditions

Parameter	Symbol	Value		Unit
		Min	Max	
Single-ended output slew rate (output impedance = $40\Omega \pm 30\%$)	SRQ_{SE}	1.5	3.5	V/ns
Single-ended output slew rate (output impedance = $60\Omega \pm 30\%$)	SRQ_{SE}	1.0	2.5	V/ns



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Characteristics and Operating Conditions

Table 112: Single-Ended Output Slew Rate (Continued)

Notes 1–5 apply to all parameters conditions

Parameter	Symbol	Value		Unit
		Min	Max	
Output slew-rate-matching ratio (pull-up to pull-down)		0.7	1.4	–

- Notes:
1. Definitions: SR = slew rate; Q = output (similar to DQ = data-in, data-out); SE = single-ended signals.
 2. Measured with output reference load.
 3. The ratio of pull-up to pull-down slew rate is specified for the same temperature and voltage over the entire temperature and voltage range. For a given output, the ratio represents the maximum difference between pull-up and pull-down drivers due to process variation.
 4. The output slew rate for falling and rising edges is defined and measured between $V_{OL(AC)}$ and $V_{OH(AC)}$.
 5. Slew rates are measured under typical simultaneous switching output (SSO) conditions, with one-half of DQ signals per data byte driving HIGH and one-half of DQ signals per data byte driving LOW.

Differential Output Slew Rate

With the reference load for timing measurements, the output slew rate for falling and rising edges is defined and measured between $V_{OL,diff(AC)}$ and $V_{OH,diff(AC)}$ for differential signals.

Table 113: Differential Output Slew Rate Definition

Description	Measured		Defined by
	From	To	
Differential output slew rate for rising edge	$V_{OL,diff(AC)}$	$V_{OH,diff(AC)}$	$[V_{OH,diff(AC)} - V_{OL,diff(AC)}] / \Delta T_{R,diff}$
Differential output slew rate for falling edge	$V_{OH,diff(AC)}$	$V_{OL,diff(AC)}$	$[V_{OH,diff(AC)} - V_{OL,diff(AC)}] / \Delta T_{F,diff}$

- Note:
1. Output slew rate is verified by design and characterization and may not be subject to production testing.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Characteristics and Operating Conditions

Figure 145: Differential Output Slew Rate Definition

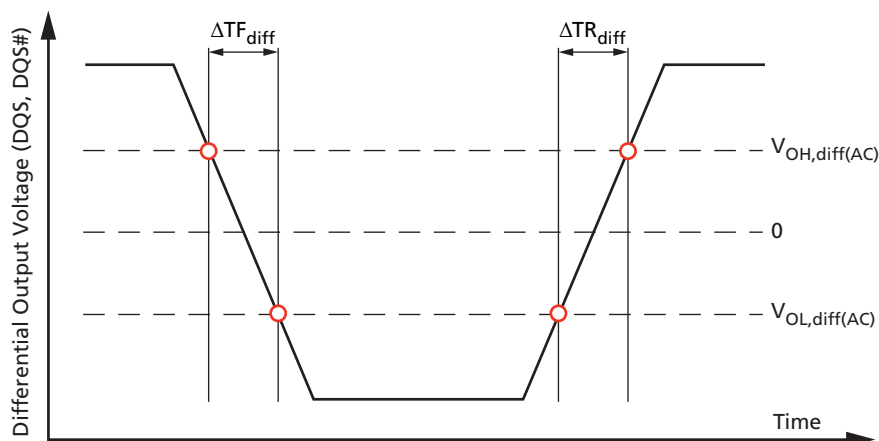


Table 114: Differential Output Slew Rate

Parameter	Symbol	Value		Unit
		Min	Max	
Differential output slew rate (output impedance = $40\Omega \pm 30\%$)	SRQ_{diff}	3.0	7.0	V/ns
Differential output slew rate (output impedance = $60\Omega \pm 30\%$)	SRQ_{diff}	2.0	5.0	V/ns

- Notes:
1. Definitions: SR = slew rate; Q = output (similar to DQ = data-in, data-out); SE = single-ended signals.
 2. Measured with output reference load.
 3. The output slew rate for falling and rising edges is defined and measured between $V_{OL(AC)}$ and $V_{OH(AC)}$.
 4. Slew rates are measured under typical simultaneous switching output (SSO) conditions, with one-half of DQ signals per data byte driving HIGH and one-half of DQ signals per data byte driving LOW.

Table 115: AC Overshoot/Undershoot Specification

Applies for CA[9:0], CS#, CKE, CK, CK#, DQ, DQS, DQS#, DM

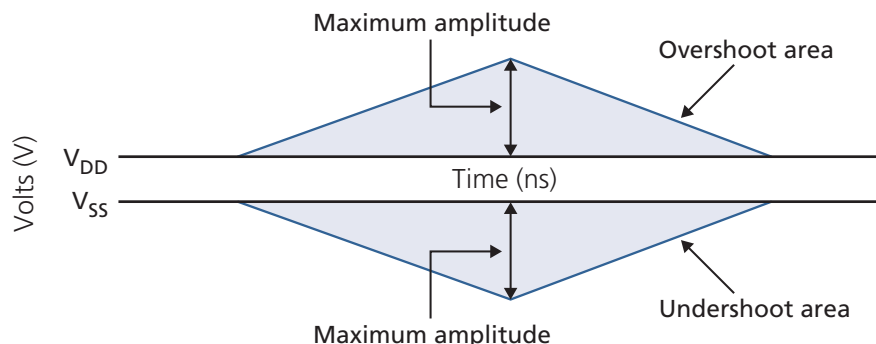
Parameter	1066	933	800	667	533	400	333	Unit
Maximum peak amplitude provided for overshoot area	0.35	0.35	0.35	0.35	0.35	0.35	0.35	V
Maximum peak amplitude provided for undershoot area	0.35	0.35	0.35	0.35	0.35	0.35	0.35	V
Maximum area above V_{DD}^1	0.15	0.17	0.20	0.24	0.30	0.40	0.48	V/ns
Maximum area below V_{SS}^2	0.15	0.17	0.20	0.24	0.30	0.40	0.48	V/ns

- Notes:
1. V_{DD} stands for V_{DDCA} for CA[9:0], CK, CK#, CS#, and CKE. V_{DD} stands for V_{DDQ} for DQ, DM, DQS, and DQS#.
 2. V_{SS} stands for V_{SSCA} for CA[9:0], CK, CK#, CS#, and CKE. V_{SS} stands for V_{SSQ} for DQ, DM, DQS, and DQS#.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Driver Impedance

Figure 146: Overshoot and Undershoot Definition

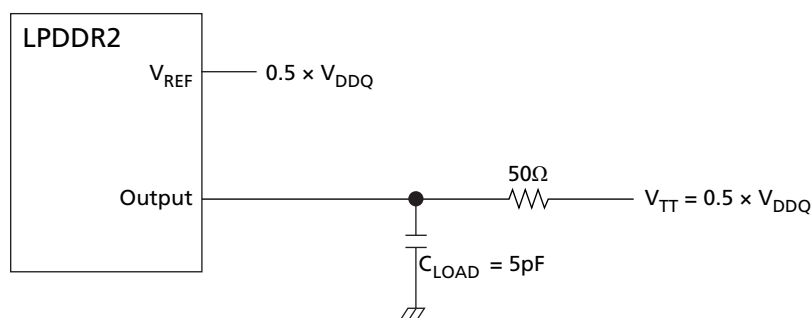


- Notes:
1. V_{DD} stands for V_{DDCA} for CA[9:0], CK, CK#, CS#, and CKE. V_{DD} stands for V_{DDQ} for DQ, DM, DQS, and DQS#.
 2. V_{SS} stands for V_{SSCA} for CA[9:0], CK, CK#, CS#, and CKE. V_{SS} stands for V_{SSQ} for DQ, DM, DQS, and DQS#.

HSUL_12 Driver Output Timing Reference Load

The timing reference loads are not intended as a precise representation of any particular system environment or a depiction of the actual load presented by a production tester. System designers should use IBIS or other simulation tools to correlate the timing reference load to a system environment. Manufacturers correlate to their production test conditions, generally with one or more coaxial transmission lines terminated at the tester electronics.

Figure 147: HSUL_12 Driver Output Reference Load for Timing and Slew Rate



- Note:
1. All output timing parameter values (t_{DQSCK} , t_{DQSQ} , t_{QHS} , t_{HZ} , t_{PRE} etc.) are reported with respect to this reference load. This reference load is also used to report slew rate.

Output Driver Impedance

Output driver impedance is selected by a mode register during initialization. To achieve tighter tolerances, ZQ calibration is required. Output specifications refer to the default output drive unless specifically stated otherwise. The output driver impedance R_{ON} is defined by the value of the external reference resistor R_{ZQ} as follows:

$$R_{ONPU} = \frac{V_{DDQ} - V_{OUT}}{ABS(I_{OUT})}$$

When R_{ONPD} is turned off.

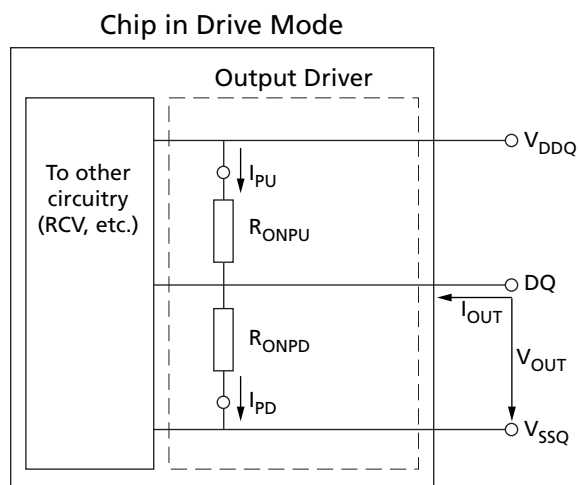


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Driver Impedance

$$R_{ONPD} = \frac{V_{OUT}}{ABS(I_{OUT})}$$

When R_{ONPU} is turned off.

Figure 148: Output Driver



Output Driver Impedance Characteristics with ZQ Calibration

Output driver impedance is defined by the value of the external reference resistor R_{ZQ} . Typical R_{ZQ} is 240 ohms.

Table 116: Output Driver DC Electrical Characteristics with ZQ Calibration

Notes 1–4 apply to all parameters and conditions

R_{ONnom}	Resistor	V_{OUT}	Min	Typ	Max	Unit	Notes
34.3Ω	R_{ON34PD}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/7$	
	R_{ON34PU}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/7$	
40.0Ω	R_{ON40PD}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/6$	
	R_{ON40PU}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/6$	
48.0Ω	R_{ON48PD}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/5$	
	R_{ON48PU}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/5$	
60.0Ω	R_{ON60PD}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/4$	
	R_{ON60PU}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/4$	
80.0Ω	R_{ON80PD}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/3$	
	R_{ON80PU}	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/3$	
120.0Ω	$R_{ON120PD}$	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/2$	
	$R_{ON120PU}$	$0.5 \times V_{DDQ}$	0.85	1.00	1.15	$R_{ZQ}/2$	
Mismatch between pull-up and pull-down	MM_{PUPD}		-15.00		+15.00	%	5

- Notes: 1. Applies across entire operating temperature range after calibration.
2. $R_{ZQ} = 240\Omega$.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Driver Impedance

- The tolerance limits are specified after calibration, with fixed voltage and temperature. For behavior of the tolerance limits if temperature or voltage changes after calibration, see Output Driver Temperature and Voltage Sensitivity.
- Pull-down and pull-up output driver impedances should be calibrated at $0.5 \times V_{DDQ}$.
- Measurement definition for mismatch between pull-up and pull-down, MM_{PUPD} : Measure R_{ONPU} and R_{ONPD} , both at $0.5 \times V_{DDQ}$:

$$MM_{PUPD} = \frac{R_{ONPU} - R_{ONPD}}{R_{ON,nom}} \times 100$$

For example, with $MM_{PUPD}(\text{MAX}) = 15\%$ and $R_{ONPD} = 0.85$, R_{ONPU} must be less than 1.0.

Output Driver Temperature and Voltage Sensitivity

If temperature and/or voltage change after calibration, the tolerance limits widen.

Table 117: Output Driver Sensitivity Definition

Resistor	V_{OUT}	Min	Max	Unit
R_{ONPD}	$0.5 \times V_{DDQ}$	$85 - (dR_{ONdT} \cdot \Delta T) - (dR_{ONdV} \cdot \Delta V)$	$115 + (dR_{ONdT} \cdot \Delta T) - (dR_{ONdV} \cdot \Delta V)$	%
R_{ONPU}				

- Notes:
- $\Delta T = T - T$ (at calibration). $\Delta V = V - V$ (at calibration).
 - dR_{ONdT} and dR_{ONdV} are not subject to production testing; they are verified by design and characterization.

Table 118: Output Driver Temperature and Voltage Sensitivity

Symbol	Parameter	Min	Max	Unit
R_{ONdT}	R_{ON} temperature sensitivity	0.00	0.75	%/°C
R_{ONdV}	R_{ON} voltage sensitivity	0.00	0.20	%/mV

Output Impedance Characteristics Without ZQ Calibration

Output driver impedance is defined by design and characterization as the default setting.

Table 119: Output Driver DC Electrical Characteristics Without ZQ Calibration

$R_{ON,nom}$	Resistor	V_{OUT}	Min	Typ	Max	Unit
34.3Ω	R_{ON34PD}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/7$
	R_{ON34PU}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/7$
40.0Ω	R_{ON40PD}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/6$
	R_{ON40PU}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/6$
48.0Ω	R_{ON48PD}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/5$
	R_{ON48PU}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/5$
60.0Ω	R_{ON60PD}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/4$
	R_{ON60PU}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/4$



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Driver Impedance

Table 119: Output Driver DC Electrical Characteristics Without ZQ Calibration (Continued)

$R_{ON_{nom}}$	Resistor	V_{OUT}	Min	Typ	Max	Unit
80.0Ω	R_{ON80PD}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/3$
	R_{ON80PU}	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/3$
120.0Ω	$R_{ON120PD}$	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/2$
	$R_{ON120PU}$	$0.5 \times V_{DDQ}$	0.70	1.00	1.30	$R_{ZQ}/2$

- Notes: 1. Applies across entire operating temperature range without calibration.
2. $R_{ZQ} = 240\Omega$.

Table 120: I-V Curves

Voltage (V)	$R_{ON} = 240\Omega (R_{ZQ})$							
	Pull-Down				Pull-Up			
	Current (mA) / R_{ON} (ohms)				Current (mA) / R_{ON} (ohms)			
	Default Value after ZQRESET		With Calibration		Default Value after ZQRESET		With Calibration	
	Min (mA)	Max (mA)	Min (mA)	Max (mA)	Min (mA)	Max (mA)	Min (mA)	Max (mA)
	Min (mA)	Max (mA)	Min (mA)	Max (mA)	Min (mA)	Max (mA)	Min (mA)	Max (mA)
0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00
0.05	0.19	0.32	0.21	0.26	-0.19	-0.32	-0.21	-0.26
0.10	0.38	0.64	0.40	0.53	-0.38	-0.64	-0.40	-0.53
0.15	0.56	0.94	0.60	0.78	-0.56	-0.94	-0.60	-0.78
0.20	0.74	1.26	0.79	1.04	-0.74	-1.26	-0.79	-1.04
0.25	0.92	1.57	0.98	1.29	-0.92	-1.57	-0.98	-1.29
0.30	1.08	1.86	1.17	1.53	-1.08	-1.86	-1.17	-1.53
0.35	1.25	2.17	1.35	1.79	-1.25	-2.17	-1.35	-1.79
0.40	1.40	2.46	1.52	2.03	-1.40	-2.46	-1.52	-2.03
0.45	1.54	2.74	1.69	2.26	-1.54	-2.74	-1.69	-2.26
0.50	1.68	3.02	1.86	2.49	-1.68	-3.02	-1.86	-2.49
0.55	1.81	3.30	2.02	2.72	-1.81	-3.30	-2.02	-2.72
0.60	1.92	3.57	2.17	2.94	-1.92	-3.57	-2.17	-2.94
0.65	2.02	3.83	2.32	3.15	-2.02	-3.83	-2.32	-3.15
0.70	2.11	4.08	2.46	3.36	-2.11	-4.08	-2.46	-3.36
0.75	2.19	4.31	2.58	3.55	-2.19	-4.31	-2.58	-3.55
0.80	2.25	4.54	2.70	3.74	-2.25	-4.54	-2.70	-3.74
0.85	2.30	4.74	2.81	3.91	-2.30	-4.74	-2.81	-3.91
0.90	2.34	4.92	2.89	4.05	-2.34	-4.92	-2.89	-4.05
0.95	2.37	5.08	2.97	4.23	-2.37	-5.08	-2.97	-4.23
1.00	2.41	5.20	3.04	4.33	-2.41	-5.20	-3.04	-4.33
1.05	2.43	5.31	3.09	4.44	-2.43	-5.31	-3.09	-4.44
1.10	2.46	5.41	3.14	4.52	-2.46	-5.41	-3.14	-4.52
1.15	2.48	5.48	3.19	4.59	-2.48	-5.48	-3.19	-4.59

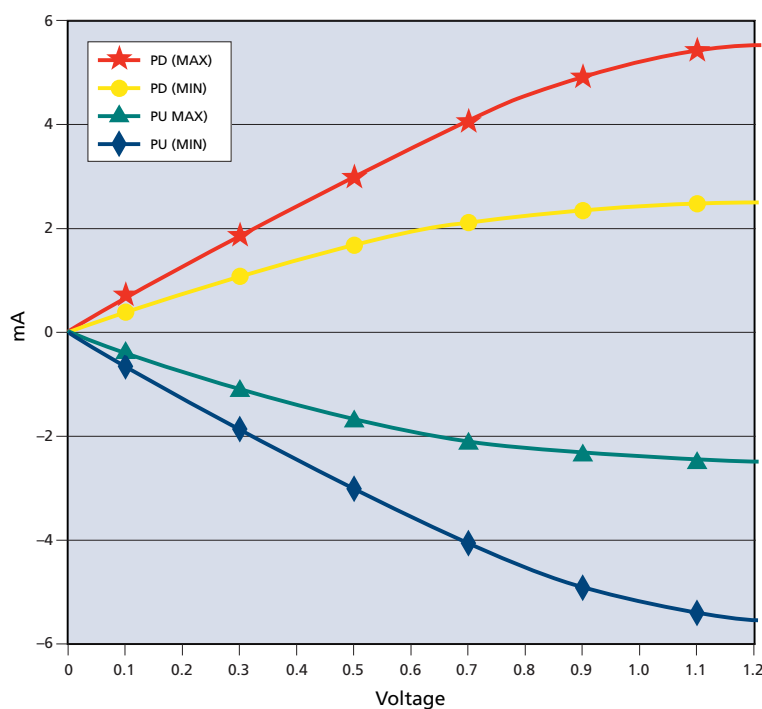


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Driver Impedance

Table 120: I-V Curves (Continued)

Voltage (V)	$R_{ON} = 240\Omega (R_{ZQ})$							
	Pull-Down				Pull-Up			
	Current (mA) / R_{ON} (ohms)				Current (mA) / R_{ON} (ohms)			
	Default Value after ZQRESET		With Calibration		Default Value after ZQRESET		With Calibration	
	Min (mA)	Max (mA)	Min (mA)	Max (mA)	Min (mA)	Max (mA)	Min (mA)	Max (mA)
1.20	2.50	5.55	3.23	4.65	-2.50	-5.55	-3.23	-4.65

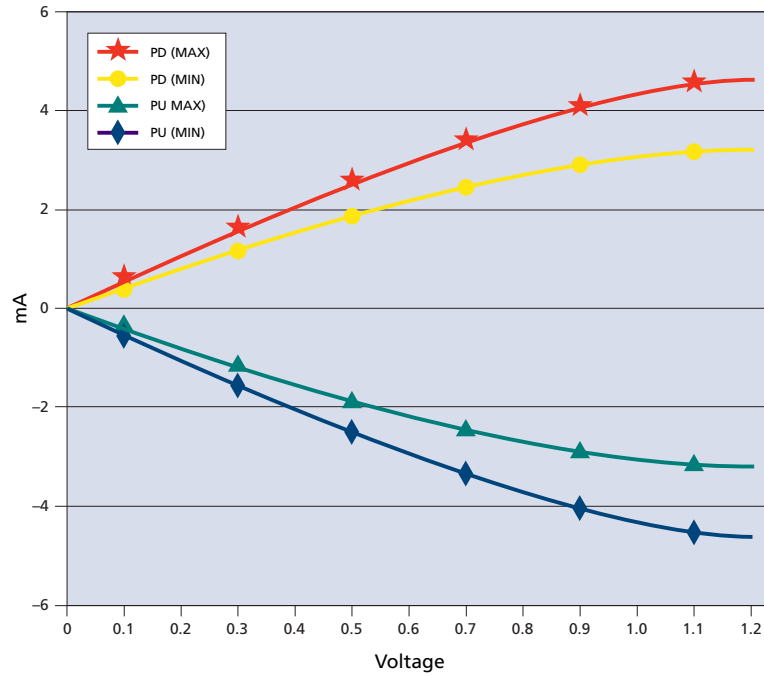
Figure 149: Output Impedance = 240 Ohms, I-V Curves After ZQRESET





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Output Driver Impedance

Figure 150: Output Impedance = 240 Ohms, I-V Curves After Calibration





Clock Specification

The specified clock jitter is a random jitter with Gaussian distribution. Input clocks violating minimum or maximum values may result in device malfunction.

Table 121: Definitions and Calculations

Symbol	Description	Calculation	Notes
$t_{CK(avg)}$ and n_{CK}	<p>The average clock period across any consecutive 200-cycle window. Each clock period is calculated from rising clock edge to rising clock edge.</p> <p>Unit $t_{CK(avg)}$ represents the actual clock average $t_{CK(avg)}$ of the input clock under operation. Unit n_{CK} represents one clock cycle of the input clock, counting from actual clock edge to actual clock edge.</p> <p>$t_{CK(avg)}$ can change no more than $\pm 1\%$ within a 100-clock-cycle window, provided that all jitter and timing specifications are met.</p>	$t_{CK(avg)} = \left(\sum_{j=1}^N t_{CKj} \right) / N$ <p>Where $N = 200$</p>	
$t_{CK(abs)}$	The absolute clock period, as measured from one rising clock edge to the next consecutive rising clock edge.		1
$t_{CH(avg)}$	The average HIGH pulse width, as calculated across any 200 consecutive HIGH pulses.	$t_{CH(avg)} = \left(\sum_{j=1}^N t_{CHj} \right) / (N \times t_{CK(avg)})$ <p>Where $N = 200$</p>	
$t_{CL(avg)}$	The average LOW pulse width, as calculated across any 200 consecutive LOW pulses.	$t_{CL(avg)} = \left(\sum_{j=1}^N t_{CLj} \right) / (N \times t_{CK(avg)})$ <p>Where $N = 200$</p>	
$t_{JIT(per)}$	The single-period jitter defined as the largest deviation of any signal t_{CK} from $t_{CK(avg)}$.	$t_{JIT(per)} = \min/\max \text{ of } \left(t_{CKi} - t_{CK(avg)} \right)$ <p>Where $i = 1 \text{ to } 200$</p>	1
$t_{JIT(per),act}$	The actual clock jitter for a given system.		
$t_{JIT(per),allowed}$	The specified clock period jitter allowance.		
$t_{JIT(cc)}$	The absolute difference in clock periods between two consecutive clock cycles. $t_{JIT(cc)}$ defines the cycle-to-cycle jitter.	$t_{JIT(cc)} = \max \text{ of } \left(t_{CK_{i+1}} - t_{CK_i} \right)$	1
$t_{ERR(nper)}$	The cumulative error across n multiple consecutive cycles from $t_{CK(avg)}$.	$t_{ERR(nper)} = \left(\sum_{j=i}^{i+n-1} t_{CKj} \right) - (n \times t_{CK(avg)})$	1
$t_{ERR(nper),act}$	The actual cumulative error over n cycles for a given system.		
$t_{ERR(nper),allowed}$	The specified cumulative error allowance over n cycles.		
$t_{ERR(nper),min}$	The minimum $t_{ERR(nper)}$.	$t_{ERR(nper),min} = (1 + 0.68LN(n)) \times t_{JIT(per),min}$	2



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Clock Period Jitter

Table 121: Definitions and Calculations (Continued)

Symbol	Description	Calculation	Notes
$t_{ERR(nper),max}$	The maximum $t_{ERR(nper)}$.	$t_{ERR(nper),max} = (1 + 0.68LN(n)) \times t_{JIT(per),max}$	2
$t_{JIT(duty)}$	Defined with absolute and average specifications for t_{CH} and t_{CL} , respectively.	$t_{JIT(duty),min} =$ $MIN((t_{CH(abs),min} - t_{CH(avg),min}),$ $(t_{CL(abs),min} - t_{CL(avg),min})) \times t_{CK(avg)}$ $t_{JIT(duty),max} =$ $MAX((t_{CH(abs),max} - t_{CH(avg),max}),$ $(t_{CL(abs),max} - t_{CL(avg),max})) \times t_{CK(avg)}$	

- Notes: 1. Not subject to production testing.
 2. Using these equations, $t_{ERR(nper)}$ tables can be generated for each $t_{JIT(per),act}$ value.

$t_{CK(abs)}$, $t_{CH(abs)}$, and $t_{CL(abs)}$

These parameters are specified with their average values; however, the relationship between the average timing and the absolute instantaneous timing (defined in the following table) is applicable at all times.

Table 122: $t_{CK(abs)}$, $t_{CH(abs)}$, and $t_{CL(abs)}$ Definitions

Parameter	Symbol	Minimum	Unit
Absolute clock period	$t_{CK(abs)}$	$t_{CK(avg),min} + t_{JIT(per),min}$	ps ¹
Absolute clock HIGH pulse width	$t_{CH(abs)}$	$t_{CH(avg),min} + t_{JIT(duty),min}^2/t_{CK(avg),min}$	$t_{CK(avg)}$
Absolute clock LOW pulse width	$t_{CL(abs)}$	$t_{CL(avg),min} + t_{JIT(duty),min}^2/t_{CK(avg),min}$	$t_{CK(avg)}$

- Notes: 1. $t_{CK(avg),min}$ is expressed in ps for this table.
 2. $t_{JIT(duty),min}$ is a negative value.

Clock Period Jitter

LPDDR2 devices can tolerate some clock period jitter without core timing parameter derating. This section describes device timing requirements with clock period jitter ($t_{JIT(per)}$) in excess of the values found in the AC Timing section. Calculating cycle time derating and clock cycle derating are also described.

Clock Period Jitter Effects on Core Timing Parameters

Core timing parameters (t_{RCD} , t_{RP} , t_{RTP} , t_{WR} , t_{WRA} , t_{WTR} , t_{RC} , t_{RAS} , t_{RRD} , t_{FAW}) extend across multiple clock cycles. Clock period jitter impacts these parameters when measured in numbers of clock cycles. Within the specification limits, the device is characterized and verified to support $n_{PARAM} = RU[t_{PARAM}/t_{CK(avg)}]$. During device operation where clock jitter is outside specification limits, the number of clocks or $t_{CK(avg)}$, may need to be increased based on the values for each core timing parameter.



Cycle Time Derating for Core Timing Parameters

For a given number of clocks (t_{nPARAM}), when $t_{CK(avg)}$ and $t_{ERR}(t_{nPARAM})_{act}$ exceed $t_{ERR}(t_{nPARAM})_{allowed}$, cycle time derating may be required for core timing parameters.

$$\text{CycleTimeDerating} = \max \left\{ \left[\frac{t_{PARAM} + t_{ERR}(t_{nPARAM})_{act} - t_{ERR}(t_{nPARAM})_{allowed}}{t_{nPARAM}} - t_{CK(avg)} \right], 0 \right\}$$

Cycle time derating analysis should be conducted for each core timing parameter. The amount of cycle time derating required is the maximum of the cycle time deratings determined for each individual core timing parameter.

Clock Cycle Derating for Core Timing Parameters

For each core timing parameter and a given number of clocks (t_{nPARAM}), clock cycle derating should be specified with $t_{JIT(per)}$.

For a given number of clocks (t_{nPARAM}), when $t_{CK(avg)}$ plus $t_{ERR}(t_{nPARAM})_{act}$ exceed the supported cumulative $t_{ERR}(t_{nPARAM})_{allowed}$, derating is required. If the equation below results in a positive value for a core timing parameter (t_{CORE}), the required clock cycle derating will be that positive value (in clocks).

$$\text{ClockCycleDerating} = RU \left\{ \frac{t_{PARAM} + t_{ERR}(t_{nPARAM})_{act} - t_{ERR}(t_{nPARAM})_{allowed}}{t_{CK(avg)}} \right\} - t_{nPARAM}$$

Cycle-time derating analysis should be conducted for each core timing parameter.

Clock Jitter Effects on Command/Address Timing Parameters

Command/address timing parameters (t_{IS} , t_{IH} , t_{ISCKE} , t_{IHCKE} , t_{ISb} , t_{IHb} , t_{ISCKEb} , t_{IHCKEb}) are measured from a command/address signal (CKE, CS, or CA[9:0]) transition edge to its respective clock signal (CK/CK#) crossing. The specification values are not affected by the $t_{JIT(per)}$ applied, because the setup and hold times are relative to the clock signal crossing that latches the command/address. Regardless of clock jitter values, these values must be met.

Clock Jitter Effects on READ Timing Parameters

t_{RPRE}

When the device is operated with input clock jitter, t_{RPRE} must be derated by the $t_{JIT(per)}_{act,max}$ of the input clock that exceeds $t_{JIT(per)}_{allowed,max}$. Output deratings are relative to the input clock:

$$t_{RPRE(min,derated)} = 0.9 - \left(\frac{t_{JIT(per)}_{act,max} - t_{JIT(per)}_{allowed,max}}{t_{CK(avg)}} \right)$$

For example, if the measured jitter into a LPDDR2-800 device has $t_{CK(avg)} = 2500ps$, $t_{JIT(per)}_{act,min} = -172ps$, and $t_{JIT(per)}_{act,max} = +193ps$, then $t_{RPRE,min,derated} = 0.9 - (t_{JIT(per)}_{act,max} - t_{JIT(per)}_{allowed,max}) / t_{CK(avg)} = 0.9 - (193 - 100) / 2500 = 0.8628 t_{CK(avg)}$.


 $t_{LZ}(DQ)$, $t_{HZ}(DQ)$, t_{DQSCK} , $t_{LZ}(DQS)$, $t_{HZ}(DQS)$

These parameters are measured from a specific clock edge to a data signal transition (DM_n or DQ_m , where: $n = 0, 1, 2$, or 3 ; and $m = DQ[31:0]$), and specified timings must be met with respect to that clock edge. Therefore, they are not affected by $t_{JIT}(per)$.

 t_{QSH} , t_{QSL}

These parameters are affected by duty cycle jitter, represented by $t_{CH}(abs)min$ and $t_{CL}(abs)min$. These parameters determine the absolute data valid window at the device pin. The absolute minimum data valid window at the device pin = $\min [(t_{QSH}(abs)min \times t_{CK}(avg)min - t_{DQSQ}max - t_{QHS}max), (t_{QSL}(abs)min \times t_{CK}(avg)min - t_{DQSQ}max - t_{QHS}max)]$. This minimum data valid window must be met at the target frequency regardless of clock jitter.

 t_{RPST}

t_{RPST} is affected by duty cycle jitter, represented by $t_{CL}(abs)$. Therefore, $t_{RPST}(abs)min$ can be specified by $t_{CL}(abs)min$. $t_{RPST}(abs)min = t_{CL}(abs)min - 0.05 = t_{QSL}(abs)min$.

Clock Jitter Effects on WRITE Timing Parameters
 t_{DS} , t_{DH}

These parameters are measured from a data signal (DM_n or DQ_m , where $n = 0, 1, 2, 3$; and $m = DQ[31:0]$) transition edge to its respective data strobe signal (DQS_n , $DQS_n\#$: $n = 0, 1, 2, 3$) crossing. The specification values are not affected by the amount of $t_{JIT}(per)$ applied because the setup and hold times are relative to the clock signal crossing that latches the command/address. Regardless of clock jitter values, these values must be met.

 t_{DSS} , t_{DSH}

These parameters are measured from a data strobe signal crossing (DQS_x , $DQS_x\#$) to its clock signal crossing ($CK/CK\#$). The specification values are not affected by the amount of $t_{JIT}(per)$ applied because the setup and hold times are relative to the clock signal crossing that latches the command/address. Regardless of clock jitter values, these values must be met.

 t_{DQSS}

t_{DQSS} is measured from the clock signal crossing ($CK/CK\#$) to the first latching data strobe signal crossing (DQS_x , $DQS_x\#$). When the device is operated with input clock jitter, this parameter must be derated by the actual $t_{JIT}(per)_{act}$ of the input clock in excess of $t_{JIT}(per)_{allowed}$.

$$t_{DQSS}(min, derated) = 0.75 - \left(\frac{t_{JIT}(per)_{act, min} - t_{JIT}(per)_{allowed, min}}{t_{CK}(avg)} \right)$$

$$t_{DQSS}(max, derated) = 1.25 - \left(\frac{t_{JIT}(per)_{act, max} - t_{JIT}(per)_{allowed, max}}{t_{CK}(avg)} \right)$$

For example, if the measured jitter into an LPDDR2-800 device has $t_{CK}(avg) = 2500ps$, $t_{JIT}(per)_{act, min} = -172ps$, and $t_{JIT}(per)_{act, max} = +193ps$, then:

$$t_{DQSS}(min, derated) = 0.75 - (t_{JIT}(per)_{act, min} - t_{JIT}(per)_{allowed, min}) / t_{CK}(avg) = 0.75 - (-172 + 100) / 2500 = 0.7788 \text{ } t_{CK}(avg), \text{ and}$$

$$t_{DQSS}(max, derated) = 1.25 - (t_{JIT}(per)_{act, max} - t_{JIT}(per)_{allowed, max}) / t_{CK}(avg) =$$



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Refresh Requirements

$$1.25 - (193 - 100)/2500 = 1.2128 \text{ } ^t\text{CK}(\text{avg}).$$

Refresh Requirements

Table 123: Refresh Requirement Parameters (Per Density)

Parameter		Symbol	64Mb	128Mb	256Mb	512Mb	1Gb	2Gb	4Gb	8Gb	Unit
Number of banks			4	4	4	4	8	8	8	8	
Refresh window: $T_{\text{CASE}} \leq 85^{\circ}$		$^t\text{REFW}$	32	32	32	32	32	32	32	32	ms
Refresh window: $85^{\circ}\text{C} < T_{\text{CASE}} \leq 105^{\circ}\text{C}$		$^t\text{REFW}$	8	8	8	8	8	8	8	8	ms
Refresh window: $105^{\circ}\text{C} < T_{\text{CASE}} \leq 125^{\circ}\text{C}$		$^t\text{REFW}$	8	8	8	8	8	8	8	8	ms
Required number of REFRESH commands (MIN)		R	2048	2048	4096	4096	4096	8192	8192	8192	
Average time between REFRESH commands (for reference only) $T_{\text{CASE}} \leq 85^{\circ}\text{C}$	REFab	$^t\text{REFI}$	15.6	15.6	7.8	7.8	7.8	3.9	3.9	3.9	μs
	REFpb	$^t\text{REFIpb}$	(REFpb not supported below 1Gb)				0.975	0.4875	0.4875	0.4875	μs
Average time between REFRESH commands (for reference only) $85^{\circ}\text{C} < T_{\text{CASE}} \leq 105^{\circ}\text{C}$	REFab	$^t\text{REFI}$	3.9	3.9	1.95	1.95	1.95	0.977	0.977	0.977	μs
	REFpb	$^t\text{REFIpb}$	(REFpb not supported below 1Gb)				0.244	0.122	0.122	0.122	μs
Average time between REFRESH commands (for reference only) $105^{\circ}\text{C} < T_{\text{CASE}} \leq 125^{\circ}\text{C}$	REFab	$^t\text{REFI}$	3.9	3.9	1.95	1.95	1.95	0.977	0.977	0.977	μs
	REFpb	$^t\text{REFIpb}$	(REFpb not supported below 1Gb)				0.244	0.122	0.122	0.122	μs
Refresh cycle time		$^t\text{RFCab}$	90	90	90	90	130	130	130	210	ns
Per-bank REFRESH cycle time		$^t\text{RFCpb}$	na				60	60	60	90	ns
Burst REFRESH window = $4 \times 8 \times ^t\text{RFCab}$		$^t\text{REFBW}$	2.88	2.88	2.88	2.88	4.16	4.16	4.16	6.72	μs



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC Timing

AC Timing

Table 124: AC Timing

Notes 1–2 apply to all parameters and conditions. AC timing parameters must satisfy the t_{CK} minimum conditions (in multiples of t_{CK}) as well as the timing specifications when values for both are indicated.

Parameter	Symbol	Min/ Max	t_{CK} Min	Data Rate							Unit	Notes
				1066	933	800	667	533	400	333		
Maximum frequency		–	–	533	466	400	333	266	200	166	MHz	
Clock Timing												
Average clock period	$t_{CK}(avg)$	MIN	–	1.875	2.15	2.5	3	3.75	5	6	ns	
		MAX	–	100	100	100	100	100	100	100		
Average HIGH pulse width	$t_{CH}(avg)$	MIN	–	0.45	0.45	0.45	0.45	0.45	0.45	0.45	t_{CK} (avg)	
		MAX	–	0.55	0.55	0.55	0.55	0.55	0.55	0.55		
Average LOW pulse width	$t_{CL}(avg)$	MIN	–	0.45	0.45	0.45	0.45	0.45	0.45	0.45	t_{CK} (avg)	
		MAX	–	0.55	0.55	0.55	0.55	0.55	0.55	0.55		
Absolute clock period	$t_{CK}(abs)$	MIN	–	$t_{CK}(avg)_{min} \pm t_{JIT(per)}_{min}$							ps	
Absolute clock HIGH pulse width	$t_{CH}(abs)$	MIN	–	0.43	0.43	0.43	0.43	0.43	0.43	0.43	t_{CK} (avg)	
		MAX	–	0.57	0.57	0.57	0.57	0.57	0.57	0.57		
Absolute clock LOW pulse width	$t_{CL}(abs)$	MIN	–	0.43	0.43	0.43	0.43	0.43	0.43	0.43	t_{CK} (avg)	
		MAX	–	0.57	0.57	0.57	0.57	0.57	0.57	0.57		
Clock period jitter (with supported jitter)	$t_{JIT(per)}$, allowed	MIN	–	–90	–95	–100	–110	–120	–140	–150	ps	
		MAX	–	90	95	100	110	120	140	150		
Maximum clock jitter between two consecutive clock cycles (with supported jitter)	$t_{JIT(cc)}$, allowed	MAX	–	180	190	200	220	240	280	300	ps	
Duty cycle jitter (with supported jitter)	$t_{JIT(duty)}$, allowed	MIN	–	MIN ($(t_{CH}(abs)_{min} - t_{CH}(avg)_{min})$, $(t_{CL}(abs)_{min} - t_{CL}(avg)_{min}) \times t_{CK}(avg)$)							ps	
		MAX	–	MAX ($(t_{CH}(abs)_{max} - t_{CH}(avg)_{max})$, $(t_{CL}(abs)_{max} - t_{CL}(avg)_{max}) \times t_{CK}(avg)$)								
Cumulative errors across 2 cycles	$t_{ERR(2per)}$, allowed	MIN	–	–132	–140	–147	–162	–177	–206	–221	ps	
		MAX	–	132	140	147	162	177	206	221		
Cumulative errors across 3 cycles	$t_{ERR(3per)}$, allowed	MIN	–	–157	–166	–175	–192	–210	–245	–262	ps	
		MAX	–	157	166	175	192	210	245	262		
Cumulative errors across 4 cycles	$t_{ERR(4per)}$, allowed	MIN	–	–175	–185	–194	–214	–233	–272	–291	ps	
		MAX	–	175	185	194	214	233	272	291		
Cumulative errors across 5 cycles	$t_{ERR(5per)}$, allowed	MIN	–	–188	–199	–209	–230	–251	–293	–314	ps	
		MAX	–	188	199	209	230	251	293	314		
Cumulative errors across 6 cycles	$t_{ERR(6per)}$, allowed	MIN	–	–200	–211	–222	–244	–266	–311	–333	ps	
		MAX	–	200	211	222	244	266	311	333		
Cumulative errors across 7 cycles	$t_{ERR(7per)}$, allowed	MIN	–	–209	–221	–232	–256	–279	–325	–348	ps	
		MAX	–	209	221	232	256	279	325	348		



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC Timing

Table 124: AC Timing (Continued)

Notes 1–2 apply to all parameters and conditions. AC timing parameters must satisfy the t_{CK} minimum conditions (in multiples of t_{CK}) as well as the timing specifications when values for both are indicated.

Parameter	Symbol	Min/ Max	tCK Min	Data Rate							Unit	Notes
				1066	933	800	667	533	400	333		
Cumulative errors across 8 cycles	tERR(8per), allowed	MIN	–	–217	–229	–241	–266	–290	–338	–362	ps	
		MAX	–	217	229	241	266	290	338	362		
Cumulative errors across 9 cycles	tERR(9per), allowed	MIN	–	–224	–237	–249	–274	–299	–349	–374	ps	
		MAX	–	224	237	249	274	299	349	374		
Cumulative errors across 10 cycles	tERR(10per), allowed	MIN	–	–231	–244	–257	–282	–308	–359	–385	ps	
		MAX	–	231	244	257	282	308	359	385		
Cumulative errors across 11 cycles	tERR(11per), allowed	MIN	–	–237	–250	–263	–289	–316	–368	–395	ps	
		MAX	–	237	250	263	289	316	368	395		
Cumulative errors across 12 cycles	tERR(12per), allowed	MIN	–	–242	–256	–269	–296	–323	–377	–403	ps	
		MAX	–	242	256	269	296	323	377	403		
Cumulative errors across $n = 13, 14, 15 \dots, 49, 50$ cycles	tERR(nper), allowed	MIN	tERR(nper),allowed,min = $(1 + 0.68\ln(n)) \times$ tJIT(per),allowed,min								ps	
		MAX	tERR(nper), allowed,max = $(1 + 0.68\ln(n)) \times$ tJIT(per),allowed,max									
ZQ Calibration Parameters												
Initialization calibration time	tZQINIT	MIN	–	1	1	1	1	1	1	1	μs	
Long calibration time	tZQCL	MIN	6	360	360	360	360	360	360	360	ns	
Short calibration time	tZQCS	MIN	6	90	90	90	90	90	90	90	ns	
Calibration RESET time	tZQRESET	MIN	3	50	50	50	50	50	50	50	ns	
READ Parameters ³												
DQS output access time from CK/CK#	tDQSCK	MIN	–	2500	2500	2500	2500	2500	2500	2500	ps	
		MAX	–	5500	5500	5500	5500	5500	5500	5500		
DQSCK delta short	tDQSCKDS	MAX	–	330	380	450	540	670	900	1080	ps	4
DQSCK delta medium	tDQSCKDM	MAX	–	680	780	900	1050	1350	1800	1900	ps	5
DQSCK delta long	tDQSCKDL	MAX	–	920	1050	1200	1400	1800	2400	–	ps	6
DQS-DQ skew	tDQSQ	MAX	–	200	220	240	280	340	400	500	ps	
Data-hold skew factor	tQHS	MAX	–	230	260	280	340	400	480	600	ps	
DQS output HIGH pulse width	tQSH	MIN	–	tCH(abs) - 0.05							tCK (avg)	
DQS output LOW pulse width	tQSL	MIN	–	tCL(abs) - 0.05							tCK (avg)	
Data half period	tQHP	MIN	–	MIN (tQSH, tQSL)							tCK (avg)	
DQ/DQS output hold time from DQS	tQH	MIN	–	tQHP - tQHS							ps	



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC Timing

Table 124: AC Timing (Continued)

Notes 1–2 apply to all parameters and conditions. AC timing parameters must satisfy the t_{CK} minimum conditions (in multiples of t_{CK}) as well as the timing specifications when values for both are indicated.

Parameter	Symbol	Min/ Max	^t CK Min	Data Rate							Unit	Notes
				1066	933	800	667	533	400	333		
READ preamble	^t RPRE	MIN	–	0.9	0.9	0.9	0.9	0.9	0.9	0.9	^t CK (avg)	7
READ postamble	^t RPST	MIN	–	^t CL(abs) - 0.05							^t CK (avg)	8
DQS Low-Z from clock	^t LZ(DQS)	MIN	–	^t DQSCK (MIN) - 300							ps	
DQ Low-Z from clock	^t LZ(DQ)	MIN	–	^t DQSCK(MIN) - (1.4 × ^t QH5(MAX))							ps	
DQS High-Z from clock	^t HZ(DQS)	MAX	–	^t DQSCK (MAX) - 100							ps	
DQ High-Z from clock	^t HZ(DQ)	MAX	–	^t DQSCK(MAX) + (1.4 × ^t DQSQ(MAX))							ps	
WRITE Parameters ³												
DQ and DM input hold time (V _{REF} based)	^t DH	MIN	–	210	235	270	350	430	480	600	ps	
DQ and DM input setup time (V _{REF} based)	^t DS	MIN	–	210	235	270	350	430	480	600	ps	
DQ and DM input pulse width	^t DIPW	MIN	–	0.35	0.35	0.35	0.35	0.35	0.35	0.35	^t CK (avg)	
Write command to first DQS latching transition	^t DQSS	MIN	–	0.75	0.75	0.75	0.75	0.75	0.75	0.75	^t CK (avg)	
		MAX	–	1.25	1.25	1.25	1.25	1.25	1.25	1.25	^t CK (avg)	
DQS input high-level width	^t DQSH	MIN	–	0.4	0.4	0.4	0.4	0.4	0.4	0.4	^t CK (avg)	
DQS input low-level width	^t DQSL	MIN	–	0.4	0.4	0.4	0.4	0.4	0.4	0.4	^t CK (avg)	
DQS falling edge to CK setup time	^t DSS	MIN	–	0.2	0.2	0.2	0.2	0.2	0.2	0.2	^t CK (avg)	
DQS falling edge hold time from CK	^t DSH	MIN	–	0.2	0.2	0.2	0.2	0.2	0.2	0.2	^t CK (avg)	
Write postamble	^t WPST	MIN	–	0.4	0.4	0.4	0.4	0.4	0.4	0.4	^t CK (avg)	
Write preamble	^t WPRE	MIN	–	0.35	0.35	0.35	0.35	0.35	0.35	0.35	^t CK (avg)	
CKE Input Parameters												
CKE minimum pulse width (HIGH and LOW pulse width)	^t CKE	MIN	3	3	3	3	3	3	3	3	^t CK (avg)	
CKE input setup time	^t ISCKE	MIN	–	0.25	0.25	0.25	0.25	0.25	0.25	0.25	^t CK (avg)	9
CKE input hold time	^t IHCKE	MIN	–	0.25	0.25	0.25	0.25	0.25	0.25	0.25	^t CK (avg)	10



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC Timing

Table 124: AC Timing (Continued)

Notes 1–2 apply to all parameters and conditions. AC timing parameters must satisfy the t_{CK} minimum conditions (in multiples of t_{CK}) as well as the timing specifications when values for both are indicated.

Parameter	Symbol	Min/ Max	tCK Min	Data Rate							Unit	Notes
				1066	933	800	667	533	400	333		
Command Address Input Parameters ³												
Address and control input setup time	t ⁱ IS	MIN	–	220	250	290	370	460	600	740	ps	11
Address and control input hold time	t ⁱ IH	MIN	–	220	250	290	370	460	600	740	ps	11
Address and control input pulse width	t ⁱ IPW	MIN	–	0.40	0.40	0.40	0.40	0.40	0.40	0.40	t ⁱ CK (avg)	
Boot Parameters (10 MHz–55 MHz) ^{12, 13, 14}												
Clock cycle time	t ⁱ CKb	MAX	–	100	100	100	100	100	100	100	ns	
		MIN	–	18	18	18	18	18	18	18		
CKE input setup time	t ⁱ ISCKEb	MIN	–	2.5	2.5	2.5	2.5	2.5	2.5	2.5	ns	
CKE input hold time	t ⁱ IHCKEb	MIN	–	2.5	2.5	2.5	2.5	2.5	2.5	2.5	ns	
Address and control input setup time	t ⁱ ISb	MIN	–	1150	1150	1150	1150	1150	1150	1150	ps	
Address and control input hold time	t ⁱ IHb	MIN	–	1150	1150	1150	1150	1150	1150	1150	ps	
DQS output data access time from CK/CK#	t ⁱ DQSCKb	MIN	–	2.0	2.0	2.0	2.0	2.0	2.0	2.0	ns	
		MAX	–	10.0	10.0	10.0	10.0	10.0	10.0	10.0		
Data strobe edge to output data edge	t ⁱ DQSQb	MAX	–	1.2	1.2	1.2	1.2	1.2	1.2	1.2	ns	
Data hold skew factor	t ⁱ QHSb	MAX	–	1.2	1.2	1.2	1.2	1.2	1.2	1.2	ns	
Mode Register Parameters												
MODE REGISTER WRITE command period	t ⁱ MRW	MIN	5	5	5	5	5	5	5	5	t ⁱ CK (avg)	
MODE REGISTER READ command period	t ⁱ MRR	MIN	2	2	2	2	2	2	2	2	t ⁱ CK (avg)	
Core Parameters ¹⁵												
READ latency	RL	MIN	3	8	7	6	5	4	3	3	t ⁱ CK (avg)	
WRITE latency	WL	MIN	1	4	4	3	2	2	1	1	t ⁱ CK (avg)	
ACTIVATE-to-ACTIVATE command period	t ⁱ RC	MIN	–	t ⁱ RAS + t ⁱ RPab (with all-bank precharge), t ⁱ RAS + t ⁱ RPpb (with per-bank precharge)							ns	17
CKE minimum pulse width during SELF REFRESH (low pulse width during SELF REFRESH)	t ⁱ CKESR	MIN	3	15	15	15	15	15	15	15	ns	
SELF REFRESH exit to next valid command delay	t ⁱ XSR	MIN	2	t ⁱ RFCab + 10							ns	



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP AC Timing

Table 124: AC Timing (Continued)

Notes 1–2 apply to all parameters and conditions. AC timing parameters must satisfy the t_{CK} minimum conditions (in multiples of t_{CK}) as well as the timing specifications when values for both are indicated.

Parameter	Symbol	Min/ Max	t_{CK} Min	Data Rate							Unit	Notes
				1066	933	800	667	533	400	333		
Exit power-down to next valid command delay	t_{XP}	MIN	2	7.5	7.5	7.5	7.5	7.5	7.5	7.5	ns	
CAS-to-CAS delay	t_{CCD}	MIN	2	2	2	2	2	2	2	2	t_{CK} (avg)	
Internal READ to PRECHARGE command delay	t_{RTP}	MIN	2	7.5	7.5	7.5	7.5	7.5	7.5	7.5	ns	
RAS-to-CAS delay	t_{RCD}	MIN	3	18	18	18	18	18	18	18	ns	
Row precharge time (single bank)	t_{RPpb}	MIN	3	18	18	18	18	18	18	18	ns	
Row precharge time (all banks)	t_{RPab} 4-bank	MIN	3	18	18	18	18	18	18	18	ns	
Row precharge time (all banks)	t_{RPab} 8-bank	MIN	3	21	21	21	21	21	21	21	ns	
Row active time	t_{RAS}	MIN	3	42	42	42	42	42	42	42	ns	17
		MAX	–	70	70	70	70	70	70	70	μs	
WRITE recovery time	t_{WR}	MIN	3	15	15	15	15	15	15	15	ns	
Internal WRITE-to-READ command delay	t_{WTR}	MIN	2	7.5	7.5	7.5	7.5	7.5	10	10	ns	
Active bank <i>a</i> to active bank <i>b</i>	t_{RRD}	MIN	2	10	10	10	10	10	10	10	ns	
Four-bank activate window	t_{FAW}	MIN	8	50	50	50	50	50	50	60	ns	
Minimum deep power-down time	t_{DPD}	MIN	–	500	500	500	500	500	500	500	μs	
Temperature Derating¹⁶												
t_{DQSCK} derating	t_{DQSCK} (derated)	MAX	–	5620	6000	6000	6000	6000	6000	6000	ps	
Core timing temperature derating	t_{RCD} (derated)	MIN	–	$t_{RCD} + 1.875$							ns	
	t_{RC} (derated)	MIN	–	$t_{RC} + 1.875$							ns	
	t_{RAS} (derated)	MIN	–	$t_{RAS} + 1.875$							ns	
	t_{RP} (derated)	MIN	–	$t_{RP} + 1.875$							ns	
	t_{RRD} (derated)	MIN	–	$t_{RRD} + 1.875$							ns	

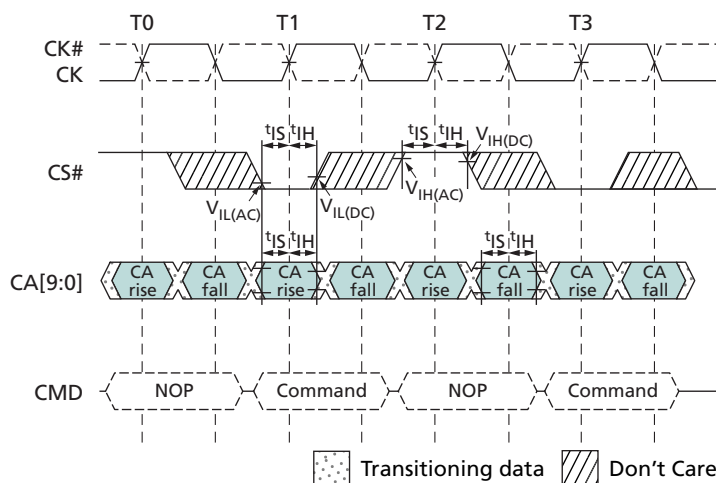
- Notes:
1. Frequency values are for reference only. Clock cycle time (t_{CK}) is used to determine device capabilities.
 2. All AC timings assume an input slew rate of 1 V/ns.
 3. READ, WRITE, and input setup and hold values are referenced to V_{REF} .



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP CA and CS# Setup, Hold, and Derating

14. The output skew parameters are measured with default output impedance settings using the reference load.
15. The minimum t_{CK} column applies only when t_{CK} is greater than 6ns.
16. Timing derating applies for operation at 85°C to 105°C when the requirement to derate is indicated by mode register 4 op-code (see the MR4 Device Temperature (MA[7:0] = 04h) table).
17. DRAM devices should be evenly addressed when being accessed. Disproportionate accesses to a particular row address may result in reduction of the product lifetime and/or reduction in data retention ability.

Figure 151: Command Input Setup and Hold Timing



- Notes:
1. The setup and hold timing shown applies to all commands.
 2. Setup and hold conditions also apply to the CKE pin. For timing diagrams related to the CKE pin, see Power-Down.

CA and CS# Setup, Hold, and Derating

For all input signals (CA and CS#), the total required setup time (t_{IS}) and hold time (t_{IH}) is calculated by adding the data sheet t_{IS} (base) and t_{IH} (base) values to the Δt_{IS} and Δt_{IH} derating values, respectively. Example: t_{IS} (total setup time) = $t_{IS}(\text{base}) + \Delta t_{IS}$. (See the series of tables following this section.)

The typical setup slew rate (t_{IS}) for a rising signal is defined as the slew rate between the last crossing of $V_{REF(DC)}$ and the first crossing of $V_{IH(AC)min}$. The typical setup slew rate for a falling signal is defined as the slew rate between the last crossing of $V_{REF(DC)}$ and the first crossing of $V_{IL(AC)max}$. If the actual signal is consistently earlier than the typical slew rate line between the shaded $V_{REF(DC)}$ -to-(AC) region, use the typical slew rate for the derating value (see the Typical Slew Rate and $V_{AC} - t_{IS}$ for CA and CS# Relative to Clock figure). If the actual signal is later than the typical slew rate line anywhere between the shaded $V_{REF(DC)}$ -to-AC region, the slew rate of a tangent line to the actual signal from the AC level to the DC level is used for the derating value (see the Tangent Line - t_{IS} for CA and CS# Relative to Clock figure).

The hold (t_{IH}) typical slew rate for a rising signal is defined as the slew rate between the last crossing of $V_{IL(DC)max}$ and the first crossing of $V_{REF(DC)}$. The hold (t_{IH}) typical slew rate for a falling signal is defined as the slew rate between the last crossing of $V_{IH(DC)min}$



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP CA and CS# Setup, Hold, and Derating

and the first crossing of $V_{REF(DC)}$. If the actual signal is consistently later than the typical slew rate line between the shaded DC-to- $V_{REF(DC)}$ region, use the typical slew rate for the derating value (see the Typical Slew Rate – t_{IH} for CA and CS# Relative to Clock figure). If the actual signal is earlier than the typical slew rate line anywhere between the shaded DC-to- $V_{REF(DC)}$ region, the slew rate of a tangent line to the actual signal from the DC level to $V_{REF(DC)}$ level is used for the derating value (see the Tangent Line – t_{IH} for CA and CS# Relative to Clock figure).

For a valid transition, the input signal must remain above or below $V_{IH}/V_{IL(AC)}$ for a specified time, t_{VAC} (see the Required Time for Valid Transition – $t_{VAC} > V_{IH(AC)}$ and $< V_{IL(AC)}$ table).

For slow slew rates the total setup time could be a negative value (that is, a valid input signal will not have reached $V_{IH}/V_{IL(AC)}$ at the time of the rising clock transition). A valid input signal is still required to complete the transition and reach $V_{IH}/V_{IL(AC)}$.

For slew rates between the values listed in the AC220 table, the derating values are obtained using linear interpolation. Slew rate values are not typically subject to production testing. They are verified by design and characterization.

Table 125: CA and CS# Setup and Hold Base Values (>400 MHz, 1 V/ns Slew Rate)

Parameter	Data Rate						Reference
	1066	933	800	667	533	466	
t_{IS} (base)	0	30	70	150	240	300	$V_{IH}/V_{IL(AC)} = V_{REF(DC)} \pm 220mV$
t_{IH} (base)	90	120	160	240	330	390	$V_{IH}/V_{IL(DC)} = V_{REF(DC)} \pm 130mV$

Note: 1. AC/DC referenced for 1 V/ns CA and CS# slew rate, and 2 V/ns differential CK/CK# slew rate.

Table 126: CA and CS# Setup and Hold Base Values (<400 MHz, 1 V/ns Slew Rate)

Parameter	Data Rate				Reference
	400	333	255	200	
t_{IS} (base)	300	440	600	850	$V_{IH}/V_{IL(AC)} = V_{REF(DC)} \pm 300mV$
t_{IH} (base)	400	540	700	950	$V_{IH}/V_{IL(DC)} = V_{REF(DC)} \pm 200mV$

Note: 1. AC/DC referenced for 1 V/ns CA and CS# slew rate, and 2 V/ns differential CK/CK# slew rate.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP CA and CS# Setup, Hold, and Derating

Table 127: Derating Values for AC/DC-Based t_{IS}/t_{IH} (AC220)
 Δt_{IS} , Δt_{IH} derating in ps

		CK, CK# Differential Slew Rate															
		4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
		Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}
CA, CS# slew rate V/ns	2.0	110	65	110	65	110	65										
	1.5	74	43	73	43	73	43	89	59								
	1.0	0	0	0	0	0	0	16	16	32	32						
	0.9			-3	-5	-3	-5	13	11	29	27	45	43				
	0.8					-8	-13	8	3	24	19	40	35	56	55		
	0.7							2	-6	18	10	34	26	50	46	66	78
	0.6									10	-3	26	13	42	33	58	65
	0.5											4	-4	20	16	36	48
	0.4													-7	2	17	34

Note: 1. Shaded cells are not supported.

Table 128: Derating Values for AC/DC-Based t_{IS}/t_{IH} (AC300)
 Δt_{IS} , Δt_{IH} derating in ps

		CK, CK# Differential Slew Rate															
		4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
		Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}
CA, CS# slew rate V/ns	2.0	150	100	150	100	150	100										
	1.5	100	67	100	67	100	67	116	83								
	1.0	0	0	0	0	0	0	16	16	32	32						
	0.9			-4	-8	-4	-8	12	8	28	24	44	40				
	0.8					-12	-20	4	-4	20	12	36	28	52	48		
	0.7							-3	-18	13	-2	29	14	45	34	61	66
	0.6									2	-21	18	-5	34	15	50	47
	0.5											-12	-32	4	-12	20	20
	0.4													-35	-40	-11	-8

Note: 1. Shaded cells are not supported.

Table 129: Required Time for Valid Transition – $t_{VAC} > V_{IH(AC)}$ and $< V_{IL(AC)}$

Slew Rate (V/ns)	t_{VAC} at 300mV (ps)		t_{VAC} at 220mV (ps)	
	Min	Max	Min	Max
>2.0	75	–	175	–
2.0	57	–	170	–
1.5	50	–	167	–
1.0	38	–	163	–

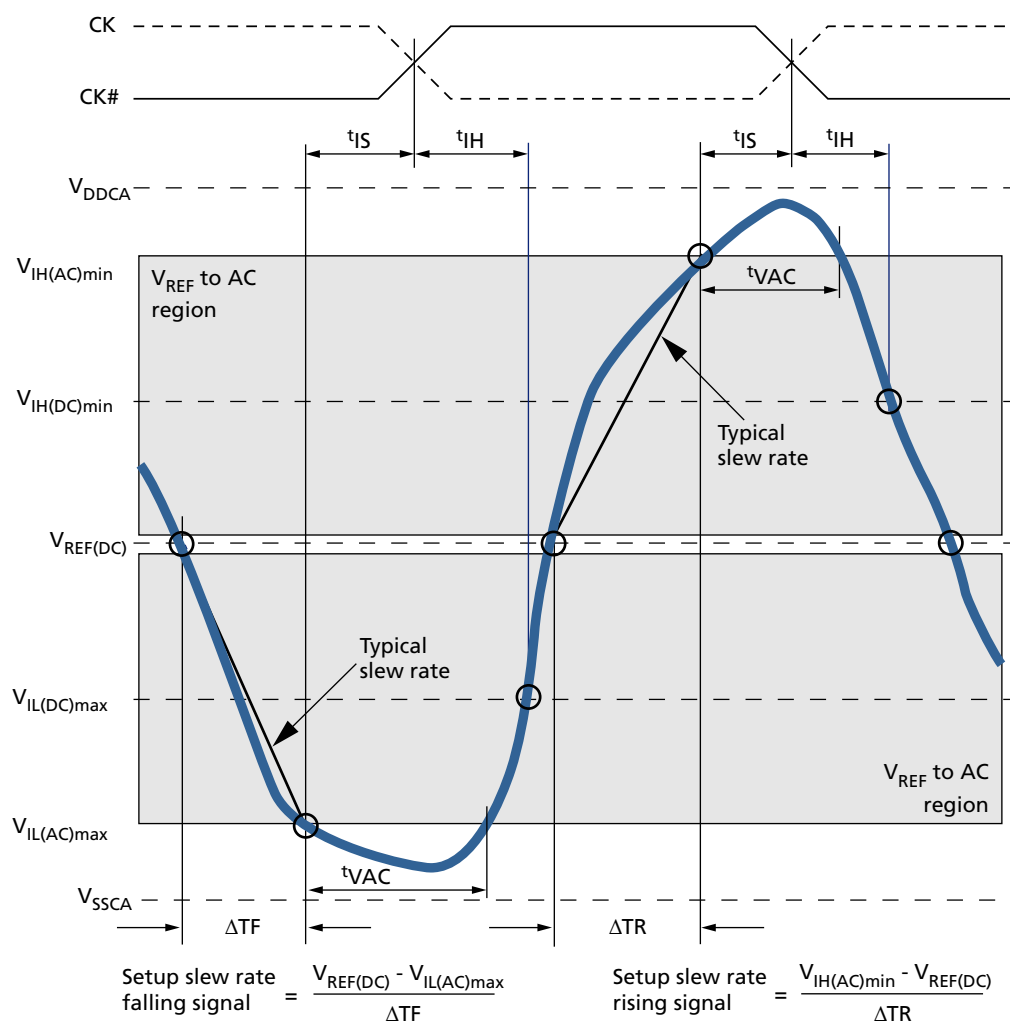


4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP CA and CS# Setup, Hold, and Derating

Table 129: Required Time for Valid Transition – $t_{VAC} > V_{IH(AC)}$ and $< V_{IL(AC)}$ (Continued)

Slew Rate (V/ns)	t_{VAC} at 300mV (ps)		t_{VAC} at 220mV (ps)	
	Min	Max	Min	Max
0.9	34	–	162	–
0.8	29	–	161	–
0.7	22	–	159	–
0.6	13	–	155	–
0.5	0	–	150	–
<0.5	0	–	150	–

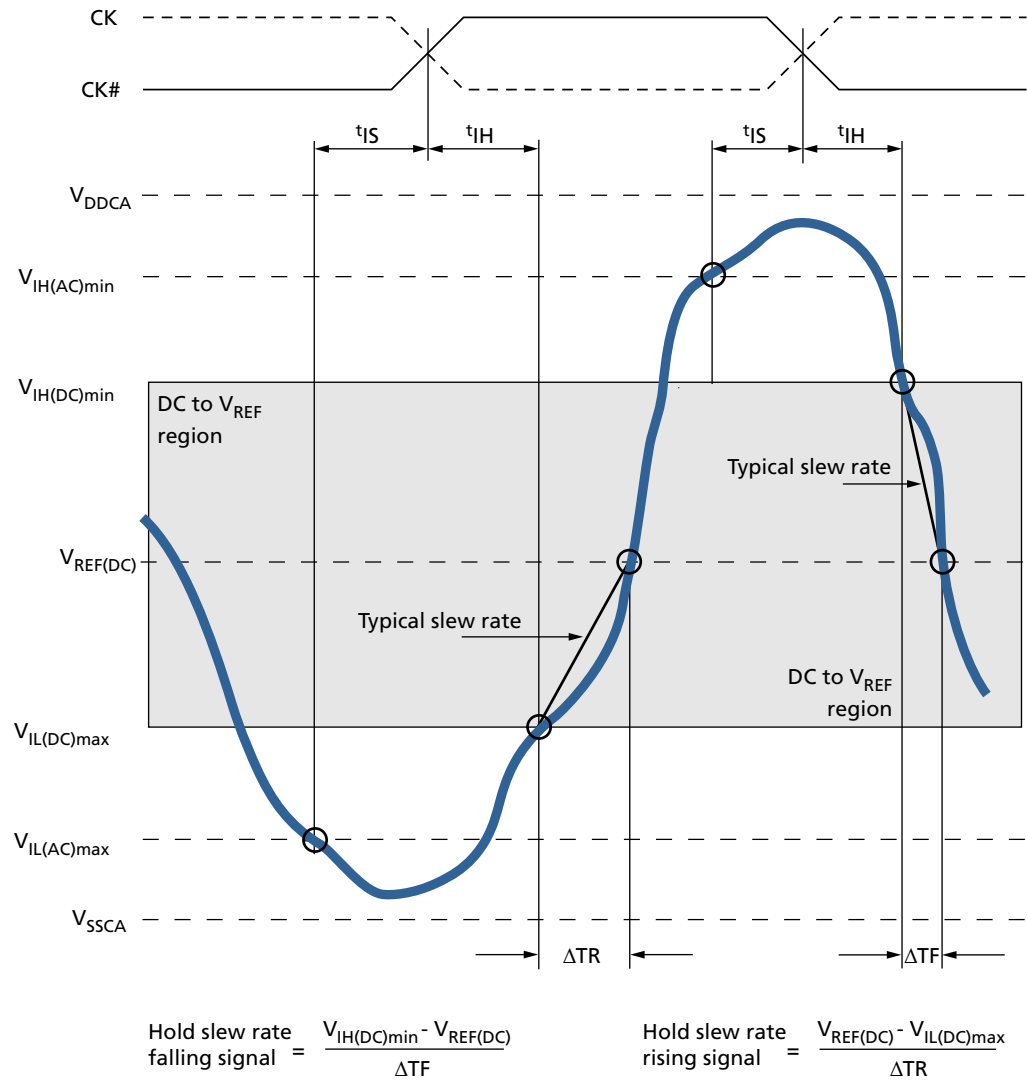
Figure 152: Typical Slew Rate and t_{VAC} – t_{IS} for CA and CS# Relative to Clock





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP CA and CS# Setup, Hold, and Derating

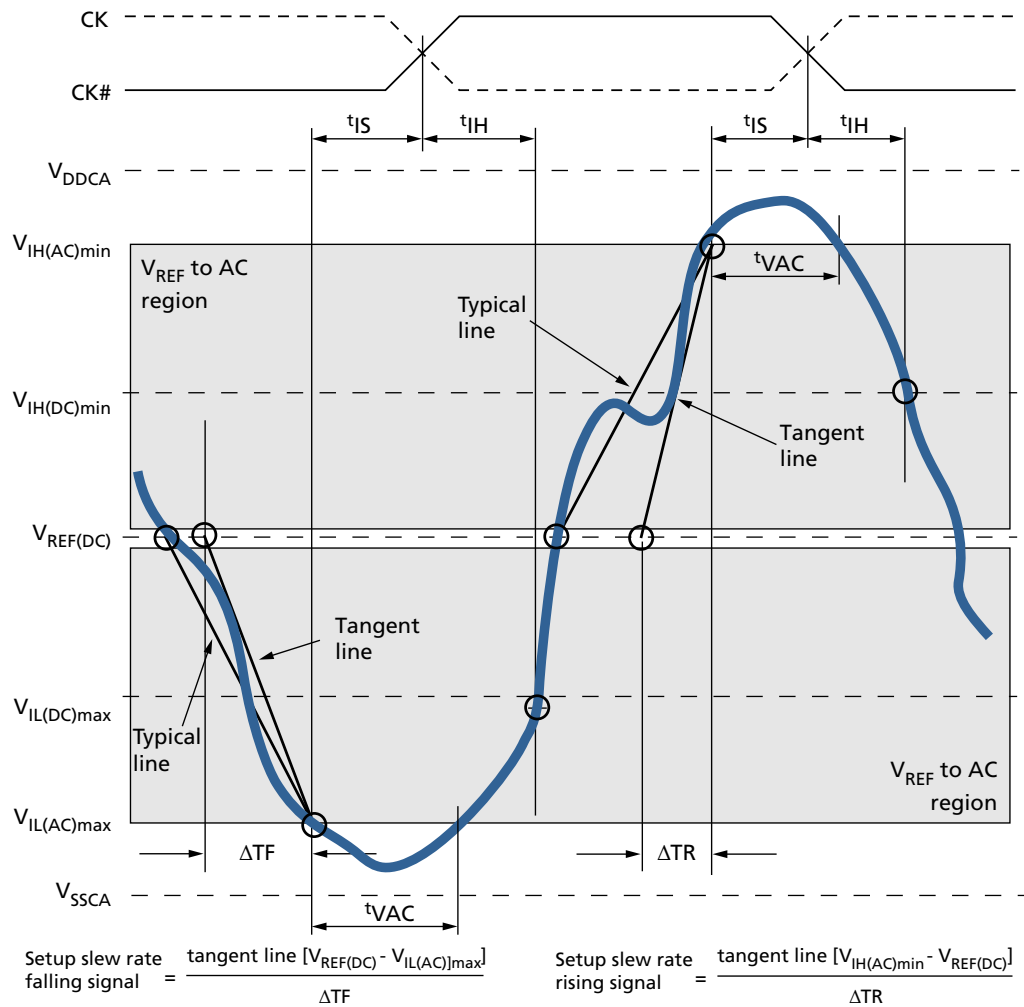
Figure 153: Typical Slew Rate – t_{IH} for CA and CS# Relative to Clock





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP CA and CS# Setup, Hold, and Derating

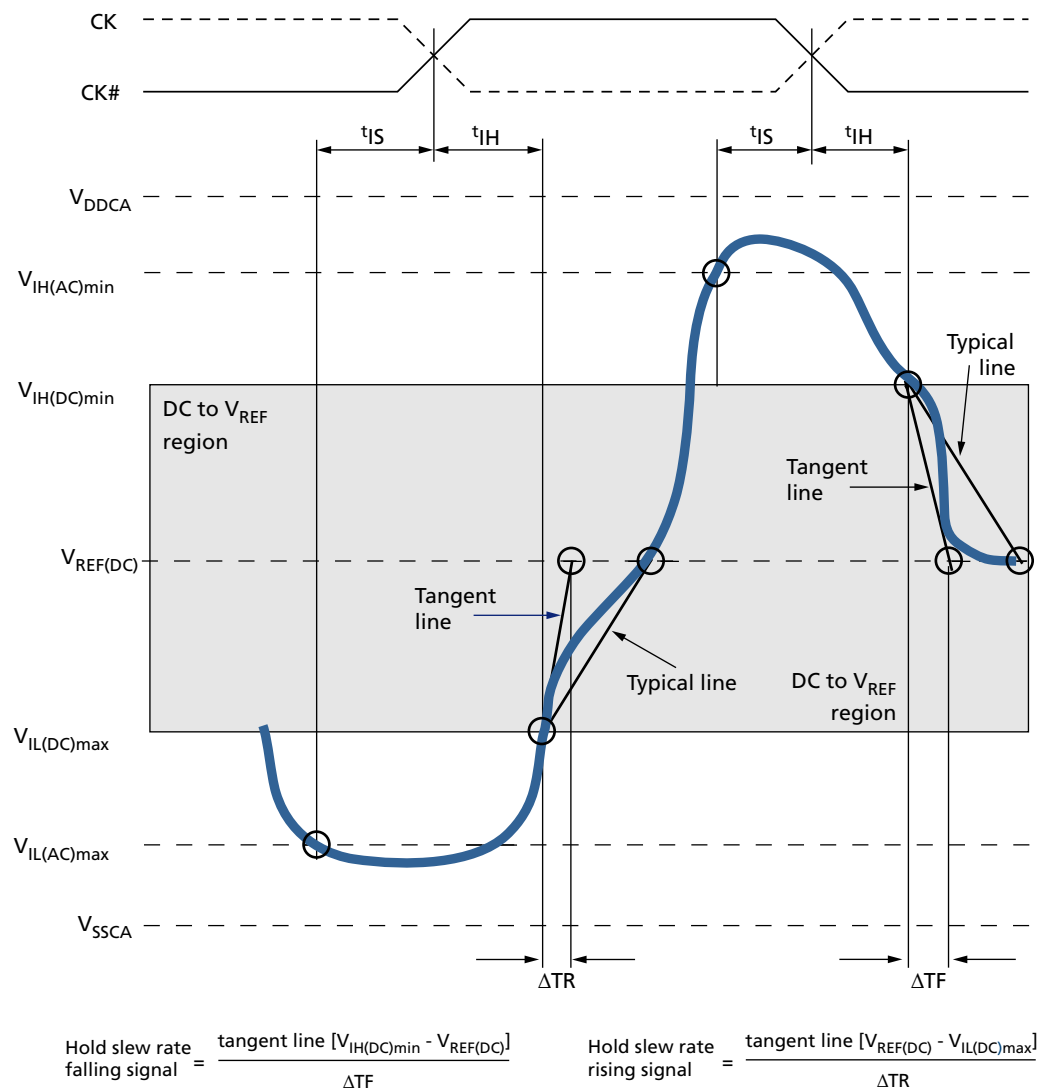
Figure 154: Tangent Line – t_{IS} for CA and CS# Relative to Clock





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP CA and CS# Setup, Hold, and Derating

Figure 155: Tangent Line – t_{IH} for CA and CS# Relative to Clock





Data Setup, Hold, and Slew Rate Derating

For all input signals (DQ, DM) calculate the total required setup time (t_{DS}) and hold time (t_{DH}) by adding the data sheet $t_{DS}(\text{base})$ and $t_{DH}(\text{base})$ values (see the following table) to the Δt_{DS} and Δt_{DH} derating values, respectively (see the following derating tables). Example: $t_{DS} = t_{DS}(\text{base}) + \Delta t_{DS}$.

The typical t_{DS} slew rate for a rising signal is defined as the slew rate between the last crossing of $V_{REF(DC)}$ and the first crossing of $V_{IH(AC)min}$. The typical t_{DS} slew rate for a falling signal is defined as the slew rate between the last crossing of $V_{REF(DC)}$ and the first crossing of $V_{IL(AC)max}$ (see the Typical Slew Rate and $t_{VAC} - t_{DS}$ for DQ Relative to Strobe figure).

If the actual signal is consistently earlier than the typical slew rate line in the figure, "Typical Slew Rate and $t_{VAC} - t_{IS}$ for CA and CS# Relative to Clock (CA and CS# Setup, Hold, and Derating), the area shaded gray between the $V_{REF(DC)}$ region and the AC region, use the typical slew rate for the derating value. If the actual signal is later than the typical slew rate line anywhere between the shaded $V_{REF(DC)}$ region and the AC region, the slew rate of a tangent line to the actual signal from the AC level to the DC level is used for the derating value (see figure "Tangent Line - t_{IS} for CA and CS# Relative to Clock" in CA and CS# Setup, Hold, and Derating).

The typical t_{DH} slew rate for a rising signal is defined as the slew rate between the last crossing of $V_{IL(DC)max}$ and the first crossing of $V_{REF(DC)}$. The typical t_{DH} slew rate for a falling signal is defined as the slew rate between the last crossing of $V_{IH(DC)min}$ and the first crossing of $V_{REF(DC)}$ (see the Typical Slew Rate - DH for DQ Relative to Strobe figure).

If the actual signal is consistently later than the typical slew rate line between the shaded DC-level-to- $V_{REF(DC)}$ region, use the typical slew rate for the derating value. If the actual signal is earlier than the typical slew rate line anywhere between shaded DC-to- $V_{REF(DC)}$ region, the slew rate of a tangent line to the actual signal from the DC level to the $V_{REF(DC)}$ level is used for the derating value (see the Tangent Line - t_{DH} for DQ with Respect to Strobe figure).

For a valid transition, the input signal must remain above or below $V_{IH}/V_{IL(AC)}$ for the specified time, t_{VAC} (see the Required Time for Valid Transition - $t_{VAC} > V_{IH(AC)}$ or $< V_{IL(AC)}$ table).

The total setup time for slow slew rates could be negative (that is, a valid input signal may not have reached $V_{IH}/V_{IL(AC)}$ at the time of the rising clock transition). A valid input signal is still required to complete the transition and reach $V_{IH}/V_{IL(AC)}$.

For slew rates between the values listed in the following tables, the derating values can be obtained using linear interpolation. Slew rate values are not typically subject to production testing. They are verified by design and characterization.

Table 130: Data Setup and Hold Base Values (>400 MHz, 1 V/ns Slew Rate)

Parameter	Data Rate						Reference
	1066	933	800	667	533	466	
$t_{DS}(\text{base})$	-10	15	50	130	210	230	$V_{IH}/V_{IL(AC)} = V_{REF(DC)} \pm 220\text{mV}$



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Data Setup, Hold, and Slew Rate Derating

Table 130: Data Setup and Hold Base Values (>400 MHz, 1 V/ns Slew Rate) (Continued)

Parameter	Data Rate						Reference
	1066	933	800	667	533	466	
t_{DH} (base)	80	105	140	220	300	320	$V_{IH}/V_{IL(DC)} = V_{REF(DC)} \pm 130mV$

Note: 1. AC/DC referenced for 1 V/ns DQ, DM slew rate, and 2 V/ns differential DQS/DQS# slew rate.

Table 131: Data Setup and Hold Base Values (<400 MHz, 1 V/ns Slew Rate)

Parameter	Data Rate				Reference
	400	333	255	200	
t_{DS} (base)	180	300	450	700	$V_{IH}/V_{IL(AC)} = V_{REF(DC)} \pm 300mV$
t_{DH} (base)	280	400	550	800	$V_{IH}/V_{IL(DC)} = V_{REF(DC)} \pm 200mV$

Note: 1. AC/DC referenced for 1 V/ns DQ, DM slew rate, and 2 V/ns differential DQS/DQS# slew rate.

Table 132: Derating Values for AC/DC-Based t_{DS}/t_{DH} (AC220)

Δt_{DS} , Δt_{DH} derating in ps

		DQS, DQS# Differential Slew Rate															
		4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
		Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}
DQ, DM slew rate V/ns	2.0	110	65	110	65	110	65										
	1.5	74	43	73	43	73	43	89	59								
	1.0	0	0	0	0	0	0	16	16	32	32						
	0.9			-3	-5	-3	-5	13	11	29	27	45	43				
	0.8					-8	-13	8	3	24	19	40	35	56	55		
	0.7							2	-6	18	10	34	26	50	46	66	78
	0.6									10	-3	26	13	42	33	58	65
	0.5											4	-4	20	16	36	48
	0.4													-7	2	17	34

Note: 1. Shaded cells are not supported.



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Data Setup, Hold, and Slew Rate Derating

Table 133: Derating Values for AC/DC-Based t_{DS}/t_{DH} (AC300)
 Δt_{DS} , Δt_{DH} derating in ps

		DQS, DQS# Differential Slew Rate															
		4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
		Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}	Δt_{DS}	Δt_{DH}
DQ, DM slew rate V/ns	2.0	150	100	150	100	150	100										
	1.5	100	67	100	67	100	67	116	83								
	1.0	0	0	0	0	0	0	16	16	32	32						
	0.9			-4	-8	-4	-8	12	8	28	24	44	40				
	0.8					-12	-20	4	-4	20	12	36	28	52	48		
	0.7							-3	-18	13	-2	29	14	45	34	61	66
	0.6									2	-21	18	-5	34	15	50	47
	0.5											-12	-32	4	-12	20	20
	0.4											4	-35	-40	-11	-8	

Note: 1. Shaded cells are not supported.

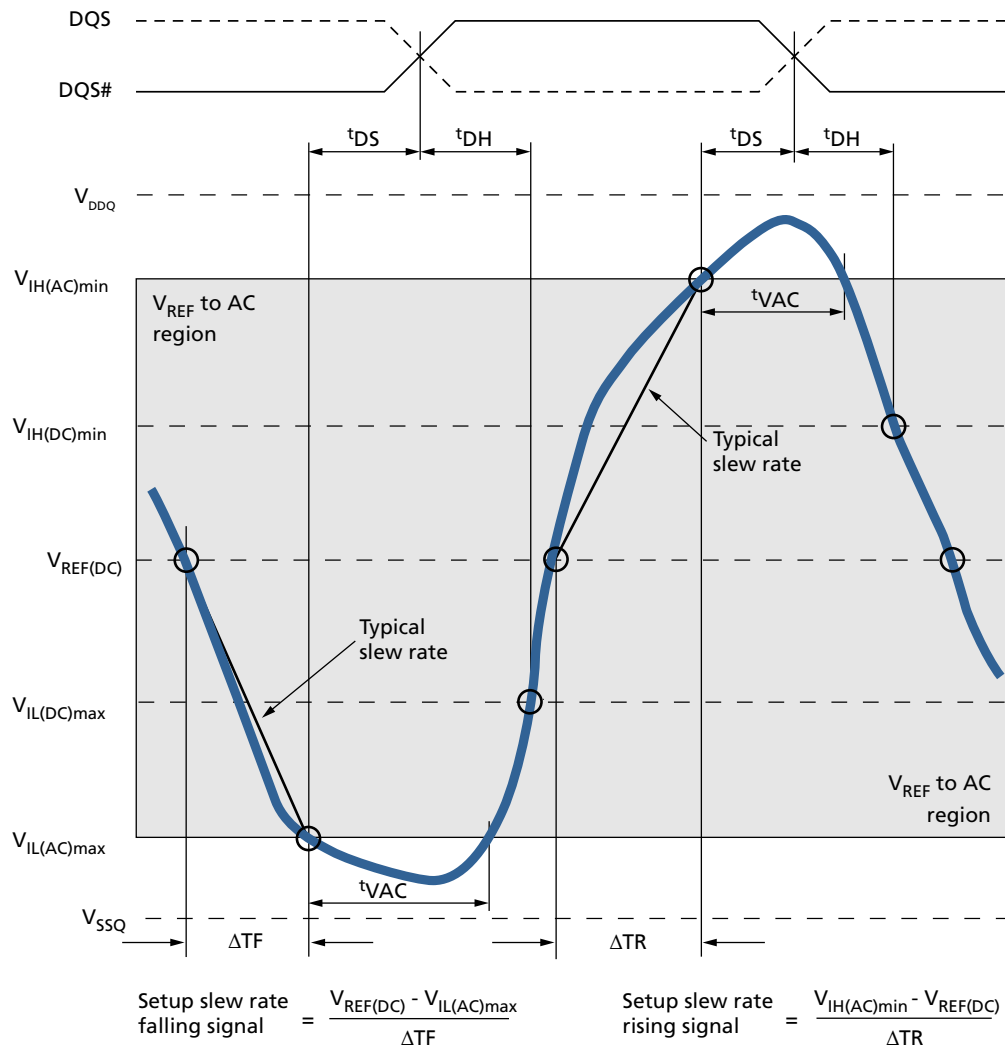
Table 134: Required Time for Valid Transition – $t_{VAC} > V_{IH(AC)}$ or $< V_{IL(AC)}$

Slew Rate (V/ns)	t_{VAC} at 300mV (ps)		t_{VAC} at 220mV (ps)	
	Min	Max	Min	Max
>2.0	75	–	175	–
2.0	57	–	170	–
1.5	50	–	167	–
1.0	38	–	163	–
0.9	34	–	162	–
0.8	29	–	161	–
0.7	22	–	159	–
0.6	13	–	155	–
0.5	0	–	150	–
<0.5	0	–	150	–



4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Data Setup, Hold, and Slew Rate Derating

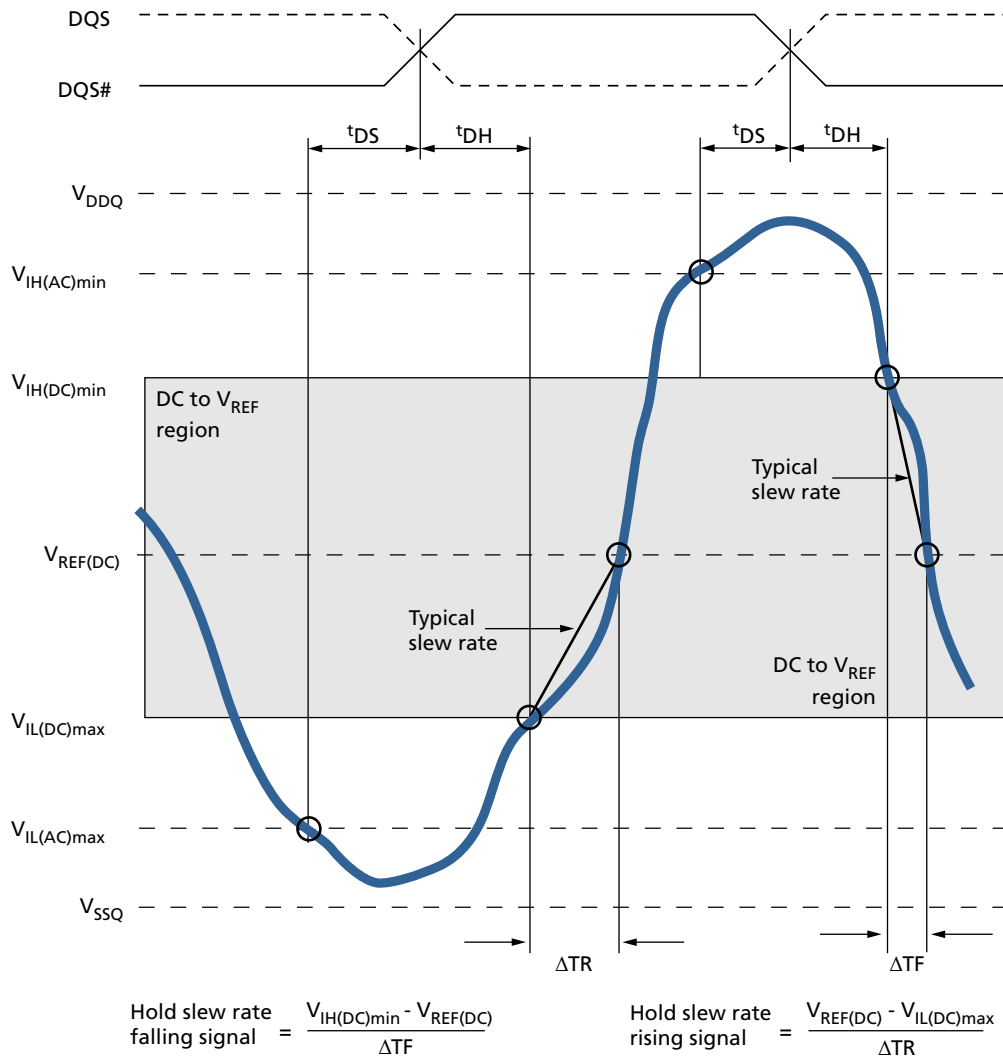
Figure 156: Typical Slew Rate and $t_{VAC} - t_{DS}$ for DQ Relative to Strobe





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Data Setup, Hold, and Slew Rate Derating

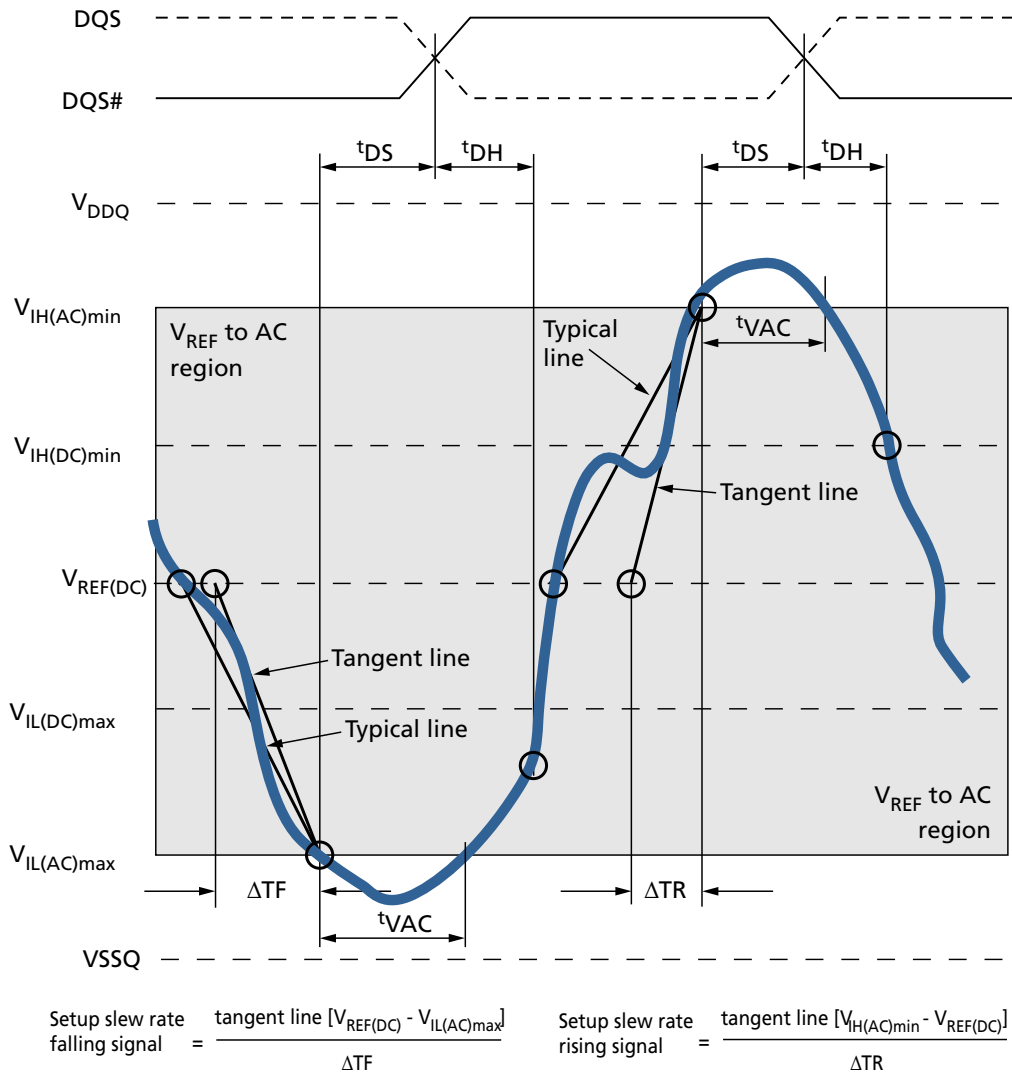
Figure 157: Typical Slew Rate – t_{DH} for DQ Relative to Strobe





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Data Setup, Hold, and Slew Rate Derating

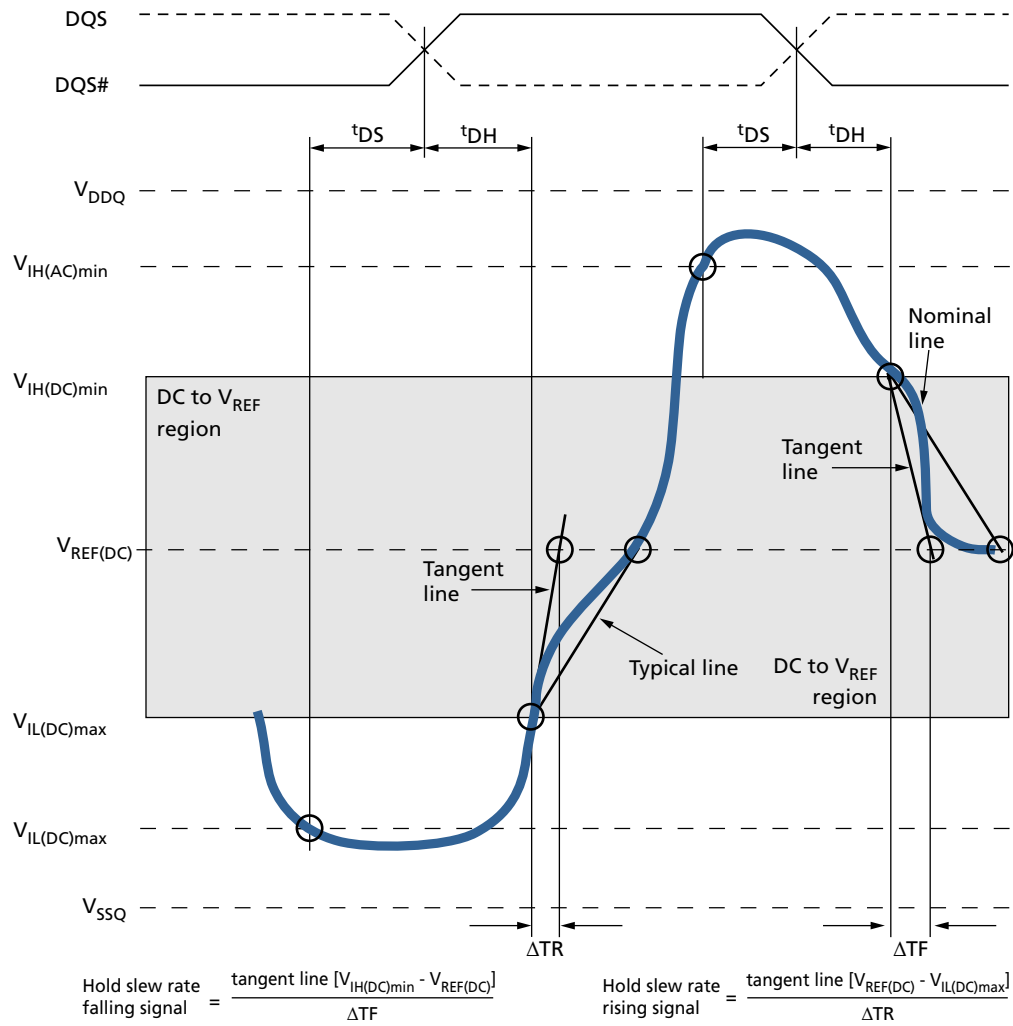
Figure 158: Tangent Line – t_{DS} for DQ with Respect to Strobe





4Gb: x8 NAND with 2Gb: x32 LPDDR2 MCP Data Setup, Hold, and Slew Rate Derating

Figure 159: Tangent Line – t_{DH} for DQ with Respect to Strobe





Revision History

Rev. C – 07/2020

- Updated legal status to Production
- Updated the endurance to 100,000 cycles for AT temperature range for the NAND
- Updated table note for ACTIVATE: Table note of Current State Bank n to Command to Bank n Truth Table in Truth Tables section

Rev. B – 03/2020

- Corrected Solder ball composition to SACQ with Cu OSP ball pads

Rev. A – 03/2020

- Initial release

8000 S. Federal Way, P.O. Box 6, Boise, ID 83707-0006, Tel: 208-368-4000
www.micron.com/products/support Sales inquiries: 800-932-4992
Micron and the Micron logo are trademarks of Micron Technology, Inc.
All other trademarks are the property of their respective owners.

This data sheet contains minimum and maximum limits specified over the power supply and temperature range set forth herein.
Although considered final, these specifications are subject to change, as further product development and data characterization some-
times occur.